EUROPEAN PATENT OFFICE
U.S. PATENT AND TRADEMARK OFFICE

CPC NOTICE OF CHANGES 1723

DATE: JANUARY 1, 2025

PROJECT RP12465

The following classification changes will be effected by this Notice of Changes:

Action	**Subclass**	**Group(s)**
SCHEME:		
Symbols Deleted:	H01L	21/06, 21/08, 21/10, 21/101, 21/103, 21/105, 21/108, 21/12, 21/14, 21/145, 21/16, 21/161, 21/162, 21/164, 21/165, 21/167, 21/168, 2021/775, 21/782, 21/784, 21/786, 21/82, 21/8206, 21/8213, 21/822, 21/8221, 21/8222, 21/8224, 21/8226, 21/8228, 21/82285, 21/8232, 21/8234, 21/823406, 21/823412, 21/823418, 21/823425, 21/823431, 21/823437, 21/823443, 21/82345, 21/823456, 21/823462, 21/823468, 21/823475, 21/823481, 21/823487, 21/823493, 21/8236, 21/8238, 21/823807, 21/823814, 21/823821, 21/823828, 21/823835, 21/823842, 21/82385, 21/823857, 21/823864, 21/823871, 21/823878, 21/823885, 21/823892, 21/8248, 21/8249, 21/8252, 21/8254, 21/8256, 21/8258, 21/84, 21/845, 21/86
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	H01L	2229/00
Symbols New:	H10D	SUBCLASS
	H10D	1/00, 1/01, 1/021, 1/025, 1/041, 1/042, 1/043, 1/045, 1/047, 1/048, 1/20, 1/40, 1/43, 1/47, 1/472, 1/474, 1/476, 1/60, 1/62, 1/64, 1/66, 1/665, 1/68, 1/682, 1/684, 1/688, 1/692, 1/694, 1/696, 1/711, 1/712, 1/714, 1/716
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	H10D	10/00, 10/01, 10/021, 10/031, 10/041, 10/051, 10/052, 10/054, 10/056, 10/058, 10/061, 10/211, 10/221, 10/231, 10/241, 10/311, 10/40, 10/421, 10/441, 10/461, 10/60, 10/80, 10/821, 10/841, 10/861, 10/881, 10/891
	H10D	12/00, 12/01, 12/021, 12/031, 12/032, 12/035, 12/038, 12/211, 12/212, 12/411, 12/415, 12/416, 12/417, 12/418, 12/421, 12/441, 12/461, 12/481, 12/491
	H10D	18/00, 18/01, 18/021, 18/031, 18/211, 18/221, 18/241, 18/251, 18/40, 18/60, 18/65, 18/655, 18/80
	H10D	30/00, 30/01, 30/012, 30/014, 30/015, 30/017, 30/019, 30/0191, 30/0193, 30/0194, 30/0195, 30/0196, 30/0197, 30/0198, 30/021, 30/0212, 30/0213, 30/0215, 30/0217, 30/0218, 30/022, 30/0221, 30/0223, 30/0225, 30/0227, 30/0229, 30/023, 30/024, 30/0241, 30/0243, 30/0245, 30/025, 30/026, 30/027, 30/0273, 30/0275, 30/0277, 30/0278, 30/028, 30/0281, 30/0285, 30/0287, 30/0289, 30/0291, 30/0293, 30/0295, 30/0297, 30/031, 30/0312, 30/0314, 30/0316, 30/0318, 30/0321, 30/0323, 30/0327, 30/0411, 30/0413, 30/0415, 30/051, 30/0512, 30/0515, 30/0516, 30/061, 30/0612, 30/0614, 30/0616, 30/0618, 30/202, 30/204, 30/40, 30/402, 30/43, 30/435, 30/47, 30/471, 30/472, 30/473, 30/4732, 30/4735, 30/4738, 30/474, 30/475, 30/4755, 30/476, 30/477, 30/478, 30/481, 30/485, 30/501, 30/502, 30/503, 30/504, 30/506, 30/507, 30/508, 30/509, 30/60, 30/601, 30/603, 30/605, 30/608, 30/611, 30/615, 30/62, 30/6211, 30/6212, 30/6213,

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	H10D	86/00, 86/01, 86/011, 86/021, 86/0212, 86/0214, 86/0221, 86/0223, 86/0225, 86/0227, 86/0229, 86/0231, 86/0241, 86/0251, 86/03, 86/201, 86/215, 86/40, 86/411, 86/421, 86/423, 86/425, 86/427, 86/431, 86/441, 86/443, 86/451, 86/471, 86/481, 86/60, 86/80, 86/85
	H10D	87/00
	H10D	88/00, 88/01, 88/101
	H10D	89/00, 89/011, 89/013, 89/015, 89/10, 89/105, 89/211, 89/213, 89/215, 89/217, 89/311, 89/60, 89/601, 89/611, 89/711, 89/713, 89/811, 89/813, 89/814, 89/815, 89/817, 89/819, 89/911, 89/921, 89/931
	H10D	99/00
Titles Changed:	H01L	21/28, 21/34
Warnings Deleted:	H10B	10/10, 12/10, 20/10, 69/00, 99/00, 99/10, 99/14, 99/16, 99/20, 99/22
	H01L	21/02104, 21/02107
	H01L	27/10, 27/101, 27/102, 27/1021, 27/1022, 27/1027, 27/1028, 27/105, 27/1214
	H01L	29/0852, 29/4991, 29/7803, 29/7811, 29/7815
Warnings Modified:	H01L	SUBCLASS
Warnings New:	H10D	1/01, 1/025, 1/045, 1/40
	H10D	8/00, 8/01, 8/043, 8/051, 8/053, 8/20
	H10D	10/01, 10/021, 10/031, 10/041, 10/051, 10/052, 10/054, 10/061
	H10D	12/01, 12/021, 12/031, 12/032, 12/035, 12/038, 12/211, 12/411, 12/415, 12/416, 12/417, 12/418, 12/421, 12/461, 12/491
	H10D	18/01, 18/40, 18/60
	H10D	30/00, 30/01, 30/012, 30/014, 30/015, 30/017, 30/019, 30/0191, 30/0195, 30/0198, 30/021, 30/0218, 30/022, 30/0223, 30/024, 30/0241, 30/0245, 30/0273, 30/028, 30/031, 30/0312,

		30/0314, 30/0316, 30/0318, 30/0321, 30/0323, 30/0327, 30/0411, 30/0415, 30/051, 30/061, 30/0612, 30/0618, 30/40, 30/43, 30/435, 30/47, 30/471, 30/4735, 30/4738, 30/477, 30/478, 30/481, 30/485, 30/501, 30/503, 30/504, 30/603, 30/605, 30/608, 30/62, 30/6211, 30/6212, 30/6213, 30/6215, 30/6217, 30/6218, 30/6219, 30/64, 30/645, 30/66, 30/662, 30/6704, 30/6728, 30/6733, 30/6734, 30/6735, 30/674, 30/6741, 30/6748, 30/6757, 30/68, 30/701, 30/751, 30/798
	H10D	48/00, 48/021, 48/031, 48/30, 48/38, 48/383, 48/3835
	H10D	62/00, 62/01, 62/051, 62/10, 62/111, 62/128, 62/129, 62/141, 62/145, 62/152, 62/156, 62/299, 62/314, 62/378, 62/80, 62/81, 62/82, 62/822, 62/824, 62/826, 62/8271, 62/8281, 62/83, 62/8303, 62/832, 62/834, 62/85, 62/8503, 62/852, 62/854, 62/86, 62/8603, 62/862, 62/864, 62/871, 62/874, 62/875, 62/881, 62/882, 62/883
	H10D	64/017, 64/23, 64/232, 64/252, 64/2523, 64/2527, 64/254, 64/256, 64/2565, 64/257, 64/529, 64/667, 64/668, 64/669, 64/671, 64/675
	H10D	84/01, 84/0107, 84/0112, 84/0123, 84/0151, 84/0153, 84/0156, 84/0198, 84/02, 84/03, 84/032, 84/035, 84/038, 84/05, 84/07, 84/08, 84/101, 84/161, 84/201, 84/206, 84/209, 84/212, 84/40, 84/401, 84/645, 84/67, 84/80, 84/811, 84/813, 84/817, 84/83, 84/8311, 84/8312, 84/83125, 84/83135, 84/83138, 84/8314, 84/8316, 84/832, 84/834, 84/835, 84/836, 84/837, 84/84, 84/85, 84/851, 84/853, 84/856
	H10D	86/85
	H10D	88/01
Notes Deleted:	H01L	27/00, 27/105
	H01L	29/00, 29/15, 29/41741, 29/4175, 29/41758, 29/49, 29/7395, 29/7834, 29/786
Notes New:	H10D	SUBCLASS
	H10D	1/00
	H10D	8/00
	H10D	10/00
	H10D	12/00
	H10D	18/00
	H10D	30/00

	H10D	44/00
	H10D	48/00
	H10D	62/13, 62/80, 62/84
	H10D	84/00
	H10D	86/00
Guidance Headings New:	H10D	1/00
	H10D	62/00
	H10D	80/00
DEFINITIONS:		
Definitions Deleted: (no frozen (F) symbol definitions should be deleted)	H01L	21/164, 2021/775, 21/786, 21/82, 21/8221, 21/823487, 21/823885
	H01L	27/00, 27/01, 27/013, 27/016, 27/02, 27/0207, 27/0211, 27/0222, 27/0225, 27/0233, 27/0248, 27/0251, 27/0255, 27/0259, 27/0262, 27/0266, 27/027, 27/0277, 27/0281, 27/0285, 27/0288, 27/0292, 27/0296, 27/0617, 27/10, 27/101, 27/1021, 27/105, 27/118, 2027/11829, 27/12, 27/1203, 27/1207, 27/1211, 27/1274, 27/13
	H01L	28/00
	H01L	29/00, 29/66227, 29/66242, 29/66363, 29/665, 29/66507, 29/66545, 29/66863, 29/66871, 29/66969
Definitions Modified:	H01L	21/28, 21/34

The following subclasses/groups are also impacted by this Notice of Changes (indicate subclasses/groups outside of the project scope, such as those listed in the CRL):
B81B, B81C, B82B, B82Y, C04B, C23F, G01J, G01L, G01N, G01R, G01S, G02B, G02F, G09G, G11C, H01C, H01F, H01G, H01L, H01S, H02H, H02M, H03K, H03M, H04L, H04N, H05K, H10B, H10K, H10N

This Notice of Changes includes the following *[Check the ones included]:*

1. CLASSIFICATION SCHEME CHANGES
   - ☒ A. New, Modified or Deleted Group(s)
   - ☒ B. New, Modified or Deleted Warning(s)
   - ☒ C. New, Modified or Deleted Note(s)
   - ☒ D. New, Modified or Deleted Guidance Heading(s)
2. DEFINITIONS
   - ☒ A. New or Modified Definitions (Full definition template)
   - ☒ B. Modified or Deleted Definitions (Definitions Quick Fix)
3. ☒ REVISION CONCORDANCE LIST (RCL)

4. ☒ CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

5. ☒ CHANGES TO THE CROSS-REFERENCE LIST (CRL)

1. CLASSIFICATION SCHEME CHANGES

A. New, Modified or Deleted Group(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 21/06	3	the devices having semiconductor bodies comprising selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials	<administrative transfer to H10D 48/04>
D	H01L 21/08	4	Preparation of the foundation plate	<administrative transfer to H10D 48/042>
D	H01L 21/10	4	Preliminary treatment of the selenium or tellurium, its application to the foundation plate, or the subsequent treatment of the combination	<administrative transfer to H10D 48/043>
D	H01L 21/101	5	{Application of the selenium or tellurium to the foundation plate}	<administrative transfer to H10D 48/0431>
D	H01L 21/103	5	Conversion of the selenium or tellurium to the conductive state	<administrative transfer to H10D 48/044>
D	H01L 21/105	5	Treatment of the surface of the selenium or tellurium layer after having been made conductive	<administrative transfer to H10D 48/045>
D	H01L 21/108	5	Provision of discrete insulating layers, i.e. non-genetic barrier layers	<administrative transfer to H10D 48/046>
D	H01L 21/12	4	Application of an electrode to the exposed surface of the selenium or tellurium after the selenium or tellurium has been applied to the foundation plate	<administrative transfer to H10D 48/047>
D	H01L 21/14	4	Treatment of the complete device, e.g. by electroforming to form a barrier	<administrative transfer to H10D 48/048>
D	H01L 21/145	5	Ageing	<administrative transfer to H10D 48/049>
D	H01L 21/16	3	the devices having semiconductor bodies comprising cuprous oxide or cuprous iodide	<administrative transfer to H10D 48/07>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 21/161	4	{Preparation of the foundation plate, preliminary treatment oxidation of the foundation plate, reduction treatment}	<administrative transfer to H10D 48/071>
D	H01L 21/162	5	{Preliminary treatment of the foundation plate}	<administrative transfer to H10D 48/073>
D	H01L 21/164	5	{Oxidation and subsequent heat treatment of the foundation plate (H01L 21/165 takes precedence)}	<administrative transfer to H10D 48/074>
D	H01L 21/165	5	{Reduction of the copper oxide, treatment of the oxide layer}	<administrative transfer to H10D 48/075>
D	H01L 21/167	5	{Application of a non-genetic conductive layer}	<administrative transfer to H10D 48/076>
D	H01L 21/168	4	{Treatment of the complete device, e.g. electroforming, ageing}	<administrative transfer to H10D 48/078>
M	H01L 21/28	4	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups H01L 21/20 - H01L 21/268	
M	H01L 21/34	3	the devices having semiconductor bodies not provided for in groups H01L 21/18, H10D 48/04 and H10D 48/07, with or without impurities, e.g. doping materials	
D	H01L 2021/775	3	{comprising a plurality of TFTs on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}	<administrative transfer to H10D 86/021>
D	H01L 21/782	4	to produce devices, each consisting of a single circuit element (H01L 21/82 takes precedence)	<administrative transfer to H10D 89/011>
D	H01L 21/784	5	the substrate being a semiconductor body	<administrative transfer to H10D 89/013>
D	H01L 21/786	5	the substrate being other than a semiconductor body, e.g. insulating body	<administrative transfer to H10D 89/015>
D	H01L 21/82	4	to produce devices, e.g. integrated circuits, each consisting of a plurality of components	<administrative transfer to H10D 84/01>
D	H01L 21/8206	5	{the substrate being a semiconductor, using diamond technology (H01L 21/8258 takes precedence)}	<administrative transfer to H10D 84/032>
D	H01L 21/8213	5	{the substrate being a semiconductor, using SiC	<administrative transfer to H10D 84/035>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
			technology (H01L 21/8258 takes precedence)}	
D	H01L 21/822	5	the substrate being a semiconductor, using silicon technology (H01L 21/8258 takes precedence)	<administrative transfer to H10D 84/038>
D	H01L 21/8221	6	{Three dimensional integrated circuits stacked in different levels}	<administrative transfer to H10D 84/038 and H10D 88/01 simultaneously>
D	H01L 21/8222	6	Bipolar technology	<administrative transfer to H10D 84/0112 and H10D 84/038 simultaneously>
D	H01L 21/8224	7	comprising a combination of vertical and lateral transistors	<administrative transfer to H10D 84/0114 and H10D 84/038 simultaneously>
D	H01L 21/8226	7	comprising merged transistor logic or integrated injection logic	<administrative transfer to H10D 84/0116 and H10D 84/038 simultaneously>
D	H01L 21/8228	7	Complementary devices, e.g. complementary transistors	<administrative transfer to H10D 84/0119 and H10D 84/038 simultaneously>
D	H01L 21/82285	8	{Complementary vertical transistors}	<administrative transfer to H10D 84/0121 and H10D 84/038 simultaneously>
D	H01L 21/8232	6	Field-effect technology	<administrative transfer to H10D 84/0123 and H10D 84/038 simultaneously>
D	H01L 21/8234	7	MIS technology {, i.e. integration processes of field effect transistors of the conductor-insulator-semiconductor type}	<administrative transfer to H10D 84/0126 and H10D 84/038 simultaneously>
D	H01L 21/823406	8	{Combination of charge coupled devices, i.e. CCD, or BBD}	<administrative transfer to H10D 84/0198 and H10D 84/038 simultaneously>
D	H01L 21/823412	8	{with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}	<administrative transfer to H10D 84/0128 and H10D 84/038 simultaneously>
D	H01L 21/823418	8	{with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}	<administrative transfer to H10D 84/013 and H10D 84/038 simultaneously>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 21/823425	9	{manufacturing common source or drain regions between a plurality of conductor-insulator-semiconductor structures}	<administrative transfer to H10D 84/0133 and H10D 84/038 simultaneously>
D	H01L 21/823431	8	{with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 84/0158 and H10D 84/038 simultaneously>
D	H01L 21/823437	8	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}	<administrative transfer to H10D 84/0135 and H10D 84/038 simultaneously>
D	H01L 21/823443	9	{silicided or salicided gate conductors}	<administrative transfer to H10D 84/0137 and H10D 84/038 simultaneously>
D	H01L 21/82345	9	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}	<administrative transfer to H10D 84/014 and H10D 84/038 simultaneously>
D	H01L 21/823456	9	{gate conductors with different shapes, lengths or dimensions}	<administrative transfer to H10D 84/0142 and H10D 84/038 simultaneously>
D	H01L 21/823462	8	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}	<administrative transfer to H10D 84/0144 and H10D 84/038 simultaneously>
D	H01L 21/823468	8	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}	<administrative transfer to H10D 84/0147 and H10D 84/038 simultaneously>
D	H01L 21/823475	8	{interconnection or wiring or contact manufacturing related aspects}	<administrative transfer to H10D 84/0149 and H10D 84/038 simultaneously>
D	H01L 21/823481	8	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}	<administrative transfer to H10D 84/0151 and H10D 84/038 simultaneously>
D	H01L 21/823487	8	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823431)}	<administrative transfer to H10D 84/016 and H10D 84/038 simultaneously>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 21/823493	8	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}	<administrative transfer to H10D 84/0156 and H10D 84/038 simultaneously>
D	H01L 21/8236	8	Combination of enhancement and depletion transistors	<administrative transfer to H10D 84/0163 and H10D 84/038 simultaneously>
D	H01L 21/8238	8	Complementary field-effect transistors, e.g. CMOS	<administrative transfer to H10D 84/0165 and H10D 84/038 simultaneously>
D	H01L 21/823807	9	{with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}	<administrative transfer to H10D 84/0167 and H10D 84/038 simultaneously>
D	H01L 21/823814	9	{with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}	<administrative transfer to H10D 84/017 and H10D 84/038 simultaneously>
D	H01L 21/823821	9	{with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 84/0193 and H10D 84/038 simultaneously>
D	H01L 21/823828	9	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}	<administrative transfer to H10D 84/0172 and H10D 84/038 simultaneously>
D	H01L 21/823835	10	{silicided or salicided gate conductors}	<administrative transfer to H10D 84/0174 and H10D 84/038 simultaneously>
D	H01L 21/823842	10	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}	<administrative transfer to H10D 84/0177 and H10D 84/038 simultaneously>
D	H01L 21/82385	10	{gate conductors with different shapes, lengths or dimensions}	<administrative transfer to H10D 84/0179 and H10D 84/038 simultaneously>
D	H01L 21/823857	9	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}	<administrative transfer to H10D 84/0181 and H10D 84/038 simultaneously>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 21/823864	9	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}	<administrative transfer to H10D 84/0184 and H10D 84/038 simultaneously>
D	H01L 21/823871	9	{interconnection or wiring or contact manufacturing related aspects}	<administrative transfer to H10D 84/0186 and H10D 84/038 simultaneously>
D	H01L 21/823878	9	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}	<administrative transfer to H10D 84/0188 and H10D 84/038 simultaneously>
D	H01L 21/823885	9	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823821)}	<administrative transfer to H10D 84/0195 and H10D 84/038 simultaneously>
D	H01L 21/823892	9	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}	<administrative transfer to H10D 84/0191 and H10D 84/038 simultaneously>
D	H01L 21/8248	6	Combination of bipolar and field-effect technology	<administrative transfer to H10D 84/0107 and H10D 84/038 simultaneously>
D	H01L 21/8249	7	Bipolar and MOS technology	<administrative transfer to H10D 84/0109 and H10D 84/038 simultaneously>
D	H01L 21/8252	5	the substrate being a semiconductor, using III-V technology (H01L 21/8258 takes precedence)	<administrative transfer to H10D 84/05>
D	H01L 21/8254	5	the substrate being a semiconductor, using II-VI technology (H01L 21/8258 takes precedence)	<administrative transfer to H10D 84/07>
D	H01L 21/8256	5	the substrate being a semiconductor, using technologies not covered by one of groups {H01L 21/8206, H01L 21/8213} , H01L 21/822, H01L 21/8252 and H01L 21/8254 (H01L 21/8258 takes precedence)	<administrative transfer to H10D 84/02>
D	H01L 21/8258	5	the substrate being a semiconductor, using a combination of technologies covered by {H01L 21/8206,	<administrative transfer to H10D 84/08>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			H01L 21/8213} , H01L 21/822, H01L 21/8252, H01L 21/8254 or H01L 21/8256	
D	H01L 21/84	5	the substrate being other than a semiconductor body, e.g. being an insulating body	<administrative transfer to H10D 86/01>
D	H01L 21/845	6	{including field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 86/011>
D	H01L 21/86	6	the insulating body being sapphire, e.g. silicon on sapphire structure, i.e. SOS	<administrative transfer to H10D 86/03>
D	H01L 27/00	0	Devices consisting of a plurality of semiconductor or other solid-state components formed in or on a common substrate (details thereof H01L 23/00, H01L 29/00 - H10K 10/00; assemblies consisting of a plurality of individual solid state devices H01L 25/00)	<administrative transfer to H10D 99/00>
D	H01L 27/01	1	comprising only passive thin-film or thick-film elements formed on a common insulating substrate {(passive two-terminal components without a potential-jump or surface barrier for integrated circuits, details thereof and multistep manufacturing processes therefor H01L 28/00)}	<administrative transfer to H10D 86/85>
D	H01L 27/013	2	{Thick-film circuits}	<administrative transfer to H10D 86/85>
D	H01L 27/016	2	{Thin-film circuits}	<administrative transfer to H10D 86/85>
D	H01L 27/02	1	including semiconductor components specially adapted for rectifying, oscillating, amplifying or switching and having potential barriers; including integrated passive circuit elements having potential barriers	<administrative transfer to H10D 89/00>
D	H01L 27/0203	2	{Particular design considerations for integrated circuits}	<administrative transfer to H10D 89/00>
D	H01L 27/0207	3	{Geometrical layout of the components, e.g. computer aided	<administrative transfer to H10D 89/10>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			design; custom LSI, semi-custom LSI, standard cell technique}	
D	H01L 27/0211	4	{adapted for requirements of temperature}	<administrative transfer to H10D 89/105>
D	H01L 27/0214	3	{for internal polarisation, e.g. I2L}	<administrative transfer to H10D 89/211>
D	H01L 27/0218	4	{of field effect structures}	<administrative transfer to H10D 89/213>
D	H01L 27/0222	5	{Charge pumping, substrate bias generation structures}	<administrative transfer to H10D 89/215>
D	H01L 27/0225	5	{Charge injection in static induction transistor logic structures [SITL]}	<administrative transfer to H10D 89/217>
D	H01L 27/0229	4	{of bipolar structures}	<administrative transfer to H10D 89/311>
D	H01L 27/0233	5	{Integrated injection logic structures [I2L]}	<administrative transfer to H10D 84/65>
D	H01L 27/0237	6	{using vertical injector structures}	<administrative transfer to H10D 84/652>
D	H01L 27/024	6	{using field effect injector structures}	<administrative transfer to H10D 84/655>
D	H01L 27/0244	6	{I2L structures integrated in combination with analog structures}	<administrative transfer to H10D 84/658>
D	H01L 27/0248	3	{for electrical or thermal protection, e.g. electrostatic discharge [ESD] protection}	<administrative transfer to H10D 89/60>
D	H01L 27/0251	4	{for MOS devices}	<administrative transfer to H10D 89/601>
D	H01L 27/0255	5	{using diodes as protective elements}	<administrative transfer to H10D 89/611>
D	H01L 27/0259	5	{using bipolar transistors as protective elements}	<administrative transfer to H10D 89/711>
D	H01L 27/0262	6	{including a PNP transistor and a NPN transistor, wherein each of said transistors has its base coupled to the collector of the other transistor, e.g. silicon controlled rectifier [SCR] devices}	<administrative transfer to H10D 89/713>
D	H01L 27/0266	5	{using field effect transistors as protective elements}	<administrative transfer to H10D 89/811>
D	H01L 27/027	6	{specially adapted to provide an electrical current path other than the field effect induced current path}	<administrative transfer to H10D 89/813>
D	H01L 27/0274	7	{involving a parasitic bipolar transistor triggered by the electrical	<administrative transfer to H10D 89/814>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			biasing of the gate electrode of the field effect transistor, e.g. gate coupled transistors}	
D	H01L 27/0277	7	{involving a parasitic bipolar transistor triggered by the local electrical biasing of the layer acting as base of said parasitic bipolar transistor}	<administrative transfer to H10D 89/815>
D	H01L 27/0281	6	{field effect transistors in a "Darlington-like" configuration}	<administrative transfer to H10D 89/817>
D	H01L 27/0285	6	{bias arrangements for gate electrode of field effect transistors, e.g. RC networks, voltage partitioning circuits (H01L 27/0281 takes precedence)}	<administrative transfer to H10D 89/819>
D	H01L 27/0288	5	{using passive elements as protective elements, e.g. resistors, capacitors, inductors, spark-gaps}	<administrative transfer to H10D 89/911>
D	H01L 27/0292	5	{using a specific configuration of the conducting means connecting the protective devices, e.g. ESD buses}	<administrative transfer to H10D 89/921>
D	H01L 27/0296	5	{involving a specific disposition of the protective devices}	<administrative transfer to H10D 89/931>
D	H01L 27/04	2	the substrate being a semiconductor body	<administrative transfer to H10D 84/00>
D	H01L 27/06	3	including a plurality of individual components in a non-repetitive configuration	<administrative transfer to H10D 84/00>
D	H01L 27/0605	4	{integrated circuits made of compound material, e.g. $A_{III}B_{V}$}	<administrative transfer to H10D 84/01>
D	H01L 27/0611	4	{integrated circuits having a two-dimensional layout of components without a common active region}	<administrative transfer to H10D 84/00>
D	H01L 27/0617	5	{comprising components of the field-effect type (H01L 27/0251 takes precedence)}	<administrative transfer to H10D 84/40>
D	H01L 27/0623	6	{in combination with bipolar transistors}	<administrative transfer to H10D 84/401>
D	H01L 27/0629	6	{in combination with diodes, or resistors, or capacitors}	<administrative transfer to H10D 84/811>
D	H01L 27/0635	6	{in combination with bipolar transistors and diodes, or resistors, or capacitors}	<administrative transfer to H10D 84/403>
D	H01L 27/0641	5	{without components of the field effect type}	<administrative transfer to H10D 84/60>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 27/0647	6	{Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. vertical bipolar transistor and bipolar lateral transistor and resistor}	<administrative transfer to H10D 84/611>
D	H01L 27/0652	7	{Vertical bipolar transistor in combination with diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/613>
D	H01L 27/0658	8	{Vertical bipolar transistor in combination with resistors or capacitors}	<administrative transfer to H10D 84/615>
D	H01L 27/0664	8	{Vertical bipolar transistor in combination with diodes}	<administrative transfer to H10D 84/617>
D	H01L 27/067	7	{Lateral bipolar transistor in combination with diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/619>
D	H01L 27/0676	6	{comprising combinations of diodes, or capacitors or resistors}	<administrative transfer to H10D 84/204>
D	H01L 27/0682	7	{comprising combinations of capacitors and resistors}	<administrative transfer to H10D 84/206>
D	H01L 27/0688	4	{Integrated circuits having a three-dimensional layout}	<administrative transfer to H10D 88/00>
D	H01L 27/0694	5	{comprising components formed on opposite sides of a semiconductor substrate}	<administrative transfer to H10D 88/101>
D	H01L 27/07	4	the components having an active region in common	<administrative transfer to H10D 84/00>
D	H01L 27/0705	5	{comprising components of the field effect type}	<administrative transfer to H10D 84/401>
D	H01L 27/0711	6	{in combination with bipolar transistors and diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/403>
D	H01L 27/0716	7	{in combination with vertical bipolar transistors and diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/406 >
D	H01L 27/0722	7	{in combination with lateral bipolar transistors and diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/409>
D	H01L 27/0727	6	{in combination with diodes, or capacitors or resistors}	<administrative transfer to H10D 84/811>
D	H01L 27/0733	7	{in combination with capacitors only}	<administrative transfer to H10D 84/813>
D	H01L 27/0738	7	{in combination with resistors only}	<administrative transfer to H10D 84/817>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 27/0744	5	{without components of the field effect type}	<administrative transfer to H10D 84/60>
D	H01L 27/075	6	{Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. lateral bipolar transistor, and vertical bipolar transistor and resistor}	<administrative transfer to H10D 84/611>
D	H01L 27/0755	7	{Vertical bipolar transistor in combination with diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/613>
D	H01L 27/0761	8	{Vertical bipolar transistor in combination with diodes only}	<administrative transfer to H10D 84/617>
D	H01L 27/0766	9	{with Schottky diodes only}	<administrative transfer to H10D 84/617 >
D	H01L 27/0772	8	{Vertical bipolar transistor in combination with resistors only}	<administrative transfer to H10D 84/615>
D	H01L 27/0777	8	{Vertical bipolar transistor in combination with capacitors only}	<administrative transfer to H10D 84/615>
D	H01L 27/0783	7	{Lateral bipolar transistors in combination with diodes, or capacitors, or resistors}	<administrative transfer to H10D 84/619>
D	H01L 27/0788	6	{comprising combinations of diodes or capacitors or resistors}	<administrative transfer to H10D 84/204>
D	H01L 27/0794	7	{Combinations of capacitors and resistors}	<administrative transfer to H10D 84/206>
D	H01L 27/08	3	including only semiconductor components of a single kind	<administrative transfer to H10D 84/00>
D	H01L 27/0802	4	{Resistors only}	<administrative transfer to H10D 84/209>
D	H01L 27/0805	4	{Capacitors only}	<administrative transfer to H10D 84/212>
D	H01L 27/0808	5	{Varactor diodes}	<administrative transfer to H10D 84/215>
D	H01L 27/0811	5	{MIS diodes}	<administrative transfer to H10D 84/217>
D	H01L 27/0814	4	{Diodes only}	<administrative transfer to H10D 84/221>
D	H01L 27/0817	4	{Thyristors only}	<administrative transfer to H10D 84/676>
D	H01L 27/082	4	including bipolar components only	<administrative transfer to H10D 84/645>
D	H01L 27/0821	5	{Combination of lateral and vertical transistors only}	<administrative transfer to H10D 84/63>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 27/0823	5	{including vertical bipolar transistors only}	<administrative transfer to H10D 84/641>
D	H01L 27/0825	6	{Combination of vertical direct transistors of the same conductivity type having different characteristics,(e.g. Darlington transistors)}	<administrative transfer to H10D 84/642>
D	H01L 27/0826	6	{Combination of vertical complementary transistors}	<administrative transfer to H10D 84/673>
D	H01L 27/0828	6	{Combination of direct and inverse vertical transistors}	<administrative transfer to H10D 84/643>
D	H01L 27/085	4	including field-effect components only	<administrative transfer to H10D 84/82>
D	H01L 27/088	5	the components being field-effect transistors with insulated gate	<administrative transfer to H10D 84/83>
D	H01L 27/0883	6	{Combination of depletion and enhancement field effect transistors}	<administrative transfer to H10D 84/84>
D	H01L 27/0886	6	{including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 84/834>
D	H01L 27/092	6	complementary MIS field-effect transistors	<administrative transfer to H10D 84/85>
D	H01L 27/0921	7	{Means for preventing a bipolar, e.g. thyristor, action between the different transistor regions, e.g. Latchup prevention}	<administrative transfer to H10D 84/854>
D	H01L 27/0922	7	{Combination of complementary transistors having a different structure, e.g. stacked CMOS, high-voltage and low-voltage CMOS}	<administrative transfer to H10D 84/856>
D	H01L 27/0924	7	{including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 84/853 >
D	H01L 27/0925	7	{comprising an N-well only in the substrate}	<administrative transfer to H10D 84/857>
D	H01L 27/0927	7	{comprising a P-well only in the substrate}	<administrative transfer to H10D 84/858>
D	H01L 27/0928	7	{comprising both N- and P- wells in the substrate, e.g. twin-tub}	<administrative transfer to H10D 84/859>
D	H01L 27/095	5	the components being Schottky barrier gate field-effect transistors	<administrative transfer to H10D 84/86>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 27/098	5	the components being PN junction gate field-effect transistors	<administrative transfer to H10D 84/87>
D	H01L 27/10	3	including a plurality of individual components in a repetitive configuration	<administrative transfer to H10D 84/00>
D	H01L 27/101	4	{including resistors or capacitors only}	<administrative transfer to H10D 84/206>
D	H01L 27/102	4	including bipolar components	<administrative transfer to H10D 84/00>
D	H01L 27/1021	5	{including diodes only}	<administrative transfer to H10D 84/221>
D	H01L 27/1022	5	{including bipolar transistors}	<administrative transfer to H10D 84/60>
D	H01L 27/1027	5	{Thyristors}	<administrative transfer to H10D 84/60>
D	H01L 27/1028	5	{Double base diodes}	<administrative transfer to H10D 84/00>
D	H01L 27/105	4	including field-effect components	<administrative transfer to H10D 84/80>
D	H01L 27/1055	5	{comprising charge coupled devices of the so-called bucket brigade type}	<administrative transfer to H10D 84/895>
D	H01L 27/1057	5	{comprising charge coupled devices [CCD] or charge injection devices [CID]}	<administrative transfer to H10D 84/891>
D	H01L 27/118	4	Masterslice integrated circuits	<administrative transfer to H10D 84/90>
D	H01L 27/11801	5	{using bipolar technology}	<administrative transfer to H10D 84/901>
D	H01L 27/11803	5	{using field effect technology}	<administrative transfer to H10D 84/903>
D	H01L 2027/11805	6	{A3B5 or A3B6 gate arrays}	<administrative transfer to H10D 84/905>
D	H01L 27/11807	6	{CMOS gate arrays}	<administrative transfer to H10D 84/907>
D	H01L 2027/11809	7	{Microarchitecture}	<administrative transfer to H10D 84/909>
D	H01L 2027/11811	8	{Basic cell P to N transistor count}	<administrative transfer to H10D 84/911>
D	H01L 2027/11812	9	{4-T CMOS basic cell}	<administrative transfer to H10D 84/912>
D	H01L 2027/11814	9	{5-T CMOS basic cell}	<administrative transfer to H10D 84/914>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 2027/11816	9	{6-T CMOS basic cell}	<administrative transfer to H10D 84/916>
D	H01L 2027/11818	9	{7-T CMOS basic cell}	<administrative transfer to H10D 84/918>
D	H01L 2027/1182	9	{8-T CMOS basic cell}	<administrative transfer to H10D 84/921>
D	H01L 2027/11822	8	{relative P to N transistor sizes}	<administrative transfer to H10D 84/922>
D	H01L 2027/11824	9	{for current drive capability}	<administrative transfer to H10D 84/924>
D	H01L 2027/11825	9	{for delay time adaptation}	<administrative transfer to H10D 84/925>
D	H01L 2027/11827	9	{for capacitive loading}	<administrative transfer to H10D 84/927>
D	H01L 2027/11829	8	{Isolation techniques}	<administrative transfer to H10D 84/929>
D	H01L 2027/11831	9	{FET isolation}	<administrative transfer to H10D 84/931>
D	H01L 2027/11833	9	{LOCOS}	<administrative transfer to H10D 84/933>
D	H01L 2027/11835	8	{Degree of specialisation for implementing specific functions}	<administrative transfer to H10D 84/935>
D	H01L 2027/11837	9	{Implementation of digital circuits}	<administrative transfer to H10D 84/937>
D	H01L 2027/11838	10	{Implementation of memory functions}	<administrative transfer to H10D 84/938>
D	H01L 2027/1184	9	{Implementation of analog circuits}	<administrative transfer to H10D 84/941>
D	H01L 2027/11842	10	{Resistors and capacitors}	<administrative transfer to H10D 84/942>
D	H01L 2027/11844	9	{Hybrid analog or digital}	<administrative transfer to H10D 84/944>
D	H01L 2027/11846	9	{Embedded IO cells}	<administrative transfer to H10D 84/946>
D	H01L 2027/11848	9	{Transmission gate}	<administrative transfer to H10D 84/948>
D	H01L 2027/1185	9	{Porous cells, i.e. pass-through elements}	<administrative transfer to H10D 84/949>
D	H01L 2027/11851	8	{Technology used, i.e. design rules}	<administrative transfer to H10D 84/951>
D	H01L 2027/11853	9	{Sub-micron technology}	<administrative transfer to H10D 84/953>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 2027/11855	9	{Twin-tub technology}	<administrative transfer to H10D 84/955>
D	H01L 2027/11857	9	{SOS, SOI technology}	<administrative transfer to H10D 84/957>
D	H01L 2027/11859	8	{Connectibility characteristics, i.e. diffusion and polysilicon geometries}	<administrative transfer to H10D 84/959>
D	H01L 2027/11861	9	{Substrate and well contacts}	<administrative transfer to H10D 84/961>
D	H01L 2027/11862	9	{Horizontal or vertical grid line density}	<administrative transfer to H10D 84/962>
D	H01L 2027/11864	9	{Yield or reliability}	<administrative transfer to H10D 84/964>
D	H01L 2027/11866	9	{Gate electrode terminals or contacts}	<administrative transfer to H10D 84/966>
D	H01L 2027/11868	7	{Macro-architecture}	<administrative transfer to H10D 84/968>
D	H01L 2027/1187	8	{Number of core or basic cells in the macro (RAM, ROM)}	<administrative transfer to H10D 84/971>
D	H01L 2027/11872	8	{Distribution function, e.g. Sea of Gates}	<administrative transfer to H10D 84/972>
D	H01L 2027/11874	8	{Layout specification, i.e. inner core region}	<administrative transfer to H10D 84/974>
D	H01L 2027/11875	9	{Wiring region, routing}	<administrative transfer to H10D 84/975>
D	H01L 2027/11877	9	{Avoiding clock-skew or clock-delay}	<administrative transfer to H10D 84/977>
D	H01L 2027/11879	9	{Data lines (buses)}	<administrative transfer to H10D 84/979>
D	H01L 2027/11881	9	{Power supply lines}	<administrative transfer to H10D 84/981>
D	H01L 2027/11883	7	{Levels of metallisation}	<administrative transfer to H10D 84/983>
D	H01L 2027/11885	8	{Two levels of metal}	<administrative transfer to H10D 84/985>
D	H01L 2027/11887	8	{Three levels of metal}	<administrative transfer to H10D 84/987>
D	H01L 2027/11888	8	{More than 3 levels of metal}	<administrative transfer to H10D 84/988>
D	H01L 2027/1189	7	{Latch-up prevention}	<administrative transfer to H10D 84/991>
D	H01L 2027/11892	7	{Noise prevention (crosstalk)}	<administrative transfer to H10D 84/992>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 2027/11894	7	{Radiation hardened circuits}	<administrative transfer to H10D 84/994>
D	H01L 27/11896	5	{using combined field effect/bipolar technology}	<administrative transfer to H10D 84/996>
D	H01L 27/11898	5	{Input and output buffer/driver structures}	<administrative transfer to H10D 84/998>
D	H01L 27/12	2	the substrate being other than a semiconductor body, e.g. an insulating body	<administrative transfer to H10D 86/00>
D	H01L 27/1203	3	{the substrate comprising an insulating body on a semiconductor body, e.g. SOI (three-dimensional layout H01L 27/0688)}	<administrative transfer to H10D 86/201>
D	H01L 27/1207	4	{combined with devices in contact with the semiconductor body, i.e. bulk/SOI hybrid circuits}	<administrative transfer to H10D 87/00>
D	H01L 27/1211	4	{combined with field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 86/215>
D	H01L 27/1214	3	{comprising a plurality of TFTs formed on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}	<administrative transfer to H10D 86/40 and H10D 86/60 simultaneously>
D	H01L 27/1218	4	{with a particular composition or structure of the substrate}	<administrative transfer to H10D 86/411 and H10D 86/60 simultaneously>
D	H01L 27/1222	4	{with a particular composition, shape or crystalline structure of the active layer}	<administrative transfer to H10D 86/60 and H10D 86/421 simultaneously>
D	H01L 27/1225	5	{with semiconductor materials not belonging to the group IV of the periodic table, e.g. InGaZnO}	<administrative transfer to H10D 86/60 and H10D 86/423 simultaneously>
D	H01L 27/1229	5	{with different crystal properties within a device or between different devices}	<administrative transfer to H10D 86/425 and H10D 86/60 simultaneously>
D	H01L 27/1233	5	{with different thicknesses of the active layer in different devices}	<administrative transfer to H10D 86/427 and H10D 86/60 simultaneously>
D	H01L 27/1237	4	{with a different composition, shape, layout or thickness of the gate insulator in different devices}	<administrative transfer to H10D 86/431 and H10D 86/60 simultaneously>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 27/124	4	{with a particular composition, shape or layout of the wiring layers specially adapted to the circuit arrangement, e.g. scanning lines in LCD pixel circuits (wiring structures per se H01L 23/52)}	<administrative transfer to H10D 86/441 and H10D 86/60 simultaneously>
D	H01L 27/1244	5	{for preventing breakage, peeling or short circuiting}	<administrative transfer to H10D 86/443 and H10D 86/60 simultaneously>
D	H01L 27/1248	4	{with a particular composition or shape of the interlayer dielectric specially adapted to the circuit arrangement}	<administrative transfer to H10D 86/451 and H10D 86/60 simultaneously>
D	H01L 27/1251	4	{comprising TFTs having a different architecture, e.g. top- and bottom gate TFTs}	<administrative transfer to H10D 86/471 and H10D 86/60 simultaneously>
D	H01L 27/1255	4	{integrated with passive devices, e.g. auxiliary capacitors}	<administrative transfer to H10D 86/481 and H10D 86/60 simultaneously>
D	H01L 27/1259	4	{Multistep manufacturing methods}	<administrative transfer to H10D 86/021>
D	H01L 27/1262	5	{with a particular formation, treatment or coating of the substrate}	<administrative transfer to H10D 86/0212>
D	H01L 27/1266	6	{the substrate on which the devices are formed not being the final device substrate, e.g. using a temporary substrate}	<administrative transfer to H10D 86/0214>
D	H01L 27/127	5	{with a particular formation, treatment or patterning of the active layer specially adapted to the circuit arrangement}	<administrative transfer to H10D 86/0221>
D	H01L 27/1274	6	{using crystallisation of amorphous semiconductor or recrystallisation of crystalline semiconductor}	<administrative transfer to H10D 86/0223>
D	H01L 27/1277	7	{using a crystallisation promoting species, e.g. local introduction of Ni catalyst}	<administrative transfer to H10D 86/0225>
D	H01L 27/1281	7	{by using structural features to control crystal growth, e.g. placement of grain filters}	<administrative transfer to H10D 86/0227>
D	H01L 27/1285	7	{using control of the annealing or irradiation parameters, e.g. using different scanning direction or intensity for different transistors}	<administrative transfer to H10D 86/0229>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 27/1288	5	{employing particular masking sequences or specially adapted masks, e.g. half-tone mask}	<administrative transfer to H10D 86/0231>
D	H01L 27/1292	5	{using liquid deposition, e.g. printing}	<administrative transfer to H10D 86/0241>
D	H01L 27/1296	5	{adapted to increase the uniformity of device parameters}	<administrative transfer to H10D 86/0251>
D	H01L 27/13	3	combined with thin-film or thick-film passive components	<administrative transfer to H10D 86/80>
D	H01L 28/00	0	{Passive two-terminal components without a potential-jump or surface barrier for integrated circuits; Details thereof; Multistep manufacturing processes therefor (testing or measuring during manufacture H01L 22/00; integration methods H01L 21/70; integrated circuits H01L 27/00; two-terminal components with a potential-jump or surface barrier H01L 29/00; resistors in general H01C; inductors in general H01F; capacitors in general H01G)}	<administrative transfer to H10D 1/00>
D	H01L 28/10	1	{Inductors}	<administrative transfer to H10D 1/20>
D	H01L 28/20	1	{Resistors}	<administrative transfer to H10D 1/47>
D	H01L 28/22	2	{with an active material comprising carbon, e.g. diamond or diamond-like carbon [DLC]}	<administrative transfer to H10D 1/472>
D	H01L 28/24	2	{with an active material comprising a refractory, transition or noble metal, metal compound or metal alloy, e.g. silicides, oxides, nitrides}	<administrative transfer to H10D 1/474>
D	H01L 28/26	2	{with an active material comprising an organic conducting material, e.g. conducting polymers}	<administrative transfer to H10D 1/476>
D	H01L 28/40	1	{Capacitors}	<administrative transfer to H10D 1/68>
D	H01L 28/55	2	{with a dielectric comprising a perovskite structure material}	<administrative transfer to H10D 1/682>
D	H01L 28/56	3	{the dielectric comprising two or more layers, e.g. comprising buffer layers, seed layers, gradient layers}	<administrative transfer to H10D 1/684>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 28/57	3	{comprising a barrier layer to prevent diffusion of hydrogen or oxygen}	<administrative transfer to H10D 1/688>
D	H01L 28/60	2	{Electrodes}	<administrative transfer to H10D 1/692>
D	H01L 28/65	3	{comprising a noble metal or a noble metal oxide, e.g. platinum (Pt), ruthenium (Ru), ruthenium dioxide (RuO_2), iridium (Ir), iridium dioxide (IrO_2)}	<administrative transfer to H10D 1/694>
D	H01L 28/75	3	{comprising two or more layers, e.g. comprising a barrier layer and a metal layer}	<administrative transfer to H10D 1/696>
D	H01L 28/82	3	{with an enlarged surface, e.g. formed by texturisation}	<administrative transfer to H10D 1/711>
D	H01L 28/84	4	{being a rough surface, e.g. using hemispherical grains}	<administrative transfer to H10D 1/712>
D	H01L 28/86	4	{having horizontal extensions}	<administrative transfer to H10D 1/714>
D	H01L 28/87	5	{made by depositing layers, e.g. by depositing alternating conductive and insulating layers}	<administrative transfer to H10D 1/042 and H10D 1/714 simultaneously>
D	H01L 28/88	5	{made by patterning layers, e.g. by etching conductive layers}	<administrative transfer to H10D 1/043 and H10D 1/714 simultaneously>
D	H01L 28/90	4	{having vertical extensions}	<administrative transfer to H10D 1/716>
D	H01L 28/91	5	{made by depositing layers, e.g. by depositing alternating conductive and insulating layers}	<administrative transfer to H10D 1/042 and H10D 1/716 simultaneously>
D	H01L 28/92	5	{made by patterning layers, e.g. by etching conductive layers}	<administrative transfer to H10D 1/043 and H10D 1/716 simultaneously>
D	H01L 29/00	0	Semiconductor devices specially adapted for rectifying, amplifying, oscillating or switching and having potential barriers; Capacitors or resistors having potential barriers, e.g. a PN-junction depletion layer or carrier concentration layer; Details of semiconductor bodies or of electrodes thereof {; Multistep manufacturing processes therefor} (H01L 31/00 - H01L 33/00, H10K 10/00, H10N take precedence; details other than of semiconductor bodies or of electrodes	<administrative transfer to H10D 99/00>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			thereof H01L 23/00; devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00)	
D	H01L 29/02	1	Semiconductor bodies {; Multistep manufacturing processes therefor}	<administrative transfer to H10D 62/00>
D	H01L 29/04	2	characterised by their crystalline structure, e.g. polycrystalline, cubic or particular orientation of crystalline planes (characterised by physical imperfections H01L 29/30)	<administrative transfer to H10D 62/40>
D	H01L 29/045	3	{by their particular orientation of crystalline planes}	<administrative transfer to H10D 62/405>
D	H01L 29/06	2	characterised by their shape; characterised by the shapes, relative sizes, or dispositions of the semiconductor regions {; characterised by the concentration or distribution of impurities within semiconductor regions}	<administrative transfer to H10D 62/10>
D	H01L 29/0603	3	{characterised by particular constructional design considerations, e.g. for preventing surface leakage, for controlling electric field concentration or for internal isolations regions (isolation regions between components H01L 21/76; design considerations for integrated circuits H01L 27/00; geometrical design considerations for devices H01L 29/0657)}	<administrative transfer to H10D 62/10>
D	H01L 29/0607	4	{for preventing surface leakage or controlling electric field concentration}	<administrative transfer to H10D 62/102>
D	H01L 29/0611	5	{for increasing or controlling the breakdown voltage of reverse biased devices (H01L 29/0661 takes precedence)}	<administrative transfer to H10D 62/103>
D	H01L 29/0615	6	{by the doping profile or the shape or the arrangement of the PN junction, or with supplementary regions, e.g. junction termination extension [JTE] (LDD or drain offset regions H01L 29/7833)}	<administrative transfer to H10D 62/105>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/0619	7	{with a supplementary region doped oppositely to or in rectifying contact with the semiconductor containing or contacting region, e.g. guard rings with PN or Schottky junction}	<administrative transfer to H10D 62/106>
D	H01L 29/0623	8	{Buried supplementary region, e.g. buried guard ring (multi-RESURF H01L 29/0634)}	<administrative transfer to H10D 62/107>
D	H01L 29/0626	7	{with a localised breakdown region, e.g. built-in avalanching region (in self-protected thyristors H01L 29/7424)}	<administrative transfer to H10D 62/108>
D	H01L 29/063	7	{Reduced surface field [RESURF] pn-junction structures}	<administrative transfer to H10D 62/109>
D	H01L 29/0634	8	{Multiple reduced surface field (multi-RESURF) structures, e.g. double RESURF, charge compensation, cool, superjunction (SJ), 3D-RESURF, composite buffer (CB) structures}	<administrative transfer to H10D 62/111>
D	H01L 29/0638	5	{for preventing surface leakage due to surface inversion layer, e.g. with channel stopper (channel stoppers in combination with isolation region for integrated circuits H01L 21/762)}	<administrative transfer to H10D 62/112>
D	H01L 29/0642	4	{Isolation within the component, i.e. internal isolation}	<administrative transfer to H10D 62/113>
D	H01L 29/0646	5	{PN junctions}	<administrative transfer to H10D 62/114>
D	H01L 29/0649	5	{Dielectric regions, e.g. SiO_2 regions, air gaps}	<administrative transfer to H10D 62/115>
D	H01L 29/0653	6	{adjoining the input or output region of a field-effect device, e.g. the source or drain region}	<administrative transfer to H10D 62/116>
D	H01L 29/0657	3	{characterised by the shape of the body}	<administrative transfer to H10D 62/117>
D	H01L 29/0661	4	{specially adapted for altering the breakdown voltage by removing semiconductor material at, or in the neighbourhood of, a reverse biased junction, e.g. by bevelling, moat etching, depletion etching}	<administrative transfer to H10D 62/104>
D	H01L 29/0665	4	{the shape of the body defining a nanostructure (nanotechnology per se B82B)}	<administrative transfer to H10D 62/118>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/0669	5	{Nanowires or nanotubes (carbon nanotubes as material of solid-state device active part H10K 85/211)}	<administrative transfer to H10D 62/119>
D	H01L 29/0673	6	{oriented parallel to a substrate}	<administrative transfer to H10D 62/121>
D	H01L 29/0676	6	{oriented perpendicular or at an angle to a substrate}	<administrative transfer to H10D 62/122>
D	H01L 29/068	6	{comprising a junction}	<administrative transfer to H10D 62/123>
D	H01L 29/0684	3	{characterised by the shape, relative sizes or dispositions of the semiconductor regions or junctions between the regions}	<administrative transfer to H10D 62/124>
D	H01L 29/0688	4	{characterised by the particular shape of a junction between semiconductor regions}	<administrative transfer to H10D 62/125>
D	H01L 29/0692	4	{Surface layout}	<administrative transfer to H10D 62/126>
D	H01L 29/0696	5	{of cellular field-effect devices, e.g. multicellular DMOS transistors or IGBTs}	<administrative transfer to H10D 62/127>
D	H01L 29/08	3	with semiconductor regions connected to an electrode carrying current to be rectified, amplified or switched and such electrode being part of a semiconductor device which comprises three or more electrodes	<administrative transfer to H10D 62/13>
D	H01L 29/0804	4	{Emitter regions of bipolar transistors}	<administrative transfer to H10D 62/133>
D	H01L 29/0808	5	{of lateral transistors}	<administrative transfer to H10D 62/134>
D	H01L 29/0813	5	{Non-interconnected multi-emitter structures}	<administrative transfer to H10D 62/135>
D	H01L 29/0817	5	{of heterojunction bipolar transistors (H01L 29/7375 takes precedence)}	<administrative transfer to H10D 62/136>
D	H01L 29/0821	4	{Collector regions of bipolar transistors}	<administrative transfer to H10D 62/137>
D	H01L 29/0826	5	{Pedestal collectors}	<administrative transfer to H10D 62/138>
D	H01L 29/083	4	{Anode or cathode regions of thyristors or gated bipolar-mode devices}	<administrative transfer to H10D 62/141>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/0834	5	{Anode regions of thyristors or gated bipolar-mode devices, e.g. supplementary regions surrounding anode regions}	<administrative transfer to H10D 62/142>
D	H01L 29/0839	5	{Cathode regions of thyristors}	<administrative transfer to H10D 62/148>
D	H01L 29/0843	4	{Source or drain regions of field-effect devices}	<administrative transfer to H10D 62/149>
D	H01L 29/0847	5	{of field-effect transistors with insulated gate (H01L 29/0653 takes precedence; with a passive supplementary region between source or drain and substrate related to punch-through, capacity or isolation phenomena H01L 29/1079; with LDD or DDD structure H01L 29/7833; for thin film transistors H01L 29/78618)}	<administrative transfer to H10D 62/151>
D	H01L 29/0852	6	{of DMOS transistors}	<administrative transfer to H10D 62/152>
D	H01L 29/0856	7	{Source regions}	<administrative transfer to H10D 62/152>
D	H01L 29/086	8	{Impurity concentration or distribution}	<administrative transfer to H10D 62/153>
D	H01L 29/0865	8	{Disposition}	<administrative transfer to H10D 62/154>
D	H01L 29/0869	8	{Shape (cell layout H01L 29/0696)}	<administrative transfer to H10D 62/155>
D	H01L 29/0873	7	{Drain regions}	<administrative transfer to H10D 62/156>
D	H01L 29/0878	8	{Impurity concentration or distribution}	<administrative transfer to H10D 62/157>
D	H01L 29/0882	8	{Disposition}	<administrative transfer to H10D 62/158>
D	H01L 29/0886	8	{Shape}	<administrative transfer to H10D 62/159>
D	H01L 29/0891	5	{of field-effect transistors with Schottky gate}	<administrative transfer to H10D 62/161>
D	H01L 29/0895	4	{Tunnel injectors}	<administrative transfer to H10D 62/165>
D	H01L 29/10	3	with semiconductor regions connected to an electrode not carrying current to be rectified, amplified or switched and such electrode being	<administrative transfer to H10D 62/17>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			part of a semiconductor device which comprises three or more electrodes	
D	H01L 29/1004	4	{Base region of bipolar transistors}	<administrative transfer to H10D 62/177>
D	H01L 29/1008	5	{of lateral transistors}	<administrative transfer to H10D 62/184>
D	H01L 29/1012	4	{Base regions of thyristors (H01L 29/083 takes precedence)}	<administrative transfer to H10D 62/192>
D	H01L 29/1016	5	{Anode base regions of thyristors}	<administrative transfer to H10D 62/199>
D	H01L 29/102	5	{Cathode base regions of thyristors}	<administrative transfer to H10D 62/206>
D	H01L 29/1025	4	{Channel region of field-effect devices}	<administrative transfer to H10D 62/213>
D	H01L 29/1029	5	{of field-effect transistors}	<administrative transfer to H10D 62/221>
D	H01L 29/1033	6	{with insulated gate, e.g. characterised by the length, the width, the geometric contour or the doping structure (with channel and gate aligned in the lengthwise direction H01L 29/42376; with buried channel H01L 29/7838)}	<administrative transfer to H10D 62/235>
D	H01L 29/1037	7	{and non-planar channel (resulting from the gate electrode disposition, e.g. within a trench, H01L 29/42356)}	<administrative transfer to H10D 62/292>
D	H01L 29/1041	7	{with a non-uniform doping structure in the channel region surface}	<administrative transfer to H10D 62/299>
D	H01L 29/1045	8	{the doping structure being parallel to the channel length, e.g. DMOS like}	<administrative transfer to H10D 62/307>
D	H01L 29/105	7	{with vertical doping variation (H01L 29/7827 takes precedence)}	<administrative transfer to H10D 62/314>
D	H01L 29/1054	7	{with a variation of the composition, e.g. channel with strained layer for increasing the mobility}	<administrative transfer to H10D 30/751>
D	H01L 29/1058	6	{with PN junction gate}	<administrative transfer to H10D 62/328>
D	H01L 29/1062	5	{of charge coupled devices}	<administrative transfer to H10D 62/335>
D	H01L 29/1066	4	{Gate region of field-effect devices with PN junction gate}	<administrative transfer to H10D 62/343>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/107	4	{Substrate region of field-effect devices}	<administrative transfer to H10D 62/351>
D	H01L 29/1075	5	{of field-effect transistors}	<administrative transfer to H10D 62/357>
D	H01L 29/1079	6	{with insulated gate}	<administrative transfer to H10D 62/364>
D	H01L 29/1083	7	{with an inactive supplementary region, e.g. for preventing punch-through, improving capacity effect or leakage current}	<administrative transfer to H10D 62/371>
D	H01L 29/1087	7	{characterised by the contact structure of the substrate region, e.g. for controlling or preventing bipolar effect}	<administrative transfer to H10D 62/378>
D	H01L 29/1091	5	{of charge coupled devices}	<administrative transfer to H10D 62/386>
D	H01L 29/1095	4	{Body region, i.e. base region, of DMOS transistors or IGBTs (cell layout H01L 29/0696)}	<administrative transfer to H10D 62/393>
D	H01L 29/12	2	characterised by the materials of which they are formed	<administrative transfer to H10D 62/81>
D	H01L 29/122	3	{Single quantum well structures (single heterojunctions, couples of materials H01L 29/165, H01L 29/205, H01L 29/225, H01L 29/267)}	<administrative transfer to H10D 62/812>
D	H01L 29/125	4	{Quantum wire structures}	<administrative transfer to H10D 62/813>
D	H01L 29/127	4	{Quantum box structures}	<administrative transfer to H10D 62/814>
D	H01L 29/15	3	Structures with periodic or quasi periodic potential variation, e.g. multiple quantum wells, superlattices (such structures applied for the control of light G02F 1/017, applied in semiconductor lasers H01S 5/34)	<administrative transfer to H10D 62/815>
D	H01L 29/151	4	{Compositional structures (H01L 29/157 and H01L 29/158 take precedence)}	<administrative transfer to H10D 62/8161>
D	H01L 29/152	5	{with quantum effects only in vertical direction, i.e. layered structures with quantum effects solely resulting from vertical potential variation}	<administrative transfer to H10D 62/8162>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/154	6	{comprising at least one long range structurally disordered material, e.g. one-dimensional vertical amorphous superlattices}	<administrative transfer to H10D 62/8163>
D	H01L 29/155	6	{Comprising only semiconductor materials (H01L 29/154 takes precedence)}	<administrative transfer to H10D 62/8164>
D	H01L 29/157	4	{Doping structures, e.g. doping superlattices, nipi superlattices (delta doping in general H01L 29/365)}	<administrative transfer to H10D 62/8171>
D	H01L 29/158	4	{Structures without potential periodicity in a direction perpendicular to a major surface of the substrate, i.e. vertical direction, e.g. lateral superlattices, lateral surface superlattices [LSS]}	<administrative transfer to H10D 62/8181>
D	H01L 29/16	3	including, apart from doping materials or other impurities, only elements of Group IV of the Periodic Table	<administrative transfer to H10D 62/83>
D	H01L 29/1602	4	{Diamond}	<administrative transfer to H10D 62/8303>
D	H01L 29/1604	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/83 simultaneously>
D	H01L 29/1606	4	{Graphene}	<administrative transfer to H10D 62/882>
D	H01L 29/1608	4	{Silicon carbide}	<administrative transfer to H10D 62/8325>
D	H01L 29/161	4	including two or more of the elements provided for in group H01L 29/16 {, e.g. alloys (H01L 29/1604 takes precedence)}	<administrative transfer to H10D 62/832>
D	H01L 29/165	5	in different semiconductor regions {, e.g. heterojunctions}	<administrative transfer to H10D 62/822>
D	H01L 29/167	4	further characterised by the doping material {(H01L 29/1604 takes precedence)}	<administrative transfer to H10D 62/834>
D	H01L 29/18	3	Selenium or tellurium only, apart from doping materials or other impurities	<administrative transfer to H10D 62/84>
D	H01L 29/185	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/84 simultaneously>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/20	3	including, apart from doping materials or other impurities, only $A_{III}B_{V}$ compounds	<administrative transfer to H10D 62/85>
D	H01L 29/2003	4	{Nitride compounds}	<administrative transfer to H10D 62/8503>
D	H01L 29/2006	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/85 simultaneously>
D	H01L 29/201	4	including two or more compounds {, e.g. alloys (H01L 29/2006 takes precedence)}	<administrative transfer to H10D 62/852>
D	H01L 29/205	5	in different semiconductor regions {, e.g. heterojunctions}	<administrative transfer to H10D 62/824>
D	H01L 29/207	4	further characterised by the doping material {(H01L 29/2006 takes precedence)}	<administrative transfer to H10D 62/854>
D	H01L 29/22	3	including, apart from doping materials or other impurities, only $A_{II}B_{VI}$ compounds	<administrative transfer to H10D 62/86>
D	H01L 29/2203	4	{Cd X compounds being one element of the 6th group of the Periodic Table (H01L 29/2206 takes precedence)}	<administrative transfer to H10D 62/8603>
D	H01L 29/2206	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/86 simultaneously>
D	H01L 29/221	4	including two or more compounds {, e.g. alloys (H01L 29/2206 takes precedence)}	<administrative transfer to H10D 62/862>
D	H01L 29/225	5	in different semiconductor regions {, e.g. heterojunctions}	<administrative transfer to H10D 62/826>
D	H01L 29/227	4	further characterised by the doping material {(H01L 29/2206 takes precedence)}	<administrative transfer to H10D 62/864>
D	H01L 29/24	3	including, apart from doping materials or other impurities, only semiconductor materials not provided for in groups H01L 29/16, H01L 29/18, H01L 29/20, H01L 29/22 (including organic materials H10K 99/00)	<administrative transfer to H10D 62/80>
D	H01L 29/242	4	{$A_{I}B_{VI}$ or $A_{I}B_{VII}$ compounds, e.g. Cu_2O, Cu I (H01L 29/247 takes precedence)}	<administrative transfer to H10D 62/871>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/245	4	{Pb compounds, e.g. PbO (H01L 29/247 takes precedence)}	<administrative transfer to H10D 62/874>
D	H01L 29/247	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/80 simultaneously >
D	H01L 29/26	3	including, apart from doping materials or other impurities, elements provided for in two or more of the groups H01L 29/16, H01L 29/18, H01L 29/20, H01L 29/22, H01L 29/24 {, e.g. alloys}	<administrative transfer to H10D 62/80>
D	H01L 29/263	4	{Amorphous materials}	<administrative transfer to H10D 62/402 and H10D 62/80 simultaneously>
D	H01L 29/267	4	in different semiconductor regions {, e.g. heterojunctions (H01L 29/263 takes precedence)}	<administrative transfer to H10D 62/82>
D	H01L 29/30	2	characterised by physical imperfections; having polished or roughened surface	<administrative transfer to H10D 62/50>
D	H01L 29/32	3	the imperfections being within the semiconductor body	<administrative transfer to H10D 62/53>
D	H01L 29/34	3	the imperfections being on the surface	<administrative transfer to H10D 62/57>
D	H01L 29/36	2	characterised by the concentration or distribution of impurities {in the bulk material (within semiconductor regions H01L 29/06)}	<administrative transfer to H10D 62/60>
D	H01L 29/365	3	{Planar doping, e.g. atomic-plane doping, delta-doping}	<administrative transfer to H10D 62/605>
D	H01L 29/40	1	Electrodes {; Multistep manufacturing processes therefor}	<administrative transfer to H10D 64/00>
D	H01L 29/401	2	{Multistep manufacturing processes}	<administrative transfer to H10D 64/01>
D	H01L 29/4011	3	{for data storage electrodes}	<administrative transfer to H10D 64/031>
D	H01L 29/40111	4	{the electrodes comprising a layer which is used for its ferroelectric properties}	<administrative transfer to H10D 64/033>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/40114	4	{the electrodes comprising a conductor-insulator-conductor-insulator-semiconductor structure}	<administrative transfer to H10D 64/035>
D	H01L 29/40117	4	{the electrodes comprising a charge-trapping insulator}	<administrative transfer to H10D 64/037>
D	H01L 29/402	2	{Field plates}	<administrative transfer to H10D 64/111>
D	H01L 29/404	3	{Multiple field plate structures}	<administrative transfer to H10D 64/112>
D	H01L 29/405	3	{Resistive arrangements, e.g. resistive or semi-insulating field plates}	<administrative transfer to H10D 64/115>
D	H01L 29/407	3	{Recessed field plates, e.g. trench field plates, buried field plates}	<administrative transfer to H10D 64/117>
D	H01L 29/408	2	{with an insulating layer with a particular dielectric or electrostatic property, e.g. with static charges or for controlling trapped charges or moving ions, or with a plate acting on the insulator potential or the insulator charges, e.g. for controlling charges effect or potential distribution in the insulating layer, or with a semi-insulating layer contacting directly the semiconductor surface}	<administrative transfer to H10D 64/118>
D	H01L 29/41	2	characterised by their shape, relative sizes or dispositions	<administrative transfer to H10D 64/20>
D	H01L 29/413	3	{Nanosized electrodes, e.g. nanowire electrodes comprising one or a plurality of nanowires (nanosized carbon materials, e.g. carbon nanotubes, per se C01B 32/15; transparent electrodes comprising carbon nano-tubes H10K 30/821, nanotechnology per se B82B)}	<administrative transfer to H10D 64/205>
D	H01L 29/417	3	carrying the current to be rectified, amplified or switched	<administrative transfer to H10D 64/23>
D	H01L 29/41708	4	{Emitter or collector electrodes for bipolar transistors}	<administrative transfer to H10D 64/231>
D	H01L 29/41716	4	{Cathode or anode electrodes for thyristors}	<administrative transfer to H10D 64/233>
D	H01L 29/41725	4	{Source or drain electrodes for field effect devices (with monocrystalline semiconductor on source/drain region H01L 29/0843)}	<administrative transfer to H10D 64/251>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/41733	5	{for thin film transistors with insulated gate}	<administrative transfer to H10D 30/6729>
D	H01L 29/41741	5	{for vertical or pseudo-vertical devices}	<administrative transfer to H10D 64/252>
D	H01L 29/4175	5	{for lateral devices where the connection to the source or drain region is done through at least one part of the semiconductor substrate thickness, e.g. with connecting sink or with via-hole}	<administrative transfer to H10D 64/254>
D	H01L 29/41758	5	{for lateral devices with structured layout for source or drain region, i.e. the source or drain region having cellular, interdigitated or ring structure or being curved or angular (H01L 29/41733 - H01L 29/4175 take precedence)}	<administrative transfer to H10D 64/257>
D	H01L 29/41766	5	{with at least part of the source or drain electrode having contact below the semiconductor surface, e.g. the source or drain electrode formed at least partially in a groove or with inclusions of conductor inside the semiconductor (H01L 29/41733 - H01L 29/41758 take precedence)}	<administrative transfer to H10D 64/256>
D	H01L 29/41775	5	{characterised by the proximity or the relative position of the source or drain electrode and the gate electrode, e.g. the source or drain electrode separated from the gate electrode by side-walls or spreading around or above the gate electrode}	<administrative transfer to H10D 64/258>
D	H01L 29/41783	6	{Raised source or drain electrodes self aligned with the gate}	<administrative transfer to H10D 64/259>
D	H01L 29/41791	5	{for transistors with a horizontal current flow in a vertical sidewall, e.g. FinFET, MuGFET}	<administrative transfer to H10D 30/6219>
D	H01L 29/423	3	not carrying the current to be rectified, amplified or switched	<administrative transfer to H10D 64/27>
D	H01L 29/42304	4	{Base electrodes for bipolar transistors}	<administrative transfer to H10D 64/281>
D	H01L 29/42308	4	{Gate electrodes for thyristors}	<administrative transfer to H10D 64/291>
D	H01L 29/42312	4	{Gate electrodes for field effect devices}	<administrative transfer to H10D 64/311>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/42316	5	{for field-effect transistors}	<administrative transfer to H10D 64/411>
D	H01L 29/4232	6	{with insulated gate}	<administrative transfer to H10D 64/511>
D	H01L 29/42324	7	{Gate electrodes for transistors with a floating gate}	<administrative transfer to H10D 30/6891>
D	H01L 29/42328	8	{with at least one additional gate other than the floating gate and the control gate, e.g. program gate, erase gate or select gate}	<administrative transfer to H10D 30/6892>
D	H01L 29/42332	8	{with the floating gate formed by two or more non connected parts, e.g. multi-particles flating gate}	<administrative transfer to H10D 30/6893>
D	H01L 29/42336	8	{with one gate at least partly formed in a trench}	<administrative transfer to H10D 30/6894>
D	H01L 29/4234	7	{Gate electrodes for transistors with charge trapping gate insulator}	<administrative transfer to H10D 30/694>
D	H01L 29/42344	8	{with at least one additional gate, e.g. program gate, erase gate or select gate}	<administrative transfer to H10D 30/696>
D	H01L 29/42348	8	{with trapping site formed by at least two separated sites, e.g. multi-particles trapping site}	<administrative transfer to H10D 30/697>
D	H01L 29/42352	8	{with the gate at least partly formed in a trench}	<administrative transfer to H10D 30/699>
D	H01L 29/42356	7	{Disposition, e.g. buried gate electrode (H01L 29/42324 and H01L 29/4234 take precedence)}	<administrative transfer to H10D 64/512>
D	H01L 29/4236	8	{within a trench, e.g. trench gate electrode, groove gate electrode}	<administrative transfer to H10D 64/513>
D	H01L 29/42364	7	{characterised by the insulating layer, e.g. thickness or uniformity (H01L 29/42324 and H01 L 29/4234 take precedence)}	<administrative transfer to H10D 64/514>
D	H01L 29/42368	8	{the thickness being non-uniform}	<administrative transfer to H10D 64/516>
D	H01L 29/42372	7	{characterised by the conducting layer, e.g. the length, the sectional shape or the lay-out (H01L 29/42324 takes precedence)}	<administrative transfer to H10D 64/517>
D	H01L 29/42376	8	{characterised by the length or the sectional shape}	<administrative transfer to H10D 64/518>
D	H01L 29/4238	8	{characterised by the surface lay-out}	<administrative transfer to H10D 64/519>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/42384	7	{for thin film field effect transistors, e.g. characterised by the thickness or the shape of the insulator or the dimensions, the shape or the lay-out of the conductor}	<administrative transfer to H10D 30/673>
D	H01L 2029/42388	8	{characterised by the shape of the insulating material}	<administrative transfer to H10D 30/6736>
D	H01L 29/42392	8	{fully surrounding the channel, e.g. gate-all-around}	<administrative transfer to H10D 30/6735>
D	H01L 29/42396	5	{for charge coupled devices}	<administrative transfer to H10D 44/45>
D	H01L 29/43	2	characterised by the materials of which they are formed	<administrative transfer to H10D 64/60>
D	H01L 29/432	3	{Heterojunction gate for field effect devices}	<administrative transfer to H10D 64/602>
D	H01L 29/435	3	{Resistive materials for field effect devices, e.g. resistive gate for MOSFET or MESFET}	<administrative transfer to H10D 64/605>
D	H01L 29/437	3	{Superconductor materials}	<administrative transfer to H10D 64/608>
D	H01L 29/45	3	Ohmic electrodes	<administrative transfer to H10D 64/62>
D	H01L 29/452	4	{on AIII-BV compounds}	<administrative transfer to H10D 62/85 and H10D 64/62 simultaneously>
D	H01L 29/454	5	{on thin film AIII-BV compounds}	<administrative transfer to H10D 30/6737 and H10D 30/675 simultaneously>
D	H01L 29/456	4	{on silicon}	<administrative transfer to H10D 62/83 and H10D 64/62 simultaneously>
D	H01L 29/458	5	{for thin film silicon, e.g. source or drain electrode}	<administrative transfer to H10D 30/6737 and H10D 30/6743 simultaneously>
D	H01L 29/47	3	Schottky barrier electrodes {(H01L 29/435 takes precedence)}	<administrative transfer to H10D 64/64>
D	H01L 29/475	4	{on AIII-BV compounds}	<administrative transfer to H10D 30/6738, H10D 30/675, H10D 62/85 and H10D 64/64 simultaneously>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/49	3	Metal-insulator-semiconductor electrodes, {e.g. gates of MOSFET (H01L 29/435 takes precedence)}	<administrative transfer to H10D 64/66>
D	H01L 29/4908	4	{for thin film semiconductor, e.g. gate of TFT}	<administrative transfer to H10D 30/6739>
D	H01L 29/4916	4	{the conductor material next to the insulator being a silicon layer, e.g. polysilicon doped with boron, phosphorus or nitrogen (H01L 29/4908, H01L 29/4983 take precedence)}	<administrative transfer to H10D 64/661>
D	H01L 29/4925	5	{with a multiple layer structure, e.g. several silicon layers with different crystal structure or grain arrangement (with only a vertical doping structure or vertical doping variation H01L 29/4916)}	<administrative transfer to H10D 64/662>
D	H01L 29/4933	6	{with a silicide layer contacting the silicon layer, e.g. Polycide gate (with a barrier layer between the silicide and silicon layers H01L 29/4941)}	<administrative transfer to H10D 64/663>
D	H01L 29/4941	6	{with a barrier layer between the silicon and the metal or metal silicide upper layer, e.g. Silicide/TiN/Polysilicon}	<administrative transfer to H10D 64/664>
D	H01L 29/495	4	{the conductor material next to the insulator being a simple metal, e.g. W, Mo (H01L 29/4908, H01L 29/4983 take precedence)}	<administrative transfer to H10D 64/665>
D	H01L 29/4958	5	{with a multiple layer structure}	<administrative transfer to H10D 64/666>
D	H01L 29/4966	4	{the conductor material next to the insulator being a composite material, e.g. organic material, TiN, $MoSi_2$ (H01L 29/4908, H01L 29/4983 take precedence)}	<administrative transfer to H10D 64/667>
D	H01L 29/4975	5	{being a silicide layer, e.g. $TiSi_2$}	<administrative transfer to H10D 64/668>
D	H01L 29/4983	4	{with a lateral structure, e.g. a Polysilicon gate with a lateral doping variation or with a lateral composition variation or characterised by the sidewalls being	<administrative transfer to H10D 64/671>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			composed of conductive, resistive or dielectric material}	
D	H01L 29/4991	5	{comprising an air gap}	<administrative transfer to H10D 64/679>
D	H01L 29/51	4	Insulating materials associated therewith {(for MIS structures on thin film semiconductor H01L 29/4908)}	<administrative transfer to H10D 64/68>
D	H01L 29/511	5	{with a compositional variation, e.g. multilayer structures (H01L 29/516 takes precedence)}	<administrative transfer to H10D 64/681>
D	H01L 29/512	6	{the variation being parallel to the channel plane}	<administrative transfer to H10D 64/683>
D	H01L 29/513	6	{the variation being perpendicular to the channel plane}	<administrative transfer to H10D 64/685>
D	H01L 29/515	5	{with cavities, e.g. containing a gas}	<administrative transfer to H10D 64/687>
D	H01L 29/516	5	{with at least one ferroelectric layer}	<administrative transfer to H10D 64/689>
D	H01L 29/517	5	{the insulating material comprising a metallic compound, e.g. metal oxide, metal silicate (H01L 29/518 takes precedence)}	<administrative transfer to H10D 64/691>
D	H01L 29/518	5	{the insulating material containing nitrogen, e.g. nitride, oxynitride, nitrogen-doped material}	<administrative transfer to H10D 64/693>
D	H01L 29/66	1	Types of semiconductor device {; Multistep manufacturing processes therefor}	<administrative transfer to H10D 48/30>
D	H01L 29/66007	2	{Multistep manufacturing processes}	<administrative transfer to H10D 48/01>
D	H01L 29/66015	3	{of devices having a semiconductor body comprising semiconducting carbon, e.g. diamond, diamond-like carbon, graphene}	<administrative transfer to H10D 48/01 and H10D 62/8303 simultaneously>
D	H01L 29/66022	4	{the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}	<administrative transfer to H10D 48/021 and H10D 62/8303 simultaneously >

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/6603	5	{Diodes}	<administrative transfer to H10D 8/051 and H10D 62/8303 simultaneously>
D	H01L 29/66037	4	{the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}	<administrative transfer to H10D 48/031 and H10D 62/8303 simultaneously>
D	H01L 29/66045	5	{Field-effect transistors}	<administrative transfer to H10D 30/01 and H10D 62/8303 simultaneously>
D	H01L 29/66053	3	{of devices having a semiconductor body comprising crystalline silicon carbide}	<administrative transfer to H10D 48/01 and H10D 62/8325 simultaneously>
D	H01L 29/6606	4	{the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}	<administrative transfer to H10D 8/051 and H10D 62/8325 simultaneously>
D	H01L 29/66068	4	{the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}	<administrative transfer to H10D 12/031 and H10D 62/8325 simultaneously>
D	H01L 29/66075	3	{of devices having semiconductor bodies comprising group 14 or group 13/15 materials (comprising semiconducting carbon H01L 29/66015; comprising crystalline silicon carbide H01L 29/66053)}	<administrative transfer to H10D 48/01>
D	H01L 29/66083	4	{the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}	<administrative transfer to H10D 48/021>
D	H01L 29/6609	5	{Diodes}	<administrative transfer to H10D 8/01>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/66098	6	{Breakdown diodes}	<administrative transfer to H10D 8/021>
D	H01L 29/66106	7	{Zener diodes}	<administrative transfer to H10D 8/022>
D	H01L 29/66113	7	{Avalanche diodes}	<administrative transfer to H10D 8/024>
D	H01L 29/66121	6	{Multilayer diodes, e.g. PNPN diodes}	<administrative transfer to H10D 8/041>
D	H01L 29/66128	6	{Planar diodes}	<administrative transfer to H10D 8/043>
D	H01L 29/66136	6	{PN junction diodes}	<administrative transfer to H10D 8/045>
D	H01L 29/66143	6	{Schottky diodes}	<administrative transfer to H10D 8/051>
D	H01L 29/66151	6	{Tunnel diodes (group 13/15 resonant tunneling diodes H01L 29/66219)}	<administrative transfer to H10D 8/053>
D	H01L 29/66159	6	{Transit time diodes, e.g. IMPATT, TRAPATT diodes}	<administrative transfer to H10D 8/055>
D	H01L 29/66166	5	{Resistors with PN junction}	<administrative transfer to H10D 1/025>
D	H01L 29/66174	5	{Capacitors with PN or Schottky junction, e.g. varactors (capacitors with PN junction combined with MOS control H01L 29/66189)}	<administrative transfer to H10D 1/045>
D	H01L 29/66181	5	{Conductor-insulator-semiconductor capacitors, e.g. trench capacitors}	<administrative transfer to H10D 1/047>
D	H01L 29/66189	6	{with PN junction, e.g. hybrid capacitors}	<administrative transfer to H10D 1/048>
D	H01L 29/66196	5	{with an active layer made of a group 13/15 material}	<administrative transfer to H10D 48/021>
D	H01L 29/66204	6	{Diodes}	<administrative transfer to H10D 8/043>
D	H01L 29/66212	7	{Schottky diodes}	<administrative transfer to H10D 8/051>
D	H01L 29/66219	7	{with a heterojunction, e.g. resonant tunneling diodes [RTD]}	<administrative transfer to H10D 8/053>
D	H01L 29/66227	4	{the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}	<administrative transfer to H10D 48/031>
D	H01L 29/66234	5	{Bipolar junction transistors [BJT]}	<administrative transfer to H10D 10/01>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/66242	6	{Heterojunction transistors [HBT] (with an active layer made of a group 13/15 material H01L 29/66318)}	<administrative transfer to H10D 10/021>
D	H01L 29/6625	6	{Lateral transistors (H01L 29/66242 and H01 L 29/66265 take precedence)}	<administrative transfer to H10D 10/061>
D	H01L 29/66257	6	{Schottky transistors}	<administrative transfer to H10D 10/031>
D	H01L 29/66265	6	{Thin film bipolar transistors (H01L 29/66242 takes precedence)}	<administrative transfer to H10D 10/041>
D	H01L 29/66272	6	{Silicon vertical transistors (H01L 29/66242, H01L 29 /66257 and H01L 29/66265 take precedence)}	<administrative transfer to H10D 10/051>
D	H01L 29/6628	7	{Inverse transistors}	<administrative transfer to H10D 10/052>
D	H01L 29/66287	7	{with a single crystalline emitter, collector or base including extrinsic, link or graft base formed on the silicon substrate, e.g. by epitaxy, recrystallisation, after insulating device isolation (H01L 29/6628 takes precedence)}	<administrative transfer to H10D 10/054>
D	H01L 29/66295	7	{with main current going through the whole silicon substrate, e.g. power bipolar transistor}	<administrative transfer to H10D 10/056>
D	H01L 29/66303	8	{with multi-emitter, e.g. interdigitated, multi-cellular or distributed emitter}	<administrative transfer to H10D 10/058>
D	H01L 29/6631	6	{with an active layer made of a group 13/15 material}	<administrative transfer to H10D 10/01>
D	H01L 29/66318	7	{Heterojunction transistors}	<administrative transfer to H10D 10/021>
D	H01L 29/66325	6	{controlled by field-effect, e.g. insulated gate bipolar transistors [IGBT]}	<administrative transfer to H10D 12/01>
D	H01L 29/66333	7	{Vertical insulated gate bipolar transistors}	<administrative transfer to H10D 12/032>
D	H01L 29/6634	8	{with a recess formed by etching in the source/emitter contact region (H01L 29/66348 takes	<administrative transfer to H10D 12/035>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			precedence; etching of semiconductor bodies H01L 21/302)}	
D	H01L 29/66348	8	{with a recessed gate}	<administrative transfer to H10D 12/038>
D	H01L 29/66356	5	{Gated diodes, e.g. field controlled diodes [FCD], static induction thyristors [SITh], field controlled thyristors [FCTh]}	<administrative transfer to H10D 12/021>
D	H01L 29/66363	5	{Thyristors}	<administrative transfer to H10D 18/01>
D	H01L 29/66371	6	{structurally associated with another device, e.g. built-in diode (making integrated circuits H01L 21/82)}	<administrative transfer to H10D 84/0102>
D	H01L 29/66378	7	{the other device being a controlling field-effect device}	<administrative transfer to H10D 84/0105>
D	H01L 29/66386	6	{Bidirectional thyristors}	<administrative transfer to H10D 18/021>
D	H01L 29/66393	6	{Lateral or planar thyristors}	<administrative transfer to H10D 18/031>
D	H01L 29/66401	6	{with an active layer made of a group 13/15 material}	<administrative transfer to H10D 18/01>
D	H01L 29/66409	5	{Unipolar field-effect transistors}	<administrative transfer to H10D 30/01>
D	H01L 29/66416	6	{Static induction transistors [SIT] (with an active layer made of a group 13/15 material H01L 29/66454)}	<administrative transfer to H10D 30/012>
D	H01L 29/66424	7	{Permeable base transistors [PBT]}	<administrative transfer to H10D 30/012>
D	H01L 29/66431	6	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT (with an active layer made of a group 13/15 material H01L 29/66462)}	<administrative transfer to H10D 30/015>
D	H01L 29/66439	6	{with a one- or zero-dimensional channel, e.g. quantum wire FET, in-plane gate transistor [IPG], single electron transistor [SET], striped channel transistor, Coulomb blockade transistor (with an active layer made of a group 13/15 material H01L 29/66469)}	<administrative transfer to H10D 30/014>
D	H01L 29/66446	6	{with an active layer made of a group 13/15 material, e.g. group 13/15	<administrative transfer to H10D 30/01>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			velocity modulation transistor [VMT], group 13/15 negative resistance FET [NERFET]}	
D	H01L 29/66454	7	{Static induction transistors [SIT], e.g. permeable base transistors [PBT]}	<administrative transfer to H10D 30/012>
D	H01L 29/66462	7	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT}	<administrative transfer to H10D 30/015>
D	H01L 29/66469	7	{with one- or zero-dimensional channel, e.g. quantum wire field-effect transistors, in-plane gate transistors [IPG], single electron transistors [SET], Coulomb blockade transistors, striped channel transistors}	<administrative transfer to H10D 30/014>
D	H01L 29/66477	6	{with an insulated gate, i.e. MISFET}	<administrative transfer to H10D 30/021>
D	H01L 29/66484	7	{with multiple gate, at least one gate being an insulated gate (H01L 29/66742 takes precedence)}	<administrative transfer to H10D 30/023>
D	H01L 29/66492	7	{with a pocket or a lightly doped drain selectively formed at the side of the gate}	<administrative transfer to H10D 30/022>
D	H01L 29/665	7	{using self aligned silicidation, i.e. salicide (formation of conductive layers comprising silicides H01L 21/28518)}	<administrative transfer to H10D 30/0212>
D	H01L 29/66507	8	{providing different silicide thicknesses on the gate and on source or drain}	<administrative transfer to H10D 30/0213>
D	H01L 29/66515	7	{using self aligned selective metal deposition simultaneously on the gate and on source or drain}	<administrative transfer to H10D 30/0215>
D	H01L 29/66522	7	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}	<administrative transfer to H10D 30/021>
D	H01L 29/6653	7	{using the removal of at least part of spacer, e.g. disposable spacer}	<administrative transfer to H10D 64/015>
D	H01L 29/66537	7	{using a self aligned punch through stopper or threshold implant under the gate region (H01L 29/66606 takes precedence)}	<administrative transfer to H10D 30/0217>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/66545	7	{using a dummy, i.e. replacement gate in a process wherein at least a part of the final gate is self aligned to the dummy gate}	<administrative transfer to H10D 64/017>
D	H01L 29/66553	7	{using inside spacers, permanent or not}	<administrative transfer to H10D 64/018>
D	H01L 29/6656	7	{using multiple spacer layers, e.g. multiple sidewall spacers}	<administrative transfer to H10D 64/021>
D	H01L 29/66568	7	{Lateral single gate silicon transistors}	<administrative transfer to H10D 30/027>
D	H01L 29/66575	8	{where the source and drain or source and drain extensions are self-aligned to the sides of the gate (H01L 29/66606 takes precedence)}	<administrative transfer to H10D 30/0223>
D	H01L 29/66583	9	{with initial gate mask or masking layer complementary to the prospective gate location, e.g. with dummy source and drain contacts}	<administrative transfer to H10D 30/0225>
D	H01L 29/6659	9	{with both lightly doped source and drain extensions and source and drain self-aligned to the sides of the gate, e.g. lightly doped drain [LDD] MOSFET, double diffused drain [DDD] MOSFET}	<administrative transfer to H10D 30/0227>
D	H01L 29/66598	10	{forming drain [D] and lightly doped drain [LDD] simultaneously, e.g. using implantation through the wings a T-shaped layer, or through a specially shaped layer}	<administrative transfer to H10D 30/0229>
D	H01L 29/66606	8	{with final source and drain contacts formation strictly before final or dummy gate formation, e.g. contact first technology (H01L 29/66621 takes precedence)}	<administrative transfer to H10D 30/0273>
D	H01L 29/66613	8	{with a gate recessing step, e.g. using local oxidation (making recessed gate LDMOS transistors H01L 29/66704)}	<administrative transfer to H10D 64/025>
D	H01L 29/66621	9	{using etching to form a recess at the gate location (etching of semiconductor bodies H01L 21/302)}	<administrative transfer to H10D 64/027>
D	H01L 29/66628	9	{recessing the gate by forming single crystalline semiconductor material at the source or drain location}	<administrative transfer to H10D 30/0275>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/66636	8	{with source or drain recessed by etching or first recessed by etching and then refilled}	<administrative transfer to H10D 62/021>
D	H01L 29/66643	8	{with source or drain regions formed by a Schottky barrier or a conductor-insulator-semiconductor structure}	<administrative transfer to H10D 30/0277>
D	H01L 29/66651	8	{with a single crystalline channel formed on the silicon substrate after insulating device isolation}	<administrative transfer to H10D 30/0278>
D	H01L 29/66659	8	{with asymmetry in the channel direction, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}	<administrative transfer to H10D 30/0221>
D	H01L 29/66666	7	{Vertical transistors (H01L 29/66712, H01L 29/66742 take precedence)}	<administrative transfer to H10D 30/025>
D	H01L 29/66674	7	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (making lateral high-voltage MISFETs with channel well and drain offset region H01L 29/66659)}	<administrative transfer to H10D 30/028>
D	H01L 29/66681	8	{Lateral DMOS transistors, i.e. LDMOS transistors}	<administrative transfer to H10D 30/0281>
D	H01L 29/66689	9	{with a step of forming an insulating sidewall spacer (forming insulating material on a substrate H01L 21/02107)}	<administrative transfer to H10D 30/0285>
D	H01L 29/66696	9	{with a step of recessing the source electrode}	<administrative transfer to H10D 30/0287>
D	H01L 29/66704	9	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}	<administrative transfer to H10D 30/0289>
D	H01L 29/66712	8	{Vertical DMOS transistors, i.e. VDMOS transistors}	<administrative transfer to H10D 30/0291>
D	H01L 29/66719	9	{With a step of forming an insulating sidewall spacer}	<administrative transfer to H10D 30/0293>
D	H01L 29/66727	9	{with a step of recessing the source electrode}	<administrative transfer to H10D 30/0295>
D	H01L 29/66734	9	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}	<administrative transfer to H10D 30/0297>
D	H01L 29/66742	7	{Thin film unipolar transistors}	<administrative transfer to H10D 30/031>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/6675	8	{Amorphous silicon or polysilicon transistors}	<administrative transfer to H10D 30/0321>
D	H01L 29/66757	9	{Lateral single gate single channel transistors with non-inverted structure, i.e. the channel layer is formed before the gate}	<administrative transfer to H10D 30/0314 and H10D 30/0321 simultaneously>
D	H01L 29/66765	9	{Lateral single gate single channel transistors with inverted structure, i.e. the channel layer is formed after the gate}	<administrative transfer to H10D 30/0316 and H10D 30/0321 simultaneously>
D	H01L 29/66772	8	{Monocristalline silicon transistors on insulating substrates, e.g. quartz substrates (H01L 29/66666 takes precedence; thin film FinFETs H01L 29/66795)}	<administrative transfer to H10D 30/0323>
D	H01L 29/6678	9	{on sapphire substrates, e.g. SOS transistors}	<administrative transfer to H10D 30/0327 and H10D 30/0323 simultaneously >
D	H01L 29/66787	7	{with a gate at the side of the channel}	<administrative transfer to H10D 30/026>
D	H01L 29/66795	8	{with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 30/024>
D	H01L 29/66803	9	{with a step of doping the vertical sidewall, e.g. using tilted or multi-angled implants}	<administrative transfer to H10D 30/0241>
D	H01L 29/6681	9	{using dummy structures having essentially the same shape as the semiconductor body, e.g. to provide stability}	<administrative transfer to H10D 30/0243>
D	H01L 29/66818	9	{the channel being thinned after patterning, e.g. sacrificial oxidation on fin}	<administrative transfer to H10D 30/0245>
D	H01L 29/66825	7	{with a floating gate (H01L 29/6684 takes precedence)}	<administrative transfer to H10D 30/0411>
D	H01L 29/66833	7	{with a charge trapping gate insulator, e.g. MNOS transistors}	<administrative transfer to H10D 30/0413>
D	H01L 29/6684	7	{with a ferroelectric gate insulator}	<administrative transfer to H10D 30/0415>
D	H01L 29/66848	6	{with a Schottky gate, i.e. MESFET}	<administrative transfer to H10D 30/061 and H10D 62/83 simultaneously>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/66856	7	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}	<administrative transfer to H10D 30/061>
D	H01L 29/66863	8	{Lateral single gate transistors}	<administrative transfer to H10D 30/0612>
D	H01L 29/66871	9	{Processes wherein the final gate is made after the formation of the source and drain regions in the active layer, e.g. dummy-gate processes}	<administrative transfer to H10D 30/0614>
D	H01L 29/66878	9	{Processes wherein the final gate is made before the formation, e.g. activation anneal, of the source and drain regions in the active layer}	<administrative transfer to H10D 30/0616>
D	H01L 29/66886	9	{Lateral transistors with two or more independent gates}	<administrative transfer to H10D 30/0618>
D	H01L 29/66893	6	{with a PN junction gate, i.e. JFET}	<administrative transfer to H10D 30/051>
D	H01L 29/66901	7	{with a PN homojunction gate}	<administrative transfer to H10D 30/0512>
D	H01L 29/66909	8	{Vertical transistors, e.g. tecnetrons}	<administrative transfer to H10D 30/0515>
D	H01L 29/66916	7	{with a PN heterojunction gate}	<administrative transfer to H10D 30/0516>
D	H01L 29/66924	7	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}	<administrative transfer to H10D 30/051>
D	H01L 29/66931	5	{BJT-like unipolar transistors, e.g. hot electron transistors [HET], metal base transistors [MBT], resonant tunneling transistor [RTT], bulk barrier transistor [BBT], planar doped barrier transistor [PDBT], charge injection transistor [CHINT]}	<administrative transfer to H10D 48/032>
D	H01L 29/66939	6	{with an active layer made of a group 13/15 material}	<administrative transfer to H10D 48/032>
D	H01L 29/66946	5	{Charge transfer devices}	<administrative transfer to H10D 44/01>
D	H01L 29/66954	6	{with an insulated gate}	<administrative transfer to H10D 44/041>
D	H01L 29/66962	6	{with a Schottky gate}	<administrative transfer to H10D 44/061>
D	H01L 29/66969	3	{of devices having semiconductor bodies not comprising group 14 or group 13/15 materials (comprising	<administrative transfer to H10D 99/00>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials, comprising cuprous oxide or cuprous iodide H01L 21/02365)}	
D	H01L 29/66977	2	{Quantum effect devices, e.g. using quantum reflection, diffraction or interference effects, i.e. Bragg- or Aharonov-Bohm effects}	<administrative transfer to H10D 48/383>
D	H01L 29/66984	2	{Devices using spin polarized carriers}	<administrative transfer to H10D 48/385>
D	H01L 29/66992	2	{controllable only by the variation of applied heat (controllable by IR radiation H01L 31/00; measuring quantity of heat G01K 17/00)}	<administrative transfer to H10D 48/387>
D	H01L 29/68	2	controllable by only the electric current supplied, or only the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched	<administrative transfer to H10D 48/32>
D	H01L 29/685	3	{Hi-Lo semiconductor devices, e.g. memory devices}	<administrative transfer to H10D 48/366>
D	H01L 29/70	3	Bipolar devices	<administrative transfer to H10D 48/34>
D	H01L 29/705	4	{Double base diodes}	<administrative transfer to H10D 48/341>
D	H01L 29/72	4	Transistor-type devices, i.e. able to continuously respond to applied control signals	<administrative transfer to H10D 48/345>
D	H01L 29/73	5	Bipolar junction transistors	<administrative transfer to H10D 10/00>
D	H01L 29/7302	6	{structurally associated with other devices (assemblies of devices H01L 25/00; integrated circuits H01L 27/00; IGBT H01L 29/7393)}	<administrative transfer to H10D 84/121>
D	H01L 29/7304	7	{the device being a resistive element, e.g. ballasting resistor (transistors integrated with resistors H01L 27/075)}	<administrative transfer to H10D 84/125>
D	H01L 29/7306	6	{Point contact transistors}	<administrative transfer to H10D 10/211>
D	H01L 29/7308	6	{Schottky transistors}	<administrative transfer to H10D 10/221>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/7311	6	{Tunnel transistors}	<administrative transfer to H10D 10/231>
D	H01L 29/7313	6	{Avalanche transistors}	<administrative transfer to H10D 10/241>
D	H01L 29/7315	6	{Transistors with hook collector}	<administrative transfer to H10D 10/00>
D	H01L 29/7317	6	{Bipolar thin film transistors}	<administrative transfer to H10D 10/311>
D	H01L 29/732	6	Vertical transistors	<administrative transfer to H10D 10/40>
D	H01L 29/7322	7	{having emitter-base and base-collector junctions leaving at the same surface of the body, e.g. planar transistor}	<administrative transfer to H10D 10/421>
D	H01L 29/7325	7	{having an emitter-base junction leaving at a main surface and a base-collector junction leaving at a peripheral surface of the body, e.g. mesa planar transistor}	<administrative transfer to H10D 10/441>
D	H01L 29/7327	7	{Inverse vertical transistors}	<administrative transfer to H10D 10/461>
D	H01L 29/735	6	Lateral transistors	<administrative transfer to H10D 10/60>
D	H01L 29/737	6	Hetero-junction transistors	<administrative transfer to H10D 10/80>
D	H01L 29/7371	7	{Vertical transistors}	<administrative transfer to H10D 10/821>
D	H01L 29/7373	8	{having a two-dimensional base, e.g. modulation-doped base, inversion layer base, delta-doped base}	<administrative transfer to H10D 10/841>
D	H01L 29/7375	8	{having an emitter comprising one or more non-monocrystalline elements of group IV, e.g. amorphous silicon, alloys comprising group IV elements}	<administrative transfer to H10D 10/861>
D	H01L 29/7376	8	{Resonant tunnelling transistors}	<administrative transfer to H10D 10/881>
D	H01L 29/7378	8	{comprising lattice mismatched active layers, e.g. SiGe strained layer transistors}	<administrative transfer to H10D 10/891>
D	H01L 29/739	5	controlled by field-effect, {e.g. bipolar static induction transistors [BSIT] (unijunction transistors H01L 29/705)}	<administrative transfer to H10D 12/00>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/7391	6	{Gated diode structures}	<administrative transfer to H10D 12/211>
D	H01L 29/7392	7	{with PN junction gate, e.g. field controlled thyristors (FCTh), static induction thyristors (SITh)}	<administrative transfer to H10D 12/212>
D	H01L 29/7393	6	{Insulated gate bipolar mode transistors, i.e. IGBT; IGT; COMFET}	<administrative transfer to H10D 12/411>
D	H01L 29/7394	7	{on an insulating layer or substrate, e.g. thin film device or device isolated from the bulk substrate (H01L 29/7398 takes precedence)}	<administrative transfer to H10D 12/421>
D	H01L 29/7395	7	{Vertical transistors, e.g. vertical IGBT}	<administrative transfer to H10D 12/441>
D	H01L 29/7396	8	{with a non planar surface, e.g. with a non planar gate or with a trench or recess or pillar in the surface of the emitter, base or collector region for improving current density or short circuiting the emitter and base regions (H01L 29/7398 takes precedence)}	<administrative transfer to H10D 12/461>
D	H01L 29/7397	9	{and a gate structure lying on a slanted or vertical surface or formed in a groove, e.g. trench gate IGBT}	<administrative transfer to H10D 12/481>
D	H01L 29/7398	8	{with both emitter and collector contacts in the same substrate side}	<administrative transfer to H10D 12/491>
D	H01L 29/74	4	Thyristor-type devices, e.g. having four-zone regenerative action {(two-terminal thyristors H01L 29/87)}	<administrative transfer to H10D 18/00>
D	H01L 29/7404	5	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}	<administrative transfer to H10D 84/131>
D	H01L 29/7408	6	{the device being a capacitor or a resistor}	<administrative transfer to H10D 84/133>
D	H01L 29/7412	6	{the device being a diode}	<administrative transfer to H10D 84/135>
D	H01L 29/7416	7	{the device being an antiparallel diode, e.g. RCT (shorted anode structures enabling reverse conduction H01L 29/0834)}	<administrative transfer to H10D 84/136>
D	H01L 29/742	6	{the device being a field effect transistor (for turn-on or turn-off by	<administrative transfer to H10D 84/138>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			field effect H01L 29/745, H01L 29/749)}	
D	H01L 29/7424	5	{having a built-in localised breakdown/breakover region, e.g. self-protected against destructive spontaneous, e.g. voltage breakover, firing}	<administrative transfer to H10D 18/211>
D	H01L 29/7428	5	{having an amplifying gate structure, e.g. cascade (Darlington) configuration}	<administrative transfer to H10D 18/221>
D	H01L 29/7432	5	{Asymmetrical thyristors (with a particular shorted anode structure H01L 29/0834)}	<administrative transfer to H10D 18/241>
D	H01L 29/7436	5	{Lateral thyristors}	<administrative transfer to H10D 18/251>
D	H01L 29/744	5	Gate-turn-off devices	<administrative transfer to H10D 18/60>
D	H01L 29/745	6	with turn-off by field effect	<administrative transfer to H10D 18/65>
D	H01L 29/7455	7	{produced by an insulated gate structure}	<administrative transfer to H10D 18/655>
D	H01L 29/747	5	Bidirectional devices, e.g. triacs	<administrative transfer to H10D 18/80>
D	H01L 29/749	5	with turn-on by field effect	<administrative transfer to H10D 18/40>
D	H01L 29/76	3	Unipolar devices {, e.g. field effect transistors}	<administrative transfer to H10D 48/36>
D	H01L 29/7606	4	{Transistor-like structures, e.g. hot electron transistor [HET]; metal base transistor [MBT]}	<administrative transfer to H10D 48/362>
D	H01L 29/7613	4	{Single electron transistors; Coulomb blockade devices (H01L 29/7888 takes precedence)}	<administrative transfer to H10D 30/402>
D	H01L 29/762	4	Charge transfer devices	<administrative transfer to H10D 44/00>
D	H01L 29/765	5	Charge-coupled devices {(peripheral circuits for CCD storage devices G11C 19/285)}	<administrative transfer to H10D 44/40>
D	H01L 29/768	6	with field effect produced by an insulated gate	<administrative transfer to H10D 44/45>
D	H01L 29/76808	7	{Input structures}	<administrative transfer to H10D 44/452>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/76816	7	{Output structures}	<administrative transfer to H10D 44/454>
D	H01L 29/76825	7	{Structures for regeneration, refreshing, leakage compensation or the like}	<administrative transfer to H10D 44/456>
D	H01L 29/76833	7	{Buried channel CCD}	<administrative transfer to H10D 44/462>
D	H01L 29/76841	8	{Two-Phase CCD}	<administrative transfer to H10D 44/464>
D	H01L 29/7685	8	{Three-Phase CCD}	<administrative transfer to H10D 44/466>
D	H01L 29/76858	8	{Four-Phase CCD}	<administrative transfer to H10D 44/468>
D	H01L 29/76866	7	{Surface Channel CCD}	<administrative transfer to H10D 44/472>
D	H01L 29/76875	8	{Two-Phase CCD}	<administrative transfer to H10D 44/474>
D	H01L 29/76883	8	{Three-Phase CCD}	<administrative transfer to H10D 44/476>
D	H01L 29/76891	8	{Four-Phase CCD}	<administrative transfer to H10D 44/478>
D	H01L 29/772	4	Field effect transistors	<administrative transfer to H10D 30/00>
D	H01L 29/7722	5	{using static field induced regions, e.g. SIT, PBT}	<administrative transfer to H10D 30/202>
D	H01L 29/7725	5	{with delta-doped channel (H01L 29/778 takes precedence)}	<administrative transfer to H10D 62/228>
D	H01L 29/7727	5	{Velocity modulation transistors, i.e. VMT}	<administrative transfer to H10D 30/204>
D	H01L 29/775	5	with one dimensional charge carrier gas channel, e.g. quantum wire FET	<administrative transfer to H10D 30/43>
D	H01L 29/778	5	with two-dimensional charge carrier gas channel, e.g. HEMT {; with two-dimensional charge-carrier layer formed at a heterojunction interface (H01L 29/803 takes precedence)}	<administrative transfer to H10D 30/47>
D	H01L 29/7781	6	{with inverted single heterostructure, i.e. with active layer formed on top of wide bandgap layer, e.g. IHEMT}	<administrative transfer to H10D 30/472>
D	H01L 29/7782	6	{with confinement of carriers by at least two heterojunctions, e.g.	<administrative transfer to H10D 30/473>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			DHHEMT, quantum well HEMT, DHMODFET}	
D	H01L 29/7783	7	{using III-V semiconductor material}	<administrative transfer to H10D 30/4732>
D	H01L 29/7784	8	{with delta or planar doped donor layer (H01L 29/7785 takes precedence)}	<administrative transfer to H10D 30/4735>
D	H01L 29/7785	8	{with more than one donor layer}	<administrative transfer to H10D 30/4738>
D	H01L 29/7786	6	{with direct single heterostructure, i.e. with wide bandgap layer formed on top of active layer, e.g. direct single heterostructure MIS-like HEMT}	<administrative transfer to H10D 30/475>
D	H01L 29/7787	7	{with wide bandgap charge-carrier supplying layer, e.g. direct single heterostructure MODFET}	<administrative transfer to H10D 30/4755>
D	H01L 29/7788	6	{Vertical transistors}	<administrative transfer to H10D 30/477>
D	H01L 29/7789	6	{the two-dimensional charge carrier gas being at least partially not parallel to a main surface of the semiconductor body}	<administrative transfer to H10D 30/478>
D	H01L 29/78	5	with field effect produced by an insulated gate {(H01L 29/7725, H01L 29/775, H01L 29/778 take precedence)}	<administrative transfer to H10D 30/60>
D	H01L 29/7801	6	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (lateral high-voltage MISFETs with channel well and drain offset region H01L 29/7835)}	<administrative transfer to H10D 30/64>
D	H01L 29/7802	7	{Vertical DMOS transistors, i.e. VDMOS transistors}	<administrative transfer to H10D 30/66>
D	H01L 29/7803	8	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}	<administrative transfer to H10D 84/141>
D	H01L 29/7804	9	{the other device being a pn-junction diode}	<administrative transfer to H10D 84/143>
D	H01L 29/7805	10	{in antiparallel, e.g. freewheel diode}	<administrative transfer to H10D 84/144>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/7806	9	{the other device being a Schottky barrier diode}	<administrative transfer to H10D 84/146>
D	H01L 29/7808	9	{the other device being a breakdown diode, e.g. Zener diode}	<administrative transfer to H10D 84/148>
D	H01L 29/7809	8	{having both source and drain contacts on the same surface, i.e. Up-Drain VDMOS transistors}	<administrative transfer to H10D 30/663>
D	H01L 29/781	8	{Inverted VDMOS transistors, i.e. Source-Down VDMOS transistors}	<administrative transfer to H10D 30/664>
D	H01L 29/7811	8	{with an edge termination structure (guard regions per se H01L 29/0619; field plates per se H01L 29/402)}	<administrative transfer to H10D 30/665>
D	H01L 29/7812	8	{with a substrate comprising an insulating layer, e.g. SOI-VDMOS transistors}	<administrative transfer to H10D 30/667>
D	H01L 29/7813	8	{with trench gate electrode, e.g. UMOS transistors (trench gate electrodes per se H01L 29/4236)}	<administrative transfer to H10D 30/668>
D	H01L 29/7815	8	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}	<administrative transfer to H10D 30/669>
D	H01L 29/7816	7	{Lateral DMOS transistors, i.e. LDMOS transistors}	<administrative transfer to H10D 30/65>
D	H01L 29/7817	8	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}	<administrative transfer to H10D 84/151>
D	H01L 29/7818	9	{the other device being a pn-junction diode}	<administrative transfer to H10D 84/153>
D	H01L 29/7819	10	{in antiparallel, e.g. freewheel diode}	<administrative transfer to H10D 84/154>
D	H01L 29/782	9	{the other device being a Schottky barrier diode}	<administrative transfer to H10D 84/156>
D	H01L 29/7821	9	{the other device being a breakdown diode, e.g. Zener diode}	<administrative transfer to H10D 84/158>
D	H01L 29/7823	8	{with an edge termination structure (guard regions per se H01L 29/0619; field plates per se H01L 29/402)}	<administrative transfer to H10D 30/655>
D	H01L 29/7824	8	{with a substrate comprising an insulating layer, e.g. SOI-LDMOS transistors}	<administrative transfer to H10D 30/657>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/7825	8	{with trench gate electrode (trench gate electrodes per se H01L 29/4236)}	<administrative transfer to H10D 30/658>
D	H01L 29/7826	8	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}	<administrative transfer to H10D 30/659>
D	H01L 29/7827	6	{Vertical transistors (H01L 29/7802, H01L 29/78642 take precedence)}	<administrative transfer to H10D 30/63>
D	H01L 29/7828	7	{without inversion channel, e.g. vertical ACCUFETs, normally-on vertical MISFETs}	<administrative transfer to H10D 30/635>
D	H01L 29/783	6	{comprising a gate to body connection, i.e. bulk dynamic threshold voltage MOSFET (for thin film transistors H01L 29/78612, H01L 29/78696)}	<administrative transfer to H10D 30/721>
D	H01L 29/7831	6	{with multiple gate structure (FinFETs or MuGFETs H01L 29/7855, thin film transistors H01L 29/78645)}	<administrative transfer to H10D 30/611>
D	H01L 29/7832	7	{the structure comprising a MOS gate and at least one non-MOS gate, e.g. JFET or MESFET gate}	<administrative transfer to H10D 30/615>
D	H01L 29/7833	6	{with lightly doped drain or source extension, e.g. LDD MOSFET's; DDD MOSFET's (for thin film transistors H01L 29/78618)}	<administrative transfer to H10D 30/601>
D	H01L 29/7834	7	{with a non-planar structure, e.g. the gate or the source or the drain being non-planar}	<administrative transfer to H10D 30/608>
D	H01L 29/7835	7	{with asymmetrical source and drain regions, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}	<administrative transfer to H10D 30/603>
D	H01L 29/7836	7	{with a significant overlap between the lightly doped extension and the gate electrode (H01L 29/7834, H01L 29/7835 take precedence)}	<administrative transfer to H10D 30/605>
D	H01L 29/7838	6	{without inversion channel, e.g. buried channel lateral MISFETs, normally-on lateral MISFETs, depletion-mode lateral MISFETs}	<administrative transfer to H10D 30/637>
D	H01L 29/7839	6	{with Schottky drain or source contact}	<administrative transfer to H10D 64/647>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/78391	6	{the gate comprising a layer which is used for its ferroelectric properties}	<administrative transfer to H10D 30/701>
D	H01L 29/7841	6	{with floating body, e.g. programmable transistors}	<administrative transfer to H10D 30/711>
D	H01L 29/7842	6	{means for exerting mechanical stress on the crystal lattice of the channel region, e.g. using a flexible substrate (variation of the composition of the channel H01L 29/1054)}	<administrative transfer to H10D 30/791>
D	H01L 29/7843	7	{the means being an applied insulating layer}	<administrative transfer to H10D 30/792>
D	H01L 29/7845	7	{the means being a conductive material, e.g. silicided S/D or Gate}	<administrative transfer to H10D 30/794>
D	H01L 29/7846	7	{the means being located in the lateral device isolation region, e.g. STI}	<administrative transfer to H10D 30/795>
D	H01L 29/7847	7	{using a memorization technique, e.g. re-crystallization under strain, bonding on a substrate having a thermal expansion coefficient different from the one of the region}	<administrative transfer to H10D 30/796>
D	H01L 29/7848	7	{the means being located in the source/drain region, e.g. SiGe source and drain}	<administrative transfer to H10D 30/797>
D	H01L 29/7849	7	{the means being provided under the channel}	<administrative transfer to H10D 30/798>
D	H01L 29/785	6	{having a channel with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	<administrative transfer to H10D 30/62>
D	H01L 29/7851	7	{with the body tied to the substrate}	<administrative transfer to H10D 30/6211>
D	H01L 29/7853	7	{the body having a non-rectangular crossection}	<administrative transfer to H10D 30/6212>
D	H01L 29/7854	8	{with rounded corners}	<administrative transfer to H10D 30/6213>
D	H01L 29/7855	7	{with at least two independent gates}	<administrative transfer to H10D 30/6215>
D	H01L 29/7856	7	{with an non-uniform gate, e.g. varying doping structure, shape or composition on different sides of the fin, or different gate insulator thickness or composition on opposing	<administrative transfer to H10D 30/6217>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			fin sides (H01L 29/7855 takes precedence)}	
D	H01L 2029/7857	7	{of the accumulation type}	<administrative transfer to H10D 30/6218>
D	H01L 2029/7858	7	{having contacts specially adapted to the FinFET geometry, e.g. wrap-around contacts}	<administrative transfer to H10D 30/6219>
D	H01L 29/786	6	Thin film transistors, {i.e. transistors with a channel being at least partly a thin film (transistors having only the source or the drain region on an insulator layer H01L 29/0653; thin film FinFETs H01L 29/785)}	<administrative transfer to H10D 30/67>
D	H01L 29/78603	7	{characterised by the insulating substrate or support (H01L 29/78657 takes precedence)}	<administrative transfer to H10D 30/6758>
D	H01L 29/78606	7	{with supplementary region or layer in the thin film or in the insulated bulk substrate supporting it for controlling or increasing the safety of the device (H01L 29/78642, H01L 29/78645 take precedence)}	<administrative transfer to H10D 30/6704>
D	H01L 29/78609	8	{for preventing leakage current (H01L 29/78618 takes precedence)}	<administrative transfer to H10D 30/6706>
D	H01L 29/78612	8	{for preventing the kink- or the snapback effect, e.g. discharging the minority carriers of the channel region for preventing bipolar effect}	<administrative transfer to H10D 30/6708>
D	H01L 29/78615	9	{with a body contact}	<administrative transfer to H10D 30/6711>
D	H01L 29/78618	8	{characterised by the drain or the source properties, e.g. the doping structure, the composition, the sectional shape or the contact structure (silicide contacts, electrodes in general H01L 29/458)}	<administrative transfer to H10D 30/6713>
D	H01L 29/78621	9	{with LDD structure or an extension or an offset region or characterised by the doping profile}	<administrative transfer to H10D 30/6715>
D	H01L 29/78624	10	{the source and the drain regions being asymmetrical}	<administrative transfer to H10D 30/6717>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/78627	10	{with a significant overlap between the lightly doped drain and the gate electrode, e.g. GOLDD}	<administrative transfer to H10D 30/6719>
D	H01L 2029/7863	10	{with an LDD consisting of more than one lightly doped zone or having a non-homogeneous dopant distribution, e.g. graded LDD}	<administrative transfer to H10D 30/6721>
D	H01L 29/78633	8	{with a light shield}	<administrative transfer to H10D 30/6723>
D	H01L 29/78636	8	{with supplementary region or layer for improving the flatness of the device}	<administrative transfer to H10D 30/6725>
D	H01L 29/78639	8	{with a drain or source connected to a bulk conducting substrate}	<administrative transfer to H10D 30/6727>
D	H01L 29/78642	7	{Vertical transistors}	<administrative transfer to H10D 30/6728>
D	H01L 29/78645	7	{with multiple gate}	<administrative transfer to H10D 30/6733>
D	H01L 29/78648	8	{arranged on opposing sides of the channel}	<administrative transfer to H10D 30/6734>
D	H01L 29/78651	7	{Silicon transistors (H01L 29/78606 - H01L 29/78645 take precedence)}	<administrative transfer to H10D 30/6743>
D	H01L 29/78654	8	{Monocrystalline silicon transistors}	<administrative transfer to H10D 30/6744>
D	H01L 29/78657	9	{SOS transistors}	<administrative transfer to H10D 30/6759>
D	H01L 29/7866	8	{Non-monocrystalline silicon transistors}	<administrative transfer to H10D 30/6743>
D	H01L 29/78663	9	{Amorphous silicon transistors}	<administrative transfer to H10D 30/6746>
D	H01L 29/78666	10	{with normal-type structure, e.g. with top gate}	<administrative transfer to H10D 30/6731 and H10D 30/6746 simultaneously>
D	H01L 29/78669	10	{with inverted-type structure, e.g. with bottom gate}	<administrative transfer to H10D 30/6732 and H10D 30/6746 simultaneously>
D	H01L 29/78672	9	{Polycrystalline or microcrystalline silicon transistor}	<administrative transfer to H10D 30/6745>
D	H01L 29/78675	10	{with normal-type structure, e.g. with top gate}	<administrative transfer to H10D 30/6731 and H10D 30/6745 simultaneously>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/78678	10	{with inverted-type structure, e.g. with bottom gate}	<administrative transfer to H10D 30/6732 and H10D 30/6745 simultaneously>
D	H01L 29/78681	7	{having a semiconductor body comprising $A_{III}B_{V}$ or $A_{II}B_{VI}$ or $A_{IV}B_{VI}$ semiconductor materials, or Se or Te}	<administrative transfer to H10D 30/675>
D	H01L 29/78684	7	{having a semiconductor body comprising semiconductor materials of Group IV not being silicon, or alloys including an element of the group IV, e.g. Ge, SiN alloys, SiC alloys (H01L 29/7869 takes precedence)}	<administrative transfer to H10D 30/6741>
D	H01L 29/78687	8	{with a multilayer structure or superlattice structure}	<administrative transfer to H10D 30/6748>
D	H01L 29/7869	7	{having a semiconductor body comprising an oxide semiconductor material, e.g. zinc oxide, copper aluminium oxide, cadmium stannate}	<administrative transfer to H10D 30/6755>
D	H01L 29/78693	8	{the semiconducting oxide being amorphous}	<administrative transfer to H10D 30/6756>
D	H01L 29/78696	7	{characterised by the structure of the channel, e.g. multichannel, transverse or longitudinal shape, length or width, doping structure, or the overlap or alignment between the channel and the gate, the source or the drain, or the contacting structure of the channel (H01L 29/78612 takes precedence; transistors having a drain offset region or a lightly doped drain [LDD] H01L 29/78621)}	<administrative transfer to H10D 30/6757>
D	H01L 29/788	6	with floating gate {(H01L 29/78391 takes precedence)}	<administrative transfer to H10D 30/68>
D	H01L 29/7881	7	{Programmable transistors with only two possible levels of programmation (H01L 29/7888 takes precedence)}	<administrative transfer to H10D 30/681>
D	H01L 29/7882	8	{charging by injection of carriers through a conductive insulator, e.g. Poole-Frankel conduction}	<administrative transfer to H10D 30/682>
D	H01L 29/7883	8	{charging by tunnelling of carriers, e.g. Fowler-Nordheim tunnelling}	<administrative transfer to H10D 30/683>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/7884	8	{charging by hot carrier injection}	<administrative transfer to H10D 30/684>
D	H01L 29/7885	9	{Hot carrier injection from the channel}	<administrative transfer to H10D 30/685>
D	H01L 29/7886	9	{Hot carrier produced by avalanche breakdown of a PN junction, e.g. FAMOS}	<administrative transfer to H10D 30/686>
D	H01L 29/7887	7	{Programmable transistors with more than two possible different levels of programmation}	<administrative transfer to H10D 30/687>
D	H01L 29/7888	7	{Transistors programmable by two single electrons}	<administrative transfer to H10D 30/688>
D	H01L 29/7889	7	{Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane}	<administrative transfer to H10D 30/689>
D	H01L 29/792	6	with charge trapping gate insulator, e.g. MNOS-memory transistors	<administrative transfer to H10D 30/69>
D	H01L 29/7923	7	{Programmable transistors with more than two possible different levels of programmation}	<administrative transfer to H10D 30/691>
D	H01L 29/7926	7	{Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane}	<administrative transfer to H10D 30/693>
D	H01L 29/80	5	with field effect produced by a PN or other rectifying junction gate {, i.e. potential-jump barrier}	<administrative transfer to H10D 30/80>
D	H01L 29/802	6	{with heterojunction gate, e.g. transistors with semiconductor layer acting as gate insulating layer, MIS-like transistors (H01L 29/806 takes precedence; with one dimensional electron gas H01L 29/775; with dimensional electron gas H01L 29/778)}	<administrative transfer to H10D 30/801>
D	H01L 29/803	7	{Programmable transistors, e.g. with charge-trapping quantum well}	<administrative transfer to H10D 30/803>
D	H01L 29/806	6	{with Schottky drain or source contact}	<administrative transfer to H10D 64/649>
D	H01L 29/808	6	with a PN junction gate {, e.g. PN homojunction gate (H01L 29/7725, H01L 29/775, H01L 29/778, H01L 29/806 take precedence)}	<administrative transfer to H10D 30/83>

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
D	H01L 29/8083	7	{Vertical transistors (SIT H01L 29/7722)}	<administrative transfer to H10D 30/831>
D	H01L 29/8086	7	{Thin film JFET's}	<administrative transfer to H10D 30/832>
D	H01L 29/812	6	with a Schottky gate {(H01L 29/7725, H01L 29/775, H01L 29/778, H01L 29/806 take precedence; with Schottky contact on top of heterojunction gate H01L 29/802)}	<administrative transfer to H10D 30/87>
D	H01L 29/8122	7	{Vertical transistors (SIT, PBT H01L 29/7722)}	<administrative transfer to H10D 30/871>
D	H01L 29/8124	7	{with multiple gate}	<administrative transfer to H10D 30/873>
D	H01L 29/8126	7	{Thin film MESFET's}	<administrative transfer to H10D 30/875>
D	H01L 29/8128	7	{with recessed gate}	<administrative transfer to H10D 30/877>
D	H01L 29/82	2	controllable by variation of the magnetic field applied to the device	<administrative transfer to H10D 48/40>
D	H01L 29/84	2	controllable by variation of applied mechanical force, e.g. of pressure	<administrative transfer to H10D 48/50>
D	H01L 29/86	2	controllable only by variation of the electric current supplied, or only the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched	<administrative transfer to H10D 1/40>
D	H01L 29/8605	3	Resistors with PN junctions	<administrative transfer to H10D 1/43>
D	H01L 29/861	3	Diodes	<administrative transfer to H10D 8/00>
D	H01L 29/8611	4	{Planar PN junction diodes}	<administrative transfer to H10D 8/411>
D	H01L 29/8613	4	{Mesa PN junction diodes}	<administrative transfer to H10D 8/422>
D	H01L 29/8615	4	{Hi-lo semiconductor devices, e.g. memory devices}	<administrative transfer to H10D 48/381>
D	H01L 29/8616	4	{Charge trapping diodes}	<administrative transfer to H10D 8/812>
D	H01L 29/8618	4	{Diodes with bulk potential barrier, e.g. Camel diodes, Planar Doped Barrier diodes, Graded bandgap diodes}	<administrative transfer to H10D 8/825>

Type*	**Symbol**	**Indent Level Number of dots (e.g. 0, 1, 2)**	**Title "CPC only" text should normally be enclosed in {curly brackets}****	**Transferred to#**
D	H01L 29/862	4	Point contact diodes	<administrative transfer to H10D 8/30>
D	H01L 29/864	4	Transit-time diodes, e.g. IMPATT, TRAPATT diodes	<administrative transfer to H10D 8/40>
D	H01L 29/866	4	Zener diodes	<administrative transfer to H10D 8/25>
D	H01L 29/868	4	PIN diodes	<administrative transfer to H10D 8/50>
D	H01L 29/87	4	Thyristor diodes, e.g. Shockley diodes, break-over diodes	<administrative transfer to H10D 8/80>
D	H01L 29/872	4	Schottky diodes	<administrative transfer to H10D 8/60>
D	H01L 29/8725	5	{of the trench MOS barrier type [TMBS]}	<administrative transfer to H10D 8/605>
D	H01L 29/88	4	Tunnel-effect diodes	<administrative transfer to H10D 8/70>
D	H01L 29/882	5	{Resonant tunneling diodes, i.e. RTD, RTBD}	<administrative transfer to H10D 8/755>
D	H01L 29/885	5	Esaki diodes	<administrative transfer to H10D 8/75>
D	H01L 29/92	3	Capacitors having potential barriers	<administrative transfer to H10D 1/62>
D	H01L 29/93	4	Variable capacitance diodes, e.g. varactors	<administrative transfer to H10D 1/64>
D	H01L 29/94	4	Metal-insulator-semiconductors, e.g. MOS	<administrative transfer to H10D 1/66>
D	H01L 29/945	5	{Trench capacitors}	<administrative transfer to H10D 1/665>
D	H01L 2229/00	0	Indexing scheme for semiconductor devices adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential-jump barrier or surface barrier, for details of semiconductor bodies or of electrodes thereof, or for multistep manufacturing processes therefor	<administrative transfer to H10D 99/00>

CPC NOTICE OF CHANGES 1723

DATE: JANUARY 1, 2025

PROJECT RP12465

SUBCLASS H10D - INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D	SUBCLASS	INORGANIC ELECTRIC SEMICONDUCTOR DEVICES	
N	H10D 1/00	0	Resistors, capacitors or inductors	
N	H10D 1/01	1	{Manufacture or treatment}	
N	H10D 1/021	2	{of resistors having no potential barriers}	
N	H10D 1/025	2	{of resistors having potential barriers}	
N	H10D 1/041	2	{of capacitors having no potential barriers}	
N	H10D 1/042	3	{using deposition processes to form electrode extensions}	
N	H10D 1/043	3	{using patterning processes to form electrode extensions, e.g. etching}	
N	H10D 1/045	2	{of capacitors having potential barriers, e.g. varactors}	
N	H10D 1/047	3	{of conductor-insulator-semiconductor capacitors, e.g. trench capacitors}	
N	H10D 1/048	4	{having PN junctions, e.g. hybrid capacitors with MOS control}	
N	H10D 1/20	1	Inductors	
Q	H10D 1/40	1	Resistors	H10D 1/40, H10D 48/38
N	H10D 1/43	2	Resistors having PN junctions	
N	H10D 1/47	2	Resistors having no potential barriers	
N	H10D 1/472	3	{having an active material comprising carbon, e.g. diamond or diamond-like carbon [DLC]}	
N	H10D 1/474	3	{comprising refractory metals, transition metals, noble metals, metal compounds or metal alloys, e.g. silicides}	
N	H10D 1/476	3	{comprising conducting organic materials, e.g. conducting polymers}	
N	H10D 1/60	1	Capacitors	
N	H10D 1/62	2	Capacitors having potential barriers	
N	H10D 1/64	3	Variable-capacitance diodes, e.g. varactors	
N	H10D 1/66	3	Conductor-insulator-semiconductor capacitors, e.g. MOS capacitors	
N	H10D 1/665	4	{Trench conductor-insulator-semiconductor capacitors, e.g. trench MOS capacitors}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 1/68	2	Capacitors having no potential barriers	
N	H10D 1/682	3	{having dielectrics comprising perovskite structures}	
N	H10D 1/684	4	{the dielectrics comprising multiple layers, e.g. comprising buffer layers, seed layers or gradient layers}	
N	H10D 1/688	4	{comprising barrier layers to prevent diffusion of hydrogen or oxygen}	
N	H10D 1/692	3	{Electrodes}	
N	H10D 1/694	4	{comprising noble metals or noble metal oxides}	
N	H10D 1/696	4	{comprising multiple layers, e.g. comprising a barrier layer and a metal layer (barrier layers to prevent diffusion of hydrogen or oxygen in perovskite based capacitors H10D 1/688)}	
N	H10D 1/711	4	{having non-planar surfaces, e.g. formed by texturisation}	
N	H10D 1/712	5	{being rough surfaces, e.g. using hemispherical grains}	
N	H10D 1/714	5	{having horizontal extensions}	
N	H10D 1/716	5	{having vertical extensions}	
Q	H10D 8/00	0	Diodes (variable-capacitance diodes H10D 1/64; gated diodes H10D 12/00)	H10D 8/00, H10D 8/20
N	H10D 8/01	1	Manufacture or treatment	
N	H10D 8/021	2	{of breakdown diodes}	
N	H10D 8/022	3	{of Zener diodes}	
N	H10D 8/024	3	{of Avalanche diodes}	
N	H10D 8/041	2	{of multilayer diodes}	
Q	H10D 8/043	2	{of planar diodes}	H10D 8/043, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D 8/041, H10D 8/045, H10D 8/055
N	H10D 8/045	2	{of PN junction diodes}	
Q	H10D 8/051	2	{of Schottky diodes}	H10D 8/051, H10D 1/01, H10D 1/025, H10D 1/045, H10D 1/047, H10D 1/048, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024,

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				H10D 8/041, H10D 8/043, H10D 8/045, H10D 8/053, H10D 8/055, H10D 48/021
N	H10D 8/053	2	{of heterojunction diodes or of tunnel diodes}	
N	H10D 8/055	2	{of transit-time diodes, e.g. IMPATT or TRAPATT diodes}	
N	H10D 8/20	1	Breakdown diodes, e.g. avalanche diodes	
N	H10D 8/25	2	Zener diodes	
N	H10D 8/30	1	Point-contact diodes	
N	H10D 8/40	1	Transit-time diodes, e.g. IMPATT or TRAPATT diodes	
N	H10D 8/411	1	{PN diodes having planar bodies}	
N	H10D 8/422	1	{PN diodes having the PN junctions in mesas}	
N	H10D 8/50	1	PIN diodes	
N	H10D 8/60	1	Schottky-barrier diodes	
N	H10D 8/605	2	{of the trench conductor-insulator-semiconductor barrier type, e.g. trench MOS barrier Schottky rectifiers [TMBS]}	
N	H10D 8/70	1	Tunnel-effect diodes	
N	H10D 8/75	2	Tunnel-effect PN diodes, e.g. Esaki diodes	
N	H10D 8/755	2	{Resonant tunneling diodes [RTD]}	
N	H10D 8/80	1	PNPN diodes, e.g. Shockley diodes or break-over diodes	
N	H10D 8/812	1	{Charge-trapping diodes}	
N	H10D 8/825	1	{Diodes having bulk potential barriers, e.g. Camel diodes, planar doped barrier diodes or graded bandgap diodes}	
N	H10D 10/00	0	Bipolar junction transistors [BJT]	
Q	H10D 10/01	1	Manufacture or treatment	H10D 10/01, H10D 10/051, H10D 10/052, H10D 10/054, H10D 10/056, H10D 10/058
N	H10D 10/021	2	{of heterojunction BJTs [HBT]}	
N	H10D 10/031	2	{of Schottky BJTs}	
N	H10D 10/041	2	{of thin-film BJTs (of heterojunction BJTs H10D 10/021)}	
N	H10D 10/051	2	{of vertical BJTs (of heterojunction BJTs H10D 10/021; of Schottky BJTs	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			H10D 10/031; of thin film BJTs H10D 10/041)}	
Q	H10D 10/052	3	{of inverted vertical BJTs}	H10D 10/052, H10D 10/054
N	H10D 10/054	3	{Forming extrinsic base regions on silicon substrate after insulating device isolation in vertical BJTs having single crystalline emitter, collector or base regions}	
N	H10D 10/056	3	{of vertical BJTs having the main current going through the whole substrate, e.g. power BJTs}	
N	H10D 10/058	4	{having multi-emitter structures, e.g. interdigitated, multi-cellular or distributed emitters}	
N	H10D 10/061	2	{of lateral BJTs (of heterojunction BJTs H10D 10/021; of thin film BJTs H10D 10/041)}	
N	H10D 10/211	1	{Point-contact BJTs}	
N	H10D 10/221	1	{Schottky barrier BJTs}	
N	H10D 10/231	1	{Tunnel BJTs}	
N	H10D 10/241	1	{Avalanche BJTs}	
N	H10D 10/311	1	{Thin-film BJTs}	
N	H10D 10/40	1	Vertical BJTs {(Vertical Heterojunction BJTs H10D 10/821)}	
N	H10D 10/421	2	{having both emitter-base and base-collector junctions ending at the same surface of the body}	
N	H10D 10/441	2	{having an emitter-base junction ending at a main surface of the body and a base-collector junction ending at a lateral surface of the body}	
N	H10D 10/461	2	{Inverted vertical BJTs}	
N	H10D 10/60	1	Lateral BJTs	
N	H10D 10/80	1	Heterojunction BJTs	
N	H10D 10/821	2	{Vertical heterojunction BJTs}	
N	H10D 10/841	3	{having a two-dimensional base, e.g. modulation-doped base, inversion layer base or delta-doped base}	
N	H10D 10/861	3	{having an emitter region comprising one or more non-monocrystalline elements of Group IV, e.g. amorphous silicon}	
N	H10D 10/881	3	{Resonant tunnelling transistors}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 10/891	3	{comprising lattice-mismatched active layers, e.g. SiGe strained-layer transistors}	
N	H10D 12/00	0	Bipolar devices controlled by the field effect, e.g. insulated-gate bipolar transistors [IGBT]	
Q	H10D 12/01	1	Manufacture or treatment	H10D 12/01, H10D 12/031
N	H10D 12/021	2	{of gated diodes, e.g. field-controlled diodes [FCD]}	
Q	H10D 12/031	2	{of IGBTs}	H10D 12/031, H10D 12/01, H10D 12/035, H10D 12/038, H10D 18/01, H10D 18/021, H10D 18/031,H10D 30/028, H10D 30/0281, H10D 30/0285, H10D 30/0287, H10D 30/0289, H10D 30/0291, H10D 30/0293, H10D 30/0295, H10D 30/0297
N	H10D 12/032	3	{of vertical IGBTs}	
N	H10D 12/035	4	{Etching a recess in the emitter region (having a recessed gate H10D 12/038)}	
N	H10D 12/038	4	{having a recessed gate, e.g. trench-gate IGBTs}	
Q	H10D 12/211	1	{Gated diodes}	H10D 12/211, H10D 18/40, H10D 18/60, H10D 18/65, H10D 18/655
N	H10D 12/212	2	{having PN junction gates, e.g. field controlled diodes}	
Q	H10D 12/411	1	{Insulated-gate bipolar transistors [IGBT]}	H10D 12/411, H10D 12/415, H10D 12/416, H10D 12/417, H10D 12/418, H10D 84/161
N	H10D 12/415	2	{having edge termination structures}	
N	H10D 12/416	2	{Bidirectional devices, e.g. trench-gate IGBTs having additional gates at the anode side}	
N	H10D 12/417	2	{having a drift region having a doping concentration that is higher at the collector side relative to other parts of the drift region}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 12/418	2	{having a drift region having a doping concentration that is higher at the emitter side relative to other parts of the drift region}	
N	H10D 12/421	2	{on insulating layers or insulating substrates, e.g. thin-film IGBTs}	
N	H10D 12/441	2	{Vertical IGBTs}	
N	H10D 12/461	3	{having non-planar surfaces, e.g. having trenches, recesses or pillars in the surfaces of the emitter, base or collector regions}	
N	H10D 12/481	4	{having gate structures on slanted surfaces, on vertical surfaces, or in grooves, e.g. trench gate IGBTs}	
Q	H10D 12/491	3	{having both emitter contacts and collector contacts in the same substrate side}	H10D 12/491, H10D 12/421, H10D 12/461, H10D 12/481
N	H10D 18/00	0	Thyristors	
N	H10D 18/01	1	Manufacture or treatment	
N	H10D 18/021	2	{of bidirectional devices, e.g. triacs}	
N	H10D 18/031	2	{of lateral or planar thyristors}	
N	H10D 18/211	1	{having built-in localised breakdown or breakover regions, e.g. self-protected against destructive spontaneous firing}	
N	H10D 18/221	1	{having amplifying gate structures, e.g. cascade configurations}	
N	H10D 18/241	1	{Asymmetrical thyristors}	
N	H10D 18/251	1	{Lateral thyristors}	
N	H10D 18/40	1	with turn-on by field effect	
N	H10D 18/60	1	Gate-turn-off devices	
N	H10D 18/65	2	with turn-off by field effect	
N	H10D 18/655	3	{produced by insulated gate structures}	
N	H10D 18/80	1	Bidirectional devices, e.g. triacs	
Q	H10D 30/00	0	Field-effect transistors [FET] (insulated-gate bipolar transistors H10D 12/00)	H10D 30/00, H10D 30/40
Q	H10D 30/01	1	Manufacture or treatment	H10D 30/01, H10D 30/012, H10D 30/014, H10D 30/015, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				30/0196, H10D 30/0197, H10D 30/0198, H10D 30/021, H10D 30/0212, H10D 30/0213, H10D 30/0215, H10D 30/0217, H10D 30/0218, H10D 30/022, H10D 30/0221, H10D 30/0223, H10D 30/0225, H10D 30/0227, H10D 30/0229, H10D 30/023, H10D 30/024, H10D 30/0241, H10D 30/0243, H10D 30/0245, H10D 30/025, H10D 30/026, H10D 30/027, H10D 30/0273, H10D 30/0275, H10D 30/0277, H10D 30/0278, H10D 30/028, H10D 30/0281, H10D 30/0285, H10D 30/0287, H10D 30/0289, H10D 30/0291, H10D 30/0293, H10D 30/0295, H10D 30/0297, H10D 30/031, H10D 30/0312, H10D 30/0314, H10D 30/0316, H10D 30/0318, H10D 30/0321, H10D 30/0323, H10D 30/0327, H10D 30/0411, H10D 30/0413, H10D 30/0415, H10D 30/051, H10D 30/0512, H10D 30/0515, H10D 30/0516, H10D 30/061, H10D 30/0612, H10D 30/0614, H10D 30/0616, H10D 30/0618
N	H10D 30/012	2	{of static induction transistors [SIT], e.g. permeable base transistors [PBT]}	
Q	H10D 30/014	2	{of FETs having zero-dimensional [0D] or one-dimensional [1D] channels, e.g. quantum wire FETs, single-electron transistors [SET] or Coulomb blockade transistors}	H10D 30/014, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/015	2	{of FETs having heterojunction interface channels or heterojunction gate electrodes, e.g. HEMT}	
N	H10D 30/017	2	{of FETs having two-dimensional material channels, e.g. TMD FETs}	
N	H10D 30/019	2	{of FETs having stacked nanowire, nanosheet or nanoribbon channels}	
N	H10D 30/0191	3	{forming stacked channels, e.g. changing their shapes or sizes}	
N	H10D 30/0193	4	{by modifying properties of the stacked channels}	
N	H10D 30/0194	4	{the stacked channels having different properties}	
N	H10D 30/0195	3	{forming inner spacers between adjacent channels, e.g. changing their shapes or sizes}	
N	H10D 30/0196	4	{by modifying properties of the inner spacers}	
N	H10D 30/0197	4	{the inner spacers having different properties}	
N	H10D 30/0198	3	{forming source or drain electrodes wherein semiconductor bodies are replaced by dielectric layers and the source or drain electrodes extend through the dielectric layers}	
N	H10D 30/021	2	{of FETs having insulated gates [IGFET]}	
N	H10D 30/0212	3	{using self-aligned silicidation}	
N	H10D 30/0213	4	{providing different silicide thicknesses on gate electrodes and on source regions or drain regions}	
N	H10D 30/0215	3	{using self-aligned selective metal deposition simultaneously on gate electrodes and the source regions or drain regions}	
N	H10D 30/0217	3	{forming self-aligned punch-through stoppers or threshold implants under gate regions}	
N	H10D 30/0218	3	{having pocket halo regions selectively formed at the sides of the gates}	
Q	H10D 30/022	3	{having lightly-doped source or drain extensions selectively formed at the sides of the gates}	H10D 30/022, H10D 30/0218
N	H10D 30/0221	3	{having asymmetry in the channel direction, e.g. lateral high-voltage	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			MISFETs having drain offset region or extended-drain MOSFETs [EDMOS]}	
N	H10D 30/0223	3	{having source and drain regions or source and drain extensions self-aligned to sides of the gate}	
N	H10D 30/0225	4	{using an initial gate mask complementary to the prospective gate location, e.g. using dummy source and drain electrodes}	
N	H10D 30/0227	4	{having both lightly-doped source and drain extensions and source and drain regions self-aligned to the sides of the gate, e.g. lightly-doped drain [LDD] MOSFET or double-diffused drain [DDD] MOSFET}	
N	H10D 30/0229	5	{forming drain regions and lightly-doped drain [LDD] simultaneously, e.g. using implantation through a T-shaped mask}	
N	H10D 30/023	3	{having multiple independently-addressable gate electrodes influencing the same channel (manufacture or treatment of dual gate TFTs H10D 30/031)}	
Q	H10D 30/024	3	{of fin field-effect transistors [FinFET]}	H10D 30/024, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198
Q	H10D 30/0241	4	{doping of vertical sidewalls, e.g. using tilted or multi-angled implants}	H10D 30/0241, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194
N	H10D 30/0243	4	{using dummy structures having essentially the same shapes as the semiconductor bodies, e.g. to provide stability}	
Q	H10D 30/0245	4	{by further thinning the channel after patterning the channel, e.g. using sacrificial oxidation on fins}	H10D 30/0245, H10D 30/0191, H10D 30/0193, H10D 30/0194
N	H10D 30/025	3	{of vertical IGFETs (of VDMOS H10D 30/0291; of vertical TFTs H10D 30/0318)}	
N	H10D 30/026	3	{having laterally-coplanar source and drain regions, a gate at the sides of	

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			the bulk channel, and both horizontal and vertical current flow (of LDMOS H10D 30/0289)}	
N	H10D 30/027	3	{of lateral single-gate IGFETs}	
Q	H10D 30/0273	4	{forming final gates or dummy gates after forming source and drain electrodes, e.g. contact first technology}	H10D 30/0273, H10D 30/0223, H10D 30/0225, H10D 30/0227, H10D 30/0229, H10D 64/017
N	H10D 30/0275	4	{forming single crystalline semiconductor source or drain regions resulting in recessed gates, e.g. forming raised source or drain regions}	
N	H10D 30/0277	4	{forming conductor-insulator-semiconductor or Schottky barrier source or drain regions}	
N	H10D 30/0278	4	{forming single crystalline channels on wafers after forming insulating device isolations}	
N	H10D 30/028	3	{of double-diffused metal oxide semiconductor [DMOS] FETs}	
N	H10D 30/0281	4	{of lateral DMOS [LDMOS] FETs}	
N	H10D 30/0285	5	{using formation of insulating sidewall spacers}	
N	H10D 30/0287	5	{using recessing of the source electrodes}	
N	H10D 30/0289	5	{using recessing of the gate electrodes, e.g. to form trench gate electrodes}	
N	H10D 30/0291	4	{of vertical DMOS [VDMOS] FETs}	
N	H10D 30/0293	5	{using formation of insulating sidewall spacers}	
N	H10D 30/0295	5	{using recessing of the source electrodes}	
N	H10D 30/0297	5	{using recessing of the gate electrodes, e.g. to form trench gate electrodes}	
Q	H10D 30/031	3	{of thin-film transistors [TFT]}	H10D 30/031, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0318
N	H10D 30/0312	4	{characterised by the gate electrodes}	

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N	H10D 30/0314	5	{of lateral top-gate TFTs comprising only a single gate}	
N	H10D 30/0316	5	{of lateral bottom-gate TFTs comprising only a single gate}	
N	H10D 30/0318	4	{of vertical TFTs}	
Q	H10D 30/0321	4	{comprising silicon, e.g. amorphous silicon or polysilicon}	H10D 30/0321, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0318
Q	H10D 30/0323	5	{comprising monocrystalline silicon}	H10D 30/0323, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198
Q	H10D 30/0327	6	{on sapphire substrates, e.g. of silicon-on-sapphire [SOS] transistor}	H10D 30/0327, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0314, H10D 30/0316, H10D 30/0318
N	H10D 30/0411	3	{of FETs having floating gates}	
N	H10D 30/0413	3	{of FETs having charge-trapping gate insulators, e.g. MNOS transistors}	
Q	H10D 30/0415	3	{of FETs having ferroelectric gate insulators}	H10D 30/0415, H10D 30/0411
N	H10D 30/051	2	{of FETs having PN junction gates (H10D 30/015 takes precedence)}	
N	H10D 30/0512	3	{of FETs having PN homojunction gates}	
N	H10D 30/0515	4	{of vertical FETs having PN homojunction gates}	
N	H10D 30/0516	3	{of FETs having PN heterojunction gates}	
Q	H10D 30/061	2	{of FETs having Schottky gates (H10D 30/015 takes precedence)}	H10D 30/061, H10D 30/0612, H10D 30/0614, H10D 30/0616, H10D 30/0618

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/0612	3	{of lateral single-gate Schottky FETs}	
N	H10D 30/0614	4	{using processes wherein the final gate is made after the completion of the source and drain regions, e.g. gate-last processes using dummy gates}	
N	H10D 30/0616	4	{using processes wherein the final gate is made before the completion of the source and drain regions, e.g. gate-first processes}	
N	H10D 30/0618	3	{of lateral Schottky gate FETs having multiple independently-addressable gate electrodes}	
N	H10D 30/202	1	{FETs having static field-induced regions, e.g. static-induction transistors [SIT] or permeable base transistors [PBT]}	
N	H10D 30/204	1	{Velocity modulation transistors [VMT]}	
N	H10D 30/40	1	FETs having zero-dimensional [0D], one-dimensional [1D] or two-dimensional [2D] charge carrier gas channels	
N	H10D 30/402	2	{Single electron transistors; Coulomb blockade transistors}	
Q	H10D 30/43	2	having 1D charge carrier gas channels, e.g. quantum wire FETs or transistors having 1D quantum-confined channels	H10D 30/43, H10D 30/435, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
N	H10D 30/435	3	{having multiple laterally adjacent 1D material channels}	
Q	H10D 30/47	2	having 2D charge carrier gas channels, e.g. nanoribbon FETs or high electron mobility transistors [HEMT]	H10D 30/47, H10D 30/471, H10D 30/474, H10D 30/476, H10D 30/481, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
N	H10D 30/471	3	{High electron mobility transistors [HEMT] or high hole mobility transistors [HHMT]}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/472	4	{having lower bandgap active layer formed on top of wider bandgap layer, e.g. inverted HEMT}	
N	H10D 30/473	4	{having confinement of carriers by multiple heterojunctions, e.g. quantum well HEMT}	
N	H10D 30/4732	5	{using Group III-V semiconductor material}	
N	H10D 30/4735	6	{having delta-doped or planar-doped donor layers}	
Q	H10D 30/4738	6	{having multiple donor layers}	H10D 30/4738, H10D 30/4735
N	H10D 30/474	4	{having multiple parallel 2D charge carrier gas channels}	
N	H10D 30/475	4	{having wider bandgap layer formed on top of lower bandgap active layer, e.g. undoped barrier HEMTs such as i-AlGaN/GaN HEMTs}	
N	H10D 30/4755	5	{having wide bandgap charge-carrier supplying layers, e.g. modulation doped HEMTs such as n-AlGaAs/GaAs HEMTs}	
N	H10D 30/476	4	{having gate trenches interrupting the 2D charge carrier gas channels, e.g. hybrid MOS-HEMTs}	
Q	H10D 30/477	4	{Vertical HEMTs or vertical HHMTs}	H10D 30/477, H10D 30/485
Q	H10D 30/478	4	{the 2D charge carrier gas being at least partially not parallel to a main surface of the semiconductor body}	H10D 30/478, H10D 30/485
N	H10D 30/481	3	{FETs having two-dimensional material channels, e.g. transition metal dichalcogenide [TMD] FETs}	
N	H10D 30/485	4	{Vertical FETs having two-dimensional material channels}	
N	H10D 30/501	1	{FETs having stacked nanowire, nanosheet or nanoribbon channels}	
N	H10D 30/502	2	{characterised by the stacked channels}	
N	H10D 30/503	3	{having non-rectangular cross-sections}	
N	H10D 30/504	3	{wherein the stacked channels have different properties}	
N	H10D 30/506	4	{having different thicknesses, sizes or shapes}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/507	2	{characterised by inner spacers between adjacent channels}	
N	H10D 30/508	3	{characterised by the relative sizes, shapes or dispositions of the inner spacers}	
N	H10D 30/509	3	{characterised by the material of the inner spacers}	
N	H10D 30/60	1	Insulated-gate field-effect transistors [IGFET] (H10D 30/40 takes precedence)	
N	H10D 30/601	2	{having lightly-doped drain or source extensions, e.g. LDD IGFETs or DDD IGFETs (lightly doped source or drain extensions for TFTs H10D 30/6715)}	
Q	H10D 30/603	3	{having asymmetry in the channel direction, e.g. lateral high-voltage MISFETs having drain offset region or extended drain IGFETs [EDMOS]}	H10D 30/603, H10D 30/605
N	H10D 30/605	3	{having significant overlap between the lightly-doped extensions and the gate electrode}	
Q	H10D 30/608	3	{having non-planar bodies, e.g. having recessed gate electrodes}	H10D 30/608, H10D 30/605
N	H10D 30/611	2	{having multiple independently-addressable gate electrodes influencing the same channel (FinFETs having multiple distinct gate electrodes H10D 30/6215; multi-gate TFT H10D 30/6733)}	
N	H10D 30/615	3	{comprising a MOS gate electrode and at least one non-MOS gate electrode}	
Q	H10D 30/62	2	Fin field-effect transistors [FinFET]	H10D 30/62, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6211	3	{having fin-shaped semiconductor bodies integral with the bulk semiconductor substrates}	H10D 30/6211, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
Q	H10D 30/6212	3	{having fin-shaped semiconductor bodies having non-rectangular cross-sections}	H10D 30/6212, H10D 30/503, H10D 30/504, H10D 30/506
Q	H10D 30/6213	4	{having rounded corners}	H10D 30/6213, H10D 30/503, H10D 30/504, H10D 30/506
Q	H10D 30/6215	3	{having multiple independently-addressable gate electrodes}	H10D 30/6215, H10D 30/6217
Q	H10D 30/6217	3	{having non-uniform gate electrodes, e.g. gate conductors having varying doping}	H10D 30/6217, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6218	3	{of the accumulation type}	H10D 30/6218, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6219	3	{characterised by the source or drain electrodes}	H10D 30/6219, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
N	H10D 30/63	2	Vertical IGFETs (H10D 30/66{, H10D 30/6728, H10D 30/689, H10D 30/693} take precedence)	
N	H10D 30/635	3	{having no inversion channels, e.g. vertical accumulation channel FETs [ACCUFET] or normally-on vertical IGFETs}	
N	H10D 30/637	2	{Lateral IGFETs having no inversion channels, e.g. buried channel lateral IGFETs, normally-on lateral IGFETs or depletion-mode lateral IGFETs}	
Q	H10D 30/64	2	Double-diffused metal-oxide semiconductor [DMOS] FETs	H10D 30/64, H10D 30/645, H10D 84/101
N	H10D 30/645	3	{Bidirectional devices}	
N	H10D 30/65	3	Lateral DMOS [LDMOS] FETs	
N	H10D 30/655	4	{having edge termination structures}	
N	H10D 30/657	4	{having substrates comprising insulating layers, e.g. SOI-LDMOS transistors}	
N	H10D 30/658	4	{having trench gate electrodes}	

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N	H10D 30/659	4	{having voltage-sensing or current-sensing structures, e.g. emulator sections or overcurrent sensing cells}	
Q	H10D 30/66	3	Vertical DMOS [VDMOS] FETs	H10D 30/66, H10D 30/662
N	H10D 30/662	4	{having a drift region having a doping concentration that is higher between adjacent body regions relative to other parts of the drift region}	
N	H10D 30/663	4	{having both source contacts and drain contacts on the same surface, i.e. up-drain VDMOS}	
N	H10D 30/664	4	{Inverted VDMOS transistors, i.e. source-down VDMOS transistors}	
N	H10D 30/665	4	{having edge termination structures}	
N	H10D 30/667	4	{having substrates comprising insulating layers, e.g. SOI-VDMOS transistors}	
N	H10D 30/668	4	{having trench gate electrodes, e.g. UMOS transistors}	
N	H10D 30/669	4	{having voltage-sensing or current-sensing structures, e.g. emulator sections or overcurrent sensing cells}	
N	H10D 30/67	2	Thin-film transistors [TFT] {(Stacked nanowire, nanosheet or nanoribbon FETs H10D 30/501)}	
N	H10D 30/6704	3	{having supplementary regions or layers in the thin films or in the insulated bulk substrates for controlling properties of the device}	
N	H10D 30/6706	4	{for preventing leakage current (TFTs characterised by the properties of the source or drain H10D 30/6713)}	
N	H10D 30/6708	4	{for preventing the kink effect or the snapback effect, e.g. discharging the minority carriers of the channel region for preventing bipolar effect}	
N	H10D 30/6711	5	{by using electrodes contacting the supplementary regions or layers}	
N	H10D 30/6713	4	{characterised by the properties of the source or drain regions, e.g. compositions or sectional shapes}	

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N	H10D 30/6715	5	{characterised by the doping profiles, e.g. having lightly-doped source or drain extensions}	
N	H10D 30/6717	6	{the source and the drain regions being asymmetrical}	
N	H10D 30/6719	6	{having significant overlap between the lightly-doped drains and the gate electrodes, e.g. gate-overlapped LDD [GOLDD] TFTs}	
N	H10D 30/6721	6	{having lightly-doped extensions consisting of multiple lightly doped zones or having non-homogeneous dopant distributions, e.g. graded LDD}	
N	H10D 30/6723	4	{having light shields}	
N	H10D 30/6725	4	{having supplementary regions or layers for improving the flatness of the device}	
N	H10D 30/6727	4	{having source or drain regions connected to bulk conducting substrates}	
Q	H10D 30/6728	3	{Vertical TFTs}	H10D 30/6728, H10D 30/6704, H10D 30/674
N	H10D 30/6729	3	{characterised by the electrodes}	
N	H10D 30/673	4	{characterised by the shapes, relative sizes or dispositions of the gate electrodes}	
N	H10D 30/6731	5	{Top-gate only TFTs}	
N	H10D 30/6732	5	{Bottom-gate only TFTs}	
Q	H10D 30/6733	5	{Multi-gate TFTs}	H10D 30/6733, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
Q	H10D 30/6734	6	{having gate electrodes arranged on both top and bottom sides of the channel, e.g. dual-gate TFTs}	H10D 30/6734, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
Q	H10D 30/6735	5	{having gates fully surrounding the channels, e.g. gate-all-around}	H10D 30/6735, H10D 30/501, H10D 30/502, H10D 30/503, H10D

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				30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
N	H10D 30/6736	5	{characterised by the shape of gate insulators}	
N	H10D 30/6737	4	{characterised by the electrode materials}	
N	H10D 30/6738	5	{Schottky barrier electrodes}	
N	H10D 30/6739	5	{Conductor-insulator-semiconductor electrodes}	
N	H10D 30/674	3	{characterised by the active materials}	
Q	H10D 30/6741	4	{Group IV materials, e.g. germanium or silicon carbide (TFTs having oxide semiconductors H10D 30/6755)}	H10D 30/6741, H10D 30/481, H10D 30/485
N	H10D 30/6743	5	{Silicon}	
N	H10D 30/6744	6	{Monocrystalline silicon}	
N	H10D 30/6745	6	{Polycrystalline or microcrystalline silicon}	
N	H10D 30/6746	6	{Amorphous silicon}	
Q	H10D 30/6748	5	{having a multilayer structure or superlattice structure}	H10D 30/6748, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
N	H10D 30/675	4	{Group III-V materials, Group II-VI materials, Group IV-VI materials, selenium or tellurium}	
N	H10D 30/6755	4	{Oxide semiconductors, e.g. zinc oxide, copper aluminium oxide or cadmium stannate}	
N	H10D 30/6756	5	{Amorphous oxide semiconductors}	
Q	H10D 30/6757	3	{characterised by the structure of the channel, e.g. transverse or longitudinal shape or doping profile (TFTs having channel structures for preventing kink or snapback effects H10D 30/6708; TFTs having lightly-doped source or drain extensions H10D 30/6715)}	H10D 30/6757, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
N	H10D 30/6758	3	{characterised by the insulating substrates}	
N	H10D 30/6759	4	{Silicon-on-sapphire [SOS] substrates}	
N	H10D 30/68	2	Floating-gate IGFETs	

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N	H10D 30/681	3	{having only two programming levels (Floating gate IGFETs programmable by two single electrons H10D 30/688)}	
N	H10D 30/682	4	{programmed by injection of carriers through a conductive insulator, e.g. Poole-Frankel conduction}	
N	H10D 30/683	4	{programmed by tunnelling of carriers, e.g. Fowler-Nordheim tunnelling}	
N	H10D 30/684	4	{programmed by hot carrier injection}	
N	H10D 30/685	5	{from the channel}	
N	H10D 30/686	5	{using hot carriers produced by avalanche breakdown of PN junctions, e.g. floating gate avalanche injection MOS [FAMOS]}	
N	H10D 30/687	3	{having more than two programming levels}	
N	H10D 30/688	3	{programmed by two single electrons}	
N	H10D 30/689	3	{Vertical floating-gate IGFETs}	
N	H10D 30/6891	3	{characterised by the shapes, relative sizes or dispositions of the floating gate electrode}	
N	H10D 30/6892	4	{having at least one additional gate other than the floating gate and the control gate, e.g. program gate, erase gate or select gate}	
N	H10D 30/6893	4	{wherein the floating gate has multiple non-connected parts, e.g. multi-particle floating gate}	
N	H10D 30/6894	4	{having one gate at least partly in a trench}	
N	H10D 30/69	2	IGFETs having charge trapping gate insulators, e.g. MNOS transistors	
N	H10D 30/691	3	{having more than two programming levels}	
N	H10D 30/693	3	{Vertical IGFETs having charge trapping gate insulators}	
N	H10D 30/694	3	{characterised by the shapes, relative sizes or dispositions of the gate electrodes}	
N	H10D 30/696	4	{having at least one additional gate, e.g. program gate, erase gate or select gate}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/697	4	{having trapping at multiple separated sites, e.g. multi-particles trapping sites}	
N	H10D 30/699	4	{having the gate at least partly formed in a trench}	
Q	H10D 30/701	2	{IGFETs having ferroelectric gate insulators, e.g. ferroelectric FETs}	H10D 30/701, H10D 30/68
N	H10D 30/711	2	{having floating bodies}	
N	H10D 30/721	2	{having a gate-to-body connection, i.e. bulk dynamic threshold voltage IGFET (TFTs having gate-to-body connection H10D 30/6708)}	
Q	H10D 30/751	2	{having composition variations in the channel regions}	H10D 30/751, H10D 30/798
N	H10D 30/791	2	{Arrangements for exerting mechanical stress on the crystal lattice of the channel regions}	
N	H10D 30/792	3	{comprising applied insulating layers, e.g. stress liners}	
N	H10D 30/794	3	{comprising conductive materials, e.g. silicided source, drain or gate electrodes}	
N	H10D 30/795	3	{being in lateral device isolation regions, e.g. STI}	
N	H10D 30/796	3	{having memorised stress for introducing strain in the channel regions, e.g. recrystallised polysilicon gates}	
N	H10D 30/797	3	{being in source or drain regions, e.g. SiGe source or drain}	
N	H10D 30/798	3	{being provided in or under the channel regions}	
N	H10D 30/80	1	FETs having rectifying junction gate electrodes (H10D 30/40 takes precedence)	
N	H10D 30/801	2	{FETs having heterojunction gate electrodes}	
N	H10D 30/803	3	{Programmable transistors, e.g. having charge-trapping quantum well}	
N	H10D 30/83	2	FETs having PN junction gate electrodes	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 30/831	3	{Vertical FETs having PN junction gate electrodes (Vertical SIT H10D 30/202)}	
N	H10D 30/832	3	{Thin-film junction FETs [JFET]}	
N	H10D 30/87	2	FETs having Schottky gate electrodes, e.g. metal-semiconductor FETs [MESFET] {(FETs having Schottky contact on top of heterojunction gate H10D 30/801)}	
N	H10D 30/871	3	{Vertical FETs having Schottky gate electrodes (Vertical SIT or PBT H10D 30/202)}	
N	H10D 30/873	3	{having multiple gate electrodes}	
N	H10D 30/875	3	{having thin-film semiconductor bodies}	
N	H10D 30/877	3	{having recessed gate electrodes}	
N	H10D 44/00	0	Charge transfer devices	
N	H10D 44/01	1	Manufacture or treatment	
N	H10D 44/041	2	{having insulated gates}	
N	H10D 44/061	2	{having Schottky gates}	
N	H10D 44/40	1	Charge-coupled devices [CCD]	
N	H10D 44/45	2	having field effect produced by insulated gate electrodes	
N	H10D 44/452	3	{Input structures}	
N	H10D 44/454	3	{Output structures}	
N	H10D 44/456	3	{Structures for regeneration, refreshing or leakage compensation}	
N	H10D 44/462	3	{Buried-channel CCD}	
N	H10D 44/464	4	{Two-phase CCD}	
N	H10D 44/466	4	{Three-phase CCD}	
N	H10D 44/468	4	{Four-phase CCD}	
N	H10D 44/472	3	{Surface-channel CCD}	
N	H10D 44/474	4	{Two-phase CCD}	
N	H10D 44/476	4	{Three-phase CCD}	
N	H10D 44/478	4	{Four-phase CCD}	
N	H10D 48/00	0	Individual devices not covered by groups H10D 1/00 - H10D 44/00	
N	H10D 48/01	1	Manufacture or treatment	
Q	H10D 48/021	2	{of two-electrode devices}	H10D 48/021, H10D 1/025, H10D 1/045, H10D 1/047, H10D 1/048, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				8/041, H10D 8/043, H10D 8/045, H10D 8/051, H10D 8/053, H10D 8/055
Q	H10D 48/031	2	{of three-or-more electrode devices}	H10D 48/031, H10D 10/01, H10D 10/021, H10D 10/031, H10D 10/041, H10D 10/051, H10D 10/052, H10D 10/054, H10D 10/056, H10D 10/058, H10D 10/061, H10D 12/01, H10D 12/021, H10D 12/031, H10D 12/032, H10D 12/035, H10D 12/038, H10D 18/01, H10D 18/021, H10D 18/031
N	H10D 48/032	3	{of unipolar transistors having ohmic electrodes on emitter-like, base-like, and collector-like regions, e.g. hot electron transistors [HET], metal base transistors [MBT], resonant tunneling transistors [RTT], bulk barrier transistors [BBT], planar doped barrier transistors [PDBT] or charge injection transistors [CHINT]}	
N	H10D 48/04	2	of devices having bodies comprising selenium or tellurium in uncombined form	
N	H10D 48/042	3	Preparation of foundation plates	
N	H10D 48/043	3	Preliminary treatment of the selenium or tellurium, its application to foundation plates or the subsequent treatment of the combination	
N	H10D 48/0431	4	{Application of the selenium or tellurium to the foundation plate}	
N	H10D 48/044	4	Conversion of the selenium or tellurium to the conductive state	
N	H10D 48/045	4	Treatment of the surface of the selenium or tellurium layer after having been made conductive	
N	H10D 48/046	4	Provision of discrete insulating layers	
N	H10D 48/047	3	Application of an electrode to the exposed surface of the selenium or tellurium after the selenium or	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			tellurium has been applied to foundation plates	
N	H10D48/048	3	Treatment of the complete device, e.g. by electroforming to form a barrier	
N	H10D48/049	4	Ageing	
N	H10D48/07	2	of devices having bodies comprising cuprous oxide [Cu_2O] or cuprous iodide [CuI]	
N	H10D48/071	3	{Preparation of the foundation plate, preliminary treatment oxidation of the foundation plate or reduction treatment}	
N	H10D48/073	4	{Preliminary treatment of the foundation plate}	
N	H10D48/074	4	{Oxidation and subsequent heat treatment of the foundation plate (Reduction of copper oxide H10D 48/075)}	
N	H10D48/075	4	{Reduction of the copper oxide or treatment of the oxide layer}	
N	H10D48/076	4	{Application of a non-genetic conductive layer}	
N	H10D48/078	3	{Treatment of the complete device, e.g. electroforming or ageing}	
Q	H10D48/30	1	Devices controlled by electric currents or voltages	H10D48/30, H10D 48/00
N	H10D48/32	2	Devices controlled by only the electric current supplied, or only the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched	
N	H10D48/34	3	Bipolar devices	
N	H10D48/341	4	{Unijunction transistors, i.e. double base diodes}	
N	H10D48/345	4	{Bipolar transistors having ohmic electrodes on emitter-like, base-like, and collector-like regions}	
N	H10D48/36	3	Unipolar devices	
N	H10D48/362	4	{Unipolar transistors having ohmic electrodes on emitter-like, base-like, and collector-like regions, e.g. hot electron transistors [HET], metal base transistors [MBT], resonant tunnelling transistors [RTT], bulk	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			barrier transistors [BBT], planar doped barrier transistors [PDBT] or charge injection transistors [CHINT]}	
N	H10D48/366	3	{Multistable devices; Devices having two or more distinct operating states}	
N	H10D48/38	2	Devices controlled only by variation of the electric current supplied, or only the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched	
N	H10D48/381	3	{Multistable devices; Devices having two or more distinct operating states}	
Q	H10D48/383	1	{Quantum effect devices, e.g. of devices using quantum reflection, diffraction or interference effects}	H10D48/383, H10D 48/3835
N	H10D48/3835	2	{Semiconductor qubit devices comprising a plurality of quantum mechanically interacting semiconductor quantum dots, e.g. Loss-DiVincenzo spin qubits}	
N	H10D48/385	1	{Devices using spin-polarised carriers}	
N	H10D48/387	1	{Devices controllable only by the variation of applied heat}	
N	H10D48/40	1	Devices controlled by magnetic fields	
N	H10D48/50	1	Devices controlled by mechanical forces, e.g. pressure	
Q	H10D62/00	0	Semiconductor bodies, or regions thereof, of devices having potential barriers	H10D62/00, H10D 62/01
N	H10D62/01	1	{Manufacture or treatment}	
N	H10D62/021	2	{Forming source or drain recesses by etching e.g. recessing by etching and then refilling}	
N	H10D62/051	2	{Forming charge compensation regions, e.g. superjunctions}	
N	H10D62/052	3	{by forming stacked epitaxial layers}	
N	H10D62/054	3	{by high energy implantations in bulk semiconductor bodies, e.g. forming pillars}	
N	H10D62/056	3	{by out-diffusing dopants from applied layers}	
N	H10D62/058	3	{by using trenches, e.g. implanting into sidewalls of trenches or refilling trenches}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
Q	H10D 62/10	1	Shapes, relative sizes or dispositions of the regions of the semiconductor bodies; Shapes of the semiconductor bodies	H10D 62/10, H10D 62/128, H10D 62/129
N	H10D 62/102	2	{Constructional design considerations for preventing surface leakage or controlling electric field concentration}	
N	H10D 62/103	3	{for increasing or controlling the breakdown voltage of reverse-biased devices}	
N	H10D 62/104	4	{having particular shapes of the bodies at or near reverse-biased junctions, e.g. having bevels or moats}	
N	H10D 62/105	4	{by having particular doping profiles, shapes or arrangements of PN junctions; by having supplementary regions, e.g. junction termination extension [JTE] (IGFETs having LDD or drain extension regions H10D 30/601)}	
N	H10D 62/106	5	{having supplementary regions doped oppositely to or in rectifying contact with regions of the semiconductor bodies, e.g. guard rings with PN or Schottky junctions}	
N	H10D 62/107	6	{Buried supplementary regions, e.g. buried guard rings (multi-RESURF H10D 62/111)}	
N	H10D 62/108	5	{having localised breakdown regions, e.g. built-in avalanching regions (in self-protected thyristors H10D 18/211)}	
N	H10D 62/109	5	{Reduced surface field [RESURF] PN junction structures}	
Q	H10D 62/111	6	{Multiple RESURF structures, e.g. double RESURF or 3D-RESURF structures}	H10D 62/111, H10D 62/051, H10D 62/052, H10D 62/054, H10D 62/056, H10D 62/058
N	H10D 62/112	3	{for preventing surface leakage due to surface inversion layers, e.g. by using channel stoppers}	
N	H10D 62/113	2	{Isolations within a component, i.e. internal isolations}	
N	H10D 62/114	3	{PN junction isolations}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 62/115	3	{Dielectric isolations, e.g. air gaps}	
N	H10D 62/116	4	{adjoining the input or output regions of field-effect devices, e.g. adjoining source or drain regions}	
N	H10D 62/117	2	{Shapes of semiconductor bodies}	
N	H10D 62/118	3	{Nanostructure semiconductor bodies}	
N	H10D 62/119	4	{Nanowire, nanosheet or nanotube semiconductor bodies}	
N	H10D 62/121	5	{oriented parallel to substrates}	
N	H10D 62/122	5	{oriented at angles to substrates, e.g. perpendicular to substrates}	
N	H10D 62/123	5	{comprising junctions}	
N	H10D 62/124	2	{Shapes, relative sizes or dispositions of the regions of semiconductor bodies or of junctions between the regions}	
N	H10D 62/125	3	{Shapes of junctions between the regions}	
N	H10D 62/126	3	{Top-view geometrical layouts of the regions or the junctions}	
N	H10D 62/127	4	{of cellular field-effect devices, e.g. multicellular DMOS transistors or IGBTs}	
N	H10D 62/128	2	{Anode regions of diodes}	
N	H10D 62/129	2	{Cathode regions of diodes}	
N	H10D 62/13	2	Semiconductor regions connected to electrodes carrying current to be rectified, amplified or switched, e.g. source or drain regions	
N	H10D 62/133	3	{Emitter regions of BJTs}	
N	H10D 62/134	4	{of lateral BJTs}	
N	H10D 62/135	4	{Non-interconnected multi-emitter structures}	
N	H10D 62/136	4	{of heterojunction BJTs (vertical heterojunction BJTs having one or more non-monocrystalline Group IV elements H10D 10/861)}	
N	H10D 62/137	3	{Collector regions of BJTs}	
N	H10D 62/138	4	{Pedestal collectors}	
Q	H10D 62/141	3	{Anode or cathode regions of thyristors; Collector or emitter regions of gated bipolar-mode devices, e.g. of IGBTs}	H10D 62/141, H10D 62/145

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 62/142	4	{Anode regions of thyristors or collector regions of gated bipolar-mode devices}	
N	H10D 62/145	4	{Emitter regions of IGBTs}	
N	H10D 62/148	4	{Cathode regions of thyristors}	
N	H10D 62/149	3	{Source or drain regions of field-effect devices}	
N	H10D 62/151	4	{of IGFETs (of IGFETs having LDD or DDD structure H10D 30/601; of thin film transistors H10D 30/6713)}	
Q	H10D 62/152	5	{Source regions of DMOS transistors}	H10D 62/152, H10D 62/156
N	H10D 62/153	6	{Impurity concentrations or distributions}	
N	H10D 62/154	6	{Dispositions}	
N	H10D 62/155	6	{Shapes (cell layout of DMOS H10D 62/127)}	
N	H10D 62/156	5	{Drain regions of DMOS transistors}	
N	H10D 62/157	6	{Impurity concentrations or distributions}	
N	H10D 62/158	6	{Dispositions}	
N	H10D 62/159	6	{Shapes}	
N	H10D 62/161	4	{of FETs having Schottky gates}	
N	H10D 62/165	3	{Tunnel injectors}	
N	H10D 62/17	2	Semiconductor regions connected to electrodes not carrying current to be rectified, amplified or switched, e.g. channel regions	
N	H10D 62/177	3	{Base regions of bipolar transistors, e.g. BJTs or IGBTs}	
N	H10D 62/184	4	{of lateral BJTs}	
N	H10D 62/192	3	{Base regions of thyristors}	
N	H10D 62/199	4	{Anode base regions of thyristors}	
N	H10D 62/206	4	{Cathode base regions of thyristors}	
N	H10D 62/213	3	{Channel regions of field-effect devices}	
N	H10D 62/221	4	{of FETs}	
N	H10D 62/228	5	{having delta-doped channels}	
N	H10D 62/235	5	{of IGFETs (IGFETs having buried channels H10D 30/637)}	
N	H10D 62/292	6	{Non-planar channels of IGFETs (resulting from the gate electrode dispositions, e.g. within trenches H10D 64/512)}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 62/299	6	{having lateral doping variations (IGFETs having lightly doped source or drain extensions H10D 30/601)}	
N	H10D 62/307	7	{the doping variations being parallel to the channel lengths}	
Q	H10D 62/314	6	{having vertical doping variations (vertical IGFETs H10D 30/63)}	H10D 62/314, H10D 62/299
N	H10D 62/328	5	{having PN junction gates}	
N	H10D 62/335	4	{of charge-coupled devices}	
N	H10D 62/343	3	{Gate regions of field-effect devices having PN junction gates}	
N	H10D 62/351	3	{Substrate regions of field-effect devices}	
N	H10D 62/357	4	{of FETs}	
N	H10D 62/364	5	{of IGFETs}	
N	H10D 62/371	6	{Inactive supplementary semiconductor regions, e.g. for preventing punch-through, improving capacity effect or leakage current}	
Q	H10D 62/378	6	{Contact regions to the substrate regions}	H10D 62/378, H10D 64/529
N	H10D 62/386	4	{of charge-coupled devices}	
N	H10D 62/393	3	{Body regions of DMOS transistors or IGBTs (cell layout of DMOS H10D 62/127)}	
N	H10D 62/40	1	Crystalline structures	
N	H10D 62/402	2	{Amorphous materials}	
N	H10D 62/405	2	{Orientations of crystalline planes}	
N	H10D 62/50	1	Physical imperfections	
N	H10D 62/53	2	the imperfections being within the semiconductor body	
N	H10D 62/57	2	the imperfections being on the surface of the semiconductor body, e.g. the body having a roughened surface	
N	H10D 62/60	1	Impurity distributions or concentrations	
N	H10D 62/605	2	{Planar doped, e.g. atomic-plane doped or delta-doped}	
Q	H10D 62/80	1	characterised by the materials	H10D 62/80, H10D 62/82, H10D 62/8271, H10D 62/8281, H10D 62/871, H10D 62/874, H10D 62/875, H10D 62/881, H10D 62/883

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
Q	H10D 62/81	2	of structures exhibiting quantum-confinement effects, e.g. single quantum wells; of structures having periodic or quasi-periodic potential variation	H10D 62/81, H10D 62/80
N	H10D 62/812	3	{Single quantum well structures}	
N	H10D 62/813	4	{Quantum wire structures}	
N	H10D 62/814	4	{Quantum box structures}	
N	H10D 62/815	3	of structures having periodic or quasi-periodic potential variation, e.g. superlattices or multiple quantum wells [MQW]	
N	H10D 62/8161	4	{potential variation due to variations in composition or crystallinity, e.g. heterojunction superlattices (lateral superlattices, lateral surface superlattices H10D 62/8181)}	
N	H10D 62/8162	5	{having quantum effects only in the vertical direction, i.e. layered structures having quantum effects solely resulting from vertical potential variation}	
N	H10D 62/8163	6	{comprising long-range structurally-disordered materials, e.g. one-dimensional vertical amorphous superlattices}	
N	H10D 62/8164	6	{comprising only semiconductor materials (potential variation in long-range structurally-disordered materials H10D 62/8163)}	
N	H10D 62/8171	4	{Doping structures, e.g. doping superlattices or nipi superlattices}	
N	H10D 62/8181	4	{Structures having no potential periodicity in the vertical direction, e.g. lateral superlattices or lateral surface superlattices [LSS]}	
Q	H10D 62/82	2	Heterojunctions	H10D 62/82, H10D 62/8271, H10D 62/8281
N	H10D 62/822	3	comprising only Group IV materials heterojunctions, e.g. Si/Ge heterojunctions	
N	H10D 62/824	3	comprising only Group III-V materials heterojunctions, e.g. GaN/AlGaN heterojunctions	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 62/826	3	comprising only Group II-VI materials heterojunctions, e.g. CdTe/HgTe heterojunctions	
N	H10D 62/8271	3	{comprising only oxide semiconductor materials heterojunctions, e.g. IGZO/IZO}	
N	H10D 62/8281	3	{comprising only transition metal dichalcogenide materials heterojunctions, e.g. MoS_2/WSe_2}	
Q	H10D 62/83	2	being Group IV materials, e.g. B-doped Si or undoped Ge	H10D 62/83, H10D 62/822, H10D 62/832, H10D 62/834, H10D 62/881
Q	H10D 62/8303	3	{Diamond}	H10D 62/8303, H10D 62/882
N	H10D 62/832	3	being Group IV materials comprising two or more elements, e.g. SiGe	
N	H10D 62/8325	4	{Silicon carbide}	
N	H10D 62/834	3	further characterised by the dopants	
N	H10D 62/84	2	being selenium or tellurium only	
Q	H10D 62/85	2	being Group III-V materials, e.g. GaAs	H10D 62/85, H10D 62/824, H10D 62/852, H10D 62/854
Q	H10D 62/8503	3	{Nitride Group III-V materials, e.g. AlN or GaN}	H10D 62/8503, H10D 62/881
N	H10D 62/852	3	being Group III-V materials comprising three or more elements, e.g. AlGaN or InAsSbP	
N	H10D 62/854	3	further characterised by the dopants	
Q	H10D 62/86	2	being Group II-VI materials, e.g. ZnO	H10D 62/86, H10D 62/826, H10D 62/8603, H10D 62/862, H10D 62/864
N	H10D 62/8603	3	{Binary Group II-VI materials wherein cadmium is the Group II element, e.g. CdTe}	
N	H10D 62/862	3	being Group II-VI materials comprising three or more elements, e.g. CdZnTe	
N	H10D 62/864	3	further characterised by the dopants	
Q	H10D 62/871	2	{being Group I-VI materials, e.g. Cu_2O; being Group I-VII materials, e.g. CuI}	H10D 62/871, H10D 62/82, H10D 62/8281, H10D 62/883
Q	H10D 62/874	2	{being Pb compounds or alloys, e.g. PbO}	H10D 62/874, H10D 62/82, H10D 62/8281, H10D 62/883

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 62/875	2	{being semiconductor metal oxide, e.g. InGaZnO (Group II-VI materials H10D 62/86; Group I-VI materials H10D 62/871; Pb compounds or alloys H10D 62/874)}	
N	H10D 62/881	2	{being a two-dimensional material}	
N	H10D 62/882	3	{Graphene}	
N	H10D 62/883	3	{Transition metal dichalcogenides, e.g. $MoSe_2$}	
N	H10D 64/00	0	Electrodes of devices having potential barriers	
N	H10D 64/01	1	Manufacture or treatment	
N	H10D 64/015	2	{removing at least parts of gate spacers, e.g. disposable spacers}	
N	H10D 64/017	2	{using dummy gates in processes wherein at least parts of the final gates are self-aligned to the dummy gates, i.e. replacement gate processes}	
N	H10D 64/018	2	{Spacers formed inside holes at the prospective gate locations, e.g. holes left by removing dummy gates}	
N	H10D 64/021	2	{using multiple gate spacer layers, e.g. bilayered sidewall spacers}	
N	H10D 64/025	2	{forming recessed gates, e.g. by using local oxidation}	
N	H10D 64/027	3	{by etching at gate locations}	
N	H10D 64/031	2	{of data-storage electrodes}	
N	H10D 64/033	3	{comprising ferroelectric layers}	
N	H10D 64/035	3	{comprising conductor-insulator-conductor-insulator-semiconductor structures}	
N	H10D 64/037	3	{comprising charge-trapping insulators}	
N	H10D 64/111	1	{Field plates}	
N	H10D 64/112	2	{comprising multiple field plate segments}	
N	H10D 64/115	2	{Resistive field plates, e.g. semi-insulating field plates}	
N	H10D 64/117	2	{Recessed field plates, e.g. trench field plates or buried field plates}	
N	H10D 64/118	1	{Electrodes comprising insulating layers having particular dielectric or electrostatic properties, e.g. having static charges}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 64/20	1	Electrodes characterised by their shapes, relative sizes or dispositions	
N	H10D 64/205	2	{Nanosized electrodes, e.g. nanowire electrodes}	
Q	H10D 64/23	2	Electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. sources, drains, anodes or cathodes	H10D 64/23, H10D 64/232
N	H10D 64/231	3	{Emitter or collector electrodes for bipolar transistors}	
N	H10D 64/232	3	{Emitter electrodes for IGBTs}	
N	H10D 64/233	3	{Cathode or anode electrodes for thyristors}	
N	H10D 64/251	3	{Source or drain electrodes for field-effect devices}	
Q	H10D 64/252	4	{for vertical or pseudo-vertical devices}	H10D 64/252, H10D 64/2523, H10D 64/2527
N	H10D 64/2523	5	{for vertical devices wherein the source or drain electrodes extend entirely through semiconductor bodies}	
N	H10D 64/2527	5	{for vertical devices wherein the source or drain electrodes are recessed in semiconductor bodies}	
Q	H10D 64/254	4	{for lateral devices wherein the source or drain electrodes extend entirely through the semiconductor bodies, e.g. via-holes for back side contacts}	H10D 64/254, H10D 64/257, H10D 64/256, H10D 64/2565
Q	H10D 64/256	4	{for lateral devices wherein the source or drain electrodes are recessed in semiconductor bodies (source or drain electrodes of TFTs H10D 30/673)}	H10D 64/256, H10D 64/2527
N	H10D 64/2565	5	{wherein the source or drain regions are on a top side of the semiconductor bodies and the recessed source or drain electrodes are on a bottom side of the semiconductor bodies}	
Q	H10D 64/257	4	{for lateral devices wherein the source or drain electrodes are characterised by top-view geometrical layouts, e.g. interdigitated, semi-circular, annular or L-shaped electrodes (source or drain electrodes of TFTs H10D 30/673)}	H10D 64/257, H10D 64/256

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 64/258	4	{characterised by the relative positions of the source or drain electrodes with respect to the gate electrode}	
N	H10D 64/259	5	{Source or drain electrodes being self-aligned with the gate electrode and having bottom surfaces higher than the interface between the channel and the gate dielectric}	
N	H10D 64/27	2	Electrodes not carrying the current to be rectified, amplified, oscillated or switched, e.g. gates	
N	H10D 64/281	3	{Base electrodes for bipolar transistors}	
N	H10D 64/291	3	{Gate electrodes for thyristors}	
N	H10D 64/311	3	{Gate electrodes for field-effect devices}	
N	H10D 64/411	4	{for FETs}	
N	H10D 64/511	5	{for IGFETs}	
N	H10D 64/512	6	{Disposition of the gate electrodes, e.g. buried gates}	
N	H10D 64/513	7	{within recesses in the substrate, e.g. trench gates, groove gates or buried gates}	
N	H10D 64/514	6	{characterised by the insulating layers}	
N	H10D 64/516	7	{the thicknesses being non-uniform}	
N	H10D 64/517	6	{characterised by the conducting layers}	
N	H10D 64/518	7	{characterised by their lengths or sectional shapes}	
N	H10D 64/519	7	{characterised by their top-view geometrical layouts}	
N	H10D 64/529	3	{Electrodes for IGFETs contacting substrate regions, e.g. for grounding or preventing parasitic effects}	
N	H10D 64/60	1	Electrodes characterised by their materials	
N	H10D 64/602	2	{Heterojunction gate electrodes for FETs}	
N	H10D 64/605	2	{Source, drain, or gate electrodes for FETs comprising highly resistive materials}	
N	H10D 64/608	2	{being superconducting}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 64/62	2	Electrodes ohmically coupled to a semiconductor	
N	H10D 64/64	2	Electrodes comprising a Schottky barrier to a semiconductor	
N	H10D 64/647	3	{Schottky drain or source electrodes for IGFETs}	
N	H10D 64/649	3	{Schottky drain or source electrodes for FETs having rectifying junction gate electrodes}	
N	H10D 64/66	2	Electrodes having a conductor capacitively coupled to a semiconductor by an insulator, e.g. MIS electrodes	
N	H10D 64/661	3	{the conductor comprising a layer of silicon contacting the insulator, e.g. polysilicon having vertical doping variation (having lateral variation in the gate structure H10D 64/671)}	
N	H10D 64/662	4	{the conductor further comprising additional layers, e.g. multiple silicon layers having different crystal structures}	
N	H10D 64/663	5	{the additional layers comprising a silicide layer contacting the layer of silicon, e.g. polycide gates}	
N	H10D 64/664	5	{the additional layers comprising a barrier layer between the layer of silicon and an upper metal or metal silicide layer}	
N	H10D 64/665	3	{the conductor comprising a layer of elemental metal contacting the insulator, e.g. tungsten or molybdenum (having lateral variation H10D 64/671)}	
N	H10D 64/666	4	{the conductor further comprising additional layers}	
Q	H10D 64/667	3	{the conductor comprising a layer of alloy material, compound material or organic material contacting the insulator, e.g. TiN work function layers (having lateral variation H10D 64/671)}	H10D 64/667, H10D 64/669
Q	H10D 64/668	4	{the layer being a silicide, e.g. $TiSi_2$}	H10D 64/668, H10D 64/669
N	H10D 64/669	4	{the conductor further comprising additional layers of alloy material,	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			compound material or organic material, e.g. TaN/TiAlN}	
Q	H10D 64/671	3	{the conductor having lateral variation in doping or structure}	H10D 64/671, H10D 64/675
N	H10D 64/675	3	{Gate sidewall spacers}	
N	H10D 64/679	4	{comprising air gaps}	
N	H10D 64/68	3	characterised by the insulator, e.g. by the gate insulator	
N	H10D 64/681	4	{having a compositional variation, e.g. multilayered}	
N	H10D 64/683	5	{being parallel to the channel plane}	
N	H10D 64/685	5	{being perpendicular to the channel plane}	
N	H10D 64/687	4	{having cavities, e.g. porous gate dielectrics having gasses therein}	
N	H10D 64/689	4	{having ferroelectric layers}	
N	H10D 64/691	4	{comprising metallic compounds, e.g. metal oxides or metal silicates (insulators comprising nitrogen H10D 64/693)}	
N	H10D 64/693	4	{the insulator comprising nitrogen, e.g. nitrides, oxynitrides or nitrogen-doped materials}	
N	H10D 80/00	0	Assemblies of multiple devices comprising at least one device covered by this subclass	
N	H10D 80/20	1	the at least one device being covered by groups H10D 1/00 - H10D 48/00, e.g. assemblies comprising capacitors, power FETs or Schottky diodes	
N	H10D 80/211	2	{Resistors, capacitors or inductors covered by H10D 1/00}	
N	H10D 80/213	3	{Resistors}	
N	H10D 80/215	3	{Capacitors}	
N	H10D 80/231	2	{Diodes covered by H10D 8/00}	
N	H10D 80/251	2	{FETs covered by H10D 30/00, e.g. power FETs}	
N	H10D 80/30	1	the at least one device being covered by groups H10D 84/00 - H10D 86/00, e.g. assemblies comprising integrated circuit processor chips	
N	H10D 84/00	0	Integrated devices formed in or on semiconductor substrates that comprise only semiconducting layers,	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			e.g. on Si wafers or on GaAs-on-Si wafers	
Q	H10D 84/01	1	Manufacture or treatment	H10D 84/01, H10D 84/02, H10D 84/03, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07, H10D 84/08
N	H10D 84/0102	2	{of thyristors having built-in components, e.g. thyristor having built-in diode}	
N	H10D 84/0105	3	{the built-in components being field-effect devices}	
N	H10D 84/0107	2	{Integrating at least one component covered by H10D 12/00 or H10D 30/00 with at least one component covered by H10D 8/00, H10D 10/00 or H10D 18/00, e.g. integrating IGFETs with BJTs}	
N	H10D 84/0109	3	{the at least one component covered by H10D 12/00 or H10D 30/00 being a MOS device}	
N	H10D 84/0112	2	{Integrating together multiple components covered by H10D 8/00, H10D 10/00 or H10D 18/00, e.g. integrating multiple BJTs}	
N	H10D 84/0114	3	{the components including vertical BJTs and lateral BJTs}	
N	H10D 84/0116	3	{the components including integrated injection logic [I2L]}	
N	H10D 84/0119	3	{the components including complementary BJTs}	
N	H10D 84/0121	4	{the complementary BJTs being vertical BJTs}	
N	H10D 84/0123	2	{Integrating together multiple components covered by H10D 12/00 or H10D 30/00, e.g. integrating multiple IGBTs}	
N	H10D 84/0126	3	{the components including insulated gates, e.g. IGFETs}	
N	H10D 84/0128	4	{Manufacturing their channels}	
N	H10D 84/013	4	{Manufacturing their source or drain regions, e.g. silicided source or drain regions}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/0133	5	{Manufacturing common source or drain regions between multiple IGFETs}	
N	H10D 84/0135	4	{Manufacturing their gate conductors}	
N	H10D 84/0137	5	{the gate conductors being silicided}	
N	H10D 84/014	5	{the gate conductors having different materials or different implants}	
N	H10D 84/0142	5	{the gate conductors having different shapes or dimensions}	
N	H10D 84/0144	4	{Manufacturing their gate insulating layers}	
N	H10D 84/0147	4	{Manufacturing their gate sidewall spacers}	
N	H10D 84/0149	4	{Manufacturing their interconnections or electrodes, e.g. source or drain electrodes}	
Q	H10D 84/0151	4	{Manufacturing their isolation regions}	H10D 84/0151, H10D 84/0153
N	H10D 84/0153	5	{using gate cut processes}	
Q	H10D 84/0156	4	{Manufacturing their doped wells}	H10D 84/0156, H10D 62/299
N	H10D 84/0158	4	{the components including FinFETs}	
N	H10D 84/016	4	{the components including vertical IGFETs}	
N	H10D 84/0163	4	{the components including enhancement-mode IGFETs and depletion-mode IGFETs}	
N	H10D 84/0165	4	{the components including complementary IGFETs, e.g. CMOS devices}	
N	H10D 84/0167	5	{Manufacturing their channels}	
N	H10D 84/017	5	{Manufacturing their source or drain regions, e.g. silicided source or drain regions}	
N	H10D 84/0172	5	{Manufacturing their gate conductors}	
N	H10D 84/0174	6	{the gate conductors being silicided}	
N	H10D 84/0177	6	{the gate conductors having different materials or different implants}	
N	H10D 84/0179	6	{the gate conductors having different shapes or dimensions}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/0181	5	{Manufacturing their gate insulating layers}	
N	H10D 84/0184	5	{Manufacturing their gate sidewall spacers}	
N	H10D 84/0186	5	{Manufacturing their interconnections or electrodes, e.g. source or drain electrodes}	
N	H10D 84/0188	5	{Manufacturing their isolation regions}	
N	H10D 84/0191	5	{Manufacturing their doped wells}	
N	H10D 84/0193	5	{the components including FinFETs}	
N	H10D 84/0195	5	{the components including vertical IGFETs}	
N	H10D 84/0198	2	{Integrating together multiple components covered by H10D 44/00, e.g. integrating charge coupled devices}	
Q	H10D 84/02	2	characterised by using material-based technologies	H10D 84/02, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 84/03, H10D 88/01

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/03	3	using Group IV technology, e.g. silicon technology or silicon-carbide [SiC] technology	
Q	H10D 84/032	4	{using diamond technology}	H10D 84/032, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/035	4	{using silicon carbide [SiC] technology}	H10D 84/035, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
N	H10D 84/038	4	{using silicon technology, e.g. SiGe}	
Q	H10D 84/05	3	using Group III-V technology	H10D 84/05, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/07	3	using Group II-VI technology	H10D 84/07, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013,

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/08	3	using combinations of technologies, e.g. using both Si and SiC technologies or using both Si and Group III-V technologies	H10D 84/08, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/101	1	{Integrated devices comprising main components and built-in components, e.g. IGBT having built-in freewheel diode}	
N	H10D 84/121	2	{BJTs having built-in components}	
N	H10D 84/125	3	{the built-in components being resistive elements, e.g. BJT having a built-in ballasting resistor}	
N	H10D 84/131	2	{Thyristors having built-in components}	
N	H10D 84/133	3	{the built-in components being capacitors or resistors}	
N	H10D 84/135	3	{the built-in components being diodes}	
N	H10D 84/136	4	{in anti-parallel configurations, e.g. reverse current thyristor [RCT]}	
N	H10D 84/138	3	{the built-in components being FETs}	
N	H10D 84/141	2	{VDMOS having built-in components}	
N	H10D 84/143	3	{the built-in components being PN junction diodes}	
N	H10D 84/144	4	{in antiparallel diode configurations}	
N	H10D 84/146	3	{the built-in components being Schottky barrier diodes}	
N	H10D 84/148	3	{the built-in components being breakdown diodes, e.g. Zener diodes}	
N	H10D 84/151	2	{LDMOS having built-in components}	
N	H10D 84/153	3	{the built-in component being PN junction diodes}	
N	H10D 84/154	4	{in antiparallel diode configurations}	
N	H10D 84/156	3	{the built-in components being Schottky barrier diodes}	
N	H10D 84/158	3	{the built-in components being breakdown diodes, e.g. Zener diodes}	
N	H10D 84/161	2	{IGBT having built-in components}	
N	H10D 84/201	1	{characterised by the integration of only components covered by H10D 1/00 or H10D 8/00, e.g. RLC circuits}	
N	H10D 84/204	2	{of combinations of diodes or capacitors or resistors}	
Q	H10D 84/206	3	{of combinations of capacitors and resistors}	H10D 84/206, H10D 84/209, H10D 84/212

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/209	3	{of only resistors}	
N	H10D 84/212	3	{of only capacitors}	
N	H10D 84/215	4	{of only varactors}	
N	H10D 84/217	4	{of only conductor-insulator-semiconductor capacitors}	
N	H10D 84/221	3	{of only diodes}	
Q	H10D 84/40	1	characterised by the integration of at least one component covered by groups H10D 12/00 or H10D 30/00 with at least one component covered by groups H10D 10/00 or H10D 18/00, e.g. integration of IGFETs with BJTs	H10D 84/40, H10D 84/80
Q	H10D 84/401	2	{Combinations of FETs or IGBTs with BJTs}	H10D 84/401, H10D 84/40
N	H10D 84/403	3	{Combinations of FETs or IGBTs with BJTs and with one or more of diodes, resistors or capacitors}	
N	H10D 84/406	4	{Combinations of FETs or IGBTs with vertical BJTs and with one or more of diodes, resistors or capacitors}	
N	H10D 84/409	4	{Combinations of FETs or IGBTs with lateral BJTs and with one or more of diodes, resistors or capacitors}	
N	H10D 84/60	1	characterised by the integration of at least one component covered by groups H10D 10/00 or H10D 18/00, e.g. integration of BJTs (H10D 84/40 takes precedence)	
N	H10D 84/611	2	{Combinations of BJTs and one or more of diodes, resistors or capacitors}	
N	H10D 84/613	3	{Combinations of vertical BJTs and one or more of diodes, resistors or capacitors}	
N	H10D 84/615	4	{Combinations of vertical BJTs and one or more of resistors or capacitors}	
N	H10D 84/617	4	{Combinations of vertical BJTs and only diodes}	
N	H10D 84/619	3	{Combinations of lateral BJTs and one or more of diodes, resistors or capacitors}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/63	2	Combinations of vertical and lateral BJTs	
N	H10D 84/641	2	{Combinations of only vertical BJTs (vertical complementary BJTs H10D 84/673)}	
N	H10D 84/642	3	{Combinations of non-inverted vertical BJTs of the same conductivity type having different characteristics, e.g. Darlington transistors}	
N	H10D 84/643	3	{Combinations of non-inverted vertical BJTs and inverted vertical BJTs}	
Q	H10D 84/645	2	{Combinations of only lateral BJTs}	H10D 84/645, H10D 84/67
N	H10D 84/65	2	Integrated injection logic	
N	H10D 84/652	3	{using vertical injector structures}	
N	H10D 84/655	3	{using field effect injector structures}	
N	H10D 84/658	3	{integrated in combination with analog structures}	
N	H10D 84/67	2	Complementary BJTs	
N	H10D 84/673	3	{Vertical complementary BJTs}	
N	H10D 84/676	2	{Combinations of only thyristors}	
N	H10D 84/80	1	characterised by the integration of at least one component covered by groups H10D 12/00 or H10D 30/00, e.g. integration of IGFETs (H10D 84/40 takes precedence)	
Q	H10D 84/811	2	{Combinations of field-effect devices and one or more diodes, capacitors or resistors}	H10D 84/811, H10D 84/813, H10D 84/817
N	H10D 84/813	3	{Combinations of field-effect devices and capacitor only}	
N	H10D 84/817	3	{Combinations of field-effect devices and resistors only}	
N	H10D 84/82	2	of only field-effect components	
Q	H10D 84/83	3	of only insulated-gate FETs [IGFET]	H10D 84/83, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832, H10D 84/833, H10D 84/835,

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				H10D 84/836, H10D 84/837, H10D 84/839
N	H10D 84/8311	4	{the IGFETs characterised by having different channel structures}	
N	H10D 84/8312	4	{the IGFETs characterised by having different source or drain region structures, e.g. IGFETs having symmetrical source or drain regions integrated with IGFETs having asymmetrical source or drain regions}	
N	H10D 84/83125	4	{the IGFETs characterised by having shared source or drain regions}	
N	H10D 84/83135	4	{the IGFETs characterised by having different gate conductor materials or different gate conductor implants}	
N	H10D 84/83138	4	{the IGFETs characterised by having different shapes or dimensions of their gate conductors}	
N	H10D 84/8314	4	{the IGFETs characterised by having gate insulating layers with different properties}	
N	H10D 84/8316	4	{the IGFETs characterised by having gate sidewall spacers specially adapted for integration}	
N	H10D 84/832	4	{comprising IGFETs having stacked nanowire, nanosheet or nanoribbon channels}	
N	H10D 84/833	5	{comprising forksheet IGFETs}	
Q	H10D 84/834	4	{comprising FinFETs}	H10D 84/834, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832, H10D 84/833, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
N	H10D 84/835	4	{comprising LDMOS}	
N	H10D 84/836	4	{comprising EDMOS}	
N	H10D 84/837	4	{comprising vertical IGFETs}	
N	H10D 84/839	5	{comprising VDMOS}	
Q	H10D 84/84	4	Combinations of enhancement-mode IGFETs and depletion-mode IGFETs	H10D 84/84, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
				84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
Q	H10D 84/85	4	Complementary IGFETs, e.g. CMOS	H10D 84/85, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/851, H10D 84/852
N	H10D 84/851	5	{comprising IGFETs having stacked nanowire, nanosheet or nanoribbon channels}	
N	H10D 84/852	6	{comprising forksheet IGFETs}	
Q	H10D 84/853	5	{comprising FinFETs}	H10D 84/853, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836 H10D 84/837, H10D 84/839, H10D 84/851, H10D 84/852
N	H10D 84/854	5	{comprising arrangements for preventing bipolar actions between the different IGFET regions, e.g. arrangements for latchup prevention}	
Q	H10D 84/856	5	{the complementary IGFETs having different architectures than each other, e.g. high-voltage and low-voltage CMOS}	H10D 84/856, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836 H10D 84/837, H10D 84/839
N	H10D 84/857	5	{comprising an N-type well but not a P-type well}	
N	H10D 84/858	5	{comprising a P-type well but not an N-type well}	
N	H10D 84/859	5	{comprising both N-type and P-type wells, e.g. twin-tub}	
N	H10D 84/86	2	of Schottky-barrier gate FETs	
N	H10D 84/87	2	of PN-junction gate FETs	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/891	1	{characterised by the integration of only components covered by H10D 44/00, e.g. integration of charge-coupled devices [CCD] or charge injection devices [CID]}	
N	H10D 84/895	2	{comprising bucket-brigade charge-coupled devices}	
N	H10D 84/90	1	Masterslice integrated circuits	
N	H10D 84/901	2	{comprising bipolar technology}	
N	H10D 84/903	2	{comprising field effect technology}	
N	H10D 84/905	3	{A3B5 or A3B6 gate arrays}	
N	H10D 84/907	3	{CMOS gate arrays}	
N	H10D 84/909	4	{Microarchitecture}	
N	H10D 84/911	5	{Basic cell P to N transistor counts}	
N	H10D 84/912	6	{4-T CMOS basic cells}	
N	H10D 84/914	6	{5-T CMOS basic cells}	
N	H10D 84/916	6	{6-T CMOS basic cells}	
N	H10D 84/918	6	{7-T CMOS basic cells}	
N	H10D 84/921	6	{8-T CMOS basic cells}	
N	H10D 84/922	5	{relative P to N transistor sizes}	
N	H10D 84/924	6	{for current drive capability}	
N	H10D 84/925	6	{for delay time adaptation}	
N	H10D 84/927	6	{for capacitive loading}	
N	H10D 84/929	5	{Isolations}	
N	H10D 84/931	6	{FET isolation}	
N	H10D 84/933	6	{LOCOS}	
N	H10D 84/935	5	{Degree of specialisation for implementing specific functions}	
N	H10D 84/937	6	{Implementation of digital circuits}	
N	H10D 84/938	7	{Implementation of memory functions}	
N	H10D 84/941	6	{Implementation of analog circuits}	
N	H10D 84/942	7	{Resistors and capacitors}	
N	H10D 84/944	6	{Hybrid analog or digital}	
N	H10D 84/946	6	{Embedded IO cells}	
N	H10D 84/948	6	{Transmission gates}	
N	H10D 84/949	6	{Porous cells, i.e. pass-through elements}	
N	H10D 84/951	5	{Technology used, i.e. design rules}	
N	H10D 84/953	6	{Sub-micron technology}	
N	H10D 84/955	6	{Twin-tub technology}	
N	H10D 84/957	6	{SOS or SOI technology}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 84/959	5	{Connectability characteristics, i.e. diffusion and polysilicon geometries}	
N	H10D 84/961	6	{Substrate and well contacts}	
N	H10D 84/962	6	{Horizontal or vertical grid line density}	
N	H10D 84/964	6	{Yield or reliability}	
N	H10D 84/966	6	{Gate electrode terminals or contacts}	
N	H10D 84/968	4	{Macro-architecture}	
N	H10D 84/971	5	{Number of core or basic cells in the macro (RAM or ROM)}	
N	H10D 84/972	5	{Distribution functions, e.g. sea of gates}	
N	H10D 84/974	5	{Layout specifications, i.e. inner core regions}	
N	H10D 84/975	6	{Wiring regions or routing}	
N	H10D 84/977	6	{Avoiding clock-skew or clock-delays}	
N	H10D 84/979	6	{Data lines, e.g. buses}	
N	H10D 84/981	6	{Power supply lines}	
N	H10D 84/983	4	{Levels of metallisation}	
N	H10D 84/985	5	{Two levels of metal}	
N	H10D 84/987	5	{Three levels of metal}	
N	H10D 84/988	5	{Four or more levels of metal}	
N	H10D 84/991	4	{Latch-up prevention}	
N	H10D 84/992	4	{Noise prevention, e.g. preventing crosstalk}	
N	H10D 84/994	4	{Radiation hardened circuits}	
N	H10D 84/996	2	{using combined field effect technology and bipolar technology}	
N	H10D 84/998	2	{Input and output buffer/driver structures}	
N	H10D 86/00	0	Integrated devices formed in or on insulating or conducting substrates, e.g. formed in silicon-on-insulator [SOI] substrates or on stainless steel or glass substrates	
N	H10D 86/01	1	Manufacture or treatment	
N	H10D 86/011	2	{comprising FinFETs}	
N	H10D 86/021	2	{of multiple TFTs}	
N	H10D 86/0212	3	{comprising manufacture, treatment or coating of substrates}	
N	H10D 86/0214	3	{using temporary substrates}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 86/0221	3	{comprising manufacture, treatment or patterning of TFT semiconductor bodies}	
N	H10D 86/0223	4	{comprising crystallisation of amorphous, microcrystalline or polycrystalline semiconductor materials}	
N	H10D 86/0225	5	{using crystallisation-promoting species, e.g. using a Ni catalyst}	
N	H10D 86/0227	5	{using structural arrangements to control crystal growth, e.g. placement of grain filters}	
N	H10D 86/0229	5	{characterised by control of the annealing or irradiation parameters}	
N	H10D 86/0231	3	{using masks, e.g. half-tone masks}	
N	H10D 86/0241	3	{using liquid deposition, e.g. printing}	
N	H10D 86/0251	3	{characterised by increasing the uniformity of device parameters}	
N	H10D 86/03	2	wherein the substrate comprises sapphire, e.g. silicon-on-sapphire [SOS]	
N	H10D 86/201	1	{the substrates comprising an insulating layer on a semiconductor body, e.g. SOI (H10D 86/40 take precedence)}	
N	H10D 86/215	2	{comprising FinFETs}	
N	H10D 86/40	1	characterised by multiple TFTs	
N	H10D 86/411	2	{characterised by materials, geometry or structure of the substrates}	
N	H10D 86/421	2	{having a particular composition, shape or crystalline structure of the active layer}	
N	H10D 86/423	3	{comprising semiconductor materials not belonging to the Group IV, e.g. InGaZnO}	
N	H10D 86/425	3	{having different crystal properties in different TFTs or within an individual TFT}	
N	H10D 86/427	3	{having different thicknesses of the semiconductor bodies in different TFTs}	
N	H10D 86/431	2	{having different compositions, shapes, layouts or thicknesses of gate insulators in different TFTs}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 86/441	2	{Interconnections, e.g. scanning lines}	
N	H10D 86/443	3	{adapted for preventing breakage, peeling or short circuiting}	
N	H10D 86/451	2	{characterised by the compositions or shapes of the interlayer dielectrics}	
N	H10D 86/471	2	{having different architectures, e.g. having both top-gate and bottom-gate TFTs}	
N	H10D 86/481	2	{integrated with passive devices, e.g. auxiliary capacitors}	
N	H10D 86/60	2	wherein the TFTs are in active matrices	
N	H10D 86/80	1	characterised by multiple passive components, e.g. resistors, capacitors or inductors	
Q	H10D 86/85	2	characterised by only passive components	H10D 86/85, H10D 84/201, H10D 84/206, H10D 84/209, H10D 84/212
N	H10D 87/00	0	Integrated devices comprising both bulk components and either SOI or SOS components on the same substrate	
N	H10D 88/00	0	Three-dimensional [3D] integrated devices	
N	H10D 88/01	1	{Manufacture or treatment}	
N	H10D 88/101	1	{comprising components on opposite major surfaces of semiconductor substrates}	
N	H10D 89/00	0	Aspects of integrated devices not covered by groups H10D 84/00 - H10D 88/00	
N	H10D 89/011	1	{Division of wafers or substrates to produce devices, each consisting of a single electric circuit element}	
N	H10D 89/013	2	{the wafers or substrates being semiconductor bodies}	
N	H10D 89/015	2	{the wafers or substrates being other than semiconductor bodies, e.g. insulating bodies}	
N	H10D 89/10	1	Integrated device layouts	
N	H10D 89/105	2	{adapted for thermal considerations}	
N	H10D 89/211	1	{Design considerations for internal polarisation (integrated injection logic H10D 84/65)}	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
N	H10D 89/213	2	{in field-effect devices}	
N	H10D 89/215	3	{comprising arrangements for charge pumping or biasing substrates}	
N	H10D 89/217	3	{comprising arrangements for charge injection in static induction transistor logic [SITL] devices}	
N	H10D 89/311	2	{in bipolar devices}	
N	H10D 89/60	1	Integrated devices comprising arrangements for electrical or thermal protection, e.g. protection circuits against electrostatic discharge [ESD]	
N	H10D 89/601	2	{for devices having insulated gate electrodes, e.g. for IGFETs or IGBTs}	
N	H10D 89/611	3	{using diodes as protective elements}	
N	H10D 89/711	3	{using bipolar transistors as protective elements}	
N	H10D 89/713	4	{including a PNP transistor and a NPN transistor, wherein each of said transistors has its base region coupled to the collector region of the other transistor, e.g. silicon controlled rectifier [SCR] devices}	
N	H10D 89/811	3	{using FETs as protective elements}	
N	H10D 89/813	4	{specially adapted to provide an electrical current path other than the field-effect induced current path}	
N	H10D 89/814	5	{involving a parasitic bipolar transistor triggered by the electrical biasing of the gate electrode of the FET, e.g. gate coupled transistors}	
N	H10D 89/815	5	{involving a parasitic bipolar transistor triggered by the local electrical biasing of the layer acting as base region of said parasitic bipolar transistor}	
N	H10D 89/817	4	{FETs in a Darlington configuration}	
N	H10D 89/819	4	{Bias arrangements for gate electrodes of FETs, e.g. RC networks or voltage partitioning circuits (FETs in a Darlington configuration H10D 89/817)}	
N	H10D 89/911	3	{using passive elements as protective elements}	
N	H10D 89/921	3	{characterised by the configuration of the interconnections connecting the	

Type*	Symbol	Indent Level Number of dots (e.g. 0, 1, 2)	Title "CPC only" text should normally be enclosed in {curly brackets}**	Transferred to#
			protective arrangements, e.g. ESD buses}	
N	H10D 89/931	3	{characterised by the dispositions of the protective arrangements}	
N	H10D 99/00	0	Subject matter not provided for in other groups of this subclass	

*N = new entries where reclassification into entries is involved; C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; T = existing entries with enlarged file scope, which receive documents from C or D entries, e.g. when a limiting reference is removed from the entry title; M = entries with no change to the file scope (no reclassification); D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed; U = entries that are unchanged.

NOTES:

- **No {curly brackets} are used for titles in CPC only subclasses, e.g. C12Y, A23Y; 2000 series symbol titles of groups found at the end of schemes (orthogonal codes); or the Y section titles. The {curly brackets} are used for 2000 series symbol titles found interspersed throughout the main trunk schemes (breakdown codes).
- U groups: it is obligatory to display the required "anchor" symbol (U group), i.e. the entry immediately preceding a new group or an array of new groups to be created (in case new groups are not clearly subgroups of C-type groups). Always include the symbol, indent level and title of the U group in the table above.
- All entry types should be included in the scheme changes table above for better understanding of the overall scheme change picture. Symbol, indent level, and title are required for all types.
- "Transferred to" column must be completed for all C, D, F, and Q type entries. F groups will be deleted once reclassification is completed.
- When multiple symbols are included in the "Transferred to" column, avoid using ranges of symbols in order to be as precise as possible.
- For administrative transfer of documents, the following text should be used: "<administrative transfer to XX>", "<administrative transfer to XX and YY simultaneously>", or "<administrative transfer to XX, YY, ...and ZZ simultaneously>" when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be "additional information".
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations "ADD" or "INV": <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or <administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the "D" entries of 2000-series or Y-series groups may not require a destination ("Transferred to") symbol, however it is required to specify "<no transfer>" in the "Transferred to" column for such cases.
- For finalization projects, the deleted "F" symbols should have <no transfer> in the "Transferred to" column.
- For more details about the types of scheme change, see CPC Guide.

B. New, Modified or Deleted Warning notice(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

Type*	Location	Old Warning notice	New/Modified Warning notice
M	H01L	1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups: H01L 21/203 covered by H01L 21/02631 H01L 21/205 covered by H01L 21/0262 H01L 21/208 covered by H01L 21/02623 H01L 21/301 covered by H01L 21/30 H01L 21/328 covered by H01L 29/66075 H01L 21/329 covered by H01L 29/66083 H01L 21/33 covered by H01L 29/66227 H01L 21/331 covered by H01L 29/66234 H01L 21/332 covered by H01L 29/66363 H01L 21/334 covered by H01L 29/66075 H01L 21/335 covered by H01L 29/66409 H01L 21/336 covered by H01L 29/66477 H01L 21/337 covered by H01L 29/66893 H01L 21/338 covered by H01L 29/66848 H01L 21/339 covered by H01L 29/66946 H01L 21/36 - H01L 21/368 covered by H01L 21/02107 H01L 21/58 covered by H01L 24/80 H01L 21/66 covered by H01L 22/00 H01L 21/98 covered by H01L 25/50 H01L 29/38 covered by H01L 29/04 - H01L 29/365 H01L 29/96 covered by H01L 29/68 - H01L 29/945	1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups: H01L 21/203 covered by H01L 21/02631 H01L 21/205 covered by H01L 21/0262 H01L 21/208 covered by H01L 21/02623 H01L 21/301 covered by H01L 21/30 H01L 21/36 - H01L 21/368 covered by H01L 21/02107 H01L 21/58 covered by H01L 24/80 H01L 21/66 covered by H01L 22/00 H01L 21/98 covered by H01L 25/50

Type*	Location	Old Warning notice	New/Modified Warning notice
D	H01L 21/02104	Groups H01L 21/02104 – H01L 21/02694 are incomplete pending reclassification of documents from groups H01L 21/06, H01L 21/16, and H01L 21/20. Groups H01L 21/02104 – H01L 21/02694, H01L 21/06, H01L 21/20,and H01L 21/16 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 21/02107	Groups H01L 21/02107 – H01L 21/02326 are incomplete pending reclassification of documents from groups H01L 21/312, H01L 21/314, H01L 21/316, and H01L 21/318. Groups H01L 21/02107 – H01L 21/02326, H01L 21/312, H01L 21/314, H01L 21/316, and H01L 21/318 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/10	Group H01L 27/10 is impacted by reclassification into group H10B 99/10. Groups H01L 27/10 and H10B 99/10 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/101	Group H01L 27/101 is impacted by reclassification into group H10B 99/14. Groups H01L 27/101 and H10B 99/14 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/102	Group H01L 27/102 is impacted by reclassification into group H10B 99/00. Groups H01L 27/102 and H10B 99/00 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/1021	Group H01L 27/1021 is impacted by reclassification into group H10B 99/16. Groups H01L 27/1021 and	Delete entire Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
		H10B 99/16 should be considered in order to perform a complete search.	
D	H01L 27/1022	Group H01L 27/1022 is impacted by reclassification into group H10B 99/00. Groups H01L 27/1022 and H10B 99/00 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/1027	Group H01L 27/1027 is impacted by reclassification into groups H10B 10/10, H10B 12/10, H10B 20/10, H10B 69/00 and H10B 99/20. All groups listed in this Warning should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/1028	Group H01L 27/1028 is impacted by reclassification into groups H10B 10/10, H10B 12/10, H10B 20/10, H10B 69/00 and H10B 99/20. All groups listed in this Warning should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/105	Group H01L 27/105 is impacted by reclassification into group H10B 99/22. Groups H01L 27/105 and H10B 99/22 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 27/1214	Group H01L 27/1218 – H01L 27/1296 are incomplete pending reclassification of documents from group H01L 27/1214. Groups H01L 27/1218 – H01L 27/1296 and H01L 27/1214 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 29/0852	Groups H01L 29/0852 – H01L 29/0886 are incomplete pending reclassification of documents from group H01L 29/0847 and H01L 29/7801. Groups H01L 29/0852 – H01L	Delete entire Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
		29/0886 and H01L 29/0847, H01L 29/7801 should be considered in order to perform a complete search.	
D	H01L 29/4991	Group H01L 29/4991 is incomplete pending reclassification of documents from group H01L 29/4983. Groups H01L 29/4991 and H01L 29/4983 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 29/7803	Groups H01L 29/7803 – H01L 29/7808 are incomplete pending reclassification of documents from group H01L 29/7802. Groups H01L 29/7803 – H01L 29/7808 and H01L 29/7802 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 29/7811	Group H01L 29/7811 is incomplete pending reclassification of documents from group H01L 29/7802. Groups H01L 29/7811 and H01L 29/7802 should be considered in order to perform a complete search.	Delete entire Warning
D	H01L 29/7815	Group H01L 29/7815 is incomplete pending reclassification of documents from group H01L 29/7802. Groups H01L 29/7815 and H01L 29/7802 should be considered in order to perform a complete search.	Delete entire Warning

SUBCLASS H10D - INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 1/01		Group H10D 1/01 is incomplete pending reclassification of documents from group H10D 8/051. Groups H10D 8/051 and H10D 1/01 should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 1/025		Group H10D 1/025 is incomplete pending reclassification of documents from groups H10D 8/051 and H10D 48/021. Groups H10D 8/051, H10D 48/021 and H10D 1/025 should be considered in order to perform a complete search.
N	H10D 1/045		Groups H10D 1/045 - H10D 1/048 are incomplete pending reclassification of documents from groups H10D 8/051 and H10D 48/021. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 1/40		Group H10D 1/40 is impacted by reclassification into group H10D 48/38. Groups H10D 1/40 and H10D 48/38 should be considered in order to perform a complete search.
N	H10D 8/00		Group H10D 8/00 is impacted by reclassification into group H10D 8/20. Groups H10D 8/00 and H10D 8/20 should be considered in order to perform a complete search.
N	H10D 8/01		Groups H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D 8/041, H10D 8/045 and H10D 8/055 are incomplete pending reclassification of documents from groups H10D 8/043, H10D 8/051 and H10D 48/021. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 8/043		Group H10D 8/043 is incomplete pending reclassification of documents from groups H10D 8/051 and H10D 48/021. Group H10D 8/043 is also impacted by reclassification into groups H10D 8/01, H10D 8/021 - H10D 8/024, H10D 8/041, H10D 8/045 and H10D 8/055. All groups listed in this Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 8/051		Group H10D 8/051 is incomplete pending reclassification of documents from group H10D 48/021. Group H10D 8/051 is also impacted by reclassification into groups H10D 1/01, H10D 1/025, H10D 1/045 - H10D 1/048, H10D 8/01, H10D 8/021 - H10D 8/024, H10D 8/041, H10D 8/043, H10D 8/045, H10D 8/053, H10D 8/055 and H10D 48/021. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 8/053		Group H10D 8/053 is incomplete pending reclassification of documents from groups H10D 8/051 and H10D 48/021. Groups H10D 8/051, H10D 48/021 and H10D 8/053 should be considered in order to perform a complete search.
N	H10D 8/20		Group H10D 8/20 is incomplete pending reclassification of documents from group H10D 8/00. Groups H10D 8/00 and H10D 8/20 should be considered in order to perform a complete search.
N	H10D 10/01		Group H10D 10/01 is incomplete pending reclassification of documents from group H10D 48/031. Group H10D 10/01 is also impacted by reclassification into groups H10D 10/051 - H10D 10/058. Groups H10D 48/031, H10D 10/01 and H10D 10/051 - H10D 10/058 should be considered in order to perform a complete search.
N	H10D 10/021		Group H10D 10/021 is incomplete pending reclassification of documents from group H10D 48/031. Groups H10D 48/031 and H10D 10/021 should be considered in order to perform a complete search.
N	H10D 10/031		Group H10D 10/031 is incomplete pending reclassification of documents from group

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 48/031. Groups H10D 48/031 and H10D 10/031 should be considered in order to perform a complete search.
N	H10D 10/041		Group H10D 10/041 is incomplete pending reclassification of documents from group H10D 48/031. Groups H10D 48/031 and H10D 10/041 should be considered in order to perform a complete search.
N	H10D 10/051		Groups H10D 10/051, H10D 10/056 and H10D 10/058 are incomplete pending reclassification of documents from groups H10D 10/01 and H10D 48/031. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 10/052		Group H10D 10/052 is incomplete pending reclassification of documents from groups H10D 10/01 and H10D 48/031. Group H10D 10/052 is also impacted by reclassification into group H10D 10/054. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 10/054		Group H10D 10/054 is incomplete pending reclassification of documents from groups H10D 10/01, H10D 10/052 and H10D 48/031. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 10/061		Group H10D 10/061 is incomplete pending reclassification of documents from group H10D 48/031. Groups H10D 48/031 and H10D 10/061 should be considered in order to perform a complete search.
N	H10D 12/01		Group H10D 12/01 is incomplete pending reclassification of documents from groups H10D 12/031 and H10D 48/031. Group H10D 12/01 is also impacted by reclassification into group H10D 12/031. All groups listed in this Warning should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 12/021		Group H10D 12/021 is incomplete pending reclassification of documents from group H10D 48/031. Groups H10D 48/031 and H10D 12/021 should be considered in order to perform a complete search.
N	H10D 12/031		Group H10D 12/031 is incomplete pending reclassification of documents from groups H10D 12/01 and H10D 48/031. Group H10D 12/031 is also impacted by reclassification into groups H10D 12/01, H10D 12/035, H10D 12/038, H10D 18/01 - H10D 18/031 and H10D 30/028 - H10D 30/0297. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 12/032		Group H10D 12/032 is incomplete pending reclassification of documents from group H10D 48/031. Groups H10D 48/031 and H10D 12/032 should be considered in order to perform a complete search.
N	H10D 12/035		Group H10D 12/035 is incomplete pending reclassification of documents from groups H10D 12/031 and H10D 48/031. Groups H10D 12/031, H10D 48/031 and H10D 12/035 should be considered in order to perform a complete search.
N	H10D 12/038		Group H10D 12/038 is incomplete pending reclassification of documents from groups H10D 12/031 and H10D 48/031. Groups H10D 12/031, H10D 48/031 and H10D 12/038 should be considered in order to perform a complete search.
N	H10D 12/211		Group H10D 12/211 is impacted by reclassification into groups H10D 18/40 and H10D 18/60 - H10D 18/655. Groups H10D 12/211, H10D 18/40 and H10D 18/60 - H10D 18/655 should

Type*	Location	Old Warning notice	New/Modified Warning notice
			be considered in order to perform a complete search.
N	H10D 12/411		Group H10D 12/411 is impacted by reclassification into groups H10D 12/415, H10D 12/416, H10D 12/417, H10D 12/418 and H10D 84/161. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 12/415		Group H10D 12/415 is incomplete pending reclassification of documents from group H10D 12/411. Groups H10D 12/411 and H10D 12/415 should be considered in order to perform a complete search.
N	H10D 12/416		Group H10D 12/416 is incomplete pending reclassification of documents from group H10D 12/411. Groups H10D 12/411 and H10D 12/416 should be considered in order to perform a complete search.
N	H10D 12/417		Group H10D 12/417 is incomplete pending reclassification of documents from group H10D 12/411. Groups H10D 12/411 and H10D 12/417 should be considered in order to perform a complete search.
N	H10D 12/418		Group H10D 12/418 is incomplete pending reclassification of documents from group H10D 12/411. Groups H10D 12/411 and H10D 12/418 should be considered in order to perform a complete search.
N	H10D 12/421		Group H10D 12/421 is incomplete pending reclassification of documents from group H10D 12/491. Groups H10D 12/491 and H10D 12/421 should be considered in order to perform a complete search.
N	H10D 12/461		Groups H10D 12/461 and H10D 12/481 are incomplete pending reclassification of documents from group H10D 12/491. Groups H10D 12/491, H10D 12/461 and H10D 12/481 should be considered

Type*	Location	Old Warning notice	New/Modified Warning notice
			in order to perform a complete search.
N	H10D 12/491		Group H10D 12/491 is impacted by reclassification into groups H10D 12/421 and H10D 12/461 - H10D 12/481. Groups H10D 12/491, H10D 12/421 and H10D 12/461 - H10D 12/481 should be considered in order to perform a complete search.
N	H10D 18/01		Groups H10D 18/01 - H10D 18/031 are incomplete pending reclassification of documents from groups H10D 12/031 and H10D 48/031. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 18/40		Group H10D 18/40 is incomplete pending reclassification of documents from group H10D 12/211. Groups H10D 12/211 and H10D 18/40 should be considered in order to perform a complete search.
N	H10D 18/60		Groups H10D 18/60 - H10D 18/655 are incomplete pending reclassification of documents from group H10D 12/211. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/00		Group H10D 30/00 is impacted by reclassification into group H10D 30/40. Groups H10D 30/00 and H10D 30/40 should be considered in order to perform a complete search.
N	H10D 30/01		Group H10D 30/01 is impacted by reclassification into groups H10D 30/012, H10D 30/014, H10D 30/015, H10D 30/017, H10D 30/019 - H10D 30/0198, H10D 30/021 - H10D 30/0415, H10D 30/051 - H10D 30/0516 and H10D 30/061 - H10D 30/0618. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/012		Group H10D 30/012 is incomplete pending reclassification of

Type*	Location	Old Warning notice	New/Modified Warning notice
			documents from group H10D 30/01. Groups H10D 30/01 and H10D 30/012 should be considered in order to perform a complete search.
N	H10D 30/014		Group H10D 30/014 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/014 is also impacted by reclassification into groups H10D 30/019 - H10D 30/0198. Groups H10D 30/01, H10D 30/014 and H10D 30/019 - H10D 30/0198 should be considered in order to perform a complete search.
N	H10D 30/015		Group H10D 30/015 is incomplete pending reclassification of documents from group H10D 30/01. Groups H10D 30/01 and H10D 30/015 should be considered in order to perform a complete search.
N	H10D 30/017		Group H10D 30/017 is incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/031 and H10D 30/0323. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/019		Group H10D 30/019 is incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/014, H10D 30/024, H10D 30/0241, H10D 30/031, H10D 30/0321, H10D 30/0323 and H10D 30/0327. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0191		Groups H10D 30/0191 - H10D 30/0194 are incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/014, H10D 30/024, H10D 30/0241, H10D 30/0245, H10D 30/031, H10D 30/0321, H10D 30/0323 and H10D 30/0327. All groups listed in this Warning should be considered

Type*	Location	Old Warning notice	New/Modified Warning notice
			in order to perform a complete search.
N	H10D 30/0195		Groups H10D 30/0195 - H10D 30/0197 are incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/014, H10D 30/024, H10D 30/031, H10D 30/0321, H10D 30/0323 and H10D 30/0327. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0198		Group H10D 30/0198 is incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/014, H10D 30/024, H10D 30/031, H10D 30/0321, H10D 30/0323 and H10D 30/0327. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/021		Groups H10D 30/021, H10D 30/0212, H10D 30/0213, H10D 30/0215, H10D 30/0217, H10D 30/0221, H10D 30/023, H10D 30/0243, H10D 30/025, H10D 30/026, H10D 30/027, H10D 30/0275, H10D 30/0277, H10D 30/0278 and H10D 30/0413 are incomplete pending reclassification of documents from group H10D 30/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0218		Group H10D 30/0218 is incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/022. Groups H10D 30/01, H10D 30/022 and H10D 30/0218 should be considered in order to perform a complete search.
N	H10D 30/022		Group H10D 30/022 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/022 is also impacted by reclassification into group H10D 30/0218. Groups H10D 30/01, H10D 30/022 and

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 30/0218 should be considered in order to perform a complete search.
N	H10D 30/0223		Groups H10D 30/0223 - H10D 30/0229 are incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/0273. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/024		Group H10D 30/024 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/024 is also impacted by reclassification into groups H10D 30/019 - H10D 30/0198. Groups H10D 30/01, H10D 30/024 and H10D 30/019 - H10D 30/0198 should be considered in order to perform a complete search.
N	H10D 30/0241		Group H10D 30/0241 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0241 is also impacted by reclassification into groups H10D 30/019 and H10D 30/0191 - H10D 30/0194. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0245		Group H10D 30/0245 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0245 is also impacted by reclassification into groups H10D 30/0191 - H10D 30/0194. Groups H10D 30/01, H10D 30/0245 and H10D 30/0191 - H10D 30/0194 should be considered in order to perform a complete search.
N	H10D 30/0273		Group H10D 30/0273 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0273 is also impacted by reclassification into groups H10D 30/0223 - H10D 30/0229 and H10D 64/017. All groups listed in this Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 30/028		Groups H10D 30/028 - H10D 30/0297 are incomplete pending reclassification of documents from groups H10D 12/031 and H10D 30/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/031		Group H10D 30/031 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/031 is also impacted by reclassification into groups H10D 30/017, H10D 30/019 - H10D 30/0198, H10D 30/0312 and H10D 30/0318. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0312		Group H10D 30/0312 is incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/031, H10D 30/0321 and H10D 30/0327. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0314		Group H10D 30/0314 is incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/0327. Groups H10D 30/01, H10D 30/0327 and H10D 30/0314 should be considered in order to perform a complete search.
N	H10D 30/0316		Group H10D 30/0316 is incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/0327. Groups H10D 30/01, H10D 30/0327 and H10D 30/0316 should be considered in order to perform a complete search.
N	H10D 30/0318		Group H10D 30/0318 is incomplete pending reclassification of documents from groups H10D 30/01, H10D 30/031, H10D 30/0321 and H10D 30/0327. All groups listed in this Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 30/0321		Group H10D 30/0321 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0321 is also impacted by reclassification into groups H10D 30/019 - H10D 30/0198, H10D 30/0312 and H10D 30/0318. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0323		Group H10D 30/0323 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0323 is also impacted by reclassification into groups H10D 30/017 and H10D 30/019 - H10D 30/0198. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0327		Group H10D 30/0327 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0327 is also impacted by reclassification into groups H10D 30/019 - H10D 30/0198, H10D 30/0312 - H10D 30/0316 and H10D 30/0318. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0411		Group H10D 30/0411 is incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/0415. Groups H10D 30/01, H10D 30/0415 and H10D 30/0411 should be considered in order to perform a complete search.
N	H10D 30/0415		Group H10D 30/0415 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/0415 is also impacted by reclassification into group H10D 30/0411. Groups H10D 30/01, H10D 30/0415 and H10D 30/0411 should be considered in order to perform a complete search.

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 30/051		Groups H10D 30/051 - H10D 30/0516 are incomplete pending reclassification of documents from group H10D 30/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/061		Group H10D 30/061 is incomplete pending reclassification of documents from group H10D 30/01. Group H10D 30/061 is also impacted by reclassification into groups H10D 30/0612 - H10D 30/0616 and H10D 30/0618. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0612		Groups H10D 30/0612 - H10D 30/0616 are incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/061. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/0618		Group H10D 30/0618 is incomplete pending reclassification of documents from groups H10D 30/01 and H10D 30/061. Groups H10D 30/01, H10D 30/061 and H10D 30/0618 should be considered in order to perform a complete search.
N	H10D 30/40		Group H10D 30/40 is incomplete pending reclassification of documents from group H10D 30/00. Groups H10D 30/00 and H10D 30/40 should be considered in order to perform a complete search.
N	H10D 30/43		Group H10D 30/43 is impacted by reclassification into groups H10D 30/435 and H10D 30/501 - H10D 30/509. Groups H10D 30/43, H10D 30/435 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/435		Group H10D 30/435 is incomplete pending reclassification of documents from group

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 30/43. Groups H10D 30/43 and H10D 30/435 should be considered in order to perform a complete search.
N	H10D 30/47		Group H10D 30/47 is impacted by reclassification into groups H10D 30/471, H10D 30/474, H10D 30/476, H10D 30/481 and H10D 30/501 - H10D 30/509. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/471		Groups H10D 30/471, H10D 30/474 and H10D 30/476 are incomplete pending reclassification of documents from group H10D 30/47. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/4735		Group H10D 30/4735 is incomplete pending reclassification of documents from group H10D 30/4738. Groups H10D 30/4738 and H10D 30/4735 should be considered in order to perform a complete search.
N	H10D 30/4738		Group H10D 30/4738 is impacted by reclassification into group H10D 30/4735. Groups H10D 30/4738 and H10D 30/4735 should be considered in order to perform a complete search.
N	H10D 30/477		Group H10D 30/477 is impacted by reclassification into group H10D 30/485. Groups H10D 30/477 and H10D 30/485 should be considered in order to perform a complete search.
N	H10D 30/478		Group H10D 30/478 is impacted by reclassification into group H10D 30/485. Groups H10D 30/478 and H10D 30/485 should be considered in order to perform a complete search.
N	H10D 30/481		Group H10D 30/481 is incomplete pending reclassification of documents from groups H10D 30/47 and H10D 30/6741. Groups H10D 30/47, H10D 30/6741 and H10D 30/481

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 30/485		Group H10D 30/485 is incomplete pending reclassification of documents from groups H10D 30/477, H10D 30/478 and H10D 30/6741. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/501		Groups H10D 30/501, H10D 30/502, H10D 30/507, H10D 30/508 and H10D 30/509 are incomplete pending reclassification of documents from groups H10D 30/43, H10D 30/47, H10D 30/62, H10D 30/6211, H10D 30/6217, H10D 30/6218, H10D 30/6219, H10D 30/6733, H10D 30/6734, H10D 30/6735, H10D 30/6748 and H10D 30/6757. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/503		Group H10D 30/503 is incomplete pending reclassification of documents from groups H10D 30/43, H10D 30/47, H10D 30/62, H10D 30/6211, H10D 30/6212, H10D 30/6213, H10D 30/6217, H10D 30/6218, H10D 30/6219, H10D 30/6733, H10D 30/6734, H10D 30/6735, H10D 30/6748 and H10D 30/6757. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/504		Groups H10D 30/504 and H10D 30/506 are incomplete pending reclassification of documents from groups H10D 30/43, H10D 30/47, H10D 30/62, H10D 30/6211, H10D 30/6212, H10D 30/6213, H10D 30/6217, H10D 30/6218, H10D 30/6219, H10D 30/6733, H10D 30/6734, H10D 30/6735, H10D 30/6748 and H10D 30/6757. All groups listed in this Warning should be considered in order to perform a complete search.

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 30/603		Group H10D 30/603 is impacted by reclassification into group H10D 30/605. Groups H10D 30/603 and H10D 30/605 should be considered in order to perform a complete search.
N	H10D 30/605		Group H10D 30/605 is incomplete pending reclassification of documents from groups H10D 30/603 and H10D 30/608. Groups H10D 30/603, H10D 30/608 and H10D 30/605 should be considered in order to perform a complete search.
N	H10D 30/608		Group H10D 30/608 is impacted by reclassification into group H10D 30/605. Groups H10D 30/608 and H10D 30/605 should be considered in order to perform a complete search.
N	H10D 30/62		Group H10D 30/62 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/62 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/6211		Group H10D 30/6211 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6211 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/6212		Group H10D 30/6212 is impacted by reclassification into groups H10D 30/503 and H10D 30/504 - H10D 30/506. Groups H10D 30/6212, H10D 30/503 and H10D 30/504 - H10D 30/506 should be considered in order to perform a complete search.
N	H10D 30/6213		Group H10D 30/6213 is impacted by reclassification into groups H10D 30/503 and H10D 30/504 - H10D 30/506. Groups H10D 30/6213, H10D 30/503 and H10D 30/504 - H10D 30/506 should be considered in order to perform a complete search.
N	H10D 30/6215		Group H10D 30/6215 is impacted by reclassification into group

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 30/6217. Groups H10D 30/6215 and H10D 30/6217 should be considered in order to perform a complete search.
N	H10D 30/6217		Group H10D 30/6217 is incomplete pending reclassification of documents from group H10D 30/6215. Group H10D 30/6217 is also impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6215, H10D 30/6217 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/6218		Group H10D 30/6218 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6218 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/6219		Group H10D 30/6219 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6219 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/64		Group H10D 30/64 is impacted by reclassification into groups H10D 30/645 and H10D 84/101. Groups H10D 30/64, H10D 30/645 and H10D 84/101 should be considered in order to perform a complete search.
N	H10D 30/645		Group H10D 30/645 is incomplete pending reclassification of documents from group H10D 30/64. Groups H10D 30/64 and H10D 30/645 should be considered in order to perform a complete search.
N	H10D 30/66		Group H10D 30/66 is impacted by reclassification into group H10D 30/662. Groups H10D 30/66 and H10D 30/662 should be considered in order to perform a complete search.
N	H10D 30/662		Group H10D 30/662 is incomplete pending reclassification of

Type*	Location	Old Warning notice	New/Modified Warning notice
			documents from group H10D 30/66. Groups H10D 30/66 and H10D 30/662 should be considered in order to perform a complete search.
N	H10D 30/6704		Group H10D 30/6704 is incomplete pending reclassification of documents from group H10D 30/6728. Groups H10D 30/6728 and H10D 30/6704 should be considered in order to perform a complete search.
N	H10D 30/6728		Group H10D 30/6728 is impacted by reclassification into groups H10D 30/6704 and H10D 30/674. Groups H10D 30/6728, H10D 30/6704 and H10D 30/674 should be considered in order to perform a complete search.
N	H10D 30/6733		Group H10D 30/6733 is impacted by reclassification into groups H10D 30/501 - H10D 30/509 and H10D 30/674. Groups H10D 30/6733, H10D 30/501 - H10D 30/509 and H10D 30/674 should be considered in order to perform a complete search.
N	H10D 30/6734		Group H10D 30/6734 is impacted by reclassification into groups H10D 30/501 - H10D 30/509 and H10D 30/674. Groups H10D 30/6734, H10D 30/501 - H10D 30/509 and H10D 30/674 should be considered in order to perform a complete search.
N	H10D 30/6735		Group H10D 30/6735 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6735 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/674		Group H10D 30/674 is incomplete pending reclassification of documents from groups H10D 30/6728, H10D 30/6733, H10D 30/6734 and H10D 30/6757. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 30/6741		Group H10D 30/6741 is impacted by reclassification into groups

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 30/481 and H10D 30/485. Groups H10D 30/6741, H10D 30/481 and H10D 30/485 should be considered in order to perform a complete search.
N	H10D 30/6748		Group H10D 30/6748 is impacted by reclassification into groups H10D 30/501 - H10D 30/509. Groups H10D 30/6748 and H10D 30/501 - H10D 30/509 should be considered in order to perform a complete search.
N	H10D 30/6757		Group H10D 30/6757 is impacted by reclassification into groups H10D 30/501 - H10D 30/509 and H10D 30/674. Groups H10D 30/6757, H10D 30/501 - H10D 30/509 and H10D 30/674 should be considered in order to perform a complete search.
N	H10D 30/68		Group H10D 30/68 is incomplete pending reclassification of documents from group H10D 30/701. Groups H10D 30/701 and H10D 30/68 should be considered in order to perform a complete search.
N	H10D 30/701		Group H10D 30/701 is impacted by reclassification into group H10D 30/68. Groups H10D 30/701 and H10D 30/68 should be considered in order to perform a complete search.
N	H10D 30/751		Group H10D 30/751 is impacted by reclassification into group H10D 30/798. Groups H10D 30/751 and H10D 30/798 should be considered in order to perform a complete search.
N	H10D 30/798		Group H10D 30/798 is incomplete pending reclassification of documents from group H10D 30/751. Groups H10D 30/751 and H10D 30/798 should be considered in order to perform a complete search.
N	H10D 48/00		Group H10D 48/00 is incomplete pending reclassification of documents from group H10D 48/30. Groups H10D 48/30 and H10D 48/00 should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 48/021		Group H10D 48/021 is incomplete pending reclassification of documents from group H10D 8/051. Group H10D 48/021 is also impacted by reclassification into groups H10D 1/025, H10D 1/045 - H10D 1/048 and H10D 8/01 - H10D 8/055. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 48/031		Group H10D 48/031 is impacted by reclassification into groups H10D 10/01 - H10D 10/061, H10D 12/01 - H10D 12/038 and H10D 18/01 - H10D 18/031. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 48/30		Group H10D 48/30 is impacted by reclassification into group H10D 48/00. Groups H10D 48/30 and H10D 48/00 should be considered in order to perform a complete search.
N	H10D 48/38		Group H10D 48/38 is incomplete pending reclassification of documents from group H10D 1/40. Groups H10D 1/40 and H10D 48/38 should be considered in order to perform a complete search.
N	H10D 48/383		Group H10D 48/383 is impacted by reclassification into group H10D 48/3835. Groups H10D 48/383 and H10D 48/3835 should be considered in order to perform a complete search.
N	H10D 48/3835		Group H10D 48/3835 is incomplete pending reclassification of documents from group H10D 48/383. Groups H10D 48/383 and H10D 48/3835 should be considered in order to perform a complete search.
N	H10D 62/00		Group H10D 62/00 is impacted by reclassification into group H10D 62/01. Groups H10D 62/00 and H10D 62/01 should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 62/01		Group H10D 62/01 is incomplete pending reclassification of documents from group H10D 62/00. Groups H10D 62/00 and H10D 62/01 should be considered in order to perform a complete search.
N	H10D 62/051		Groups H10D 62/051 - H10D 62/058 are incomplete pending reclassification of documents from group H10D 62/111. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/10		Group H10D 62/10 is impacted by reclassification into groups H10D 62/128 and H10D 62/129. Groups H10D 62/10, H10D 62/128 and H10D 62/129 should be considered in order to perform a complete search.
N	H10D 62/111		Group H10D 62/111 is impacted by reclassification into groups H10D 62/051 - H10D 62/058. Groups H10D 62/111 and H10D 62/051 - H10D 62/058 should be considered in order to perform a complete search.
N	H10D 62/128		Group H10D 62/128 is incomplete pending reclassification of documents from group H10D 62/10. Groups H10D 62/10 and H10D 62/128 should be considered in order to perform a complete search.
N	H10D 62/129		Group H10D 62/129 is incomplete pending reclassification of documents from group H10D 62/10. Groups H10D 62/10 and H10D 62/129 should be considered in order to perform a complete search.
N	H10D 62/141		Group H10D 62/141 is impacted by reclassification into group H10D 62/145. Groups H10D 62/141 and H10D 62/145 should be considered in order to perform a complete search.

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 62/145		Group H10D 62/145 is incomplete pending reclassification of documents from group H10D 62/141. Groups H10D 62/141 and H10D 62/145 should be considered in order to perform a complete search.
N	H10D 62/152		Group H10D 62/152 is impacted by reclassification into group H10D 62/156. Groups H10D 62/152 and H10D 62/156 should be considered in order to perform a complete search.
N	H10D 62/156		Group H10D 62/156 is incomplete pending reclassification of documents from group H10D 62/152. Groups H10D 62/152 and H10D 62/156 should be considered in order to perform a complete search.
N	H10D 62/299		Group H10D 62/299 is incomplete pending reclassification of documents from groups H10D 62/314 and H10D 84/0156. Groups H10D 62/314, H10D 84/0156 and H10D 62/299 should be considered in order to perform a complete search.
N	H10D 62/314		Group H10D 62/314 is impacted by reclassification into group H10D 62/299. Groups H10D 62/314 and H10D 62/299 should be considered in order to perform a complete search.
N	H10D 62/378		Group H10D 62/378 is impacted by reclassification into group H10D 64/529. Groups H10D 62/378 and H10D 64/529 should be considered in order to perform a complete search.
N	H10D 62/80		Group H10D 62/80 is incomplete pending reclassification of documents from group H10D 62/81. Group H10D 62/80 is also impacted by reclassification into groups H10D 62/82, H10D 62/8271, H10D 62/8281, H10D 62/871, H10D 62/874, H10D 62/875, H10D 62/881 and H10D 62/883. All groups listed in this Warning should be considered

Type*	Location	Old Warning notice	New/Modified Warning notice
			in order to perform a complete search.
N	H10D 62/81		Group H10D 62/81 is impacted by reclassification into group H10D 62/80. Groups H10D 62/81 and H10D 62/80 should be considered in order to perform a complete search.
N	H10D 62/82		Group H10D 62/82 is incomplete pending reclassification of documents from groups H10D 62/80, H10D 62/871 and H10D 62/874. Group H10D 62/82 is also impacted by reclassification into groups H10D 62/8271 and H10D 62/8281. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/822		Group H10D 62/822 is incomplete pending reclassification of documents from group H10D 62/83. Groups H10D 62/83 and H10D 62/822 should be considered in order to perform a complete search.
N	H10D 62/824		Group H10D 62/824 is incomplete pending reclassification of documents from group H10D 62/85. Groups H10D 62/85 and H10D 62/824 should be considered in order to perform a complete search.
N	H10D 62/826		Group H10D 62/826 is incomplete pending reclassification of documents from group H10D 62/86. Groups H10D 62/86 and H10D 62/826 should be considered in order to perform a complete search.
N	H10D 62/8271		Group H10D 62/8271 is incomplete pending reclassification of documents from groups H10D 62/80 and H10D 62/82. Groups H10D 62/80, H10D 62/82 and H10D 62/8271 should be considered in order to perform a complete search.
N	H10D 62/8281		Group H10D 62/8281 is incomplete pending reclassification of documents from groups H10D 62/80, H10D 62/82,

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 62/871 and H10D 62/874. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/83		Group H10D 62/83 is impacted by reclassification into groups H10D 62/822, H10D 62/832, H10D 62/834 and H10D 62/881. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/8303		Group H10D 62/8303 is impacted by reclassification into group H10D 62/882. Groups H10D 62/8303 and H10D 62/882 should be considered in order to perform a complete search.
N	H10D 62/832		Group H10D 62/832 is incomplete pending reclassification of documents from group H10D 62/83. Groups H10D 62/83 and H10D 62/832 should be considered in order to perform a complete search.
N	H10D 62/834		Group H10D 62/834 is incomplete pending reclassification of documents from group H10D 62/83. Groups H10D 62/83 and H10D 62/834 should be considered in order to perform a complete search.
N	H10D 62/85		Group H10D 62/85 is impacted by reclassification into groups H10D 62/824, H10D 62/852 and H10D 62/854. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/8503		Group H10D 62/8503 is impacted by reclassification into group H10D 62/881. Groups H10D 62/8503 and H10D 62/881 should be considered in order to perform a complete search.
N	H10D 62/852		Group H10D 62/852 is incomplete pending reclassification of documents from group H10D 62/85. Groups H10D 62/85 and H10D 62/852 should be considered in order to perform a complete search.

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 62/854		Group H10D 62/854 is incomplete pending reclassification of documents from group H10D 62/85. Groups H10D 62/85 and H10D 62/854 should be considered in order to perform a complete search.
N	H10D 62/86		Group H10D 62/86 is impacted by reclassification into groups H10D 62/826, H10D 62/8603, H10D 62/862 and H10D 62/864. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/8603		Group H10D 62/8603 is incomplete pending reclassification of documents from group H10D 62/86. Groups H10D 62/86 and H10D 62/8603 should be considered in order to perform a complete search.
N	H10D 62/862		Group H10D 62/862 is incomplete pending reclassification of documents from group H10D 62/86. Groups H10D 62/86 and H10D 62/862 should be considered in order to perform a complete search.
N	H10D 62/864		Group H10D 62/864 is incomplete pending reclassification of documents from group H10D 62/86. Groups H10D 62/86 and H10D 62/864 should be considered in order to perform a complete search.
N	H10D 62/871		Group H10D 62/871 is incomplete pending reclassification of documents from group H10D 62/80. Group H10D 62/871 is also impacted by reclassification into groups H10D 62/82, H10D 62/8281 and H10D 62/883. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/874		Group H10D 62/874 is incomplete pending reclassification of documents from group H10D 62/80. Group H10D 62/874 is also impacted by reclassification into groups H10D 62/82, H10D 62/8281 and H10D 62/883.

Type*	Location	Old Warning notice	New/Modified Warning notice
			All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/875		Group H10D 62/875 is incomplete pending reclassification of documents from group H10D 62/80. Groups H10D 62/80 and H10D 62/875 should be considered in order to perform a complete search.
N	H10D 62/881		Group H10D 62/881 is incomplete pending reclassification of documents from groups H10D 62/80, H10D 62/83 and H10D 62/8503. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 62/882		Group H10D 62/882 is incomplete pending reclassification of documents from group H10D 62/8303. Groups H10D 62/8303 and H10D 62/882 should be considered in order to perform a complete search.
N	H10D 62/883		Group H10D 62/883 is incomplete pending reclassification of documents from groups H10D 62/80, H10D 62/871 and H10D 62/874. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/017		Group H10D 64/017 is incomplete pending reclassification of documents from group H10D 30/0273. Groups H10D 30/0273 and H10D 64/017 should be considered in order to perform a complete search.
N	H10D 64/23		Group H10D 64/23 is impacted by reclassification into group H10D 64/232. Groups H10D 64/23 and H10D 64/232 should be considered in order to perform a complete search.
N	H10D 64/232		Group H10D 64/232 is incomplete pending reclassification of documents from group H10D 64/23. Groups H10D 64/23 and H10D 64/232 should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 64/252		Group H10D 64/252 is impacted by reclassification into groups H10D 64/2523 and H10D 64/2527. Groups H10D 64/252, H10D 64/2523 and H10D 64/2527 should be considered in order to perform a complete search.
N	H10D 64/2523		Group H10D 64/2523 is incomplete pending reclassification of documents from group H10D 64/252. Groups H10D 64/252 and H10D 64/2523 should be considered in order to perform a complete search.
N	H10D 64/2527		Group H10D 64/2527 is incomplete pending reclassification of documents from groups H10D 64/252 and H10D 64/256. Groups H10D 64/252, H10D 64/256 and H10D 64/2527 should be considered in order to perform a complete search.
N	H10D 64/254		Group H10D 64/254 is impacted by reclassification into groups H10D 64/256 - H10D 64/2565 and H10D 64/257. Groups H10D 64/254, H10D 64/256 - H10D 64/2565 and H10D 64/257 should be considered in order to perform a complete search.
N	H10D 64/256		Group H10D 64/256 is incomplete pending reclassification of documents from groups H10D 64/254 and H10D 64/257. Group H10D 64/256 is also impacted by reclassification into group H10D 64/2527. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 64/2565		Group H10D 64/2565 is incomplete pending reclassification of documents from group H10D 64/254. Groups H10D 64/254 and H10D 64/2565 should be considered in order to perform a complete search.
N	H10D 64/257		Group H10D 64/257 is incomplete pending reclassification of documents from group

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 64/254. Group H10D 64/257 is also impacted by reclassification into group H10D 64/256. Groups H10D 64/254, H10D 64/257 and H10D 64/256 should be considered in order to perform a complete search.
N	H10D 64/529		Group H10D 64/529 is incomplete pending reclassification of documents from group H10D 62/378. Groups H10D 62/378 and H10D 64/529 should be considered in order to perform a complete search.
N	H10D 64/667		Group H10D 64/667 is impacted by reclassification into group H10D 64/669. Groups H10D 64/667 and H10D 64/669 should be considered in order to perform a complete search.
N	H10D 64/668		Group H10D 64/668 is impacted by reclassification into group H10D 64/669. Groups H10D 64/668 and H10D 64/669 should be considered in order to perform a complete search.
N	H10D 64/669		Group H10D 64/669 is incomplete pending reclassification of documents from groups H10D 64/667 and H10D 64/668. Groups H10D 64/667, H10D 64/668 and H10D 64/669 should be considered in order to perform a complete search.
N	H10D 64/671		Group H10D 64/671 is impacted by reclassification into group H10D 64/675. Groups H10D 64/671 and H10D 64/675 should be considered in order to perform a complete search.
N	H10D 64/675		Group H10D 64/675 is incomplete pending reclassification of documents from group H10D 64/671. Groups H10D 64/671 and H10D 64/675 should be considered in order to perform a complete search.
N	H10D 84/01		Group H10D 84/01 is impacted by reclassification into groups H10D 84/02, H10D 84/03, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07 and

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0107		Groups H10D 84/0107 and H10D 84/0109 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0112		Groups H10D 84/0112 - H10D 84/0121 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0123		Groups H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193 and H10D 84/0195 are incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0151		Group H10D 84/0151 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05,

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 84/07 and H10D 84/08. Group H10D 84/0151 is also impacted by reclassification into group H10D 84/0153. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0153		Group H10D 84/0153 is incomplete pending reclassification of documents from groups H10D 84/0151, H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0156		Group H10D 84/0156 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. Group H10D 84/0156 is also impacted by reclassification into group H10D 62/299. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/0198		Group H10D 84/0198 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/02		Group H10D 84/02 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/02 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158,

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198, H10D 84/03 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/03		Group H10D 84/03 is incomplete pending reclassification of documents from groups H10D 84/01 and H10D 84/02. Groups H10D 84/01, H10D 84/02 and H10D 84/03 should be considered in order to perform a complete search.
N	H10D 84/032		Group H10D 84/032 is impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/035		Group H10D 84/035 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/035 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.

Type*	Location	Old Warning notice	New/Modified Warning notice
N	H10D 84/038		Group H10D 84/038 is incomplete pending reclassification of documents from group H10D 84/01. Groups H10D 84/01 and H10D 84/038 should be considered in order to perform a complete search.
N	H10D 84/05		Group H10D 84/05 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/05 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/07		Group H10D 84/07 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/07 is also impacted by reclassification into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/08		Group H10D 84/08 is incomplete pending reclassification of documents from group H10D 84/01. Group H10D 84/08 is also impacted by reclassification

Type*	Location	Old Warning notice	New/Modified Warning notice
			into groups H10D 84/0107 - H10D 84/0109, H10D 84/0112 - H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013 - H10D 84/0133, H10D 84/0135 - H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151 - H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165 - H10D 84/0195, H10D 84/0198 and H10D 88/01. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/101		Group H10D 84/101 is incomplete pending reclassification of documents from group H10D 30/64. Groups H10D 30/64 and H10D 84/101 should be considered in order to perform a complete search.
N	H10D 84/161		Group H10D 84/161 is incomplete pending reclassification of documents from group H10D 12/411. Groups H10D 12/411 and H10D 84/161 should be considered in order to perform a complete search.
N	H10D 84/201		Group H10D 84/201 is incomplete pending reclassification of documents from group H10D 86/85. Groups H10D 86/85 and H10D 84/201 should be considered in order to perform a complete search.
N	H10D 84/206		Group H10D 84/206 is incomplete pending reclassification of documents from group H10D 86/85. Group H10D 84/206 is also impacted by reclassification into groups H10D 84/209 and H10D 84/212. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/209		Group H10D 84/209 is incomplete pending reclassification of documents from groups H10D 84/206 and H10D 86/85. Groups H10D 84/206, H10D 86/85 and H10D 84/209 should be

Type*	Location	Old Warning notice	New/Modified Warning notice
			considered in order to perform a complete search.
N	H10D 84/212		Group H10D 84/212 is incomplete pending reclassification of documents from groups H10D 84/206 and H10D 86/85. Groups H10D 84/206, H10D 86/85 and H10D 84/212 should be considered in order to perform a complete search.
N	H10D 84/40		Group H10D 84/40 is incomplete pending reclassification of documents from group H10D 84/401. Group H10D 84/40 is also impacted by reclassification into group H10D 84/80. Groups H10D 84/401, H10D 84/40 and H10D 84/80 should be considered in order to perform a complete search.
N	H10D 84/401		Group H10D 84/401 is impacted by reclassification into group H10D 84/40. Groups H10D 84/401 and H10D 84/40 should be considered in order to perform a complete search.
N	H10D 84/645		Group H10D 84/645 is impacted by reclassification into group H10D 84/67. Groups H10D 84/645 and H10D 84/67 should be considered in order to perform a complete search.
N	H10D 84/67		Group H10D 84/67 is incomplete pending reclassification of documents from group H10D 84/645. Groups H10D 84/645 and H10D 84/67 should be considered in order to perform a complete search.
N	H10D 84/80		Group H10D 84/80 is incomplete pending reclassification of documents from group H10D 84/40. Groups H10D 84/40 and H10D 84/80 should be considered in order to perform a complete search.
N	H10D 84/811		Group H10D 84/811 is impacted by reclassification into groups H10D 84/813 and H10D 84/817. Groups H10D 84/811, H10D 84/813 and H10D 84/817

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 84/813		Group H10D 84/813 is incomplete pending reclassification of documents from group H10D 84/811. Groups H10D 84/811 and H10D 84/813 should be considered in order to perform a complete search.
N	H10D 84/817		Group H10D 84/817 is incomplete pending reclassification of documents from group H10D 84/811. Groups H10D 84/811 and H10D 84/817 should be considered in order to perform a complete search.
N	H10D 84/83		Group H10D 84/83 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832 - H10D 84/833, H10D 84/835, H10D 84/836 and H10D 84/837 - H10D 84/839. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/8311		Group H10D 84/8311 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/8312		Group H10D 84/8312 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/83125		Group H10D 84/83125 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834 and H10D 84/84. All groups listed in this Warning should be considered

Type*	Location	Old Warning notice	New/Modified Warning notice
			in order to perform a complete search.
N	H10D 84/83135		Group H10D 84/83135 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/83138		Group H10D 84/83138 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/8314		Group H10D 84/8314 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/8316		Group H10D 84/8316 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/85, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/832		Groups H10D 84/832 and H10D 84/833 are incomplete pending reclassification of documents from groups H10D 84/83 and H10D 84/834. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/834		Group H10D 84/834 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832 -

Type*	Location	Old Warning notice	New/Modified Warning notice
			H10D 84/833, H10D 84/835, H10D 84/836 and H10D 84/837 - H10D 84/839. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/835		Group H10D 84/835 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/836		Group H10D 84/836 is incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/837		Groups H10D 84/837 and H10D 84/839 are incomplete pending reclassification of documents from groups H10D 84/83, H10D 84/834, H10D 84/84, H10D 84/853 and H10D 84/856. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/84		Group H10D 84/84 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836 and H10D 84/837 - H10D 84/839. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/85		Group H10D 84/85 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316 and H10D 84/851 - H10D 84/852. All groups listed in this Warning

Type*	Location	Old Warning notice	New/Modified Warning notice
			should be considered in order to perform a complete search.
N	H10D 84/851		Groups H10D 84/851 and H10D 84/852 are incomplete pending reclassification of documents from groups H10D 84/85 and H10D 84/853. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/853		Group H10D 84/853 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836, H10D 84/837 - H10D 84/839 and H10D 84/851 - H10D 84/852. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 84/856		Group H10D 84/856 is impacted by reclassification into groups H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836 and H10D 84/837 - H10D 84/839. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 86/85		Group H10D 86/85 is impacted by reclassification into groups H10D 84/201, H10D 84/206, H10D 84/209 and H10D 84/212. All groups listed in this Warning should be considered in order to perform a complete search.
N	H10D 88/01		Group H10D 88/01 is incomplete pending reclassification of documents from groups H10D 84/02, H10D 84/032, H10D 84/035, H10D 84/05, H10D 84/07 and H10D 84/08. All groups listed in this Warning should be considered in order to perform a complete search.

*N = new warning, M = modified warning, D = deleted warning

NOTE: The "Location" column only requires the symbol PRIOR to the location of the warning. No further directions such as "before" or "after" are required.

C. New, Modified or Deleted Note(s)

SUBCLASS H01L - SEMICONDUCTOR DEVICES NOT COVERED BY CLASS H10

Type*	Location	Old Note	New/Modified Note
D	H01L 27/00	In this group the last place priority rule is applied, i.e. at each hierarchical level, in the absence of an indication to the contrary, classification is made in the last appropriate place.	Delete entire Note
D	H01L 27/105	In this group and its subgroups classification is made in any appropriate place	Delete entire Note
D	H01L 29/00	In this main group, classification is made both in groups H01L 29/02 - H01L 29/51 and in groups H01L 29/66 - H01L 29/94 if both of these sets of groups are relevant.	Delete entire Note
D	H01L 29/15	Group H01L 29/15 takes precedence over groups H01L 29/16 - H01L 29/26.	Delete entire Note
D	H01L 29/41741	A pseudo-vertical device is a device with the drain and source electrodes on the same main surface and where the main current is vertical at least in a part of its path	Delete entire Note
D	H01L 29/4175	The sink or via-hole leading to the source or drain region is considered to form part of the source or drain electrode	Delete entire Note
D	H01L 29/41758	Interdigitated structure means that at least one of the source or drain region has two or more fingers	Delete entire Note
D	H01L 29/49	This group covers also devices using any other conductor material in place of metal	Delete entire Note
D	H01L 29/7395	The transistor is called vertical if the emitter and the collector are not on the same main surface or, if they are on the same main surface, at least a part of the main current has a component substantially not parallel to the main surface	Delete entire Note
D	H01L 29/7834	Field oxide sunken in the substrate and not filling a groove is not an element characterising a non-planar structure	Delete entire Note

Type*	Location	Old Note	New/Modified Note
D	H01L 29/786	In groups H01L 29/78651 - H01L 29/78696, the materials specified for the transistors are the material of the channel region	Delete entire Note

SUBCLASS H10D - INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

Type*	Location	Old Note	New/Modified Note
N	H10D		1. This subclass covers electric semiconductor devices having inorganic semiconductor bodies. This includes the following kind of devices: • inorganic semiconductor devices specially adapted for rectifying, amplifying, oscillating or switching, e.g. transistors or diodes; • individual inorganic resistors or capacitors having potential barriers; • individual resistors, capacitors or inductors having no potential barriers, and specially adapted for integration with other semiconductor components; • semiconductor bodies, or regions thereof, of devices covered by this subclass; • electrodes of devices covered by this subclass; • integrated devices, e.g. CMOS integrated devices; • processes or apparatus specially adapted for the manufacture or treatment of such devices. 2. This subclass does not cover: • electronic memory devices, which are

Type*	Location	Old Note	New/Modified Note
			covered by subclass H10B; • semiconductor devices sensitive to infrared radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation, which are covered by subclass H10F; • light-emitting semiconductor devices having at least one potential barrier, which are covered by subclass H10H; • thermoelectric, thermomagnetic, piezoelectric, electrostrictive, magnetostrictive, magnetic-effect, superconducting or other electric solid-state devices, which are covered by subclass H10N; • constructional details other than semiconductor bodies or electrodes, which are covered by group H01L 23/00. 3. In this subclass, the periodic system used is the I to VIII group system indicated in the Periodic Table under Note (3) of section C.
N	H10D 1/00		This group covers: • individual inorganic resistors or capacitors having potential barriers; • individual resistors, capacitors or inductors having no potential barriers, and specially

Type*	Location	Old Note	New/Modified Note
			adapted for integration with other semiconductor components.
N	H10D 8/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 10/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 12/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 18/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 30/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 44/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 48/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 62/13		This group covers only semiconductor regions for devices that comprise three or more electrodes.

Type*	**Location**	**Old Note**	**New/Modified Note**
N	H10D 62/80		1. When classifying in this group, constituents of a material are considered irrespective of any dopants or other impurities. 2. In this group: • groups H10D 62/81 - {H10D 62/8181}, covering quantum or superlattice structures, take precedence over groups H10D 62/82 - {H10D 62/8281}, covering heterojunctions; • groups H10D 62/82 - {H10D 62/8281}, covering heterojunctions, take precedence over groups H10D 62/83 - {H10D 62/883}, covering other materials; • {groups H10D 62/881 - H10D 62/883, covering two-dimensional materials, take precedence over groups H10D 62/83 - H10D 62/875, covering other materials.}
N	H10D 62/84		This group <u>does not cover</u> chemical compounds of selenium or tellurium.
N	H10D 84/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.
N	H10D 86/00		In this group, when the manufacture or treatment of a device is determined to be novel and non-obvious, the device itself is also classified.

*N = new note, M = modified note, D = deleted note

NOTE: The "Location" column only requires the symbol PRIOR to the location of the note. No further directions such as "before" or "after" are required.

D. New, Modified or Deleted Guidance Heading(s)

SUBCLASS H10D - INORGANIC ELECTRIC SEMICONDUCTOR DEVICES

Type*	Location	Old Guidance Heading	New/Modified Guidance Heading
N	H10D 1/00 - H10D 48/00		Individual devices
N	H10D 62/00 - H10D 64/00		Constructional details
N	H10D 80/00 - H10D 89/00		Integrated devices; Assemblies of multiple devices

*N = new guidance heading, M =modified guidance heading, D = deleted guidance heading

NOTES:

- The "Location" column requires the symbol AFTER the guidance heading location. No further directions such as "before" or "after" are required.
- In cases where there may be confusion as to whether a new group falls within the scope of a guidance heading, indicate the guidance heading and whether the group does or does not go with the guidance heading. This can be included in the "Location" column. For example, the guidance heading "Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen" encompasses groups C07C 301/00-395/00 only. If a new group C07C 398/00 is proposed and is included in the guidance heading scope, indicate this in the "Location" column as follows: 398/00 to be included under the guidance heading: "Compounds containing carbon together with sulfur, selenium or tellurium with or without hydrogen, halogens, oxygen or nitrogen."

2. A. DEFINITIONS (modified)

H01L 21/28

Definition statement

Replace: the existing Definition statement text with the following revised text:

Includes processes for forming

- conductor-semiconductor,
- conductor-insulator-semiconductor, or
- conductor-insulator-conductor-insulator-semiconductor structures.

Multistep processes for manufacturing electrodes on semiconductor bodies characterised by

- a sequence of single steps, possibly including steps like deposition conductive material, alloying, silicidation,
- the structure or the shape of the electrode.

References

Delete: The entire Limiting references section.

Informative references

Replace: The existing Informative references table with the following updated table:

Diffusion of dopants	H01L 21/22
Alloying of electrode materials	H01L 21/24
Implantation of dopants	H01L 21/265
Etching the insulating layers	H01L 21/311
Physical or chemical etching of the layers	H01L 21/3213
Depositing or patterning electrodes for capacitors	H10D 1/042, H10D 1/043
Manufacturing electrodes for devices having potential barriers	H10D 64/01

Special rules of classification

Insert: periods at the end of both paragraphs of text so that the Special rules section appears as follows:

Formation of electrodes only involving an etching of conductive materials, including silicide on polysilicon: H01L21/3213 and subgroups.

Information peculiar to single-step processes should also be classified in the corresponding group, e.g.

- H01L21/311 or H01L21/3213 for etching,
- H01L21/027, H01L21/033, H01L21/31144 or H01L21/32139 for masking,
- H01L21/3105 or H01L21/321 for planarising.

H01L 21/34

References

Delete: The entire Limiting references section.

Insert: The following new Informative references section:

Informative references

Attention is drawn to the following places, which may be of interest for search:

Manufacturing radiation sensitive devices	H10F 71/00
Group II-IV active materials for radiation sensitive devices	H10F 77/123
Manufacturing light-emitting devices	H10H 20/01
Group II-IV active materials for light-emitting devices	H10H 20/823

Special rules of classification

Delete: The entire Special rules section.

2. B. DEFINITIONS QUICK FIX

Symbol	Location of change (e.g., section title)	Existing reference symbol or text	Action; New symbol; New text
H01L 21/164			Delete entire Definition
H01L 2021/775			Delete entire Definition
H01L 21/786			Delete entire Definition
H01L 21/82			Delete entire Definition
H01L 21/8221			Delete entire Definition
H01L 21/823487			Delete entire Definition
H01L 21/823885			Delete entire Definition
H01L 27/00			Delete entire Definition
H01L 27/01			Delete entire Definition
H01L 27/013			Delete entire Definition
H01L 27/016			Delete entire Definition
H01L 27/02			Delete entire Definition
H01L 27/0207			Delete entire Definition
H01L 27/0211			Delete entire Definition
H01L 27/0222			Delete entire Definition
H01L 27/0225			Delete entire Definition
H01L 27/0233			Delete entire Definition
H01L 27/0248			Delete entire Definition
H01L 27/0251			Delete entire Definition

H01L 27/0255			Delete entire Definition
H01L 27/0259			Delete entire Definition
H01L 27/0262			Delete entire Definition
H01L 27/0266			Delete entire Definition
H01L 27/027			Delete entire Definition
H01L 27/0277			Delete entire Definition
H01L 27/0281			Delete entire Definition
H01L 27/0285			Delete entire Definition
H01L 27/0288			Delete entire Definition
H01L 27/0292			Delete entire Definition
H01L 27/0296			Delete entire Definition
H01L 27/0617			Delete entire Definition
H01L 27/10			Delete entire Definition
H01L 27/101			Delete entire Definition
H01L 27/1021			Delete entire Definition
H01L 27/105			Delete entire Definition
H01L 27/118			Delete entire Definition
H01L 2027/11829			Delete entire Definition
H01L 27/12			Delete entire Definition
H01L 27/1203			Delete entire Definition
H01L 27/1207			Delete entire Definition
H01L 27/1211			Delete entire Definition

H01L 27/1274			Delete entire Definition
H01L 27/13			Delete entire Definition
H01L 28/00			Delete entire Definition
H01L 29/00			Delete entire Definition
H01L 29/66227			Delete entire Definition
H01L 29/66242			Delete entire Definition
H01L 29/66363			Delete entire Definition
H01L 29/665			Delete entire Definition
H01L 29/66507			Delete entire Definition
H01L 29/66545			Delete entire Definition
H01L 29/66863			Delete entire Definition
H01L 29/66871			Delete entire Definition
H01L 29/66969			Delete entire Definition

Notes:
Use this Definitions Quick Fix (DQF) table to:

- Delete an entire definition
- Delete an entire section
- Change a reference symbol
- Delete a reference symbol
- Delete text in a References section
- Correct one error in spelling, article use, or verb tense

Otherwise, use the standard template.

Reminder: Never delete F symbol definitions.

3. REVISION CONCORDANCE LIST (RCL)

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/06	<administrative transfer to H10D 48/04>
D	H01L 21/08	<administrative transfer to H10D 48/042>
D	H01L 21/10	<administrative transfer to H10D 48/043>
D	H01L 21/101	<administrative transfer to H10D 48/0431>
D	H01L 21/103	<administrative transfer to H10D 48/044>
D	H01L 21/105	<administrative transfer to H10D 48/045>
D	H01L 21/108	<administrative transfer to H10D 48/046>
D	H01L 21/12	<administrative transfer to H10D 48/047>
D	H01L 21/14	<administrative transfer to H10D 48/048>
D	H01L 21/145	<administrative transfer to H10D 48/049>
D	H01L 21/16	<administrative transfer to H10D 48/07>
D	H01L 21/161	<administrative transfer to H10D 48/071>
D	H01L 21/162	<administrative transfer to H10D 48/073>
D	H01L 21/164	<administrative transfer to H10D 48/074>
D	H01L 21/165	<administrative transfer to H10D 48/075>
D	H01L 21/167	<administrative transfer to H10D 48/076>
D	H01L 21/168	<administrative transfer to H10D 48/078>
D	H01L 2021/775	<administrative transfer to H10D 86/021>
D	H01L 21/782	<administrative transfer to H10D 89/011>
D	H01L 21/784	<administrative transfer to H10D 89/013>
D	H01L 21/786	<administrative transfer to H10D 89/015>
D	H01L 21/82	<administrative transfer to H10D 84/01>
D	H01L 21/8206	<administrative transfer to H10D 84/032>
D	H01L 21/8213	<administrative transfer to H10D 84/035>
D	H01L 21/822	<administrative transfer to H10D 84/038>
D	H01L 21/8221	<administrative transfer to H10D 84/038 and H10D 88/01 simultaneously>
D	H01L 21/8222	<administrative transfer to H10D 84/0112 and H10D 84/038 simultaneously>
D	H01L 21/8224	<administrative transfer to H10D 84/0114 and H10D 84/038 simultaneously>
D	H01L 21/8226	<administrative transfer to H10D 84/0116 and H10D 84/038 simultaneously>
D	H01L 21/8228	<administrative transfer to H10D 84/0119 and H10D 84/038 simultaneously>
D	H01L 21/82285	<administrative transfer to H10D 84/0121 and H10D 84/038 simultaneously>
D	H01L 21/8232	<administrative transfer to H10D 84/0123 and H10D 84/038 simultaneously>
D	H01L 21/8234	<administrative transfer to H10D 84/0126 and H10D 84/038 simultaneously>
D	H01L 21/823406	<administrative transfer to H10D 84/0198 and H10D 84/038 simultaneously>
D	H01L 21/823412	<administrative transfer to H10D 84/0128 and H10D 84/038 simultaneously>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 21/823418	<administrative transfer to H10D 84/013 and H10D 84/038 simultaneously>
D	H01L 21/823425	<administrative transfer to H10D 84/0133 and H10D 84/038 simultaneously>
D	H01L 21/823431	<administrative transfer to H10D 84/0158 and H10D 84/038 simultaneously>
D	H01L 21/823437	<administrative transfer to H10D 84/0135 and H10D 84/038 simultaneously>
D	H01L 21/823443	<administrative transfer to H10D 84/0137 and H10D 84/038 simultaneously>
D	H01L 21/82345	<administrative transfer to H10D 84/014 and H10D 84/038 simultaneously>
D	H01L 21/823456	<administrative transfer to H10D 84/0142 and H10D 84/038 simultaneously>
D	H01L 21/823462	<administrative transfer to H10D 84/0144 and H10D 84/038 simultaneously>
D	H01L 21/823468	<administrative transfer to H10D 84/0147 and H10D 84/038 simultaneously>
D	H01L 21/823475	<administrative transfer to H10D 84/0149 and H10D 84/038 simultaneously>
D	H01L 21/823481	<administrative transfer to H10D 84/0151 and H10D 84/038 simultaneously>
D	H01L 21/823487	<administrative transfer to H10D 84/016 and H10D 84/038 simultaneously>
D	H01L 21/823493	<administrative transfer to H10D 84/0156 and H10D 84/038 simultaneously>
D	H01L 21/8236	<administrative transfer to H10D 84/0163 and H10D 84/038 simultaneously>
D	H01L 21/8238	<administrative transfer to H10D 84/0165 and H10D 84/038 simultaneously>
D	H01L 21/823807	<administrative transfer to H10D 84/0167 and H10D 84/038 simultaneously>
D	H01L 21/823814	<administrative transfer to H10D 84/017 and H10D 84/038 simultaneously>
D	H01L 21/823821	<administrative transfer to H10D 84/0193 and H10D 84/038 simultaneously>
D	H01L 21/823828	<administrative transfer to H10D 84/0172 and H10D 84/038 simultaneously>
D	H01L 21/823835	<administrative transfer to H10D 84/0174 and H10D 84/038 simultaneously>
D	H01L 21/823842	<administrative transfer to H10D 84/0177 and H10D 84/038 simultaneously>
D	H01L 21/82385	<administrative transfer to H10D 84/0179 and H10D 84/038 simultaneously>
D	H01L 21/823857	<administrative transfer to H10D 84/0181 and H10D 84/038 simultaneously>
D	H01L 21/823864	<administrative transfer to H10D 84/0184 and H10D 84/038 simultaneously>
D	H01L 21/823871	<administrative transfer to H10D 84/0186 and H10D 84/038 simultaneously>

Type*	**From CPC Symbol (existing)**	**To CPC Symbol(s)**
D	H01L 21/823878	<administrative transfer to H10D 84/0188 and H10D 84/038 simultaneously>
D	H01L 21/823885	<administrative transfer to H10D 84/0195 and H10D 84/038 simultaneously>
D	H01L 21/823892	<administrative transfer to H10D 84/0191 and H10D 84/038 simultaneously>
D	H01L 21/8248	<administrative transfer to H10D 84/0107 and H10D 84/038 simultaneously>
D	H01L 21/8249	<administrative transfer to H10D 84/0109 and H10D 84/038 simultaneously>
D	H01L 21/8252	<administrative transfer to H10D 84/05>
D	H01L 21/8254	<administrative transfer to H10D 84/07>
D	H01L 21/8256	<administrative transfer to H10D 84/02>
D	H01L 21/8258	<administrative transfer to H10D 84/08>
D	H01L 21/84	<administrative transfer to H10D 86/01>
D	H01L 21/845	<administrative transfer to H10D 86/011>
D	H01L 21/86	<administrative transfer to H10D 86/03>
D	H01L 27/00	<administrative transfer to H10D 99/00>
D	H01L 27/01	<administrative transfer to H10D 86/85>
D	H01L 27/013	<administrative transfer to H10D 86/85>
D	H01L 27/016	<administrative transfer to H10D 86/85>
D	H01L 27/02	<administrative transfer to H10D 89/00>
D	H01L 27/0203	<administrative transfer to H10D 89/00 >
D	H01L 27/0207	<administrative transfer to H10D 89/10>
D	H01L 27/0211	<administrative transfer to H10D 89/105>
D	H01L 27/0214	<administrative transfer to H10D 89/211>
D	H01L 27/0218	<administrative transfer to H10D 89/213>
D	H01L 27/0222	<administrative transfer to H10D 89/215>
D	H01L 27/0225	<administrative transfer to H10D 89/217>
D	H01L 27/0229	<administrative transfer to H10D 89/311>
D	H01L 27/0233	<administrative transfer to H10D 84/65>
D	H01L 27/0237	<administrative transfer to H10D 84/652>
D	H01L 27/024	<administrative transfer to H10D 84/655>
D	H01L 27/0244	<administrative transfer to H10D 84/658>
D	H01L 27/0248	<administrative transfer to H10D 89/60>
D	H01L 27/0251	<administrative transfer to H10D 89/601>
D	H01L 27/0255	<administrative transfer to H10D 89/611>
D	H01L 27/0259	<administrative transfer to H10D 89/711>
D	H01L 27/0262	<administrative transfer to H10D 89/713>
D	H01L 27/0266	<administrative transfer to H10D 89/811>
D	H01L 27/027	<administrative transfer to H10D 89/813>
D	H01L 27/0274	<administrative transfer to H10D 89/814>
D	H01L 27/0277	<administrative transfer to H10D 89/815>
D	H01L 27/0281	<administrative transfer to H10D 89/817>
D	H01L 27/0285	<administrative transfer to H10D 89/819>
D	H01L 27/0288	<administrative transfer to H10D 89/911>
D	H01L 27/0292	<administrative transfer to H10D 89/921>
D	H01L 27/0296	<administrative transfer to H10D 89/931>
D	H01L 27/04	<administrative transfer to H10D 84/00>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 27/06	<administrative transfer to H10D 84/00>
D	H01L 27/0605	<administrative transfer to H10D 84/01>
D	H01L 27/0611	<administrative transfer to H10D 84/00>
D	H01L 27/0617	<administrative transfer to H10D 84/40>
D	H01L 27/0623	<administrative transfer to H10D 84/401>
D	H01L 27/0629	<administrative transfer to H10D 84/811>
D	H01L 27/0635	<administrative transfer to H10D 84/403>
D	H01L 27/0641	<administrative transfer to H10D 84/60>
D	H01L 27/0647	<administrative transfer to H10D 84/611>
D	H01L 27/0652	<administrative transfer to H10D 84/613>
D	H01L 27/0658	<administrative transfer to H10D 84/615>
D	H01L 27/0664	<administrative transfer to H10D 84/617>
D	H01L 27/067	<administrative transfer to H10D 84/619>
D	H01L 27/0676	<administrative transfer to H10D 84/204>
D	H01L 27/0682	<administrative transfer to H10D 84/206>
D	H01L 27/0688	<administrative transfer to H10D 88/00>
D	H01L 27/0694	<administrative transfer to H10D 88/101>
D	H01L 27/07	<administrative transfer to H10D 84/00>
D	H01L 27/0705	<administrative transfer to H10D 84/401>
D	H01L 27/0711	<administrative transfer to H10D 84/403>
D	H01L 27/0716	<administrative transfer to H10D 84/406>
D	H01L 27/0722	<administrative transfer to H10D 84/409>
D	H01L 27/0727	<administrative transfer to H10D 84/811>
D	H01L 27/0733	<administrative transfer to H10D 84/813>
D	H01L 27/0738	<administrative transfer to H10D 84/817>
D	H01L 27/0744	<administrative transfer to H10D 84/60>
D	H01L 27/075	<administrative transfer to H10D 84/611>
D	H01L 27/0755	<administrative transfer to H10D 84/613>
D	H01L 27/0761	<administrative transfer to H10D 84/617>
D	H01L 27/0766	<administrative transfer to H10D 84/617>
D	H01L 27/0772	<administrative transfer to H10D 84/615>
D	H01L 27/0777	<administrative transfer to H10D 84/615>
D	H01L 27/0783	<administrative transfer to H10D 84/619>
D	H01L 27/0788	<administrative transfer to H10D 84/204>
D	H01L 27/0794	<administrative transfer to H10D 84/206>
D	H01L 27/08	<administrative transfer to H10D 84/00>
D	H01L 27/0802	<administrative transfer to H10D 84/209>
D	H01L 27/0805	<administrative transfer to H10D 84/212>
D	H01L 27/0808	<administrative transfer to H10D 84/215>
D	H01L 27/0811	<administrative transfer to H10D 84/217>
D	H01L 27/0814	<administrative transfer to H10D 84/221>
D	H01L 27/0817	<administrative transfer to H10D 84/676>
D	H01L 27/082	<administrative transfer to H10D 84/645>
D	H01L 27/0821	<administrative transfer to H10D 84/63>
D	H01L 27/0823	<administrative transfer to H10D 84/641>
D	H01L 27/0825	<administrative transfer to H10D 84/642>
D	H01L 27/0826	<administrative transfer to H10D 84/673>
D	H01L 27/0828	<administrative transfer to H10D 84/643>
D	H01L 27/085	<administrative transfer to H10D 84/82>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 27/088	<administrative transfer to H10D 84/83>
D	H01L 27/0883	<administrative transfer to H10D 84/84>
D	H01L 27/0886	<administrative transfer to H10D 84/834>
D	H01L 27/092	<administrative transfer to H10D 84/85>
D	H01L 27/0921	<administrative transfer to H10D 84/854>
D	H01L 27/0922	<administrative transfer to H10D 84/856>
D	H01L 27/0924	<administrative transfer to H10D 84/853 >
D	H01L 27/0925	<administrative transfer to H10D 84/857>
D	H01L 27/0927	<administrative transfer to H10D 84/858>
D	H01L 27/0928	<administrative transfer to H10D 84/859>
D	H01L 27/095	<administrative transfer to H10D 84/86>
D	H01L 27/098	<administrative transfer to H10D 84/87>
D	H01L 27/10	<administrative transfer to H10D 84/00>
D	H01L 27/101	<administrative transfer to H10D 84/206>
D	H01L 27/102	<administrative transfer to H10D 84/00>
D	H01L 27/1021	<administrative transfer to H10D 84/221>
D	H01L 27/1022	<administrative transfer to H10D 84/60>
D	H01L 27/1027	<administrative transfer to H10D 84/60>
D	H01L 27/1028	<administrative transfer to H10D 84/00>
D	H01L 27/105	<administrative transfer to H10D 84/80 >
D	H01L 27/1055	<administrative transfer to H10D 84/895>
D	H01L 27/1057	<administrative transfer to H10D 84/891>
D	H01L 27/118	<administrative transfer to H10D 84/90>
D	H01L 27/11801	<administrative transfer to H10D 84/901>
D	H01L 27/11803	<administrative transfer to H10D 84/903>
D	H01L 2027/11805	<administrative transfer to H10D 84/905>
D	H01L 27/11807	<administrative transfer to H10D 84/907>
D	H01L 2027/11809	<administrative transfer to H10D 84/909>
D	H01L 2027/11811	<administrative transfer to H10D 84/911>
D	H01L 2027/11812	<administrative transfer to H10D 84/912>
D	H01L 2027/11814	<administrative transfer to H10D 84/914>
D	H01L 2027/11816	<administrative transfer to H10D 84/916>
D	H01L 2027/11818	<administrative transfer to H10D 84/918>
D	H01L 2027/1182	<administrative transfer to H10D 84/921>
D	H01L 2027/11822	<administrative transfer to H10D 84/922>
D	H01L 2027/11824	<administrative transfer to H10D 84/924>
D	H01L 2027/11825	<administrative transfer to H10D 84/925>
D	H01L 2027/11827	<administrative transfer to H10D 84/927>
D	H01L 2027/11829	<administrative transfer to H10D 84/929>
D	H01L 2027/11831	<administrative transfer to H10D 84/931>
D	H01L 2027/11833	<administrative transfer to H10D 84/933>
D	H01L 2027/11835	<administrative transfer to H10D 84/935>
D	H01L 2027/11837	<administrative transfer to H10D 84/937>
D	H01L 2027/11838	<administrative transfer to H10D 84/938>
D	H01L 2027/1184	<administrative transfer to H10D 84/941>
D	H01L 2027/11842	<administrative transfer to H10D 84/942>
D	H01L 2027/11844	<administrative transfer to H10D 84/944>
D	H01L 2027/11846	<administrative transfer to H10D 84/946>
D	H01L 2027/11848	<administrative transfer to H10D 84/948>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 2027/1185	<administrative transfer to H10D 84/949>
D	H01L 2027/11851	<administrative transfer to H10D 84/951>
D	H01L 2027/11853	<administrative transfer to H10D 84/953>
D	H01L 2027/11855	<administrative transfer to H10D 84/955>
D	H01L 2027/11857	<administrative transfer to H10D 84/957>
D	H01L 2027/11859	<administrative transfer to H10D 84/959>
D	H01L 2027/11861	<administrative transfer to H10D 84/961>
D	H01L 2027/11862	<administrative transfer to H10D 84/962>
D	H01L 2027/11864	<administrative transfer to H10D 84/964>
D	H01L 2027/11866	<administrative transfer to H10D 84/966>
D	H01L 2027/11868	<administrative transfer to H10D 84/968>
D	H01L 2027/1187	<administrative transfer to H10D 84/971>
D	H01L 2027/11872	<administrative transfer to H10D 84/972>
D	H01L 2027/11874	<administrative transfer to H10D 84/974>
D	H01L 2027/11875	<administrative transfer to H10D 84/975>
D	H01L 2027/11877	<administrative transfer to H10D 84/977>
D	H01L 2027/11879	<administrative transfer to H10D 84/979>
D	H01L 2027/11881	<administrative transfer to H10D 84/981>
D	H01L 2027/11883	<administrative transfer to H10D 84/983>
D	H01L 2027/11885	<administrative transfer to H10D 84/985>
D	H01L 2027/11887	<administrative transfer to H10D 84/987>
D	H01L 2027/11888	<administrative transfer to H10D 84/988>
D	H01L 2027/1189	<administrative transfer to H10D 84/991>
D	H01L 2027/11892	<administrative transfer to H10D 84/992>
D	H01L 2027/11894	<administrative transfer to H10D 84/994>
D	H01L 27/11896	<administrative transfer to H10D 84/996>
D	H01L 27/11898	<administrative transfer to H10D 84/998>
D	H01L 27/12	<administrative transfer to H10D 86/00>
D	H01L 27/1203	<administrative transfer to H10D 86/201>
D	H01L 27/1207	<administrative transfer to H10D 87/00>
D	H01L 27/1211	<administrative transfer to H10D 86/215>
D	H01L 27/1214	<administrative transfer to H10D 86/40 and H10D 86/60 simultaneously >
D	H01L 27/1218	<administrative transfer to H10D 86/411 and H10D 86/60 simultaneously >
D	H01L 27/1222	<administrative transfer to H10D 86/60 and H10D 86/421 simultaneously>
D	H01L 27/1225	<administrative transfer to H10D 86/60 and H10D 86/423 simultaneously>
D	H01L 27/1229	<administrative transfer to H10D 86/425 and H10D 86/60 simultaneously>
D	H01L 27/1233	<administrative transfer to H10D 86/427 and H10D 86/60 simultaneously>
D	H01L 27/1237	<administrative transfer to H10D 86/431 and H10D 86/60 simultaneously>
D	H01L 27/124	<administrative transfer to H10D 86/441 and H10D 86/60 simultaneously>
D	H01L 27/1244	<administrative transfer to H10D 86/443 and H10D 86/60 simultaneously>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 27/1248	<administrative transfer to H10D 86/451 and H10D 86/60 simultaneously>
D	H01L 27/1251	<administrative transfer to H10D 86/471 and H10D 86/60 simultaneously>
D	H01L 27/1255	<administrative transfer to H10D 86/481 and H10D 86/60 simultaneously>
D	H01L 27/1259	<administrative transfer to H10D 86/021>
D	H01L 27/1262	<administrative transfer to H10D 86/0212>
D	H01L 27/1266	<administrative transfer to H10D 86/0214>
D	H01L 27/127	<administrative transfer to H10D 86/0221>
D	H01L 27/1274	<administrative transfer to H10D 86/0223>
D	H01L 27/1277	<administrative transfer to H10D 86/0225>
D	H01L 27/1281	<administrative transfer to H10D 86/0227>
D	H01L 27/1285	<administrative transfer to H10D 86/0229>
D	H01L 27/1288	<administrative transfer to H10D 86/0231>
D	H01L 27/1292	<administrative transfer to H10D 86/0241>
D	H01L 27/1296	<administrative transfer to H10D 86/0251>
D	H01L 27/13	<administrative transfer to H10D 86/80>
D	H01L 28/00	<administrative transfer to H10D 1/00>
D	H01L 28/10	<administrative transfer to H10D 1/20>
D	H01L 28/20	<administrative transfer to H10D 1/47>
D	H01L 28/22	<administrative transfer to H10D 1/472>
D	H01L 28/24	<administrative transfer to H10D 1/474>
D	H01L 28/26	<administrative transfer to H10D 1/476>
D	H01L 28/40	<administrative transfer to H10D 1/68>
D	H01L 28/55	<administrative transfer to H10D 1/682>
D	H01L 28/56	<administrative transfer to H10D 1/684>
D	H01L 28/57	<administrative transfer to H10D 1/688>
D	H01L 28/60	<administrative transfer to H10D 1/692>
D	H01L 28/65	<administrative transfer to H10D 1/694>
D	H01L 28/75	<administrative transfer to H10D 1/696>
D	H01L 28/82	<administrative transfer to H10D 1/711>
D	H01L 28/84	<administrative transfer to H10D 1/712>
D	H01L 28/86	<administrative transfer to H10D 1/714>
D	H01L 28/87	<administrative transfer to H10D 1/042 and H10D 1/714 simultaneously>
D	H01L 28/88	<administrative transfer to H10D 1/043 and H10D 1/714 simultaneously>
D	H01L 28/90	<administrative transfer to H10D 1/716>
D	H01L 28/91	<administrative transfer to H10D 1/042 and H10D 1/716 simultaneously>
D	H01L 28/92	<administrative transfer to H10D 1/043 and H10D 1/716 simultaneously>
D	H01L 29/00	<administrative transfer to H10D 99/00>
D	H01L 29/02	<administrative transfer to H10D 62/00>
D	H01L 29/04	<administrative transfer to H10D 62/40>
D	H01L 29/045	<administrative transfer to H10D 62/405>
D	H01L 29/06	<administrative transfer to H10D 62/10>
D	H01L 29/0603	<administrative transfer to H10D 62/10>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/0607	<administrative transfer to H10D 62/102>
D	H01L 29/0611	<administrative transfer to H10D 62/103>
D	H01L 29/0615	<administrative transfer to H10D 62/105>
D	H01L 29/0619	<administrative transfer to H10D 62/106>
D	H01L 29/0623	<administrative transfer to H10D 62/107>
D	H01L 29/0626	<administrative transfer to H10D 62/108>
D	H01L 29/063	<administrative transfer to H10D 62/109>
D	H01L 29/0634	<administrative transfer to H10D 62/111>
D	H01L 29/0638	<administrative transfer to H10D 62/112>
D	H01L 29/0642	<administrative transfer to H10D 62/113>
D	H01L 29/0646	<administrative transfer to H10D 62/114>
D	H01L 29/0649	<administrative transfer to H10D 62/115>
D	H01L 29/0653	<administrative transfer to H10D 62/116>
D	H01L 29/0657	<administrative transfer to H10D 62/117>
D	H01L 29/0661	<administrative transfer to H10D 62/104>
D	H01L 29/0665	<administrative transfer to H10D 62/118>
D	H01L 29/0669	<administrative transfer to H10D 62/119>
D	H01L 29/0673	<administrative transfer to H10D 62/121>
D	H01L 29/0676	<administrative transfer to H10D 62/122>
D	H01L 29/068	<administrative transfer to H10D 62/123>
D	H01L 29/0684	<administrative transfer to H10D 62/124>
D	H01L 29/0688	<administrative transfer to H10D 62/125>
D	H01L 29/0692	<administrative transfer to H10D 62/126>
D	H01L 29/0696	<administrative transfer to H10D 62/127>
D	H01L 29/08	<administrative transfer to H10D 62/13>
D	H01L 29/0804	<administrative transfer to H10D 62/133>
D	H01L 29/0808	<administrative transfer to H10D 62/134>
D	H01L 29/0813	<administrative transfer to H10D 62/135>
D	H01L 29/0817	<administrative transfer to H10D 62/136>
D	H01L 29/0821	<administrative transfer to H10D 62/137>
D	H01L 29/0826	<administrative transfer to H10D 62/138>
D	H01L 29/083	<administrative transfer to H10D 62/141>
D	H01L 29/0834	<administrative transfer to H10D 62/142>
D	H01L 29/0839	<administrative transfer to H10D 62/148>
D	H01L 29/0843	<administrative transfer to H10D 62/149>
D	H01L 29/0847	<administrative transfer to H10D 62/151>
D	H01L 29/0852	<administrative transfer to H10D 62/152>
D	H01L 29/0856	<administrative transfer to H10D 62/152>
D	H01L 29/086	<administrative transfer to H10D 62/153>
D	H01L 29/0865	<administrative transfer to H10D 62/154>
D	H01L 29/0869	<administrative transfer to H10D 62/155>
D	H01L 29/0873	<administrative transfer to H10D 62/156>
D	H01L 29/0878	<administrative transfer to H10D 62/157>
D	H01L 29/0882	<administrative transfer to H10D 62/158>
D	H01L 29/0886	<administrative transfer to H10D 62/159>
D	H01L 29/0891	<administrative transfer to H10D 62/161>
D	H01L 29/0895	<administrative transfer to H10D 62/165>
D	H01L 29/10	<administrative transfer to H10D 62/17>
D	H01L 29/1004	<administrative transfer to H10D 62/177>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/1008	<administrative transfer to H10D 62/184>
D	H01L 29/1012	<administrative transfer to H10D 62/192>
D	H01L 29/1016	<administrative transfer to H10D 62/199>
D	H01L 29/102	<administrative transfer to H10D 62/206>
D	H01L 29/1025	<administrative transfer to H10D 62/213>
D	H01L 29/1029	<administrative transfer to H10D 62/221>
D	H01L 29/1033	<administrative transfer to H10D 62/235>
D	H01L 29/1037	<administrative transfer to H10D 62/292>
D	H01L 29/1041	<administrative transfer to H10D 62/299>
D	H01L 29/1045	<administrative transfer to H10D 62/307>
D	H01L 29/105	<administrative transfer to H10D 62/314>
D	H01L 29/1054	<administrative transfer to H10D 30/751>
D	H01L 29/1058	<administrative transfer to H10D 62/328>
D	H01L 29/1062	<administrative transfer to H10D 62/335>
D	H01L 29/1066	<administrative transfer to H10D 62/343>
D	H01L 29/107	<administrative transfer to H10D 62/351>
D	H01L 29/1075	<administrative transfer to H10D 62/357>
D	H01L 29/1079	<administrative transfer to H10D 62/364>
D	H01L 29/1083	<administrative transfer to H10D 62/371>
D	H01L 29/1087	<administrative transfer to H10D 62/378>
D	H01L 29/1091	<administrative transfer to H10D 62/386>
D	H01L 29/1095	<administrative transfer to H10D 62/393>
D	H01L 29/12	<administrative transfer to H10D 62/81>
D	H01L 29/122	<administrative transfer to H10D 62/812>
D	H01L 29/125	<administrative transfer to H10D 62/813>
D	H01L 29/127	<administrative transfer to H10D 62/814>
D	H01L 29/15	<administrative transfer to H10D 62/815>
D	H01L 29/151	<administrative transfer to H10D 62/8161>
D	H01L 29/152	<administrative transfer to H10D 62/8162>
D	H01L 29/154	<administrative transfer to H10D 62/8163>
D	H01L 29/155	<administrative transfer to H10D 62/8164>
D	H01L 29/157	<administrative transfer to H10D 62/8171>
D	H01L 29/158	<administrative transfer to H10D 62/8181>
D	H01L 29/16	<administrative transfer to H10D 62/83>
D	H01L 29/1602	<administrative transfer to H10D 62/8303>
D	H01L 29/1604	<administrative transfer to H10D 62/402 and H10D 62/83 simultaneously>
D	H01L 29/1606	<administrative transfer to H10D 62/882>
D	H01L 29/1608	<administrative transfer to H10D 62/8325>
D	H01L 29/161	<administrative transfer to H10D 62/832>
D	H01L 29/165	<administrative transfer to H10D 62/822>
D	H01L 29/167	<administrative transfer to H10D 62/834>
D	H01L 29/18	<administrative transfer to H10D 62/84>
D	H01L 29/185	<administrative transfer to H10D 62/402 and H10D 62/84 simultaneously>
D	H01L 29/20	<administrative transfer to H10D 62/85>
D	H01L 29/2003	<administrative transfer to H10D 62/8503>
D	H01L 29/2006	<administrative transfer to H10D 62/402 and H10D 62/85 simultaneously>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/201	<administrative transfer to H10D 62/852>
D	H01L 29/205	<administrative transfer to H10D 62/824>
D	H01L 29/207	<administrative transfer to H10D 62/854>
D	H01L 29/22	<administrative transfer to H10D 62/86>
D	H01L 29/2203	<administrative transfer to H10D 62/8603>
D	H01L 29/2206	<administrative transfer to H10D 62/402 and H10D 62/86 simultaneously>
D	H01L 29/221	<administrative transfer to H10D 62/862>
D	H01L 29/225	<administrative transfer to H10D 62/826>
D	H01L 29/227	<administrative transfer to H10D 62/864>
D	H01L 29/24	<administrative transfer to H10D 62/80>
D	H01L 29/242	<administrative transfer to H10D 62/871>
D	H01L 29/245	<administrative transfer to H10D 62/874>
D	H01L 29/247	<administrative transfer to H10D 62/402 and H10D 62/80 simultaneously >
D	H01L 29/26	<administrative transfer to H10D 62/80>
D	H01L 29/263	<administrative transfer to H10D 62/402 and H10D 62/80 simultaneously>
D	H01L 29/267	<administrative transfer to H10D 62/82>
D	H01L 29/30	<administrative transfer to H10D 62/50>
D	H01L 29/32	<administrative transfer to H10D 62/53>
D	H01L 29/34	<administrative transfer to H10D 62/57>
D	H01L 29/36	<administrative transfer to H10D 62/60>
D	H01L 29/365	<administrative transfer to H10D 62/605>
D	H01L 29/40	<administrative transfer to H10D 64/00>
D	H01L 29/401	<administrative transfer to H10D 64/01>
D	H01L 29/4011	<administrative transfer to H10D 64/031>
D	H01L 29/40111	<administrative transfer to H10D 64/033>
D	H01L 29/40114	<administrative transfer to H10D 64/035>
D	H01L 29/40117	<administrative transfer to H10D 64/037>
D	H01L 29/402	<administrative transfer to H10D 64/111>
D	H01L 29/404	<administrative transfer to H10D 64/112>
D	H01L 29/405	<administrative transfer to H10D 64/115>
D	H01L 29/407	<administrative transfer to H10D 64/117>
D	H01L 29/408	<administrative transfer to H10D 64/118>
D	H01L 29/41	<administrative transfer to H10D 64/20>
D	H01L 29/413	<administrative transfer to H10D 64/205>
D	H01L 29/417	<administrative transfer to H10D 64/23>
D	H01L 29/41708	<administrative transfer to H10D 64/231>
D	H01L 29/41716	<administrative transfer to H10D 64/233>
D	H01L 29/41725	<administrative transfer to H10D 64/251>
D	H01L 29/41733	<administrative transfer to H10D 30/6729>
D	H01L 29/41741	<administrative transfer to H10D 64/252>
D	H01L 29/4175	<administrative transfer to H10D 64/254>
D	H01L 29/41758	<administrative transfer to H10D 64/257>
D	H01L 29/41766	<administrative transfer to H10D 64/256>
D	H01L 29/41775	<administrative transfer to H10D 64/258>
D	H01L 29/41783	<administrative transfer to H10D 64/259>
D	H01L 29/41791	<administrative transfer to H10D 30/6219>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/423	<administrative transfer to H10D 64/27>
D	H01L 29/42304	<administrative transfer to H10D 64/281>
D	H01L 29/42308	<administrative transfer to H10D 64/291>
D	H01L 29/42312	<administrative transfer to H10D 64/311>
D	H01L 29/42316	<administrative transfer to H10D 64/411>
D	H01L 29/4232	<administrative transfer to H10D 64/511>
D	H01L 29/42324	<administrative transfer to H10D 30/6891>
D	H01L 29/42328	<administrative transfer to H10D 30/6892>
D	H01L 29/42332	<administrative transfer to H10D 30/6893>
D	H01L 29/42336	<administrative transfer to H10D 30/6894>
D	H01L 29/4234	<administrative transfer to H10D 30/694>
D	H01L 29/42344	<administrative transfer to H10D 30/696>
D	H01L 29/42348	<administrative transfer to H10D 30/697>
D	H01L 29/42352	<administrative transfer to H10D 30/699>
D	H01L 29/42356	<administrative transfer to H10D 64/512>
D	H01L 29/4236	<administrative transfer to H10D 64/513>
D	H01L 29/42364	<administrative transfer to H10D 64/514>
D	H01L 29/42368	<administrative transfer to H10D 64/516>
D	H01L 29/42372	<administrative transfer to H10D 64/517>
D	H01L 29/42376	<administrative transfer to H10D 64/518>
D	H01L 29/4238	<administrative transfer to H10D 64/519>
D	H01L 29/42384	<administrative transfer to H10D 30/673>
D	H01L 2029/42388	<administrative transfer to H10D 30/6736>
D	H01L 29/42392	<administrative transfer to H10D 30/6735>
D	H01L 29/42396	<administrative transfer to H10D 44/45>
D	H01L 29/43	<administrative transfer to H10D 64/60>
D	H01L 29/432	<administrative transfer to H10D 64/602>
D	H01L 29/435	<administrative transfer to H10D 64/605>
D	H01L 29/437	<administrative transfer to H10D 64/608>
D	H01L 29/45	<administrative transfer to H10D 64/62>
D	H01L 29/452	<administrative transfer to H10D 62/85 and H10D 64/62 simultaneously>
D	H01L 29/454	<administrative transfer to H10D 30/6737 and H10D 30/675 simultaneously>
D	H01L 29/456	<administrative transfer to H10D 62/83 and H10D 64/62 simultaneously>
D	H01L 29/458	<administrative transfer to H10D 30/6737 and H10D 30/6743 simultaneously>
D	H01L 29/47	<administrative transfer to H10D 64/64>
D	H01L 29/475	<administrative transfer to H10D 30/6738, H10D 30/675, H10D 62/85 and H10D 64/64 simultaneously>
D	H01L 29/49	<administrative transfer to H10D 64/66>
D	H01L 29/4908	<administrative transfer to H10D 30/6739>
D	H01L 29/4916	<administrative transfer to H10D 64/661>
D	H01L 29/4925	<administrative transfer to H10D 64/662>
D	H01L 29/4933	<administrative transfer to H10D 64/663>
D	H01L 29/4941	<administrative transfer to H10D 64/664>
D	H01L 29/495	<administrative transfer to H10D 64/665>
D	H01L 29/4958	<administrative transfer to H10D 64/666>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/4966	<administrative transfer to H10D 64/667>
D	H01L 29/4975	<administrative transfer to H10D 64/668>
D	H01L 29/4983	<administrative transfer to H10D 64/671>
D	H01L 29/4991	<administrative transfer to H10D 64/679>
D	H01L 29/51	<administrative transfer to H10D 64/68>
D	H01L 29/511	<administrative transfer to H10D 64/681>
D	H01L 29/512	<administrative transfer to H10D 64/683>
D	H01L 29/513	<administrative transfer to H10D 64/685>
D	H01L 29/515	<administrative transfer to H10D 64/687>
D	H01L 29/516	<administrative transfer to H10D 64/689>
D	H01L 29/517	<administrative transfer to H10D 64/691>
D	H01L 29/518	<administrative transfer to H10D 64/693>
D	H01L 29/66	<administrative transfer to H10D 48/30>
D	H01L 29/66007	<administrative transfer to H10D 48/01>
D	H01L 29/66015	<administrative transfer to H10D 48/01 and H10D 62/8303 simultaneously>
D	H01L 29/66022	<administrative transfer to H10D 48/021 and H10D 62/8303 simultaneously >
D	H01L 29/6603	<administrative transfer to H10D 8/051 and H10D 62/8303 simultaneously>
D	H01L 29/66037	<administrative transfer to H10D 48/031 and H10D 62/8303 simultaneously>
D	H01L 29/66045	<administrative transfer to H10D 30/01 and H10D 62/8303 simultaneously>
D	H01L 29/66053	<administrative transfer to H10D 48/01 and H10D 62/8325 simultaneously>
D	H01L 29/6606	<administrative transfer to H10D 8/051 and H10D 62/8325 simultaneously>
D	H01L 29/66068	<administrative transfer to H10D 12/031 and H10D 62/8325 simultaneously>
D	H01L 29/66075	<administrative transfer to H10D 48/01>
D	H01L 29/66083	<administrative transfer to H10D 48/021>
D	H01L 29/6609	<administrative transfer to H10D 8/01>
D	H01L 29/66098	<administrative transfer to H10D 8/021>
D	H01L 29/66106	<administrative transfer to H10D 8/022>
D	H01L 29/66113	<administrative transfer to H10D 8/024>
D	H01L 29/66121	<administrative transfer to H10D 8/041>
D	H01L 29/66128	<administrative transfer to H10D 8/043>
D	H01L 29/66136	<administrative transfer to H10D 8/045>
D	H01L 29/66143	<administrative transfer to H10D 8/051>
D	H01L 29/66151	<administrative transfer to H10D 8/053>
D	H01L 29/66159	<administrative transfer to H10D 8/055>
D	H01L 29/66166	<administrative transfer to H10D 1/025>
D	H01L 29/66174	<administrative transfer to H10D 1/045>
D	H01L 29/66181	<administrative transfer to H10D 1/047>
D	H01L 29/66189	<administrative transfer to H10D 1/048>
D	H01L 29/66196	<administrative transfer to H10D 48/021>
D	H01L 29/66204	<administrative transfer to H10D 8/043>
D	H01L 29/66212	<administrative transfer to H10D 8/051>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/66219	<administrative transfer to H10D 8/053>
D	H01L 29/66227	<administrative transfer to H10D 48/031>
D	H01L 29/66234	<administrative transfer to H10D 10/01>
D	H01L 29/66242	<administrative transfer to H10D 10/021>
D	H01L 29/6625	<administrative transfer to H10D 10/061>
D	H01L 29/66257	<administrative transfer to H10D 10/031>
D	H01L 29/66265	<administrative transfer to H10D 10/041>
D	H01L 29/66272	<administrative transfer to H10D 10/051>
D	H01L 29/6628	<administrative transfer to H10D 10/052>
D	H01L 29/66287	<administrative transfer to H10D 10/054>
D	H01L 29/66295	<administrative transfer to H10D 10/056>
D	H01L 29/66303	<administrative transfer to H10D 10/058>
D	H01L 29/6631	<administrative transfer to H10D 10/01>
D	H01L 29/66318	<administrative transfer to H10D 10/021>
D	H01L 29/66325	<administrative transfer to H10D 12/01>
D	H01L 29/66333	<administrative transfer to H10D 12/032>
D	H01L 29/6634	<administrative transfer to H10D 12/035>
D	H01L 29/66348	<administrative transfer to H10D 12/038>
D	H01L 29/66356	<administrative transfer to H10D 12/021>
D	H01L 29/66363	<administrative transfer to H10D 18/01>
D	H01L 29/66371	<administrative transfer to H10D 84/0102>
D	H01L 29/66378	<administrative transfer to H10D 84/0105>
D	H01L 29/66386	<administrative transfer to H10D 18/021>
D	H01L 29/66393	<administrative transfer to H10D 18/031>
D	H01L 29/66401	<administrative transfer to H10D 18/01>
D	H01L 29/66409	<administrative transfer to H10D 30/01>
D	H01L 29/66416	<administrative transfer to H10D 30/012>
D	H01L 29/66424	<administrative transfer to H10D 30/012>
D	H01L 29/66431	<administrative transfer to H10D 30/015>
D	H01L 29/66439	<administrative transfer to H10D 30/014>
D	H01L 29/66446	<administrative transfer to H10D 30/01>
D	H01L 29/66454	<administrative transfer to H10D 30/012>
D	H01L 29/66462	<administrative transfer to H10D 30/015>
D	H01L 29/66469	<administrative transfer to H10D 30/014>
D	H01L 29/66477	<administrative transfer to H10D 30/021>
D	H01L 29/66484	<administrative transfer to H10D 30/023>
D	H01L 29/66492	<administrative transfer to H10D 30/022>
D	H01L 29/665	<administrative transfer to H10D 30/0212>
D	H01L 29/66507	<administrative transfer to H10D 30/0213>
D	H01L 29/66515	<administrative transfer to H10D 30/0215>
D	H01L 29/66522	<administrative transfer to H10D 30/021>
D	H01L 29/6653	<administrative transfer to H10D 64/015>
D	H01L 29/66537	<administrative transfer to H10D 30/0217>
D	H01L 29/66545	<administrative transfer to H10D 64/017>
D	H01L 29/66553	<administrative transfer to H10D 64/018>
D	H01L 29/6656	<administrative transfer to H10D 64/021>
D	H01L 29/66568	<administrative transfer to H10D 30/027>
D	H01L 29/66575	<administrative transfer to H10D 30/0223>
D	H01L 29/66583	<administrative transfer to H10D 30/0225>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/6659	<administrative transfer to H10D 30/0227>
D	H01L 29/66598	<administrative transfer to H10D 30/0229>
D	H01L 29/66606	<administrative transfer to H10D 30/0273>
D	H01L 29/66613	<administrative transfer to H10D 64/025>
D	H01L 29/66621	<administrative transfer to H10D 64/027>
D	H01L 29/66628	<administrative transfer to H10D 30/0275>
D	H01L 29/66636	<administrative transfer to H10D 62/021>
D	H01L 29/66643	<administrative transfer to H10D 30/0277>
D	H01L 29/66651	<administrative transfer to H10D 30/0278>
D	H01L 29/66659	<administrative transfer to H10D 30/0221>
D	H01L 29/66666	<administrative transfer to H10D 30/025>
D	H01L 29/66674	<administrative transfer to H10D 30/028>
D	H01L 29/66681	<administrative transfer to H10D 30/0281>
D	H01L 29/66689	<administrative transfer to H10D 30/0285>
D	H01L 29/66696	<administrative transfer to H10D 30/0287>
D	H01L 29/66704	<administrative transfer to H10D 30/0289>
D	H01L 29/66712	<administrative transfer to H10D 30/0291>
D	H01L 29/66719	<administrative transfer to H10D 30/0293>
D	H01L 29/66727	<administrative transfer to H10D 30/0295>
D	H01L 29/66734	<administrative transfer to H10D 30/0297>
D	H01L 29/66742	<administrative transfer to H10D 30/031>
D	H01L 29/6675	<administrative transfer to H10D 30/0321>
D	H01L 29/66757	<administrative transfer to H10D 30/0314 and H10D 30/0321 simultaneously>
D	H01L 29/66765	<administrative transfer to H10D 30/0316 and H10D 30/0321 simultaneously>
D	H01L 29/66772	<administrative transfer to H10D 30/0323>
D	H01L 29/6678	<administrative transfer to H10D 30/0327 and H10D 30/0323 simultaneously >
D	H01L 29/66787	<administrative transfer to H10D 30/026>
D	H01L 29/66795	<administrative transfer to H10D 30/024>
D	H01L 29/66803	<administrative transfer to H10D 30/0241>
D	H01L 29/6681	<administrative transfer to H10D 30/0243>
D	H01L 29/66818	<administrative transfer to H10D 30/0245>
D	H01L 29/66825	<administrative transfer to H10D 30/0411>
D	H01L 29/66833	<administrative transfer to H10D 30/0413>
D	H01L 29/6684	<administrative transfer to H10D 30/0415>
D	H01L 29/66848	<administrative transfer to H10D 30/061 and H10D 62/83 simultaneously>
D	H01L 29/66856	<administrative transfer to H10D 30/061>
D	H01L 29/66863	<administrative transfer to H10D 30/0612>
D	H01L 29/66871	<administrative transfer to H10D 30/0614>
D	H01L 29/66878	<administrative transfer to H10D 30/0616>
D	H01L 29/66886	<administrative transfer to H10D 30/0618>
D	H01L 29/66893	<administrative transfer to H10D 30/051>
D	H01L 29/66901	<administrative transfer to H10D 30/0512>
D	H01L 29/66909	<administrative transfer to H10D 30/0515>
D	H01L 29/66916	<administrative transfer to H10D 30/0516>
D	H01L 29/66924	<administrative transfer to H10D 30/051>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/66931	<administrative transfer to H10D 48/032>
D	H01L 29/66939	<administrative transfer to H10D 48/032>
D	H01L 29/66946	<administrative transfer to H10D 44/01>
D	H01L 29/66954	<administrative transfer to H10D 44/041>
D	H01L 29/66962	<administrative transfer to H10D 44/061>
D	H01L 29/66969	<administrative transfer to H10D 99/00>
D	H01L 29/66977	<administrative transfer to H10D 48/383>
D	H01L 29/66984	<administrative transfer to H10D 48/385>
D	H01L 29/66992	<administrative transfer to H10D 48/387>
D	H01L 29/68	<administrative transfer to H10D 48/32>
D	H01L 29/685	<administrative transfer to H10D 48/366>
D	H01L 29/70	<administrative transfer to H10D 48/34>
D	H01L 29/705	<administrative transfer to H10D 48/341>
D	H01L 29/72	<administrative transfer to H10D 48/345>
D	H01L 29/73	<administrative transfer to H10D 10/00>
D	H01L 29/7302	<administrative transfer to H10D 84/121>
D	H01L 29/7304	<administrative transfer to H10D 84/125>
D	H01L 29/7306	<administrative transfer to H10D 10/211>
D	H01L 29/7308	<administrative transfer to H10D 10/221>
D	H01L 29/7311	<administrative transfer to H10D 10/231>
D	H01L 29/7313	<administrative transfer to H10D 10/241>
D	H01L 29/7315	<administrative transfer to H10D 10/00>
D	H01L 29/7317	<administrative transfer to H10D 10/311>
D	H01L 29/732	<administrative transfer to H10D 10/40>
D	H01L 29/7322	<administrative transfer to H10D 10/421>
D	H01L 29/7325	<administrative transfer to H10D 10/441>
D	H01L 29/7327	<administrative transfer to H10D 10/461>
D	H01L 29/735	<administrative transfer to H10D 10/60>
D	H01L 29/737	<administrative transfer to H10D 10/80>
D	H01L 29/7371	<administrative transfer to H10D 10/821>
D	H01L 29/7373	<administrative transfer to H10D 10/841>
D	H01L 29/7375	<administrative transfer to H10D 10/861>
D	H01L 29/7376	<administrative transfer to H10D 10/881>
D	H01L 29/7378	<administrative transfer to H10D 10/891>
D	H01L 29/739	<administrative transfer to H10D 12/00>
D	H01L 29/7391	<administrative transfer to H10D 12/211>
D	H01L 29/7392	<administrative transfer to H10D 12/212>
D	H01L 29/7393	<administrative transfer to H10D 12/411>
D	H01L 29/7394	<administrative transfer to H10D 12/421>
D	H01L 29/7395	<administrative transfer to H10D 12/441>
D	H01L 29/7396	<administrative transfer to H10D 12/461>
D	H01L 29/7397	<administrative transfer to H10D 12/481>
D	H01L 29/7398	<administrative transfer to H10D 12/491>
D	H01L 29/74	<administrative transfer to H10D 18/00>
D	H01L 29/7404	<administrative transfer to H10D 84/131>
D	H01L 29/7408	<administrative transfer to H10D 84/133>
D	H01L 29/7412	<administrative transfer to H10D 84/135>
D	H01L 29/7416	<administrative transfer to H10D 84/136>
D	H01L 29/742	<administrative transfer to H10D 84/138>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/7424	<administrative transfer to H10D 18/211>
D	H01L 29/7428	<administrative transfer to H10D 18/221>
D	H01L 29/7432	<administrative transfer to H10D 18/241>
D	H01L 29/7436	<administrative transfer to H10D 18/251>
D	H01L 29/744	<administrative transfer to H10D 18/60>
D	H01L 29/745	<administrative transfer to H10D 18/65>
D	H01L 29/7455	<administrative transfer to H10D 18/655>
D	H01L 29/747	<administrative transfer to H10D 18/80>
D	H01L 29/749	<administrative transfer to H10D 18/40>
D	H01L 29/76	<administrative transfer to H10D 48/36>
D	H01L 29/7606	<administrative transfer to H10D 48/362>
D	H01L 29/7613	<administrative transfer to H10D 30/402>
D	H01L 29/762	<administrative transfer to H10D 44/00>
D	H01L 29/765	<administrative transfer to H10D 44/40>
D	H01L 29/768	<administrative transfer to H10D 44/45>
D	H01L 29/76808	<administrative transfer to H10D 44/452>
D	H01L 29/76816	<administrative transfer to H10D 44/454>
D	H01L 29/76825	<administrative transfer to H10D 44/456>
D	H01L 29/76833	<administrative transfer to H10D 44/462>
D	H01L 29/76841	<administrative transfer to H10D 44/464>
D	H01L 29/7685	<administrative transfer to H10D 44/466>
D	H01L 29/76858	<administrative transfer to H10D 44/468>
D	H01L 29/76866	<administrative transfer to H10D 44/472>
D	H01L 29/76875	<administrative transfer to H10D 44/474>
D	H01L 29/76883	<administrative transfer to H10D 44/476>
D	H01L 29/76891	<administrative transfer to H10D 44/478>
D	H01L 29/772	<administrative transfer to H10D 30/00>
D	H01L 29/7722	<administrative transfer to H10D 30/202>
D	H01L 29/7725	<administrative transfer to H10D 62/228>
D	H01L 29/7727	<administrative transfer to H10D 30/204>
D	H01L 29/775	<administrative transfer to H10D 30/43>
D	H01L 29/778	<administrative transfer to H10D 30/47>
D	H01L 29/7781	<administrative transfer to H10D 30/472>
D	H01L 29/7782	<administrative transfer to H10D 30/473>
D	H01L 29/7783	<administrative transfer to H10D 30/4732>
D	H01L 29/7784	<administrative transfer to H10D 30/4735>
D	H01L 29/7785	<administrative transfer to H10D 30/4738>
D	H01L 29/7786	<administrative transfer to H10D 30/475>
D	H01L 29/7787	<administrative transfer to H10D 30/4755>
D	H01L 29/7788	<administrative transfer to H10D 30/477>
D	H01L 29/7789	<administrative transfer to H10D 30/478>
D	H01L 29/78	<administrative transfer to H10D 30/60>
D	H01L 29/7801	<administrative transfer to H10D 30/64>
D	H01L 29/7802	<administrative transfer to H10D 30/66>
D	H01L 29/7803	<administrative transfer to H10D 84/141>
D	H01L 29/7804	<administrative transfer to H10D 84/143>
D	H01L 29/7805	<administrative transfer to H10D 84/144>
D	H01L 29/7806	<administrative transfer to H10D 84/146>
D	H01L 29/7808	<administrative transfer to H10D 84/148>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/7809	<administrative transfer to H10D 30/663>
D	H01L 29/781	<administrative transfer to H10D 30/664>
D	H01L 29/7811	<administrative transfer to H10D 30/665>
D	H01L 29/7812	<administrative transfer to H10D 30/667>
D	H01L 29/7813	<administrative transfer to H10D 30/668>
D	H01L 29/7815	<administrative transfer to H10D 30/669>
D	H01L 29/7816	<administrative transfer to H10D 30/65>
D	H01L 29/7817	<administrative transfer to H10D 84/151>
D	H01L 29/7818	<administrative transfer to H10D 84/153>
D	H01L 29/7819	<administrative transfer to H10D 84/154>
D	H01L 29/782	<administrative transfer to H10D 84/156>
D	H01L 29/7821	<administrative transfer to H10D 84/158>
D	H01L 29/7823	<administrative transfer to H10D 30/655>
D	H01L 29/7824	<administrative transfer to H10D 30/657>
D	H01L 29/7825	<administrative transfer to H10D 30/658>
D	H01L 29/7826	<administrative transfer to H10D 30/659>
D	H01L 29/7827	<administrative transfer to H10D 30/63>
D	H01L 29/7828	<administrative transfer to H10D 30/635>
D	H01L 29/783	<administrative transfer to H10D 30/721>
D	H01L 29/7831	<administrative transfer to H10D 30/611>
D	H01L 29/7832	<administrative transfer to H10D 30/615>
D	H01L 29/7833	<administrative transfer to H10D 30/601>
D	H01L 29/7834	<administrative transfer to H10D 30/608>
D	H01L 29/7835	<administrative transfer to H10D 30/603>
D	H01L 29/7836	<administrative transfer to H10D 30/605>
D	H01L 29/7838	<administrative transfer to H10D 30/637>
D	H01L 29/7839	<administrative transfer to H10D 64/647>
D	H01L 29/78391	<administrative transfer to H10D 30/701>
D	H01L 29/7841	<administrative transfer to H10D 30/711>
D	H01L 29/7842	<administrative transfer to H10D 30/791>
D	H01L 29/7843	<administrative transfer to H10D 30/792>
D	H01L 29/7845	<administrative transfer to H10D 30/794>
D	H01L 29/7846	<administrative transfer to H10D 30/795>
D	H01L 29/7847	<administrative transfer to H10D 30/796>
D	H01L 29/7848	<administrative transfer to H10D 30/797>
D	H01L 29/7849	<administrative transfer to H10D 30/798>
D	H01L 29/785	<administrative transfer to H10D 30/62>
D	H01L 29/7851	<administrative transfer to H10D 30/6211>
D	H01L 29/7853	<administrative transfer to H10D 30/6212>
D	H01L 29/7854	<administrative transfer to H10D 30/6213>
D	H01L 29/7855	<administrative transfer to H10D 30/6215>
D	H01L 29/7856	<administrative transfer to H10D 30/6217>
D	H01L 2029/7857	<administrative transfer to H10D 30/6218>
D	H01L 2029/7858	<administrative transfer to H10D 30/6219>
D	H01L 29/786	<administrative transfer to H10D 30/67>
D	H01L 29/78603	<administrative transfer to H10D 30/6758>
D	H01L 29/78606	<administrative transfer to H10D 30/6704>
D	H01L 29/78609	<administrative transfer to H10D 30/6706>
D	H01L 29/78612	<administrative transfer to H10D 30/6708>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/78615	<administrative transfer to H10D 30/6711>
D	H01L 29/78618	<administrative transfer to H10D 30/6713>
D	H01L 29/78621	<administrative transfer to H10D 30/6715>
D	H01L 29/78624	<administrative transfer to H10D 30/6717>
D	H01L 29/78627	<administrative transfer to H10D 30/6719>
D	H01L 2029/7863	<administrative transfer to H10D 30/6721>
D	H01L 29/78633	<administrative transfer to H10D 30/6723>
D	H01L 29/78636	<administrative transfer to H10D 30/6725>
D	H01L 29/78639	<administrative transfer to H10D 30/6727>
D	H01L 29/78642	<administrative transfer to H10D 30/6728>
D	H01L 29/78645	<administrative transfer to H10D 30/6733>
D	H01L 29/78648	<administrative transfer to H10D 30/6734>
D	H01L 29/78651	<administrative transfer to H10D 30/6743>
D	H01L 29/78654	<administrative transfer to H10D 30/6744>
D	H01L 29/78657	<administrative transfer to H10D 30/6759>
D	H01L 29/7866	<administrative transfer to H10D 30/6743>
D	H01L 29/78663	<administrative transfer to H10D 30/6746>
D	H01L 29/78666	<administrative transfer to H10D 30/6731 and H10D 30/6746 simultaneously>
D	H01L 29/78669	<administrative transfer to H10D 30/6732 and H10D 30/6746 simultaneously>
D	H01L 29/78672	<administrative transfer to H10D 30/6745>
D	H01L 29/78675	<administrative transfer to H10D 30/6731 and H10D 30/6745 simultaneously>
D	H01L 29/78678	<administrative transfer to H10D 30/6732 and H10D 30/6745 simultaneously>
D	H01L 29/78681	<administrative transfer to H10D 30/675>
D	H01L 29/78684	<administrative transfer to H10D 30/6741>
D	H01L 29/78687	<administrative transfer to H10D 30/6748>
D	H01L 29/7869	<administrative transfer to H10D 30/6755>
D	H01L 29/78693	<administrative transfer to H10D 30/6756>
D	H01L 29/78696	<administrative transfer to H10D 30/6757>
D	H01L 29/788	<administrative transfer to H10D 30/68>
D	H01L 29/7881	<administrative transfer to H10D 30/681>
D	H01L 29/7882	<administrative transfer to H10D 30/682>
D	H01L 29/7883	<administrative transfer to H10D 30/683>
D	H01L 29/7884	<administrative transfer to H10D 30/684>
D	H01L 29/7885	<administrative transfer to H10D 30/685>
D	H01L 29/7886	<administrative transfer to H10D 30/686>
D	H01L 29/7887	<administrative transfer to H10D 30/687>
D	H01L 29/7888	<administrative transfer to H10D 30/688>
D	H01L 29/7889	<administrative transfer to H10D 30/689>
D	H01L 29/792	<administrative transfer to H10D 30/69>
D	H01L 29/7923	<administrative transfer to H10D 30/691>
D	H01L 29/7926	<administrative transfer to H10D 30/693>
D	H01L 29/80	<administrative transfer to H10D 30/80>
D	H01L 29/802	<administrative transfer to H10D 30/801>
D	H01L 29/803	<administrative transfer to H10D 30/803>
D	H01L 29/806	<administrative transfer to H10D 64/649>

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
D	H01L 29/808	<administrative transfer to H10D 30/83>
D	H01L 29/8083	<administrative transfer to H10D 30/831>
D	H01L 29/8086	<administrative transfer to H10D 30/832>
D	H01L 29/812	<administrative transfer to H10D 30/87>
D	H01L 29/8122	<administrative transfer to H10D 30/871>
D	H01L 29/8124	<administrative transfer to H10D 30/873>
D	H01L 29/8126	<administrative transfer to H10D 30/875>
D	H01L 29/8128	<administrative transfer to H10D 30/877>
D	H01L 29/82	<administrative transfer to H10D 48/40>
D	H01L 29/84	<administrative transfer to H10D 48/50>
D	H01L 29/86	<administrative transfer to H10D 1/40>
D	H01L 29/8605	<administrative transfer to H10D 1/43>
D	H01L 29/861	<administrative transfer to H10D 8/00>
D	H01L 29/8611	<administrative transfer to H10D 8/411>
D	H01L 29/8613	<administrative transfer to H10D 8/422>
D	H01L 29/8615	<administrative transfer to H10D 48/381>
D	H01L 29/8616	<administrative transfer to H10D 8/812>
D	H01L 29/8618	<administrative transfer to H10D 8/825>
D	H01L 29/862	<administrative transfer to H10D 8/30>
D	H01L 29/864	<administrative transfer to H10D 8/40>
D	H01L 29/866	<administrative transfer to H10D 8/25>
D	H01L 29/868	<administrative transfer to H10D 8/50>
D	H01L 29/87	<administrative transfer to H10D 8/80>
D	H01L 29/872	<administrative transfer to H10D 8/60>
D	H01L 29/8725	<administrative transfer to H10D 8/605>
D	H01L 29/88	<administrative transfer to H10D 8/70>
D	H01L 29/882	<administrative transfer to H10D 8/755>
D	H01L 29/885	<administrative transfer to H10D 8/75>
D	H01L 29/92	<administrative transfer to H10D 1/62>
D	H01L 29/93	<administrative transfer to H10D 1/64>
D	H01L 29/94	<administrative transfer to H10D 1/66>
D	H01L 29/945	<administrative transfer to H10D 1/665>
D	H01L 2229/00	<administrative transfer to H10D 99/00>
Q	H10D 1/40	H10D 1/40, H10D 48/38
Q	H10D 8/00	H10D 8/00, H10D 8/20
Q	H10D 8/043	H10D 8/043, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D 8/041, H10D 8/045, H10D 8/055
Q	H10D 8/051	H10D 8/051, H10D 1/01, H10D 1/025, H10D 1/045, H10D 1/047, H10D 1/048, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D 8/041, H10D 8/043, H10D 8/045, H10D 8/053, H10D 8/055, H10D 48/021
Q	H10D 10/01	H10D 10/01, H10D 10/051, H10D 10/052, H10D 10/054, H10D 10/056, H10D 10/058
Q	H10D 10/052	H10D 10/052, H10D 10/054
Q	H10D 12/01	H10D 12/01, H10D 12/031

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10D 12/031	H10D 12/031, H10D 12/01, H10D 12/035, H10D 12/038, H10D 18/01, H10D 18/021, H10D 18/031,H10D 30/028, H10D 30/0281, H10D 30/0285, H10D 30/0287, H10D 30/0289, H10D 30/0291, H10D 30/0293, H10D 30/0295, H10D 30/0297
Q	H10D 12/211	H10D 12/211, H10D 18/40, H10D 18/60, H10D 18/65, H10D 18/655
Q	H10D 12/411	H10D 12/411, H10D 12/415, H10D 12/416, H10D 12/417, H10D 12/418, H10D 84/161
Q	H10D 12/491	H10D 12/491, H10D 12/421, H10D 12/461, H10D 12/481
Q	H10D 30/00	H10D 30/00, H10D 30/40
Q	H10D 30/01	H10D 30/01, H10D 30/012, H10D 30/014, H10D 30/015, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/021, H10D 30/0212, H10D 30/0213, H10D 30/0215, H10D 30/0217, H10D 30/0218, H10D 30/022, H10D 30/0221, H10D 30/0223, H10D 30/0225, H10D 30/0227, H10D 30/0229, H10D 30/023, H10D 30/024, H10D 30/0241, H10D 30/0243, H10D 30/0245, H10D 30/025, H10D 30/026, H10D 30/027, H10D 30/0273, H10D 30/0275, H10D 30/0277, H10D 30/0278, H10D 30/028, H10D 30/0281, H10D 30/0285, H10D 30/0287, H10D 30/0289, H10D 30/0291, H10D 30/0293, H10D 30/0295, H10D 30/0297, H10D 30/031, H10D 30/0312, H10D 30/0314, H10D 30/0316, H10D 30/0318, H10D 30/0321, H10D 30/0323, H10D 30/0327, H10D 30/0411, H10D 30/0413, H10D 30/0415, H10D 30/051, H10D 30/0512, H10D 30/0515, H10D 30/0516, H10D 30/061, H10D 30/0612, H10D 30/0614, H10D 30/0616, H10D 30/0618
Q	H10D 30/014	H10D 30/014, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198
Q	H10D 30/022	H10D 30/022, H10D 30/0218
Q	H10D 30/024	H10D 30/024, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198
Q	H10D 30/0241	H10D 30/0241, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194
Q	H10D 30/0245	H10D 30/0245, H10D 30/0191, H10D 30/0193, H10D 30/0194
Q	H10D 30/0273	H10D 30/0273, H10D 30/0223, H10D 30/0225, H10D 30/0227, H10D 30/0229, H10D 64/017
Q	H10D 30/031	H10D 30/031, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0318

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10D 30/0321	H10D 30/0321, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0318
Q	H10D 30/0323	H10D 30/0323, H10D 30/017, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198
Q	H10D 30/0327	H10D 30/0327, H10D 30/019, H10D 30/0191, H10D 30/0193, H10D 30/0194, H10D 30/0195, H10D 30/0196, H10D 30/0197, H10D 30/0198, H10D 30/0312, H10D 30/0314, H10D 30/0316, H10D 30/0318
Q	H10D 30/0415	H10D 30/0415, H10D 30/0411
Q	H10D 30/061	H10D 30/061, H10D 30/0612, H10D 30/0614, H10D 30/0616, H10D 30/0618
Q	H10D 30/43	H10D 30/43, H10D 30/435, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/47	H10D 30/47, H10D 30/471, H10D 30/474, H10D 30/476, H10D 30/481, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/4738	H10D 30/4738, H10D 30/4735
Q	H10D 30/477	H10D 30/477, H10D 30/485
Q	H10D 30/478	H10D 30/478, H10D 30/485
Q	H10D 30/603	H10D 30/603, H10D 30/605
Q	H10D 30/608	H10D 30/608, H10D 30/605
Q	H10D 30/62	H10D 30/62, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6211	H10D 30/6211, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6212	H10D 30/6212, H10D 30/503, H10D 30/504, H10D 30/506
Q	H10D 30/6213	H10D 30/6213, H10D 30/503, H10D 30/504, H10D 30/506
Q	H10D 30/6215	H10D 30/6215, H10D 30/6217
Q	H10D 30/6217	H10D 30/6217, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6218	H10D 30/6218, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6219	H10D 30/6219, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/64	H10D 30/64, H10D 30/645, H10D 84/101
Q	H10D 30/66	H10D 30/66, H10D 30/662
Q	H10D 30/6728	H10D 30/6728, H10D 30/6704, H10D 30/674

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10D 30/6733	H10D 30/6733, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
Q	H10D 30/6734	H10D 30/6734, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
Q	H10D 30/6735	H10D 30/6735, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6741	H10D 30/6741, H10D 30/481, H10D 30/485
Q	H10D 30/6748	H10D 30/6748, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509
Q	H10D 30/6757	H10D 30/6757, H10D 30/501, H10D 30/502, H10D 30/503, H10D 30/504, H10D 30/506, H10D 30/507, H10D 30/508, H10D 30/509, H10D 30/674
Q	H10D 30/701	H10D 30/701, H10D 30/68
Q	H10D 30/751	H10D 30/751, H10D 30/798
Q	H10D 48/021	H10D 48/021, H10D 1/025, H10D 1/045, H10D 1/047, H10D 1/048, H10D 8/01, H10D 8/021, H10D 8/022, H10D 8/024, H10D 8/041, H10D 8/043, H10D 8/045, H10D 8/051, H10D 8/053, H10D 8/055
Q	H10D 48/031	H10D 48/031, H10D 10/01, H10D 10/021, H10D 10/031, H10D 10/041, H10D 10/051, H10D 10/052, H10D 10/054, H10D 10/056, H10D 10/058, H10D 10/061, H10D 12/01, H10D 12/021, H10D 12/031, H10D 12/032, H10D 12/035, H10D 12/038, H10D 18/01, H10D 18/021, H10D 18/031
Q	H10D 48/30	H10D 48/30, H10D 48/00
Q	H10D 48/383	H10D 48/383, H10D 48/3835
Q	H10D 62/00	H10D 62/00, H10D 62/01
Q	H10D 62/10	H10D 62/10, H10D 62/128, H10D 62/129
Q	H10D 62/111	H10D 62/111, H10D 62/051, H10D 62/052, H10D 62/054, H10D 62/056, H10D 62/058
Q	H10D 62/141	H10D 62/141, H10D 62/145
Q	H10D 62/152	H10D 62/152, H10D 62/156
Q	H10D 62/314	H10D 62/314, H10D 62/299
Q	H10D 62/378	H10D 62/378, H10D 64/529
Q	H10D 62/80	H10D 62/80, H10D 62/82, H10D 62/8271, H10D 62/8281, H10D 62/871, H10D 62/874, H10D 62/875, H10D 62/881, H10D 62/883
Q	H10D 62/81	H10D 62/81, H10D 62/80
Q	H10D 62/82	H10D 62/82, H10D 62/8271, H10D 62/8281
Q	H10D 62/83	H10D 62/83, H10D 62/822, H10D 62/832, H10D 62/834, H10D 62/881
Q	H10D 62/8303	H10D 62/8303, H10D 62/882
Q	H10D 62/85	H10D 62/85, H10D 62/824, H10D 62/852, H10D 62/854
Q	H10D 62/8503	H10D 62/8503, H10D 62/881
Q	H10D 62/86	H10D 62/86, H10D 62/826, H10D 62/8603, H10D 62/862, H10D 62/864
Q	H10D 62/871	H10D 62/871, H10D 62/82, H10D 62/8281, H10D 62/883

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10D 62/874	H10D 62/874, H10D 62/82, H10D 62/8281, H10D 62/883
Q	H10D 64/23	H10D 64/23, H10D 64/232
Q	H10D 64/252	H10D 64/252, H10D 64/2523, H10D 64/2527
Q	H10D 64/254	H10D 64/254, H10D 64/257, H10D 64/256, H10D 64/2565
Q	H10D 64/256	H10D 64/256, H10D 64/2527
Q	H10D 64/257	H10D 64/257, H10D 64/256
Q	H10D 64/667	H10D 64/667, H10D 64/669
Q	H10D 64/668	H10D 64/668, H10D 64/669
Q	H10D 64/671	H10D 64/671, H10D 64/675
Q	H10D 84/01	H10D 84/01, H10D 84/02, H10D 84/03, H10D 84/035, H10D 84/038, H10D 84/05, H10D 84/07, H10D 84/08
Q	H10D 84/0151	H10D 84/0151, H10D 84/0153
Q	H10D 84/0156	H10D 84/0156, H10D 62/299
Q	H10D 84/02	H10D 84/02, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 84/03, H10D 88/01
Q	H10D 84/032	H10D 84/032, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01

Type*	**From CPC Symbol (existing)**	**To CPC Symbol(s)**
Q	H10D 84/035	H10D 84/035, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/05	H10D 84/05, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/07	H10D 84/07, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01

Type*	From CPC Symbol (existing)	To CPC Symbol(s)
Q	H10D 84/08	H10D 84/08, H10D 84/0107, H10D 84/0109, H10D 84/0112, H10D 84/0114, H10D 84/0116, H10D 84/0119, H10D 84/0121, H10D 84/0123, H10D 84/0126, H10D 84/0128, H10D 84/013, H10D 84/0133, H10D 84/0135, H10D 84/0137, H10D 84/014, H10D 84/0142, H10D 84/0144, H10D 84/0147, H10D 84/0151, H10D 84/0153, H10D 84/0156, H10D 84/0158, H10D 84/016, H10D 84/0163, H10D 84/0165, H10D 84/0167, H10D 84/017, H10D 84/0172, H10D 84/0174, H10D 84/0177, H10D 84/0179, H10D 84/0181, H10D 84/0184, H10D 84/0186, H10D 84/0188, H10D 84/0191, H10D 84/0193, H10D 84/0195, H10D 84/0198, H10D 88/01
Q	H10D 84/206	H10D 84/206, H10D 84/209, H10D 84/212
Q	H10D 84/40	H10D 84/40, H10D 84/80
Q	H10D 84/401	H10D 84/401, H10D 84/40
Q	H10D 84/645	H10D 84/645, H10D 84/67
Q	H10D 84/811	H10D 84/811, H10D 84/813, H10D 84/817
Q	H10D 84/83	H10D 84/83, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832, H10D 84/833, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
Q	H10D 84/834	H10D 84/834, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/832, H10D 84/833, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
Q	H10D 84/84	H10D 84/84, H10D 84/8311, H10D 84/8312, H10D 84/83125, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
Q	H10D 84/85	H10D 84/85, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/851, H10D 84/852
Q	H10D 84/853	H10D 84/853, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839, H10D 84/851, H10D 84/852
Q	H10D 84/856	H10D 84/856, H10D 84/8311, H10D 84/8312, H10D 84/83135, H10D 84/83138, H10D 84/8314, H10D 84/8316, H10D 84/835, H10D 84/836, H10D 84/837, H10D 84/839
Q	H10D 86/85	H10D 86/85, H10D 84/201, H10D 84/206, H10D 84/209, H10D 84/212

* C = entries with modified file scope where reclassification of documents from the entries is involved; Q = new entries which are firstly populated with documents via administrative transfers from deleted (D) entries. Afterwards, the transferred documents into the Q entry will either stay or be moved to more appropriate entries, as determined by intellectual reclassification; D = deleted entries; F = frozen entries will be deleted once reclassification of documents from the entries is completed.

NOTES:

- Only C, D, F, and Q type entries are included in the table above.
- When multiple symbols are included in the "To" column, do not use ranges of symbols.
- For administrative transfer of documents, the following text should be used: "< administrative transfer to XX>", "<administrative transfer to XX and YY simultaneously>", or "<administrative transfer to XX, YY, ...and ZZ simultaneously>" when administrative transfer of the same documents is to more than one place.
- Administrative transfer to main trunk groups is assumed to be the source allocation type, unless otherwise indicated.
- Administrative transfer to 2000/Y series groups is assumed to be "additional information".
- If needed, instructions for allocation type should be indicated within the angle brackets using the abbreviations "ADD" or "INV": <administrative transfer to XX ADD>, <administrative transfer to XX INV>, or < administrative transfer to XX ADD, YY INV, ... and ZZ ADD simultaneously>.
- In certain situations, the "D" entries of 2000-series or Y-series groups may not require a destination ("To") symbol, however it is required to specify "<no transfer>" in the "To" column for such cases.
- RCL is not needed for finalisation projects.

4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

CPC	**IPC**	**Action***
H01L 21/06		DELETE
H01L 21/08		DELETE
H01L 21/10		DELETE
H01L 21/101		DELETE
H01L 21/103		DELETE
H01L 21/105		DELETE
H01L 21/108		DELETE
H01L 21/12		DELETE
H01L 21/14		DELETE
H01L 21/145		DELETE
H01L 21/16		DELETE
H01L 21/161		DELETE
H01L 21/162		DELETE
H01L 21/164		DELETE
H01L 21/165		DELETE
H01L 21/167		DELETE
H01L 21/168		DELETE
H01L 2021/775		DELETE
H01L 21/782		DELETE
H01L 21/784		DELETE
H01L 21/786		DELETE
H01L 21/82		DELETE
H01L 21/8206		DELETE
H01L 21/8213		DELETE
H01L 21/822		DELETE
H01L 21/8221		DELETE
H01L 21/8222		DELETE
H01L 21/8224		DELETE
H01L 21/8226		DELETE
H01L 21/8228		DELETE
H01L 21/82285		DELETE
H01L 21/8232		DELETE
H01L 21/8234		DELETE
H01L 21/823406		DELETE
H01L 21/823412		DELETE
H01L 21/823418		DELETE
H01L 21/823425		DELETE
H01L 21/823431		DELETE
H01L 21/823437		DELETE
H01L 21/823443		DELETE
H01L 21/82345		DELETE

CPC	**IPC**	**Action***
H01L 21/823456		DELETE
H01L 21/823462		DELETE
H01L 21/823468		DELETE
H01L 21/823475		DELETE
H01L 21/823481		DELETE
H01L 21/823487		DELETE
H01L 21/823493		DELETE
H01L 21/8236		DELETE
H01L 21/8238		DELETE
H01L 21/823807		DELETE
H01L 21/823814		DELETE
H01L 21/823821		DELETE
H01L 21/823828		DELETE
H01L 21/823835		DELETE
H01L 21/823842		DELETE
H01L 21/82385		DELETE
H01L 21/823857		DELETE
H01L 21/823864		DELETE
H01L 21/823871		DELETE
H01L 21/823878		DELETE
H01L 21/823885		DELETE
H01L 21/823892		DELETE
H01L 21/8248		DELETE
H01L 21/8249		DELETE
H01L 21/8252		DELETE
H01L 21/8254		DELETE
H01L 21/8256		DELETE
H01L 21/8258		DELETE
H01L 21/84		DELETE
H01L 21/845		DELETE
H01L 21/86		DELETE
H01L 27/00		DELETE
H01L 27/01		DELETE
H01L 27/013		DELETE
H01L 27/016		DELETE
H01L 27/02		DELETE
H01L 27/0203		DELETE
H01L 27/0207		DELETE
H01L 27/0211		DELETE
H01L 27/0214		DELETE
H01L 27/0218		DELETE
H01L 27/0222		DELETE
H01L 27/0225		DELETE
H01L 27/0229		DELETE
H01L 27/0233		DELETE

CPC NOTICE OF CHANGES 1723

DATE: JANUARY 1, 2025

PROJECT RP12465

CPC	**IPC**	**Action***
H01L 27/0237		DELETE
H01L 27/024		DELETE
H01L 27/0244		DELETE
H01L 27/0248		DELETE
H01L 27/0251		DELETE
H01L 27/0255		DELETE
H01L 27/0259		DELETE
H01L 27/0262		DELETE
H01L 27/0266		DELETE
H01L 27/027		DELETE
H01L 27/0274		DELETE
H01L 27/0277		DELETE
H01L 27/0281		DELETE
H01L 27/0285		DELETE
H01L 27/0288		DELETE
H01L 27/0292		DELETE
H01L 27/0296		DELETE
H01L 27/04		DELETE
H01L 27/06		DELETE
H01L 27/0605		DELETE
H01L 27/0611		DELETE
H01L 27/0617		DELETE
H01L 27/0623		DELETE
H01L 27/0629		DELETE
H01L 27/0635		DELETE
H01L 27/0641		DELETE
H01L 27/0647		DELETE
H01L 27/0652		DELETE
H01L 27/0658		DELETE
H01L 27/0664		DELETE
H01L 27/067		DELETE
H01L 27/0676		DELETE
H01L 27/0682		DELETE
H01L 27/0688		DELETE
H01L 27/0694		DELETE
H01L 27/07		DELETE
H01L 27/0705		DELETE
H01L 27/0711		DELETE
H01L 27/0716		DELETE
H01L 27/0722		DELETE
H01L 27/0727		DELETE
H01L 27/0733		DELETE
H01L 27/0738		DELETE
H01L 27/0744		DELETE
H01L 27/075		DELETE

CPC	**IPC**	**Action***
H01L 27/0755		DELETE
H01L 27/0761		DELETE
H01L 27/0766		DELETE
H01L 27/0772		DELETE
H01L 27/0777		DELETE
H01L 27/0783		DELETE
H01L 27/0788		DELETE
H01L 27/0794		DELETE
H01L 27/08		DELETE
H01L 27/0802		DELETE
H01L 27/0805		DELETE
H01L 27/0808		DELETE
H01L 27/0811		DELETE
H01L 27/0814		DELETE
H01L 27/0817		DELETE
H01L 27/082		DELETE
H01L 27/0821		DELETE
H01L 27/0823		DELETE
H01L 27/0825		DELETE
H01L 27/0826		DELETE
H01L 27/0828		DELETE
H01L 27/085		DELETE
H01L 27/088		DELETE
H01L 27/0883		DELETE
H01L 27/0886		DELETE
H01L 27/092		DELETE
H01L 27/0921		DELETE
H01L 27/0922		DELETE
H01L 27/0924		DELETE
H01L 27/0925		DELETE
H01L 27/0927		DELETE
H01L 27/0928		DELETE
H01L 27/095		DELETE
H01L 27/098		DELETE
H01L 27/10		DELETE
H01L 27/101		DELETE
H01L 27/102		DELETE
H01L 27/1021		DELETE
H01L 27/1022		DELETE
H01L 27/1027		DELETE
H01L 27/1028		DELETE
H01L 27/105		DELETE
H01L 27/1055		DELETE
H01L 27/1057		DELETE
H01L 27/118		DELETE

CPC	**IPC**	**Action***
H01L 27/11801		DELETE
H01L 27/11803		DELETE
H01L 2027/11805		DELETE
H01L 27/11807		DELETE
H01L 2027/11809		DELETE
H01L 2027/11811		DELETE
H01L 2027/11812		DELETE
H01L 2027/11814		DELETE
H01L 2027/11816		DELETE
H01L 2027/11818		DELETE
H01L 2027/1182		DELETE
H01L 2027/11822		DELETE
H01L 2027/11824		DELETE
H01L 2027/11825		DELETE
H01L 2027/11827		DELETE
H01L 2027/11829		DELETE
H01L 2027/11831		DELETE
H01L 2027/11833		DELETE
H01L 2027/11835		DELETE
H01L 2027/11837		DELETE
H01L 2027/11838		DELETE
H01L 2027/1184		DELETE
H01L 2027/11842		DELETE
H01L 2027/11844		DELETE
H01L 2027/11846		DELETE
H01L 2027/11848		DELETE
H01L 2027/1185		DELETE
H01L 2027/11851		DELETE
H01L 2027/11853		DELETE
H01L 2027/11855		DELETE
H01L 2027/11857		DELETE
H01L 2027/11859		DELETE
H01L 2027/11861		DELETE
H01L 2027/11862		DELETE
H01L 2027/11864		DELETE
H01L 2027/11866		DELETE
H01L 2027/11868		DELETE
H01L 2027/1187		DELETE
H01L 2027/11872		DELETE
H01L 2027/11874		DELETE
H01L 2027/11875		DELETE
H01L 2027/11877		DELETE
H01L 2027/11879		DELETE
H01L 2027/11881		DELETE
H01L 2027/11883		DELETE

CPC	**IPC**	**Action***
H01L 2027/11885		DELETE
H01L 2027/11887		DELETE
H01L 2027/11888		DELETE
H01L 2027/1189		DELETE
H01L 2027/11892		DELETE
H01L 2027/11894		DELETE
H01L 27/11896		DELETE
H01L 27/11898		DELETE
H01L 27/12		DELETE
H01L 27/1203		DELETE
H01L 27/1207		DELETE
H01L 27/1211		DELETE
H01L 27/1214		DELETE
H01L 27/1218		DELETE
H01L 27/1222		DELETE
H01L 27/1225		DELETE
H01L 27/1229		DELETE
H01L 27/1233		DELETE
H01L 27/1237		DELETE
H01L 27/124		DELETE
H01L 27/1244		DELETE
H01L 27/1248		DELETE
H01L 27/1251		DELETE
H01L 27/1255		DELETE
H01L 27/1259		DELETE
H01L 27/1262		DELETE
H01L 27/1266		DELETE
H01L 27/127		DELETE
H01L 27/1274		DELETE
H01L 27/1277		DELETE
H01L 27/1281		DELETE
H01L 27/1285		DELETE
H01L 27/1288		DELETE
H01L 27/1292		DELETE
H01L 27/1296		DELETE
H01L 27/13		DELETE
H01L 28/00		DELETE
H01L 28/10		DELETE
H01L 28/20		DELETE
H01L 28/22		DELETE
H01L 28/24		DELETE
H01L 28/26		DELETE
H01L 28/40		DELETE
H01L 28/55		DELETE
H01L 28/56		DELETE

CPC	**IPC**	**Action***
H01L 28/57		DELETE
H01L 28/60		DELETE
H01L 28/65		DELETE
H01L 28/75		DELETE
H01L 28/82		DELETE
H01L 28/84		DELETE
H01L 28/86		DELETE
H01L 28/87		DELETE
H01L 28/88		DELETE
H01L 28/90		DELETE
H01L 28/91		DELETE
H01L 28/92		DELETE
H01L 29/00		DELETE
H01L 29/02		DELETE
H01L 29/04		DELETE
H01L 29/045		DELETE
H01L 29/06		DELETE
H01L 29/0603		DELETE
H01L 29/0607		DELETE
H01L 29/0611		DELETE
H01L 29/0615		DELETE
H01L 29/0619		DELETE
H01L 29/0623		DELETE
H01L 29/0626		DELETE
H01L 29/063		DELETE
H01L 29/0634		DELETE
H01L 29/0638		DELETE
H01L 29/0642		DELETE
H01L 29/0646		DELETE
H01L 29/0649		DELETE
H01L 29/0653		DELETE
H01L 29/0657		DELETE
H01L 29/0661		DELETE
H01L 29/0665		DELETE
H01L 29/0669		DELETE
H01L 29/0673		DELETE
H01L 29/0676		DELETE
H01L 29/068		DELETE
H01L 29/0684		DELETE
H01L 29/0688		DELETE
H01L 29/0692		DELETE
H01L 29/0696		DELETE
H01L 29/08		DELETE
H01L 29/0804		DELETE
H01L 29/0808		DELETE

CPC	**IPC**	**Action***
H01L 29/0813		DELETE
H01L 29/0817		DELETE
H01L 29/0821		DELETE
H01L 29/0826		DELETE
H01L 29/083		DELETE
H01L 29/0834		DELETE
H01L 29/0839		DELETE
H01L 29/0843		DELETE
H01L 29/0847		DELETE
H01L 29/0852		DELETE
H01L 29/0856		DELETE
H01L 29/086		DELETE
H01L 29/0865		DELETE
H01L 29/0869		DELETE
H01L 29/0873		DELETE
H01L 29/0878		DELETE
H01L 29/0882		DELETE
H01L 29/0886		DELETE
H01L 29/0891		DELETE
H01L 29/0895		DELETE
H01L 29/10		DELETE
H01L 29/1004		DELETE
H01L 29/1008		DELETE
H01L 29/1012		DELETE
H01L 29/1016		DELETE
H01L 29/102		DELETE
H01L 29/1025		DELETE
H01L 29/1029		DELETE
H01L 29/1033		DELETE
H01L 29/1037		DELETE
H01L 29/1041		DELETE
H01L 29/1045		DELETE
H01L 29/105		DELETE
H01L 29/1054		DELETE
H01L 29/1058		DELETE
H01L 29/1062		DELETE
H01L 29/1066		DELETE
H01L 29/107		DELETE
H01L 29/1075		DELETE
H01L 29/1079		DELETE
H01L 29/1083		DELETE
H01L 29/1087		DELETE
H01L 29/1091		DELETE
H01L 29/1095		DELETE
H01L 29/12		DELETE

CPC	**IPC**	**Action***
H01L 29/122		DELETE
H01L 29/125		DELETE
H01L 29/127		DELETE
H01L 29/15		DELETE
H01L 29/151		DELETE
H01L 29/152		DELETE
H01L 29/154		DELETE
H01L 29/155		DELETE
H01L 29/157		DELETE
H01L 29/158		DELETE
H01L 29/16		DELETE
H01L 29/1602		DELETE
H01L 29/1604		DELETE
H01L 29/1606		DELETE
H01L 29/1608		DELETE
H01L 29/161		DELETE
H01L 29/165		DELETE
H01L 29/167		DELETE
H01L 29/18		DELETE
H01L 29/185		DELETE
H01L 29/20		DELETE
H01L 29/2003		DELETE
H01L 29/2006		DELETE
H01L 29/201		DELETE
H01L 29/205		DELETE
H01L 29/207		DELETE
H01L 29/22		DELETE
H01L 29/2203		DELETE
H01L 29/2206		DELETE
H01L 29/221		DELETE
H01L 29/225		DELETE
H01L 29/227		DELETE
H01L 29/24		DELETE
H01L 29/242		DELETE
H01L 29/245		DELETE
H01L 29/247		DELETE
H01L 29/26		DELETE
H01L 29/263		DELETE
H01L 29/267		DELETE
H01L 29/30		DELETE
H01L 29/32		DELETE
H01L 29/34		DELETE
H01L 29/36		DELETE
H01L 29/365		DELETE
H01L 29/40		DELETE

CPC	**IPC**	**Action***
H01L 29/401		DELETE
H01L 29/4011		DELETE
H01L 29/40111		DELETE
H01L 29/40114		DELETE
H01L 29/40117		DELETE
H01L 29/402		DELETE
H01L 29/404		DELETE
H01L 29/405		DELETE
H01L 29/407		DELETE
H01L 29/408		DELETE
H01L 29/41		DELETE
H01L 29/413		DELETE
H01L 29/417		DELETE
H01L 29/41708		DELETE
H01L 29/41716		DELETE
H01L 29/41725		DELETE
H01L 29/41733		DELETE
H01L 29/41741		DELETE
H01L 29/4175		DELETE
H01L 29/41758		DELETE
H01L 29/41766		DELETE
H01L 29/41775		DELETE
H01L 29/41783		DELETE
H01L 29/41791		DELETE
H01L 29/423		DELETE
H01L 29/42304		DELETE
H01L 29/42308		DELETE
H01L 29/42312		DELETE
H01L 29/42316		DELETE
H01L 29/4232		DELETE
H01L 29/42324		DELETE
H01L 29/42328		DELETE
H01L 29/42332		DELETE
H01L 29/42336		DELETE
H01L 29/4234		DELETE
H01L 29/42344		DELETE
H01L 29/42348		DELETE
H01L 29/42352		DELETE
H01L 29/42356		DELETE
H01L 29/4236		DELETE
H01L 29/42364		DELETE
H01L 29/42368		DELETE
H01L 29/42372		DELETE
H01L 29/42376		DELETE
H01L 29/4238		DELETE

CPC	**IPC**	**Action***
H01L 29/42384		DELETE
H01L 2029/42388		DELETE
H01L 29/42392		DELETE
H01L 29/42396		DELETE
H01L 29/43		DELETE
H01L 29/432		DELETE
H01L 29/435		DELETE
H01L 29/437		DELETE
H01L 29/45		DELETE
H01L 29/452		DELETE
H01L 29/454		DELETE
H01L 29/456		DELETE
H01L 29/458		DELETE
H01L 29/47		DELETE
H01L 29/475		DELETE
H01L 29/49		DELETE
H01L 29/4908		DELETE
H01L 29/4916		DELETE
H01L 29/4925		DELETE
H01L 29/4933		DELETE
H01L 29/4941		DELETE
H01L 29/495		DELETE
H01L 29/4958		DELETE
H01L 29/4966		DELETE
H01L 29/4975		DELETE
H01L 29/4983		DELETE
H01L 29/4991		DELETE
H01L 29/51		DELETE
H01L 29/511		DELETE
H01L 29/512		DELETE
H01L 29/513		DELETE
H01L 29/515		DELETE
H01L 29/516		DELETE
H01L 29/517		DELETE
H01L 29/518		DELETE
H01L 29/66		DELETE
H01L 29/66007		DELETE
H01L 29/66015		DELETE
H01L 29/66022		DELETE
H01L 29/6603		DELETE
H01L 29/66037		DELETE
H01L 29/66045		DELETE
H01L 29/66053		DELETE
H01L 29/6606		DELETE
H01L 29/66068		DELETE

CPC	**IPC**	**Action***
H01L 29/66075		DELETE
H01L 29/66083		DELETE
H01L 29/6609		DELETE
H01L 29/66098		DELETE
H01L 29/66106		DELETE
H01L 29/66113		DELETE
H01L 29/66121		DELETE
H01L 29/66128		DELETE
H01L 29/66136		DELETE
H01L 29/66143		DELETE
H01L 29/66151		DELETE
H01L 29/66159		DELETE
H01L 29/66166		DELETE
H01L 29/66174		DELETE
H01L 29/66181		DELETE
H01L 29/66189		DELETE
H01L 29/66196		DELETE
H01L 29/66204		DELETE
H01L 29/66212		DELETE
H01L 29/66219		DELETE
H01L 29/66227		DELETE
H01L 29/66234		DELETE
H01L 29/66242		DELETE
H01L 29/6625		DELETE
H01L 29/66257		DELETE
H01L 29/66265		DELETE
H01L 29/66272		DELETE
H01L 29/6628		DELETE
H01L 29/66287		DELETE
H01L 29/66295		DELETE
H01L 29/66303		DELETE
H01L 29/6631		DELETE
H01L 29/66318		DELETE
H01L 29/66325		DELETE
H01L 29/66333		DELETE
H01L 29/6634		DELETE
H01L 29/66348		DELETE
H01L 29/66356		DELETE
H01L 29/66363		DELETE
H01L 29/66371		DELETE
H01L 29/66378		DELETE
H01L 29/66386		DELETE
H01L 29/66393		DELETE
H01L 29/66401		DELETE
H01L 29/66409		DELETE

CPC	**IPC**	**Action***
H01L 29/66416		DELETE
H01L 29/66424		DELETE
H01L 29/66431		DELETE
H01L 29/66439		DELETE
H01L 29/66446		DELETE
H01L 29/66454		DELETE
H01L 29/66462		DELETE
H01L 29/66469		DELETE
H01L 29/66477		DELETE
H01L 29/66484		DELETE
H01L 29/66492		DELETE
H01L 29/665		DELETE
H01L 29/66507		DELETE
H01L 29/66515		DELETE
H01L 29/66522		DELETE
H01L 29/6653		DELETE
H01L 29/66537		DELETE
H01L 29/66545		DELETE
H01L 29/66553		DELETE
H01L 29/6656		DELETE
H01L 29/66568		DELETE
H01L 29/66575		DELETE
H01L 29/66583		DELETE
H01L 29/6659		DELETE
H01L 29/66598		DELETE
H01L 29/66606		DELETE
H01L 29/66613		DELETE
H01L 29/66621		DELETE
H01L 29/66628		DELETE
H01L 29/66636		DELETE
H01L 29/66643		DELETE
H01L 29/66651		DELETE
H01L 29/66659		DELETE
H01L 29/66666		DELETE
H01L 29/66674		DELETE
H01L 29/66681		DELETE
H01L 29/66689		DELETE
H01L 29/66696		DELETE
H01L 29/66704		DELETE
H01L 29/66712		DELETE
H01L 29/66719		DELETE
H01L 29/66727		DELETE
H01L 29/66734		DELETE
H01L 29/66742		DELETE
H01L 29/6675		DELETE

CPC	**IPC**	**Action***
H01L 29/66757		DELETE
H01L 29/66765		DELETE
H01L 29/66772		DELETE
H01L 29/6678		DELETE
H01L 29/66787		DELETE
H01L 29/66795		DELETE
H01L 29/66803		DELETE
H01L 29/6681		DELETE
H01L 29/66818		DELETE
H01L 29/66825		DELETE
H01L 29/66833		DELETE
H01L 29/6684		DELETE
H01L 29/66848		DELETE
H01L 29/66856		DELETE
H01L 29/66863		DELETE
H01L 29/66871		DELETE
H01L 29/66878		DELETE
H01L 29/66886		DELETE
H01L 29/66893		DELETE
H01L 29/66901		DELETE
H01L 29/66909		DELETE
H01L 29/66916		DELETE
H01L 29/66924		DELETE
H01L 29/66931		DELETE
H01L 29/66939		DELETE
H01L 29/66946		DELETE
H01L 29/66954		DELETE
H01L 29/66962		DELETE
H01L 29/66969		DELETE
H01L 29/66977		DELETE
H01L 29/66984		DELETE
H01L 29/66992		DELETE
H01L 29/68		DELETE
H01L 29/685		DELETE
H01L 29/70		DELETE
H01L 29/705		DELETE
H01L 29/72		DELETE
H01L 29/73		DELETE
H01L 29/7302		DELETE
H01L 29/7304		DELETE
H01L 29/7306		DELETE
H01L 29/7308		DELETE
H01L 29/7311		DELETE
H01L 29/7313		DELETE
H01L 29/7315		DELETE

CPC	**IPC**	**Action***
H01L 29/7317		DELETE
H01L 29/732		DELETE
H01L 29/7322		DELETE
H01L 29/7325		DELETE
H01L 29/7327		DELETE
H01L 29/735		DELETE
H01L 29/737		DELETE
H01L 29/7371		DELETE
H01L 29/7373		DELETE
H01L 29/7375		DELETE
H01L 29/7376		DELETE
H01L 29/7378		DELETE
H01L 29/739		DELETE
H01L 29/7391		DELETE
H01L 29/7392		DELETE
H01L 29/7393		DELETE
H01L 29/7394		DELETE
H01L 29/7395		DELETE
H01L 29/7396		DELETE
H01L 29/7397		DELETE
H01L 29/7398		DELETE
H01L 29/74		DELETE
H01L 29/7404		DELETE
H01L 29/7408		DELETE
H01L 29/7412		DELETE
H01L 29/7416		DELETE
H01L 29/742		DELETE
H01L 29/7424		DELETE
H01L 29/7428		DELETE
H01L 29/7432		DELETE
H01L 29/7436		DELETE
H01L 29/744		DELETE
H01L 29/745		DELETE
H01L 29/7455		DELETE
H01L 29/747		DELETE
H01L 29/749		DELETE
H01L 29/76		DELETE
H01L 29/7606		DELETE
H01L 29/7613		DELETE
H01L 29/762		DELETE
H01L 29/765		DELETE
H01L 29/768		DELETE
H01L 29/76808		DELETE
H01L 29/76816		DELETE
H01L 29/76825		DELETE

CPC	**IPC**	**Action***
H01L 29/76833		DELETE
H01L 29/76841		DELETE
H01L 29/7685		DELETE
H01L 29/76858		DELETE
H01L 29/76866		DELETE
H01L 29/76875		DELETE
H01L 29/76883		DELETE
H01L 29/76891		DELETE
H01L 29/772		DELETE
H01L 29/7722		DELETE
H01L 29/7725		DELETE
H01L 29/7727		DELETE
H01L 29/775		DELETE
H01L 29/778		DELETE
H01L 29/7781		DELETE
H01L 29/7782		DELETE
H01L 29/7783		DELETE
H01L 29/7784		DELETE
H01L 29/7785		DELETE
H01L 29/7786		DELETE
H01L 29/7787		DELETE
H01L 29/7788		DELETE
H01L 29/7789		DELETE
H01L 29/78		DELETE
H01L 29/7801		DELETE
H01L 29/7802		DELETE
H01L 29/7803		DELETE
H01L 29/7804		DELETE
H01L 29/7805		DELETE
H01L 29/7806		DELETE
H01L 29/7808		DELETE
H01L 29/7809		DELETE
H01L 29/781		DELETE
H01L 29/7811		DELETE
H01L 29/7812		DELETE
H01L 29/7813		DELETE
H01L 29/7815		DELETE
H01L 29/7816		DELETE
H01L 29/7817		DELETE
H01L 29/7818		DELETE
H01L 29/7819		DELETE
H01L 29/782		DELETE
H01L 29/7821		DELETE
H01L 29/7823		DELETE
H01L 29/7824		DELETE

CPC	**IPC**	**Action***
H01L 29/7825		DELETE
H01L 29/7826		DELETE
H01L 29/7827		DELETE
H01L 29/7828		DELETE
H01L 29/783		DELETE
H01L 29/7831		DELETE
H01L 29/7832		DELETE
H01L 29/7833		DELETE
H01L 29/7834		DELETE
H01L 29/7835		DELETE
H01L 29/7836		DELETE
H01L 29/7838		DELETE
H01L 29/7839		DELETE
H01L 29/78391		DELETE
H01L 29/7841		DELETE
H01L 29/7842		DELETE
H01L 29/7843		DELETE
H01L 29/7845		DELETE
H01L 29/7846		DELETE
H01L 29/7847		DELETE
H01L 29/7848		DELETE
H01L 29/7849		DELETE
H01L 29/785		DELETE
H01L 29/7851		DELETE
H01L 29/7853		DELETE
H01L 29/7854		DELETE
H01L 29/7855		DELETE
H01L 29/7856		DELETE
H01L 2029/7857		DELETE
H01L 2029/7858		DELETE
H01L 29/786		DELETE
H01L 29/78603		DELETE
H01L 29/78606		DELETE
H01L 29/78609		DELETE
H01L 29/78612		DELETE
H01L 29/78615		DELETE
H01L 29/78618		DELETE
H01L 29/78621		DELETE
H01L 29/78624		DELETE
H01L 29/78627		DELETE
H01L 2029/7863		DELETE
H01L 29/78633		DELETE
H01L 29/78636		DELETE
H01L 29/78639		DELETE
H01L 29/78642		DELETE

CPC	**IPC**	**Action***
H01L 29/78645		DELETE
H01L 29/78648		DELETE
H01L 29/78651		DELETE
H01L 29/78654		DELETE
H01L 29/78657		DELETE
H01L 29/7866		DELETE
H01L 29/78663		DELETE
H01L 29/78666		DELETE
H01L 29/78669		DELETE
H01L 29/78672		DELETE
H01L 29/78675		DELETE
H01L 29/78678		DELETE
H01L 29/78681		DELETE
H01L 29/78684		DELETE
H01L 29/78687		DELETE
H01L 29/7869		DELETE
H01L 29/78693		DELETE
H01L 29/78696		DELETE
H01L 29/788		DELETE
H01L 29/7881		DELETE
H01L 29/7882		DELETE
H01L 29/7883		DELETE
H01L 29/7884		DELETE
H01L 29/7885		DELETE
H01L 29/7886		DELETE
H01L 29/7887		DELETE
H01L 29/7888		DELETE
H01L 29/7889		DELETE
H01L 29/792		DELETE
H01L 29/7923		DELETE
H01L 29/7926		DELETE
H01L 29/80		DELETE
H01L 29/802		DELETE
H01L 29/803		DELETE
H01L 29/806		DELETE
H01L 29/808		DELETE
H01L 29/8083		DELETE
H01L 29/8086		DELETE
H01L 29/812		DELETE
H01L 29/8122		DELETE
H01L 29/8124		DELETE
H01L 29/8126		DELETE
H01L 29/8128		DELETE
H01L 29/82		DELETE
H01L 29/84		DELETE

CPC	**IPC**	**Action***
H01L 29/86		DELETE
H01L 29/8605		DELETE
H01L 29/861		DELETE
H01L 29/8611		DELETE
H01L 29/8613		DELETE
H01L 29/8615		DELETE
H01L 29/8616		DELETE
H01L 29/8618		DELETE
H01L 29/862		DELETE
H01L 29/864		DELETE
H01L 29/866		DELETE
H01L 29/868		DELETE
H01L 29/87		DELETE
H01L 29/872		DELETE
H01L 29/8725		DELETE
H01L 29/88		DELETE
H01L 29/882		DELETE
H01L 29/885		DELETE
H01L 29/92		DELETE
H01L 29/93		DELETE
H01L 29/94		DELETE
H01L 29/945		DELETE
H01L 2229/00		DELETE
H10D 1/00	H10D 1/00	NEW
H10D 1/01	H10D 1/00	NEW
H10D 1/021	H10D 1/00	NEW
H10D 1/025	H10D 1/00	NEW
H10D 1/041	H10D 1/00	NEW
H10D 1/042	H10D 1/00	NEW
H10D 1/043	H10D 1/00	NEW
H10D 1/045	H10D 1/00	NEW
H10D 1/047	H10D 1/00	NEW
H10D 1/048	H10D 1/00	NEW
H10D 1/20	H10D 1/20	NEW
H10D 1/40	H10D 1/40	NEW
H10D 1/43	H10D 1/43	NEW
H10D 1/47	H10D 1/47	NEW
H10D 1/472	H10D 1/47	NEW
H10D 1/474	H10D 1/47	NEW
H10D 1/476	H10D 1/47	NEW
H10D 1/60	H10D 1/60	NEW
H10D 1/62	H10D 1/62	NEW
H10D 1/64	H10D 1/64	NEW
H10D 1/66	H10D 1/66	NEW
H10D 1/665	H10D 1/66	NEW

CPC	**IPC**	**Action***
H10D 1/68	H10D 1/68	NEW
H10D 1/682	H10D 1/68	NEW
H10D 1/684	H10D 1/68	NEW
H10D 1/688	H10D 1/68	NEW
H10D 1/692	H10D 1/68	NEW
H10D 1/694	H10D 1/68	NEW
H10D 1/696	H10D 1/68	NEW
H10D 1/711	H10D 1/68	NEW
H10D 1/712	H10D 1/68	NEW
H10D 1/714	H10D 1/68	NEW
H10D 1/716	H10D 1/68	NEW
H10D 8/00	H10D 8/00	NEW
H10D 8/01	H10D 8/01	NEW
H10D 8/021	H10D 8/01	NEW
H10D 8/022	H10D 8/01	NEW
H10D 8/024	H10D 8/01	NEW
H10D 8/041	H10D 8/01	NEW
H10D 8/043	H10D 8/01	NEW
H10D 8/045	H10D 8/01	NEW
H10D 8/051	H10D 8/01	NEW
H10D 8/053	H10D 8/01	NEW
H10D 8/055	H10D 8/01	NEW
H10D 8/20	H10D 8/20	NEW
H10D 8/25	H10D 8/25	NEW
H10D 8/30	H10D 8/30	NEW
H10D 8/40	H10D 8/40	NEW
H10D 8/411	H10D 8/00	NEW
H10D 8/422	H10D 8/00	NEW
H10D 8/50	H10D 8/50	NEW
H10D 8/60	H10D 8/60	NEW
H10D 8/605	H10D 8/60	NEW
H10D 8/70	H10D 8/70	NEW
H10D 8/75	H10D 8/75	NEW
H10D 8/755	H10D 8/75	NEW
H10D 8/80	H10D 8/80	NEW
H10D 8/812	H10D 8/00	NEW
H10D 8/825	H10D 8/00	NEW
H10D 10/00	H10D 10/00	NEW
H10D 10/01	H10D 10/01	NEW
H10D 10/021	H10D 10/01	NEW
H10D 10/031	H10D 10/01	NEW
H10D 10/041	H10D 10/01	NEW
H10D 10/051	H10D 10/01	NEW
H10D 10/052	H10D 10/01	NEW
H10D 10/054	H10D 10/01	NEW

CPC NOTICE OF CHANGES 1723

DATE: JANUARY 1, 2025

PROJECT RP12465

CPC	**IPC**	**Action***
H10D 10/056	H10D 10/01	NEW
H10D 10/058	H10D 10/01	NEW
H10D 10/061	H10D 10/01	NEW
H10D 10/211	H10D 10/00	NEW
H10D 10/221	H10D 10/00	NEW
H10D 10/231	H10D 10/00	NEW
H10D 10/241	H10D 10/00	NEW
H10D 10/311	H10D 10/00	NEW
H10D 10/40	H10D 10/40	NEW
H10D 10/421	H10D 10/40	NEW
H10D 10/441	H10D 10/40	NEW
H10D 10/461	H10D 10/40	NEW
H10D 10/60	H10D 10/60	NEW
H10D 10/80	H10D 10/80	NEW
H10D 10/821	H10D 10/80	NEW
H10D 10/841	H10D 10/80	NEW
H10D 10/861	H10D 10/80	NEW
H10D 10/881	H10D 10/80	NEW
H10D 10/891	H10D 10/80	NEW
H10D 12/00	H10D 12/00	NEW
H10D 12/01	H10D 12/01	NEW
H10D 12/021	H10D 12/01	NEW
H10D 12/031	H10D 12/01	NEW
H10D 12/032	H10D 12/01	NEW
H10D 12/035	H10D 12/01	NEW
H10D 12/038	H10D 12/01	NEW
H10D 12/211	H10D 12/00	NEW
H10D 12/212	H10D 12/00	NEW
H10D 12/411	H10D 12/00	NEW
H10D 12/415	H10D 12/00	NEW
H10D 12/416	H10D 12/00	NEW
H10D 12/417	H10D 12/00	NEW
H10D 12/418	H10D 12/00	NEW
H10D 12/421	H10D 12/00	NEW
H10D 12/441	H10D 12/00	NEW
H10D 12/461	H10D 12/00	NEW
H10D 12/481	H10D 12/00	NEW
H10D 12/491	H10D 12/00	NEW
H10D 18/00	H10D 18/00	NEW
H10D 18/01	H10D 18/01	NEW
H10D 18/021	H10D 18/01	NEW
H10D 18/031	H10D 18/01	NEW
H10D 18/211	H10D 18/00	NEW
H10D 18/221	H10D 18/00	NEW
H10D 18/241	H10D 18/00	NEW

CPC	**IPC**	**Action***
H10D 18/251	H10D 18/00	NEW
H10D 18/40	H10D 18/40	NEW
H10D 18/60	H10D 18/60	NEW
H10D 18/65	H10D 18/65	NEW
H10D 18/655	H10D 18/65	NEW
H10D 18/80	H10D 18/80	NEW
H10D 30/00	H10D 30/00	NEW
H10D 30/01	H10D 30/01	NEW
H10D 30/012	H10D 30/01	NEW
H10D 30/014	H10D 30/01	NEW
H10D 30/015	H10D 30/01	NEW
H10D 30/017	H10D 30/01	NEW
H10D 30/019	H10D 30/01	NEW
H10D 30/0191	H10D 30/01	NEW
H10D 30/0193	H10D 30/01	NEW
H10D 30/0194	H10D 30/01	NEW
H10D 30/0195	H10D 30/01	NEW
H10D 30/0196	H10D 30/01	NEW
H10D 30/0197	H10D 30/01	NEW
H10D 30/0198	H10D 30/01	NEW
H10D 30/021	H10D 30/01	NEW
H10D 30/0212	H10D 30/01	NEW
H10D 30/0213	H10D 30/01	NEW
H10D 30/0215	H10D 30/01	NEW
H10D 30/0217	H10D 30/01	NEW
H10D 30/0218	H10D 30/01	NEW
H10D 30/022	H10D 30/01	NEW
H10D 30/0221	H10D 30/01	NEW
H10D 30/0223	H10D 30/01	NEW
H10D 30/0225	H10D 30/01	NEW
H10D 30/0227	H10D 30/01	NEW
H10D 30/0229	H10D 30/01	NEW
H10D 30/023	H10D 30/01	NEW
H10D 30/024	H10D 30/01	NEW
H10D 30/0241	H10D 30/01	NEW
H10D 30/0243	H10D 30/01	NEW
H10D 30/0245	H10D 30/01	NEW
H10D 30/025	H10D 30/01	NEW
H10D 30/026	H10D 30/01	NEW
H10D 30/027	H10D 30/01	NEW
H10D 30/0273	H10D 30/01	NEW
H10D 30/0275	H10D 30/01	NEW
H10D 30/0277	H10D 30/01	NEW
H10D 30/0278	H10D 30/01	NEW
H10D 30/028	H10D 30/01	NEW

CPC	**IPC**	**Action***
H10D30/0281	H10D30/01	NEW
H10D30/0285	H10D30/01	NEW
H10D30/0287	H10D30/01	NEW
H10D30/0289	H10D30/01	NEW
H10D30/0291	H10D30/01	NEW
H10D30/0293	H10D30/01	NEW
H10D30/0295	H10D30/01	NEW
H10D30/0297	H10D30/01	NEW
H10D30/031	H10D30/01	NEW
H10D30/0312	H10D30/01	NEW
H10D30/0314	H10D30/01	NEW
H10D30/0316	H10D30/01	NEW
H10D30/0318	H10D30/01	NEW
H10D30/0321	H10D30/01	NEW
H10D30/0323	H10D30/01	NEW
H10D30/0327	H10D30/01	NEW
H10D30/0411	H10D30/01	NEW
H10D30/0413	H10D30/01	NEW
H10D30/0415	H10D30/01	NEW
H10D30/051	H10D30/01	NEW
H10D30/0512	H10D30/01	NEW
H10D30/0515	H10D30/01	NEW
H10D30/0516	H10D30/01	NEW
H10D30/061	H10D30/01	NEW
H10D30/0612	H10D30/01	NEW
H10D30/0614	H10D30/01	NEW
H10D30/0616	H10D30/01	NEW
H10D30/0618	H10D30/01	NEW
H10D30/202	H10D30/00	NEW
H10D30/204	H10D30/00	NEW
H10D30/40	H10D30/40	NEW
H10D30/402	H10D30/40	NEW
H10D30/43	H10D30/43	NEW
H10D30/435	H10D30/43	NEW
H10D30/47	H10D30/47	NEW
H10D30/471	H10D30/47	NEW
H10D30/472	H10D30/47	NEW
H10D30/473	H10D30/47	NEW
H10D30/4732	H10D30/47	NEW
H10D30/4735	H10D30/47	NEW
H10D30/4738	H10D30/47	NEW
H10D30/474	H10D30/47	NEW
H10D30/475	H10D30/47	NEW
H10D30/4755	H10D30/47	NEW
H10D30/476	H10D30/47	NEW

CPC	IPC	Action*
H10D 30/477	H10D 30/47	NEW
H10D 30/478	H10D 30/47	NEW
H10D 30/481	H10D 30/47	NEW
H10D 30/485	H10D 30/47	NEW
H10D 30/501	H10D 30/00	NEW
H10D 30/502	H10D 30/00	NEW
H10D 30/503	H10D 30/00	NEW
H10D 30/504	H10D 30/00	NEW
H10D 30/506	H10D 30/00	NEW
H10D 30/507	H10D 30/00	NEW
H10D 30/508	H10D 30/00	NEW
H10D 30/509	H10D 30/00	NEW
H10D 30/60	H10D 30/60	NEW
H10D 30/601	H10D 30/60	NEW
H10D 30/603	H10D 30/60	NEW
H10D 30/605	H10D 30/60	NEW
H10D 30/608	H10D 30/60	NEW
H10D 30/611	H10D 30/60	NEW
H10D 30/615	H10D 30/60	NEW
H10D 30/62	H10D 30/62	NEW
H10D 30/6211	H10D 30/62	NEW
H10D 30/6212	H10D 30/62	NEW
H10D 30/6213	H10D 30/62	NEW
H10D 30/6215	H10D 30/62	NEW
H10D 30/6217	H10D 30/62	NEW
H10D 30/6218	H10D 30/62	NEW
H10D 30/6219	H10D 30/62	NEW
H10D 30/63	H10D 30/63	NEW
H10D 30/635	H10D 30/63	NEW
H10D 30/637	H10D 30/63	NEW
H10D 30/64	H10D 30/64	NEW
H10D 30/645	H10D 30/64	NEW
H10D 30/65	H10D 30/65	NEW
H10D 30/655	H10D 30/65	NEW
H10D 30/657	H10D 30/65	NEW
H10D 30/658	H10D 30/65	NEW
H10D 30/659	H10D 30/65	NEW
H10D 30/66	H10D 30/66	NEW
H10D 30/662	H10D 30/66	NEW
H10D 30/663	H10D 30/66	NEW
H10D 30/664	H10D 30/66	NEW
H10D 30/665	H10D 30/66	NEW
H10D 30/667	H10D 30/66	NEW
H10D 30/668	H10D 30/66	NEW
H10D 30/669	H10D 30/66	NEW

CPC	IPC	Action*
H10D 30/67	H10D 30/67	NEW
H10D 30/6704	H10D 30/67	NEW
H10D 30/6706	H10D 30/67	NEW
H10D 30/6708	H10D 30/67	NEW
H10D 30/6711	H10D 30/67	NEW
H10D 30/6713	H10D 30/67	NEW
H10D 30/6715	H10D 30/67	NEW
H10D 30/6717	H10D 30/67	NEW
H10D 30/6719	H10D 30/67	NEW
H10D 30/6721	H10D 30/67	NEW
H10D 30/6723	H10D 30/67	NEW
H10D 30/6725	H10D 30/67	NEW
H10D 30/6727	H10D 30/67	NEW
H10D 30/6728	H10D 30/67	NEW
H10D 30/6729	H10D 30/67	NEW
H10D 30/673	H10D 30/67	NEW
H10D 30/6731	H10D 30/67	NEW
H10D 30/6732	H10D 30/67	NEW
H10D 30/6733	H10D 30/67	NEW
H10D 30/6734	H10D 30/67	NEW
H10D 30/6735	H10D 30/67	NEW
H10D 30/6736	H10D 30/67	NEW
H10D 30/6737	H10D 30/67	NEW
H10D 30/6738	H10D 30/67	NEW
H10D 30/6739	H10D 30/67	NEW
H10D 30/674	H10D 30/67	NEW
H10D 30/6741	H10D 30/67	NEW
H10D 30/6743	H10D 30/67	NEW
H10D 30/6744	H10D 30/67	NEW
H10D 30/6745	H10D 30/67	NEW
H10D 30/6746	H10D 30/67	NEW
H10D 30/6748	H10D 30/67	NEW
H10D 30/675	H10D 30/67	NEW
H10D 30/6755	H10D 30/67	NEW
H10D 30/6756	H10D 30/67	NEW
H10D 30/6757	H10D 30/67	NEW
H10D 30/6758	H10D 30/67	NEW
H10D 30/6759	H10D 30/67	NEW
H10D 30/68	H10D 30/68	NEW
H10D 30/681	H10D 30/68	NEW
H10D 30/682	H10D 30/68	NEW
H10D 30/683	H10D 30/68	NEW
H10D 30/684	H10D 30/68	NEW
H10D 30/685	H10D 30/68	NEW
H10D 30/686	H10D 30/68	NEW

CPC	**IPC**	**Action***
H10D30/687	H10D30/68	NEW
H10D30/688	H10D30/68	NEW
H10D30/689	H10D30/68	NEW
H10D30/6891	H10D30/68	NEW
H10D30/6892	H10D30/68	NEW
H10D30/6893	H10D30/68	NEW
H10D30/6894	H10D30/68	NEW
H10D30/69	H10D30/69	NEW
H10D30/691	H10D30/69	NEW
H10D30/693	H10D30/69	NEW
H10D30/694	H10D30/69	NEW
H10D30/696	H10D30/69	NEW
H10D30/697	H10D30/69	NEW
H10D30/699	H10D30/69	NEW
H10D30/701	H10D30/69	NEW
H10D30/711	H10D30/69	NEW
H10D30/721	H10D30/69	NEW
H10D30/751	H10D30/69	NEW
H10D30/791	H10D30/69	NEW
H10D30/792	H10D30/69	NEW
H10D30/794	H10D30/69	NEW
H10D30/795	H10D30/69	NEW
H10D30/796	H10D30/69	NEW
H10D30/797	H10D30/69	NEW
H10D30/798	H10D30/69	NEW
H10D30/80	H10D30/80	NEW
H10D30/801	H10D30/80	NEW
H10D30/803	H10D30/80	NEW
H10D30/83	H10D30/83	NEW
H10D30/831	H10D30/83	NEW
H10D30/832	H10D30/83	NEW
H10D30/87	H10D30/87	NEW
H10D30/871	H10D30/87	NEW
H10D30/873	H10D30/87	NEW
H10D30/875	H10D30/87	NEW
H10D30/877	H10D30/87	NEW
H10D44/00	H10D44/00	NEW
H10D44/01	H10D44/01	NEW
H10D44/041	H10D44/01	NEW
H10D44/061	H10D44/01	NEW
H10D44/40	H10D44/40	NEW
H10D44/45	H10D44/45	NEW
H10D44/452	H10D44/45	NEW
H10D44/454	H10D44/45	NEW
H10D44/456	H10D44/45	NEW

CPC	**IPC**	**Action***
H10D44/462	H10D44/45	NEW
H10D44/464	H10D44/45	NEW
H10D44/466	H10D44/45	NEW
H10D44/468	H10D44/45	NEW
H10D44/472	H10D44/45	NEW
H10D44/474	H10D44/45	NEW
H10D44/476	H10D44/45	NEW
H10D44/478	H10D44/45	NEW
H10D48/00	H10D48/00	NEW
H10D48/01	H10D48/01	NEW
H10D48/021	H10D48/01	NEW
H10D48/031	H10D48/01	NEW
H10D48/032	H10D48/01	NEW
H10D48/04	H10D48/04	NEW
H10D48/042	H10D48/042	NEW
H10D48/043	H10D48/043	NEW
H10D48/0431	H10D48/043	NEW
H10D48/044	H10D48/044	NEW
H10D48/045	H10D48/045	NEW
H10D48/046	H10D48/046	NEW
H10D48/047	H10D48/047	NEW
H10D48/048	H10D48/048	NEW
H10D48/049	H10D48/049	NEW
H10D48/07	H10D48/07	NEW
H10D48/071	H10D48/07	NEW
H10D48/073	H10D48/07	NEW
H10D48/074	H10D48/07	NEW
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H10D48/076	H10D48/07	NEW
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H10D48/32	H10D48/32	NEW
H10D48/34	H10D48/34	NEW
H10D48/341	H10D48/34	NEW
H10D48/345	H10D48/34	NEW
H10D48/36	H10D48/36	NEW
H10D48/362	H10D48/36	NEW
H10D48/366	H10D48/32	NEW
H10D48/38	H10D48/38	NEW
H10D48/381	H10D48/38	NEW
H10D48/383	H10D48/00	NEW
H10D48/3835	H10D48/00	NEW
H10D48/385	H10D48/00	NEW
H10D48/387	H10D48/00	NEW
H10D48/40	H10D48/40	NEW

CPC	**IPC**	**Action***
H10D48/50	H10D48/50	NEW
H10D62/00	H10D62/00	NEW
H10D62/01	H10D62/00	NEW
H10D62/021	H10D62/00	NEW
H10D62/051	H10D62/00	NEW
H10D62/052	H10D62/00	NEW
H10D62/054	H10D62/00	NEW
H10D62/056	H10D62/00	NEW
H10D62/058	H10D62/00	NEW
H10D62/10	H10D62/10	NEW
H10D62/102	H10D62/10	NEW
H10D62/103	H10D62/10	NEW
H10D62/104	H10D62/10	NEW
H10D62/105	H10D62/10	NEW
H10D62/106	H10D62/10	NEW
H10D62/107	H10D62/10	NEW
H10D62/108	H10D62/10	NEW
H10D62/109	H10D62/10	NEW
H10D62/111	H10D62/10	NEW
H10D62/112	H10D62/10	NEW
H10D62/113	H10D62/10	NEW
H10D62/114	H10D62/10	NEW
H10D62/115	H10D62/10	NEW
H10D62/116	H10D62/10	NEW
H10D62/117	H10D62/10	NEW
H10D62/118	H10D62/10	NEW
H10D62/119	H10D62/10	NEW
H10D62/121	H10D62/10	NEW
H10D62/122	H10D62/10	NEW
H10D62/123	H10D62/10	NEW
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H10D62/125	H10D62/10	NEW
H10D62/126	H10D62/10	NEW
H10D62/127	H10D62/10	NEW
H10D62/128	H10D62/10	NEW
H10D62/129	H10D62/10	NEW
H10D62/13	H10D62/13	NEW
H10D62/133	H10D62/13	NEW
H10D62/134	H10D62/13	NEW
H10D62/135	H10D62/13	NEW
H10D62/136	H10D62/13	NEW
H10D62/137	H10D62/13	NEW
H10D62/138	H10D62/13	NEW
H10D62/141	H10D62/13	NEW
H10D62/142	H10D62/13	NEW

CPC	**IPC**	**Action***
H10D62/145	H10D62/13	NEW
H10D62/148	H10D62/13	NEW
H10D62/149	H10D62/13	NEW
H10D62/151	H10D62/13	NEW
H10D62/152	H10D62/13	NEW
H10D62/153	H10D62/13	NEW
H10D62/154	H10D62/13	NEW
H10D62/155	H10D62/13	NEW
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H10D62/157	H10D62/13	NEW
H10D62/158	H10D62/13	NEW
H10D62/159	H10D62/13	NEW
H10D62/161	H10D62/13	NEW
H10D62/165	H10D62/13	NEW
H10D62/17	H10D62/17	NEW
H10D62/177	H10D62/17	NEW
H10D62/184	H10D62/17	NEW
H10D62/192	H10D62/17	NEW
H10D62/199	H10D62/17	NEW
H10D62/206	H10D62/17	NEW
H10D62/213	H10D62/17	NEW
H10D62/221	H10D62/17	NEW
H10D62/228	H10D62/17	NEW
H10D62/235	H10D62/17	NEW
H10D62/292	H10D62/17	NEW
H10D62/299	H10D62/17	NEW
H10D62/307	H10D62/17	NEW
H10D62/314	H10D62/17	NEW
H10D62/328	H10D62/17	NEW
H10D62/335	H10D62/17	NEW
H10D62/343	H10D62/17	NEW
H10D62/351	H10D62/17	NEW
H10D62/357	H10D62/17	NEW
H10D62/364	H10D62/17	NEW
H10D62/371	H10D62/17	NEW
H10D62/378	H10D62/17	NEW
H10D62/386	H10D62/17	NEW
H10D62/393	H10D62/17	NEW
H10D62/40	H10D62/40	NEW
H10D62/402	H10D62/40	NEW
H10D62/405	H10D62/40	NEW
H10D62/50	H10D62/50	NEW
H10D62/53	H10D62/53	NEW
H10D62/57	H10D62/57	NEW
H10D62/60	H10D62/60	NEW

CPC	**IPC**	**Action***
H10D 62/605	H10D 62/60	NEW
H10D 62/80	H10D 62/80	NEW
H10D 62/81	H10D 62/81	NEW
H10D 62/812	H10D 62/81	NEW
H10D 62/813	H10D 62/81	NEW
H10D 62/814	H10D 62/81	NEW
H10D 62/815	H10D 62/815	NEW
H10D 62/8161	H10D 62/815	NEW
H10D 62/8162	H10D 62/815	NEW
H10D 62/8163	H10D 62/815	NEW
H10D 62/8164	H10D 62/815	NEW
H10D 62/8171	H10D 62/815	NEW
H10D 62/8181	H10D 62/815	NEW
H10D 62/82	H10D 62/82	NEW
H10D 62/822	H10D 62/822	NEW
H10D 62/824	H10D 62/824	NEW
H10D 62/826	H10D 62/826	NEW
H10D 62/8271	H10D 62/82	NEW
H10D 62/8281	H10D 62/82	NEW
H10D 62/83	H10D 62/83	NEW
H10D 62/8303	H10D 62/83	NEW
H10D 62/832	H10D 62/832	NEW
H10D 62/8325	H10D 62/832	NEW
H10D 62/834	H10D 62/834	NEW
H10D 62/84	H10D 62/84	NEW
H10D 62/85	H10D 62/85	NEW
H10D 62/8503	H10D 62/85	NEW
H10D 62/852	H10D 62/852	NEW
H10D 62/854	H10D 62/854	NEW
H10D 62/86	H10D 62/86	NEW
H10D 62/8603	H10D 62/86	NEW
H10D 62/862	H10D 62/862	NEW
H10D 62/864	H10D 62/864	NEW
H10D 62/871	H10D 62/80	NEW
H10D 62/874	H10D 62/80	NEW
H10D 62/875	H10D 62/80	NEW
H10D 62/881	H10D 62/80	NEW
H10D 62/882	H10D 62/80	NEW
H10D 62/883	H10D 62/80	NEW
H10D 64/00	H10D 64/00	NEW
H10D 64/01	H10D 64/01	NEW
H10D 64/015	H10D 64/01	NEW
H10D 64/017	H10D 64/01	NEW
H10D 64/018	H10D 64/01	NEW
H10D 64/021	H10D 64/01	NEW

CPC	**IPC**	**Action***
H10D 64/025	H10D 64/01	NEW
H10D 64/027	H10D 64/01	NEW
H10D 64/031	H10D 64/01	NEW
H10D 64/033	H10D 64/01	NEW
H10D 64/035	H10D 64/01	NEW
H10D 64/037	H10D 64/01	NEW
H10D 64/111	H10D 64/00	NEW
H10D 64/112	H10D 64/00	NEW
H10D 64/115	H10D 64/00	NEW
H10D 64/117	H10D 64/00	NEW
H10D 64/118	H10D 64/00	NEW
H10D 64/20	H10D 64/20	NEW
H10D 64/205	H10D 64/20	NEW
H10D 64/23	H10D 64/23	NEW
H10D 64/231	H10D 64/23	NEW
H10D 64/232	H10D 64/23	NEW
H10D 64/233	H10D 64/23	NEW
H10D 64/251	H10D 64/23	NEW
H10D 64/252	H10D 64/23	NEW
H10D 64/2523	H10D 64/23	NEW
H10D 64/2527	H10D 64/23	NEW
H10D 64/254	H10D 64/23	NEW
H10D 64/256	H10D 64/23	NEW
H10D 64/2565	H10D 64/23	NEW
H10D 64/257	H10D 64/23	NEW
H10D 64/258	H10D 64/23	NEW
H10D 64/259	H10D 64/23	NEW
H10D 64/27	H10D 64/27	NEW
H10D 64/281	H10D 64/27	NEW
H10D 64/291	H10D 64/27	NEW
H10D 64/311	H10D 64/27	NEW
H10D 64/411	H10D 64/27	NEW
H10D 64/511	H10D 64/27	NEW
H10D 64/512	H10D 64/27	NEW
H10D 64/513	H10D 64/27	NEW
H10D 64/514	H10D 64/27	NEW
H10D 64/516	H10D 64/27	NEW
H10D 64/517	H10D 64/27	NEW
H10D 64/518	H10D 64/27	NEW
H10D 64/519	H10D 64/27	NEW
H10D 64/529	H10D 64/27	NEW
H10D 64/60	H10D 64/60	NEW
H10D 64/602	H10D 64/60	NEW
H10D 64/605	H10D 64/60	NEW
H10D 64/608	H10D 64/60	NEW

CPC	**IPC**	**Action***
H10D 64/62	H10D 64/62	NEW
H10D 64/64	H10D 64/64	NEW
H10D 64/647	H10D 64/64	NEW
H10D 64/649	H10D 64/64	NEW
H10D 64/66	H10D 64/66	NEW
H10D 64/661	H10D 64/66	NEW
H10D 64/662	H10D 64/66	NEW
H10D 64/663	H10D 64/66	NEW
H10D 64/664	H10D 64/66	NEW
H10D 64/665	H10D 64/66	NEW
H10D 64/666	H10D 64/66	NEW
H10D 64/667	H10D 64/66	NEW
H10D 64/668	H10D 64/66	NEW
H10D 64/669	H10D 64/66	NEW
H10D 64/671	H10D 64/66	NEW
H10D 64/675	H10D 64/66	NEW
H10D 64/679	H10D 64/66	NEW
H10D 64/68	H10D 64/68	NEW
H10D 64/681	H10D 64/68	NEW
H10D 64/683	H10D 64/68	NEW
H10D 64/685	H10D 64/68	NEW
H10D 64/687	H10D 64/68	NEW
H10D 64/689	H10D 64/68	NEW
H10D 64/691	H10D 64/68	NEW
H10D 64/693	H10D 64/68	NEW
H10D 80/00	H10D 80/00	NEW
H10D 80/20	H10D 80/20	NEW
H10D 80/211	H10D 80/20	NEW
H10D 80/213	H10D 80/20	NEW
H10D 80/215	H10D 80/20	NEW
H10D 80/231	H10D 80/20	NEW
H10D 80/251	H10D 80/20	NEW
H10D 80/30	H10D 80/30	NEW
H10D 84/00	H10D 84/00	NEW
H10D 84/01	H10D 84/01	NEW
H10D 84/0102	H10D 84/01	NEW
H10D 84/0105	H10D 84/01	NEW
H10D 84/0107	H10D 84/01	NEW
H10D 84/0109	H10D 84/01	NEW
H10D 84/0112	H10D 84/01	NEW
H10D 84/0114	H10D 84/01	NEW
H10D 84/0116	H10D 84/01	NEW
H10D 84/0119	H10D 84/01	NEW
H10D 84/0121	H10D 84/01	NEW
H10D 84/0123	H10D 84/01	NEW

CPC NOTICE OF CHANGES 1723

DATE: JANUARY 1, 2025

PROJECT RP12465

CPC	**IPC**	**Action***
H10D 84/0126	H10D 84/01	NEW
H10D 84/0128	H10D 84/01	NEW
H10D 84/013	H10D 84/01	NEW
H10D 84/0133	H10D 84/01	NEW
H10D 84/0135	H10D 84/01	NEW
H10D 84/0137	H10D 84/01	NEW
H10D 84/014	H10D 84/01	NEW
H10D 84/0142	H10D 84/01	NEW
H10D 84/0144	H10D 84/01	NEW
H10D 84/0147	H10D 84/01	NEW
H10D 84/0149	H10D 84/01	NEW
H10D 84/0151	H10D 84/01	NEW
H10D 84/0153	H10D 84/01	NEW
H10D 84/0156	H10D 84/01	NEW
H10D 84/0158	H10D 84/01	NEW
H10D 84/016	H10D 84/01	NEW
H10D 84/0163	H10D 84/01	NEW
H10D 84/0165	H10D 84/01	NEW
H10D 84/0167	H10D 84/01	NEW
H10D 84/017	H10D 84/01	NEW
H10D 84/0172	H10D 84/01	NEW
H10D 84/0174	H10D 84/01	NEW
H10D 84/0177	H10D 84/01	NEW
H10D 84/0179	H10D 84/01	NEW
H10D 84/0181	H10D 84/01	NEW
H10D 84/0184	H10D 84/01	NEW
H10D 84/0186	H10D 84/01	NEW
H10D 84/0188	H10D 84/01	NEW
H10D 84/0191	H10D 84/01	NEW
H10D 84/0193	H10D 84/01	NEW
H10D 84/0195	H10D 84/01	NEW
H10D 84/0198	H10D 84/01	NEW
H10D 84/02	H10D 84/02	NEW
H10D 84/03	H10D 84/03	NEW
H10D 84/032	H10D 84/03	NEW
H10D 84/035	H10D 84/03	NEW
H10D 84/038	H10D 84/03	NEW
H10D 84/05	H10D 84/05	NEW
H10D 84/07	H10D 84/07	NEW
H10D 84/08	H10D 84/08	NEW
H10D 84/101	H10D 84/00	NEW
H10D 84/121	H10D 84/00	NEW
H10D 84/125	H10D 84/00	NEW
H10D 84/131	H10D 84/00	NEW
H10D 84/133	H10D 84/00	NEW

CPC	**IPC**	**Action***
H10D 84/135	H10D 84/00	NEW
H10D 84/136	H10D 84/00	NEW
H10D 84/138	H10D 84/00	NEW
H10D 84/141	H10D 84/00	NEW
H10D 84/143	H10D 84/00	NEW
H10D 84/144	H10D 84/00	NEW
H10D 84/146	H10D 84/00	NEW
H10D 84/148	H10D 84/00	NEW
H10D 84/151	H10D 84/00	NEW
H10D 84/153	H10D 84/00	NEW
H10D 84/154	H10D 84/00	NEW
H10D 84/156	H10D 84/00	NEW
H10D 84/158	H10D 84/00	NEW
H10D 84/161	H10D 84/00	NEW
H10D 84/201	H10D 84/00	NEW
H10D 84/204	H10D 84/00	NEW
H10D 84/206	H10D 84/00	NEW
H10D 84/209	H10D 84/00	NEW
H10D 84/212	H10D 84/00	NEW
H10D 84/215	H10D 84/00	NEW
H10D 84/217	H10D 84/00	NEW
H10D 84/221	H10D 84/00	NEW
H10D 84/40	H10D 84/40	NEW
H10D 84/401	H10D 84/40	NEW
H10D 84/403	H10D 84/40	NEW
H10D 84/406	H10D 84/40	NEW
H10D 84/409	H10D 84/40	NEW
H10D 84/60	H10D 84/60	NEW
H10D 84/611	H10D 84/60	NEW
H10D 84/613	H10D 84/60	NEW
H10D 84/615	H10D 84/60	NEW
H10D 84/617	H10D 84/60	NEW
H10D 84/619	H10D 84/60	NEW
H10D 84/63	H10D 84/63	NEW
H10D 84/641	H10D 84/60	NEW
H10D 84/642	H10D 84/60	NEW
H10D 84/643	H10D 84/60	NEW
H10D 84/645	H10D 84/60	NEW
H10D 84/65	H10D 84/65	NEW
H10D 84/652	H10D 84/65	NEW
H10D 84/655	H10D 84/65	NEW
H10D 84/658	H10D 84/65	NEW
H10D 84/67	H10D 84/67	NEW
H10D 84/673	H10D 84/67	NEW
H10D 84/676	H10D 84/60	NEW

CPC	**IPC**	**Action***
H10D 84/80	H10D 84/80	NEW
H10D 84/811	H10D 84/80	NEW
H10D 84/813	H10D 84/80	NEW
H10D 84/817	H10D 84/80	NEW
H10D 84/82	H10D 84/82	NEW
H10D 84/83	H10D 84/83	NEW
H10D 84/8311	H10D 84/83	NEW
H10D 84/8312	H10D 84/83	NEW
H10D 84/83125	H10D 84/83	NEW
H10D 84/83135	H10D 84/83	NEW
H10D 84/83138	H10D 84/83	NEW
H10D 84/8314	H10D 84/83	NEW
H10D 84/8316	H10D 84/83	NEW
H10D 84/832	H10D 84/83	NEW
H10D 84/833	H10D 84/83	NEW
H10D 84/834	H10D 84/83	NEW
H10D 84/835	H10D 84/83	NEW
H10D 84/836	H10D 84/83	NEW
H10D 84/837	H10D 84/83	NEW
H10D 84/839	H10D 84/83	NEW
H10D 84/84	H10D 84/84	NEW
H10D 84/85	H10D 84/85	NEW
H10D 84/851	H10D 84/85	NEW
H10D 84/852	H10D 84/85	NEW
H10D 84/853	H10D 84/85	NEW
H10D 84/854	H10D 84/85	NEW
H10D 84/856	H10D 84/85	NEW
H10D 84/857	H10D 84/85	NEW
H10D 84/858	H10D 84/85	NEW
H10D 84/859	H10D 84/85	NEW
H10D 84/86	H10D 84/86	NEW
H10D 84/87	H10D 84/87	NEW
H10D 84/891	H10D 84/00	NEW
H10D 84/895	H10D 84/00	NEW
H10D 84/90	H10D 84/90	NEW
H10D 84/901	H10D 84/90	NEW
H10D 84/903	H10D 84/90	NEW
H10D 84/905	H10D 84/90	NEW
H10D 84/907	H10D 84/90	NEW
H10D 84/909	H10D 84/90	NEW
H10D 84/911	H10D 84/90	NEW
H10D 84/912	H10D 84/90	NEW
H10D 84/914	H10D 84/90	NEW
H10D 84/916	H10D 84/90	NEW
H10D 84/918	H10D 84/90	NEW

CPC	**IPC**	**Action***
H10D 84/921	H10D 84/90	NEW
H10D 84/922	H10D 84/90	NEW
H10D 84/924	H10D 84/90	NEW
H10D 84/925	H10D 84/90	NEW
H10D 84/927	H10D 84/90	NEW
H10D 84/929	H10D 84/90	NEW
H10D 84/931	H10D 84/90	NEW
H10D 84/933	H10D 84/90	NEW
H10D 84/935	H10D 84/90	NEW
H10D 84/937	H10D 84/90	NEW
H10D 84/938	H10D 84/90	NEW
H10D 84/941	H10D 84/90	NEW
H10D 84/942	H10D 84/90	NEW
H10D 84/944	H10D 84/90	NEW
H10D 84/946	H10D 84/90	NEW
H10D 84/948	H10D 84/90	NEW
H10D 84/949	H10D 84/90	NEW
H10D 84/951	H10D 84/90	NEW
H10D 84/953	H10D 84/90	NEW
H10D 84/955	H10D 84/90	NEW
H10D 84/957	H10D 84/90	NEW
H10D 84/959	H10D 84/90	NEW
H10D 84/961	H10D 84/90	NEW
H10D 84/962	H10D 84/90	NEW
H10D 84/964	H10D 84/90	NEW
H10D 84/966	H10D 84/90	NEW
H10D 84/968	H10D 84/90	NEW
H10D 84/971	H10D 84/90	NEW
H10D 84/972	H10D 84/90	NEW
H10D 84/974	H10D 84/90	NEW
H10D 84/975	H10D 84/90	NEW
H10D 84/977	H10D 84/90	NEW
H10D 84/979	H10D 84/90	NEW
H10D 84/981	H10D 84/90	NEW
H10D 84/983	H10D 84/90	NEW
H10D 84/985	H10D 84/90	NEW
H10D 84/987	H10D 84/90	NEW
H10D 84/988	H10D 84/90	NEW
H10D 84/991	H10D 84/90	NEW
H10D 84/992	H10D 84/90	NEW
H10D 84/994	H10D 84/90	NEW
H10D 84/996	H10D 84/90	NEW
H10D 84/998	H10D 84/90	NEW
H10D 86/00	H10D 86/00	NEW
H10D 86/01	H10D 86/01	NEW

CPC	**IPC**	**Action***
H10D 86/011	H10D 86/01	NEW
H10D 86/021	H10D 86/01	NEW
H10D 86/0212	H10D 86/01	NEW
H10D 86/0214	H10D 86/01	NEW
H10D 86/0221	H10D 86/01	NEW
H10D 86/0223	H10D 86/01	NEW
H10D 86/0225	H10D 86/01	NEW
H10D 86/0227	H10D 86/01	NEW
H10D 86/0229	H10D 86/01	NEW
H10D 86/0231	H10D 86/01	NEW
H10D 86/0241	H10D 86/01	NEW
H10D 86/0251	H10D 86/01	NEW
H10D 86/03	H10D 86/03	NEW
H10D 86/201	H10D 86/00	NEW
H10D 86/215	H10D 86/00	NEW
H10D 86/40	H10D 86/40	NEW
H10D 86/411	H10D 86/40	NEW
H10D 86/421	H10D 86/40	NEW
H10D 86/423	H10D 86/40	NEW
H10D 86/425	H10D 86/40	NEW
H10D 86/427	H10D 86/40	NEW
H10D 86/431	H10D 86/40	NEW
H10D 86/441	H10D 86/40	NEW
H10D 86/443	H10D 86/40	NEW
H10D 86/451	H10D 86/40	NEW
H10D 86/471	H10D 86/40	NEW
H10D 86/481	H10D 86/40	NEW
H10D 86/60	H10D 86/60	NEW
H10D 86/80	H10D 86/80	NEW
H10D 86/85	H10D 86/85	NEW
H10D 87/00	H10D 87/00	NEW
H10D 88/00	H10D 88/00	NEW
H10D 88/01	H10D 88/00	NEW
H10D 88/101	H10D 88/00	NEW
H10D 89/00	H10D 89/00	NEW
H10D 89/011	H10D 89/00	NEW
H10D 89/013	H10D 89/00	NEW
H10D 89/015	H10D 89/00	NEW
H10D 89/10	H10D 89/10	NEW
H10D 89/105	H10D 89/10	NEW
H10D 89/211	H10D 89/00	NEW
H10D 89/213	H10D 89/00	NEW
H10D 89/215	H10D 89/00	NEW
H10D 89/217	H10D 89/00	NEW
H10D 89/311	H10D 89/00	NEW

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H10D 89/60	H10D 89/60	NEW
H10D 89/601	H10D 89/60	NEW
H10D 89/611	H10D 89/60	NEW
H10D 89/711	H10D 89/60	NEW
H10D 89/713	H10D 89/60	NEW
H10D 89/811	H10D 89/60	NEW
H10D 89/813	H10D 89/60	NEW
H10D 89/814	H10D 89/60	NEW
H10D 89/815	H10D 89/60	NEW
H10D 89/817	H10D 89/60	NEW
H10D 89/819	H10D 89/60	NEW
H10D 89/911	H10D 89/60	NEW
H10D 89/921	H10D 89/60	NEW
H10D 89/931	H10D 89/60	NEW
H10D 99/00	H10D 99/00	NEW

*Action column:

- For an (N) or (Q) entry, provide an IPC symbol and complete the Action column with “NEW.”
- For an existing CPC main trunk entry or indexing entry where the existing IPC symbol needs to be changed, provide an updated IPC symbol and complete the Action column with “UPDATED.”
- For a (D) CPC entry or indexing entry complete the Action column with “DELETE.” IPC symbol does not need to be included in the IPC column.
- For an (N) 2000 series CPC entry which is positioned within the main trunk scheme (breakdown code) provide an IPC symbol and complete the action column with “NEW”.
- For an (N) 2000 series CPC entry positioned at the end of the CPC scheme (orthogonal code), with no IPC equivalent, complete the IPC column with “CPCONLY” and complete the action column with “NEW”.

NOTES:

- F symbols are <u>not</u> included in the CICL table above.
- T and M symbols are not included in the CICL table above unless a change to the existing IPC is desired.

5. CROSS-REFERENCE LIST (CRL)

Scheme references impacted by this revision project

Location of reference to be changed	**Referenced subclass or group to be changed**	**Action; New reference symbol; New text**
B82B (Note)	H01L29/775	H10D30/43
B82Y (Note)	H01L29/775	H10D30/43
H10B 10/10	Group H10B 10/10 is incomplete pending reclassification of documents from groups H01L 27/1027, H01 L 27/1028 and H10B 99/00. All groups listed in this Warning should be considered in order to perform a complete search.	Delete the entire warning.
H10B 12/10	Group H10B 12/10 is incomplete pending reclassification of documents from groups H01L 27/1027, H01 L 27/1028 and H10B 99/00. All groups listed in this Warning should be considered in order to perform a complete search.	Delete the entire warning.
H10B 20/10	Group H10B 20/10 is incomplete pending reclassification of documents from groups H01L 27/1027, H01 L 27/1028 and H10B 99/00. All groups listed in this Warning should be considered in order to perform a complete search.	Delete the entire warning.

Location of reference to be changed	**Referenced subclass or group to be changed**	**Action; New reference symbol; New text**
H10B 69/00	Group H10B 69/00 is incomplete pending reclassification of documents from groups H01L 27/1027 and H01L 27/1028. Groups H01L 27/1027, H01L 27/1028 and H10B 69/00 should be considered in order to perform a complete search.	Delete the entire warning.
H10B 99/00	Group H10B 99/00 is incomplete pending reclassification of documents from groups H01L 27/102 and H01L 27/1022. Group H10B 99/00 is also impacted by reclassification into groups H10B 10/10, H10B 12/10 and H10B 20/10. All groups listed in this Warning should be considered in order to perform a complete search.	Delete the entire warning.
H10B 99/10	Group H10B 99/10 is incomplete pending reclassification of documents from group H01L 27/10. Groups H01L 27/10 and H10B 99/10 should be considered in order to perform a complete search.	Delete the entire warning.
H10B 99/14	Group H10B 99/14 is incomplete pending reclassification of documents from group H01L 27/101. Groups H01L 27/101 and H10B 99/14 should be considered in order to perform a complete search.	Delete the entire warning.

Location of reference to be changed	Referenced subclass or group to be changed	Action; New reference symbol; New text
H10B 99/16	Group H10B 99/16 is incomplete pending reclassification of documents from group H01L 27/1021. Groups H01L 27/1021 and H10B 99/16 should be considered in order to perform a complete search.	Delete the entire warning.
H10B 99/20	Group H10B 99/20 is incomplete pending reclassification of documents from groups H01L 27/1027 and H 01L 27/1028. Groups H01L 27/1027, H01 L 27/1028 and H10B 99/20 should be considered in order to perform a complete search.	Delete the entire warning.
H10B 99/22	Group H10B 99/22 is incomplete pending reclassification of documents from group H01L 27/105. Groups H01L 27/105 and H 10B 99/22 should be considered in order to perform a complete search.	Delete the entire warning.
H01L 21/0405	H01L 29/66015	Delete entire reference (symbol and text).
H01L 21/0445	H01L 29/66053	Delete entire reference (symbol and text).
H01L 21/48	H01L21/06-H01L21/326	Replace: “subgroups H01L 21/06 - H01L 21/326” With: “groups H01L 21/18 - H01L 21/326 or H10D 48/04 - H10D 48/07”
H01L 21/50	H01L21/06-H01L21/326	Replace: “subgroups H01L 21/06 - H01L 21/326” With: “groups H01L 21/18 - H01L 21/326 or H10D 48/04 - H10D 48/07”

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Location of reference to be changed	Referenced subclass or group to be changed	Action; New reference symbol; New text
H01L 21/7624	H01L 21/76297, H01L 21/84, H01L 21/86	Delete the entirety of all references (symbols and related text) so that the title reads as follows: {using semiconductor on insulator [SOI] technology}
H01L 21/76897	H01L 29/665	Delete entire reference (symbol and text).
H01L 23/482	H01L 29/40	Delete entire reference (symbol and text).
H01L 23/49562	H01L 29/00	Replace the entire title with: {for individual devices of subclass H10D}
H01L 23/49844	H01L 29/00	Replace the entire title with: {for individual devices of subclass H10D}
H01L 23/528	H01L 27/0207, G06F 30/00	Replace the entire title with: Layout of the interconnection structure
H01L 25/065	H01L 27/00	H10D 89/00
H01L 25/07	H01L 29/00	Replace: "group H01L 29/00" With: "subclass H10D"
H01L 25/105	H01L 27/00	Replace the entire title with: {the devices being integrated devices of class H10}
H01L 25/11	H01L 29/00	Replace: "group H01L 29/00" With: "subclass H10D"
H01L 25/50	H01L 27/00, H01L 29/00	Replace the entire title with: "{Multistep manufacturing processes of assemblies consisting of devices, the devices being individual devices of subclass H10D or integrated devices of class H10 (H01L 21/50 takes precedence)}"
H01L 2225/065	H01L 27/00	Replace the entire title with: "All the devices being of a type provided for in the same main group of the same subclass of class H10"
H01L 2225/1005	H01L 27/00	Replace the entire title with: "the devices being integrated devices of class H10"
G01N 27/4148	H01L 21/82	Delete entire reference (symbol and text).

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Location of reference to be changed	Referenced subclass or group to be changed	Action; New reference symbol; New text
G02B 6/12	H01L 27/00	H10B, H10D 84/00 - H10D 89/00, H10F 19/00, H10F 39/00, H10H 29/00, H10K 19/00, H10K 39/00, H10K 59/00, H10N 19/00, H10N 39/00, H10N 59/00, H10N 69/00, H10N 79/00, H10N 89/00
H01G	H01L 29/00	H10D 1/62, H10K 10/10
H01G 4/33	H01L 27/00	Delete entire reference
H01G 4/33	H01L 28/40	Delete entire reference
G11C 5/025	H01L 27/0207	Replace: "geometrical lay-out of the components in integrated circuits, H01L 27/0207" With: "geometrical lay-out of the components in integrated circuits H10D 89/10"
B81B 7/0022	H01L 27/0248	Replace with new symbol H10D 89/60 so that the title reads as follows: {Protection against electrostatic discharge (circuit arrangements for protecting electronic switching circuits used for pulse technique against overcurrent or overvoltage H03K 17/08; electrostatic discharge protection for electronic semiconductor circuits H10D 89/60)}
H02H 9/046	H01L 27/0248	Delete entire reference (symbol and text).
H01F 10/3213	H01L 29/12	Delete entire reference (symbol and text).
H01F 17/00	H01L 28/10	Delete entire reference so that the title reads as follows: Fixed inductances of the signal type {(coils in general H01F 5/00)}
G01R 33/1284	H01L 29/66984	Delete entire reference (symbol and text).
G01L 1/2293	H01L 29/84	Delete entire reference (symbol and text).

Definitions references impacted by this revision project

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
B81B	H01L 29/0665	Informative references	H10D 62/118
B81B	H01L 29/267	Informative references	H10D 62/82

Location of reference to be changed	Referenced subclass or group to be changed	Section of definition	Action; New reference symbol; New text
B81C	H01L 29/0665	Informative references	H10D 62/118
B81C	H01L 29/267	Informative references	H10D 62/82
B82B	H01L 29/06	Informative references	H10D 62/118
B82Y	H01L 29/775	Informative references	H10D 30/43
C04B 35/44	H01L 29/7869	Informative references	Delete entire reference (symbol and text).
C04B 35/453	H01L 29/7869	Informative references	Delete entire reference (symbol and text).
C04B 35/465	H01L 28/55	Informative references	Delete entire reference (symbol and text).
C04B 35/491	H01L 28/55	Informative references	Delete entire reference (symbol and text).
C04B 35/52	H01L 29/1602	Informative references	Delete entire reference (symbol and text).
C04B 35/58	H01L 29/2003	Informative references	Delete entire reference (symbol and text).
C04B 35/58	H01L 29/518	Informative references	Delete entire reference (symbol and text).
C04B 35/58014	H01L 29/4966	Informative references	Delete entire reference (symbol and text).
C04B 35/58085	H01L 21/823443	Informative references	Delete entire reference (symbol and text).
C04B 35/58085	H01L 21/823835	Informative references	Delete entire reference (symbol and text).
C04B 35/58085	H01L 29/4975	Informative references	Delete entire reference (symbol and text).
C04B 35/58092	H01L 29/4975	Informative references	Delete entire reference (symbol and text).
C04B 35/584	H01L 29/78684	Informative references	Delete entire reference (symbol and text).
C04B 2235/761	H01L 29/04	Informative references	Delete entire reference (symbol and text).
C23F	H01L 28/00	Application-oriented references	Replace the symbol and related text so that they appear as follows: Manufacture of passive two-terminal components for integrated circuits, e.g. resistors, capacitors, inductors by etching conductive layers H10D 1/00

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Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
G01J 1/44	H01L 29/74	Informative references	H10D 18/00
G01J 5/03	H01L 27/00	Informative references	H10B
G01J 5/20	H01L 27/00	Informative references	H10F 39/00
G01L	H01L 29/84	Informative references	H10D 48/50
G01L 1/00	H01L 29/84	Special rules of classification	H10D 48/50
G02F 1/01	H01L 21/00, H01L 27/00	Application-oriented references	Delete entire reference (text and symbols)
G02F 1/01	H01L 27/12	Informative references	H10D 86/60
G09G	Indexing Code symbols of the type G09G 2xx represent information orthogonal to one or to more than one ECLA group and should be used to classify information relevant for the invention, although it need not be invention information.	Special rules of classification	Delete the entire second paragraph of text.
G09G 3/3644	H01L 27/00	Relationships with other classification places	H10D 86/00
G09G 3/3666	H01L 27/00	Relationships with other classification places	H10D 86/60
G11C 5/00	H01L 27/0207	Informative references	H10D 89/10
G11C 5/025	H01L 27/0207	Limiting references	H10D 89/10
G11C 11/14	H01L 29/82	Informative references	H10N 50/00, H10B 61/00

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
G11C 11/22	H01L 29/516	Informative references	Delete the reference symbol and related text and replace with the following two Informative reference entries: Ferroelectric data-storage electrodes H10D 64/033, H10D 64/689 Ferroelectric transistors H10D 30/0415, H10D 30/701
G11C 11/34	H01L 27/00	Informative references	Replace the symbol and related text so that they appear as follows: Semiconductor memory structures H10B
G11C 16/00	H10B 69/00, H01L 29/788, H01L 29/792	Informative references	Replace the symbol and related text so that they appear as follows: Individual transistor structures H10D 30/00
G11C 16/00	Fabrication of EPROM H10B 69/00	Informative references	Replace the symbol and related text so that they appear as follows: EPROM memory structures and fabrication thereof H10B 41/00, H10B 43/00, H10B 51/00, H10B 53/00, H10B 69/00
G11C 16/00	EPROM memory structures H10B 69/00	Informative references	Delete entire reference (symbol and text).
G11C 27/04	H01L 29/76	Informative references	H10D 44/40
H01F	H01L 29/82	Informative references	H10D 48/40
H01F 10/00	H01L 29/82	Informative references	H10D 48/40

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H01F 17/00	H01L 28/10	Application-oriented references	H10D 1/20
H01F 17/00	H01L 27/01	Informative references	Delete entire reference (symbol and text).
H01F 2017/0086	H01L 28/10	Informative references	H10D 1/20
H01G	H01L 27/00	Application-oriented references	Replace the symbol and related text so that they appear as follows: Capacitors specially adapted for integration, e.g. stacked capacitors in DRAM H10B 12/00, H10D 1/68
H01G	H01L 28/40	Application-oriented references	Delete entire reference (symbol and text).
H01G	H01L 29/00, H10K 10/10	Limiting references	H10D 1/62, H10K 10/10
H01G 11/00	H01L 28/40	Informative references	H10D 1/62
H01L 21/02002	H01L 27/00	Limiting references	Delete the entire Limiting references section. Insert a new Informative references section with the following table rows: Thermal smoothening H01L 21/324 Fabrication of inhomogeneous wafer, e.g. SOI H01L 21/76 Marking of wafers H01L 23/544 Forming flats C30B 33/00
H01L 21/02002	H01L 21/8258	Relationships with other classification places	H10D 84/00

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Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H01L 21/02002	H01L 29/06	Special rules of classification	Delete the entire Special rules section.
H01L 21/04	H01L 29/02	Informative references	H10D 62/01
H01L 21/04	H01L 29/401	Informative references	H10D 64/01
H01L 21/04	H01L 29/66007	Informative references	H10D 1/01, H10D 8/01, H10D 10/01, H10D 12/01, H10D 18/01, H10D 30/01, H10D 44/01, H10D 48/01
H01L 21/0405	H01L 29/1602	Special rules of classification	H10D 62/8303
H01L 21/0445	H01L 29/1608	Special rules of classification	H10D 62/8325
H01L 21/283	H01L 28/00	Limiting references	Delete the entire Limiting references section. Insert a new Informative references section with the following table rows: Formation of electrodes of capacitors, resistors, inductors H10D 1/01 Formation of electrodes of semiconductor devices H10D 64/01
H01L 21/48	H01L21/06-H01L21/326	Limiting references	Delete entire reference (symbols and text).
H01L 21/7624	H01L 21/84	Informative references	H10D 86/01
H01L 21/7624	H01L 21/86	Informative references	H10D 86/03
H01L 21/7687	H01L 28/60	Informative references	H10D 1/041, H10D 1/692
H01L 21/76897	H01L 29/66583	Informative references	H10D 30/0212

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Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H01L 23/482	H01L 29/40	Limiting references	Delete the entire Limiting references section.
H01L 23/49544	H01L 29/00	Limiting references	Replace only the reference text with: Lead-frames: geometry for individual devices of subclass H10D
H01L 23/49548	H01L 29/00	Limiting references	Replace only the reference text with: Lead-frames: geometry for individual devices of subclass H10D
H01L 23/528	H01L 27/0207	Limiting references	Delete entire reference (text and symbol).
H01L 23/60	H01L 27/0248	Informative references	H10D 89/60
H01L 25/50	H01L21/06-H01L21/326	Limiting references	H01L 21/18 - H01L 21/326
H01L 25/50	H01L 25/00	Limiting references	Delete entire reference (text and symbol).
H01L 2223/6661	H01L 28/00	Informative references	H10D 1/00
H01L 2223/6672	H01L 27/01	Informative references	H10D 84/201, H10D 86/80
H01L 2224/036	H01L21/06-H01L21/326	Informative references	H01L 21/18 - H01L 21/326
H01L 2224/116	H01L21/06-H01L21/326	Informative references	H01L 21/18 - H01L 21/326
H01L 2224/276	H01L21/06-H01L21/326	Informative references	H01L 21/18 - H01L 21/326
H02H 9/00	H01L 27/0248	Informative references	H10D 89/60
H02H 9/046	H01L 27/0248	Informative references	H10D 89/60
H02M 3/07	H01L 27/0222	Informative references	H10D 89/215

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H03K 5/08	H01L 27/0251	Limiting references	Delete the Limiting references entry. Insert a new Informative references section with the following table row: Clamping for ESD protection H10D 89/601
H03M 1/00	H01L 27/00, H01L 29/00	Informative references	Replace the symbol and related text so that they appear as follows: Integrated device structure H10D 84/00 - H10D 89/00
H04L 12/40136	H01L 29/66469	Informative references	Delete entire reference (text and symbol).
H04N 5/40	H01L 27/04, H01L 27/12, H10N 39/00	Informative references	H04L 27/00
H05K	H01L 27/01, H01L 27/13	Informative references	Delete entire reference (text and symbols).

Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H05K 1/16	H01L 27/01, H01L 27/13	Informative references	Replace the symbol and related text so that they appear as follows: Integrated devices having multiple passive components formed in or on insulating or conducting substrates H10D 86/80 Insert a new Informative reference entry: Integrated devices having multiple passive components formed in or on semiconductor substrates H10D 84/201
H05K 3/00	H01L 27/00	Relationships with other classification places	H10D 84/201, H10D 86/80
H05K 3/00	H01L	Relationships with other classification places	H01L, H10
H10B 10/00	H01L 28/20	Informative references	H10D 1/00
H10B 12/00	H01L 28/40	Informative references	H10D 1/00
H10B 41/00	H01L 29/40114	Informative references	H10D 64/035
H10B 41/00	H01L 29/788	Informative references	H10D 30/0411, H10D 30/68
H10B 43/00	H01L 29/40117	Informative references	H10D 64/037
H10B 43/00	H01L 29/792	Informative references	H10D 30/0413, H10D 30/69
H10B 51/00	H01L 29/40111	Informative references	H10D 64/033

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Location of reference to be changed	**Referenced subclass or group to be changed**	**Section of definition**	**Action; New reference symbol; New text**
H10B 51/00	H01L 29/78391	Informative references	H10D 30/0415, H10D 30/701
H10B 53/00	H01L 28/55	Informative references	H10D 1/682
H10K 10/00	H01L 29/00	Informative references	H10D
H10K 19/00	H01L 27/02	Informative references	H10D 84/00 - H10D 89/00
H10K 59/10	H01L 27/1214	Informative references	H10D 86/40, H10D 86/60
H10N 30/00	H01L 29/68	Informative references	H10D 48/32
H10N 30/00	H01L 29/84	Informative references	H10D 48/50
H10N 50/00	H01L 29/82	Informative references	H10D 48/40
H10N 52/00	H01L 29/82	Informative references	H10D 48/40
H10N 60/00	H01L 29/12	Informative references	H10D 62/81
H10N 80/00	H01L 29/88	Informative references	H10D 8/70
H01L 21/02104	H01L 28/40	Special rules of classification	H10D 1/041

NOTES:

- The CRL tables above are used for changes to locations **outside** of the project scope. Changes to references in scheme titles or definitions inside the project scope will be reflected in the "scheme change" template or one of the "definition" templates.
- In addition to other changes proposed in the tables above, in the column titled "Referenced subclass or group to be changed," **referenced** D symbols should indicate an action of "delete" or should indicate a replacement symbol and **referenced** F symbols should indicate a replacement symbol.
- When a reference is deleted, text related to that reference will also be deleted unless other references or a range of references associated with the same text remain.